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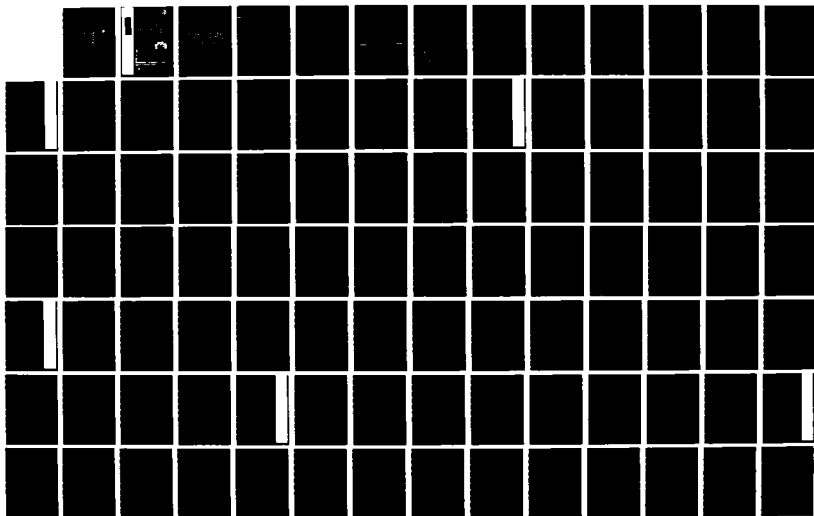
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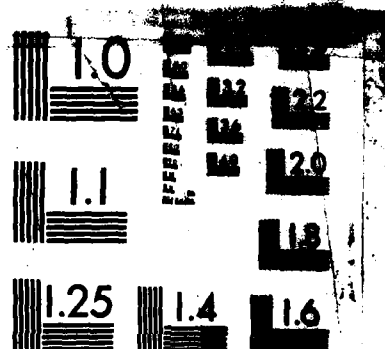
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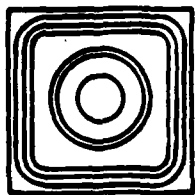
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Technical Reliability Studies

SEARCH and RETRIEVAL INDEX to EOS/ESD SYMPOSIUM PROCEEDINGS

1979 to 1984

Spring 85

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Under Contract To:

Rome Air Development Center
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<p>►This book contains indexes used in searching for information contained in papers produced in Electrical Overstress/Electrostatic Discharge (EOS/ESD) Symposium 1979 to 1984. These indexes are the Alphabetical List of Index Terms, Subject Index, Author Index, Corporate Index, Keywords in Title Index, and Chronological List of Papers Index. These indexes provide a clear, easy-to-read, and concise method of searching for and retrieving the valuable information contained in IRPS Proceedings.</p>					
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PREFACE

The Reliability Analysis Center is pleased to publish TRS-4, "The Search and Retrieval Index to EOS/ESD Symposium Proceedings From 1979 to 1984." TRS-4 provides quick and efficient access to EOS/ESD-related references.

The EOS/ESD Index makes more accessible present information on failure mechanisms, failure causes, and potential technology problems from electrical overstress/electrostatic discharge. The information from the documents in the Proceedings provides recommendations for circumventing or mitigating potential EOS/ESD problems and also provides references to evaluation and qualification testing. Increased information retrieval capability given by this index avoids duplication of previous studies and unreliable processes.

R. Wanner developed the software support programs, with input assistance from J. Race. D. Rash provided organization, coordination and control of processes under the supervision of W. Turkowski. W. Crowell defined extra EOS/ESD index terms for inclusion into this document. The entire RAC technical staff participated in the indexing of the documents contained in the EOS/ESD Symposium Proceedings.

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TABLE OF CONTENTS

	<u>Page</u>
1.0 INTRODUCTION.....	1
2.0 IMPLEMENTATION.....	1
3.0 INDEXING RATIONALE.....	1
4.0 ARRANGEMENT.....	2
5.0 SEARCH EXAMPLE.....	4
6.0 CONCLUSION.....	5
SECTION 1: ALPHABETICAL LISTING OF TERMS.....	I-1
SECTION 2: SUBJECT INDEX.....	II-1
SECTION 3: AUTHOR INDEX.....	III-1
SECTION 4: CORPORATE INDEX.....	IV-1
SECTION 5: KEYWORD IN TITLE INDEX.....	V-1
SECTION 6: CHRONOLOGICAL LIST OF PAPERS.....	VI-1
APPENDIX: ADDITIONAL RAC SERVICES.....	A-1

1.0 INTRODUCTION

The RAC developed "The Search and Retrieval Index to EOS/ESD Symposium Proceedings From 1979 to 1984" to provide ready access to current information on EOS/ESD-related topics.

Containing indexes plus users' guide material, this document serves as a reference to aid in the utilization of information concerning all aspects of electrical overstress/electrostatic discharge as presented in the EOS/ESD Symposium Proceedings. This structured index provides a quick and efficient access to references for a given topic. The increased information retrieval capability provided by this index prevents duplication of previous efforts and will help avoid the use of unreliable processes.

The EOS/ESD Symposium Proceedings are available from IIT Research Institute. Orders for EOS/ESD Symposium Proceedings should be directed to: Charles A. Cox, IITRI/Reliability Analysis Center, RADC/RAC, Griffiss Air Force Base, NY 13441-5700. To determine price and availability call (315) 330-4151, Autovon 587-4151.

2.0 IMPLEMENTATION

These indexes were composed by IITRI's Plexus P/60 computer using the UNIX Operating System. The manuscript was printed out on an Anderson Jacobson (Model AJ832) terminal.

3.0 INDEXING RATIONALE

For each paper in the Proceedings, two engineers with relevant expertise in that subject were assigned to independently read and index that article. The terms for these indexes were selected from a list of preselected index terms. The engineers' instructions included selecting those index terms for which the article had relevant information. To maintain flexibility in the index term list, periodic reviews and evaluations add new index terms.

4.0 ARRANGEMENT

This publication is arranged in six selections:

- (1) Alphabetical Listing of Index Terms
- (2) Subject Index
- (3) Author Index
- (4) Corporate Index
- (5) Keyword in Title Index
- (6) Chronological Paper Index

Each entry in each index uses the document accession number for location purposes in the RAC library. The document accession number also provides for traceability purposes to access abstracts which are not computerized.

The Alphabetical List of Index Terms, a 5-page list of terms without citations, serves as a lookup table for the subject index, which it precedes. The alphabetical list of terms identifies the category under which the index term appears by listing first the index term, then the categories for each index term, and then the number of documents for that index term within the category.

<u>Index Term</u>	<u>Categories</u>	<u>Documents</u>
Reliability	Design Considerations Semiconductor Technology	2
Reliability	Systems	5

This format allows the index term to remain generic while the categories narrow the focus to a single area of interest for the Subject Index. Using the Subject Index necessitates scanning these tables first to provide the following useful benefits: the researcher develops a search

strategy by (1) relevant association of subjects contained in the Alphabetical List of Terms with items of interest, (2) minimizing the likelihood of overlooking a highly relevant citation, and (3) constructing a source availability within the EOSs by the number of documents dealing with the item of interest.

The Subject Index alphabetically lists index terms from Section I with citations. The index terms and categories remain in this section except the categories follow the index term on the same line in brackets.

INDEX TERM - CATEGORY

DOCUMENT - SEQUENCE NUMBER	TITLE	YEAR	PAGE
Reliability	[Design Considerations, Semiconductor Technology]		
18214- 5	Latent ESD Failures	82	[41-48]

The citations include the RAC document accession number, the title of the paper and the paper number. Including the title provides a possibility for selecting the most conveniently appropriate papers and eliminating those not applicable without the necessity of looking up more information elsewhere. Skillful use of this index can lead to deeper insight into EOS/ESD phenomena and perhaps new discoveries from the cross-pollination of related studies.

The Author Index alphabetically lists authors cited in the EOS/ESD Proceedings, whether principal or secondary. For each paper up to three authors were identified as they appeared on the paper.

The Corporate Index alphabetically lists corporations, companies, institutions, and government agencies with whom the authors were affiliated at the time the papers were prepared. Citations in the index include paper number and title. For each paper only the first company that appeared on the paper was cited.

The Keyword in Title Index alphabetically lists selected keywords in the title of the paper. Citations include paper number and title. The use of this index locates papers for which the keyword is a principal topic.

The Chronological List of Papers lists by page and document accession numbers the last paper of the 1984 Proceedings first, then the following papers in descending numerical order until the first paper in the 1979 Proceedings appears as the last entry. Following each document accession number appears the title of the paper, pages, author(s), their corporate affiliation, and an alphabetical list of all the index terms applied to the particular paper. When an index of another section cites a paper, a profile of the paper's content can be deduced from the index terms appearing within the chronological paper list. The categories of the index terms remain the same, except for occasional abbreviations.

.0 SEARCH EXAMPLE

The following example illustrates the use of Section I, Alphabetical List of Terms, and Section II, Subject Index:

Suppose we are interested in studying EOS Models. The possible terms for finding applicable citations, we decide, would be "Models," "Modeling," and "Mathematical Models." Scanning Section I for these terms we find the following terms listed by relevant association:

Reliability Modeling Techniques
Models/Theory/Equations
Mathematical Analysis

When these terms are looked up in the Subject Index (Section II) the following citations are accepted for study:

79	126-132	82	56-61
79	133-139	82	62-70
81	132-138	82	76-81
82	19-33	84	136-143

By examining the index terms of the above list of papers as they appear in Section 6, Chronological List of Papers, an additional number of apparently applicable terms could be selected to obtain additional citations for further related study.

6.0 CONCLUSION

The Reliability Analysis Center published this document to provide a faster and more efficient method of searching for valuable information contained in the EOS/ESD Proceedings. The Reliability Analysis Center intended with this document, as with previous publications, to maintain up-to-date information on electrical overstress/electrostatic discharge implications for advanced technologies and to provide a knowledge base necessary to control EOS/ESD.

EOS/ESD SYMPOSIUM INDEX

TERM-CATEGORY ENT-SEQUENCE NO.	TITLE	YEAR	PAGES
TIME [ESD, MATERIALS AND EQUIPMENT, TESTING]			
5-19	AN ELECTROTHERMAL MODEL FOR CURRENT FILAMENTATION IN SECOND BREAKDOWN OF SILICON-ON-SAPPHIRE DIODES	79	[126-132]
IN CONSIDERATIONS [SEMICONDUCTOR TECHNOLOGY]			
15-16	CRITICAL CONSIDERATIONS FOR ESD TESTING	84	[104-111]
12- 1	ESD-HOW OFTEN DOES IT HAPPEN?	83	[1-5]
12-25	USING SCR'S AS TRANSIENT PROTECTION STRUCTURES IN INTEGRATED CIRCUITS	83	[177-180]
12-26	A SUMMARY OF MOST EFFECTIVE ELECTROSTATIC DISCHARGE PROTECTION CIRCUITS FOR MOS MEMORIES AND THEIR OBSERVED FAILURE MODES	83	[181-184]
14-17	CHARACTERIZATION OF ESD SAFE REQUIREMENTS FOR FLOOR SURFACES	82	[124-130]
14-18	ESD AND CONTAMINATION FROM CLEAN ROOM GARMENTS - PROBLEMS AND SOLUTIONS	82	[131-135]
17- 2	QUANTITATIVE EFFECTS OF RELATIVE & ABSOLUTE HUMIDITY ON ESD GENERATION/SUPPRESSION	81	[9-13]
16-13	SOS PROTECTION: THE DESIGN PROBLEM	80	[81-86]
16-14	LSI DESIGN CONSIDERATIONS FOR ESD PROTECTION STRUCTURES RELATED TO PROCESS AND LAYOUT VARIATIONS	80	[87-94]
16-25	LIGHTNING PROTECTION DESIGN FOR A PHOTOVOLTAIC CONCENTRATOR	80	[167-175]
15- 2	CONTROLLING ELECTROSTATIC PROBLEMS IN THE FABRICATION AND HANDLING OF SPACECRAFT HARDWARE	79	[4-6]
15- 6	PROPOSED MIL-STD AND MIL-HDBK FOR AN ELECTROSTATIC DISCHARGE CONTROL PROGRAM - BACKGROUND AND STATUS	79	[27-35]
GN FOR TESTABILITY [DESIGN CONSIDERATIONS, SEMICONDUCTOR TECHNOLOGY]			
72- 7	CONSTRUCTION AND APPLICATION OF A TESTER FOR MEASURING EOS/ESD THRESHOLDS TO 15KV	83	[37-47]
14-13	TEST METHODS FOR STATIC CONTROL PRODUCTS	82	[94-109]
14-14	METALLOPLASTICS	82	[110-114]
14-15	ELECTROACTIVE POLYMERS AS ALTERNATE ESD PROTECTIVE MATERIALS	82	[115-119]
14-16	DRASTIC LOSSES OF CONDUCTIVITY IN ANTISTATIC PLASTICS	82	[120-123]
14-17	CHARACTERIZATION OF ESD SAFE REQUIREMENTS FOR FLOOR SURFACES	82	[124-130]
14-22	ESD MINIMIZATION TECHNIQUE FOR MOS MANUFACTURING FINAL TEST AREA	82	[157-164]
14-24	CIRCUIT DESIGN FOR EOS/ESD PROTECTION	82	[169-174]
14-25	IN-CIRCUIT ANALYSIS OF ESD DAMAGED DEVICES	82	[175-178]
14-26	ELECTROSTATIC DISCHARGE AT THE PRODUCT LEVEL	82	[179-184]
14-27	ELECTROSTATIC DISCHARGE IMMUNITY IN COMPUTER SYSTEMS	82	[185-189]
17- 1	A CLOSER LOOK AT THE HUMAN ESD EVENT	81	[1-8]
16-32	AN EVALUATION OF WRIST STRAP PARAMETERS	80	[218-224]
16-33	MEASUREMENT OF FAST TRANSIENTS AND APPLICATION TO HUMAN ESD	80	[225-230]
15-13	FAILURE ANALYSIS OF MICROCIRCUITS SUBJECTED TO ELECTRICAL OVERSTRESS	79	[88-96]
15-15	ESD SUSCEPTIBILITIES OF HIGH PERFORMANCE ANALOG INTEGRATED CIRCUITS	79	[104-108]
CTOR/SENSOR [OPTOELECTRONIC, SEMICONDUCTOR DEVICE]			
17-33	EOS DAMAGE IN SILICON SOLAR CELLS	81	[209-235]
LOPMENT PROGRAM [SEMICONDUCTOR TECHNOLOGY]			
72- 3	THE PRODUCTION OPERATOR: WEAK LINK OR WARRIOR IN THE ESD BATTLE?	83	[12-16]
72- 5	AIR FORCE MAINTENANCE PROGRAM FOR ELECTRICAL OVERSTRESS/ELECTROSTATIC DISCHARGE (EOS/ESD) CONTROL	83	[21-28]
14-19	BASIC SPECIFICATION FOR ESD PROTECTION IN INDUSTRY	82	[136-141]
14-20	ESD IN I.C. ASSEMBLY (A BASE LINE SOLUTION)	82	[142-144]
14-21	AN EFFECTIVE ELECTROSTATIC DISCHARGE PROTECTION PROGRAM	82	[145-156]
14-23	UNIFORM ESD PROTECTION IN A LARGE MULTI-DEPARTMENT ASSEMBLY PLANT	82	[165-168]
17- 4	THE PERFECT "10" - CAN YOU REALLY HAVE ONE?	81	[21-27]
17- 5	THE ECONOMIC BENEFITS OF AN EFFECTIVE ESD AWARENESS AND CONTROL PROGRAM - AN EMPIRICAL ANALYSIS	81	[29-33]
17- 6	A PRAGMATIC APPROACH TO ESD PROBLEM SOLVING IN THE MANUFACTURING ENVIRONMENT A CASE HISTORY	81	[34-39]
17- 7	A LOW-COST PROGRAM FOR EVALUATION OF ESD PROTECTIVE MATERIALS AND EQUIPMENT	81	[41-43]
15- 1	AN EFFECTIVE ESD AWARENESS TRAINING PROGRAM	79	[1-3]

EOS/ESD SYMPOSIUM INDEX

TERM-CATEGORY ENT-SEQUENCE NO.	TITLE	YEAR	PAGES
CTIVE ESD PROTECTIVE MATERIAL [ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]			
7- 7	A LOW-COST PROGRAM FOR EVALUATION OF ESD PROTECTIVE MATERIALS AND EQUIPMENT	81	[41-43]
6- 1	PASSIVE STATIC PROTECTION: THEORY AND PRACTICE	80	[1-11]
5- 3	ELECTROSTATIC CONDUCTIVITY CHARACTERISTICS OF WORKBENCH-TOP SURFACE MATERIALS	79	[7-12]
5- 9	THE DEFICIENCIES IN MILITARY SPECIFICATION MIL-B-81705: CONSIDERATIONS AND A SIMPLE MODEL FOR STATIC PROTECTION	79	[45-54]
5-18	HUMAN FACTORS IN ELECTROSTATIC DISCHARGE PROTECTION	79	[122-125]
CTIVE FOAM [ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]			
4-13	TEST METHODS FOR STATIC CONTROL PRODUCTS	82	[94-109]
6- 1	PASSIVE STATIC PROTECTION: THEORY AND PRACTICE	80	[1-11]
MINATION [MISC. FAILURE PHENOMENA, SEMICONDUCTOR TECHNOLOGY]			
4-18	ESD AND CONTAMINATION FROM CLEAN ROOM GARMENTS - PROBLEMS AND SOLUTIONS	82	[131-135]
4-22	ESD MINIMIZATION TECHNIQUE FOR MOS MANUFACTURING FINAL TEST AREA	82	[157-164]
OL [EQUIPMENT TYPE/FUNCTION]			
2-11	THE ROOM AIR IONIZATION SYSTEM, A BETTER ALTERNATIVE THAN 40% RELATIVE HUMIDITY	83	[67-75]
2-12	MEASURING EFFECTIVENESS OF AIR IONIZERS	83	[76-86]
2-13	PERMANENCE OF THE ANTISTATIC PROPERTY OF COMMERCIAL ANTISTATIC BAGS AND TOTE BOXES	83	[87-94]
[SYSTEMS]			
5- 1	A REALISTIC AND SYSTEMATIC ESD CONTROL PLAN	84	[1-6]
2- 2	ESD CONTROL IMPLEMENTATION AND COST AVOIDANCE ANALYSIS	83	[6-11]
4-19	BASIC SPECIFICATION FOR ESD PROTECTION IN INDUSTRY	82	[136-141]
4-23	UNIFORM ESD PROTECTION IN A LARGE MULTI-DEPARTMENT ASSEMBLY PLANT	82	[165-168]
7- 7	A LOW-COST PROGRAM FOR EVALUATION OF ESD PROTECTIVE MATERIALS AND EQUIPMENT	81	[41-43]
COLLECTION SYS./TECHNIQUES [RELIABILITY MODELS/DATA/ANALYSIS]			
4- 6	A SURVEY OF EOS/ESD DATA SOURCES	82	[49-55]
TIME [ESD, MATERIALS AND EQUIPMENT, TESTING]			
5- 7	A ROOM IONIZATION SYSTEM FOR ELECTROSTATIC CHARGE AND DUST CONTROL	84	[40-44]
5- 8	STATIC-ELECTRIC CHARACTERIZATION OF SEMI-INSULATING MATERIALS	84	[45-49]
5-10	TRIBOELECTRIC TESTING FOR ELECTROSTATIC CHARGES ON MATERIALS AT KENNEDY SPACE CENTER	84	[58-63]
5-11	TRIBOELECTRIC CHARGE: ITS ESD ABILITY AND A MEASUREMENT METHOD FOR ITS PROPENSITY ON PACKING MATERIALS	84	[64-77]
5-13	A MATERIAL EVALUATION PROGRAM FOR DECORATIVE STATIC CONTROL TABLE TOP LAMINATES	84	[85-93]
5-15	TESTING OF ELECTROSTATIC MATERIALS FED. STD. 101C, METHOD 4046.1	84	[97-103]
5-19	SECONDARY DISCHARGE: A NEW JEOPARDY AND A NEW TOOL	84	[131-135]
2-11	THE ROOM AIR IONIZATION SYSTEM, A BETTER ALTERNATIVE THAN 40% RELATIVE HUMIDITY	83	[67-75]
2-12	MEASURING EFFECTIVENESS OF AIR IONIZERS	83	[76-86]
4-13	TEST METHODS FOR STATIC CONTROL PRODUCTS	82	[94-109]
4-16	DRASTIC LOSSES OF CONDUCTIVITY IN ANTISTATIC PLASTICS	82	[120-123]
4-17	CHARACTERIZATION OF ESD SAFE REQUIREMENTS FOR FLOOR SURFACES	82	[124-130]
7- 2	QUANTITATIVE EFFECTS OF RELATIVE & ABSOLUTE HUMIDITY ON ESD GENERATION/SUPPRESSION	81	[9-13]
7- 8	AN ANALYSIS OF ANTISTATIC CUSHIONING MATERIALS	81	[44-48]
7-11	INCOMING INSPECTION OF ANTISTATIC PACKAGING MATERIALS	81	[65-74]
6- 2	THE EFFECTS OF HIGH HUMIDITY ENVIRONMENTS ON ELECTROSTATIC GENERATION AND DISCHARGE	80	[12-16]
6-20	OSCILLATING VOLTAGE PULSES AND SECOND BREAKDOWN	80	[130-139]
6-24	TEST WAVEFORMS AND TECHNIQUES TO ASSESS THE THREAT TO ELECTRONIC DEVICES OF LIGHTNING-INDUCED TRANSIENTS	80	[161-166]
6-29	FACILITY EVALUATION: ISOLATING ENVIRONMENTAL ESD PROBLEMS	80	[192-205]
5- 4	STATIC CONTROL USING TOPICAL ANTISTATS	79	[13-21]

EOS/ESD SYMPOSIUM INDEX

INDEX TERM-CATEGORY DOCUMENT-SEQUENCE NO.	TITLE	YEAR	PAGES
CIRCUIT PROTECTION DEVICES [NON-ELECTRONICS]			
17517-14	ON CHIP PROTECTION OF HIGH DENSITY NMOS DEVICES	81	[90-96]
17517-15	INPUT PROTECTION DESIGN FOR THE 3-MICRON NMOS PROCESS	81	[97-100]
17517-30	LIGHTNING PROTECTION FOR COMPUTER DATA LINES	81	[212-218]
17516- 7	GAS TUBE SURGE ARRESTERS FOR CONTROL OF TRANSIENT VOLTAGES	80	[44-53]
17516-12	PROTECTION OF MOS INTEGRATED CIRCUITS FROM DESTRUCTION BY ELECTROSTATIC DISCHARGE	80	[73-80]
17516-13	SOS PROTECTION: THE DESIGN PROBLEM	80	[81-86]
17516-15	ELECTROSTATIC SENSITIVITY OF VARIOUS INPUT PROTECTION NETWORKS	80	[95-103]
17515-26	ELECTRICAL OVERSTRESS VERSUS DEVICE GEOMETRY	79	[183-187]
17515-28	ELECTROSTATIC DISCHARGE PROTECTION USING SILICON TRANSIENT SUPPRESSORS	79	[193-197]
CLEAN ROOM [ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]			
18214-18	ESD AND CONTAMINATION FROM CLEAN ROOM GARMENTS - PROBLEMS AND SOLUTIONS	82	[131-135]
COMPONENT [LEVEL OF ASSEMBLY]			
18172- 1	ESD-HOW OFTEN DOES IT HAPPEN?	83	[1-5]
18172-15	CALCULATIONS OF SECOND BREAKDOWN IN SILICON DIODES AT MICROWAVE FREQUENCIES	83	[102-107]
18214- 5	LATENT ESD FAILURES	82	[41-48]
17517- 4	THE PERFECT "10" - CAN YOU REALLY HAVE ONE?	81	[21-27]
17517- 5	THE ECONOMIC BENEFITS OF AN EFFECTIVE ESD AWARENESS AND CONTROL PROGRAM - AN EMPIRICAL ANALYSIS	81	[29-33]
COMPUTATION [EQUIPMENT TYPE/FUNCTION]			
17517-30	LIGHTNING PROTECTION FOR COMPUTER DATA LINES	81	[212-218]
COMPUTER AIDED DESIGN, (CAD) [DESIGN TOOLS & TECHNIQUES, SEMICONDUCTOR TECHNOLOGY]			
18172- 8	A PROGRAMMABLE EQUIPMENT FOR ELECTROSTATIC DISCHARGE TESTING TO HUMAN BODY MODELS	83	[48-55]
18172-16	MODELING AND TESTING FOR SECOND BREAKDOWN PHENOMENA	83	[108-117]
18214- 4	ELECTRICAL OVERSTRESS THRESHOLD TESTING	82	[34-40]
COMPUTERIZED [DATA COLLECTION SYS./TECHNIQUES, RELIABILITY MODELS/DATA/ANALYSIS]			
18172-15	CALCULATIONS OF SECOND BREAKDOWN IN SILICON DIODES AT MICROWAVE FREQUENCIES	83	[102-107]
18214-27	ELECTROSTATIC DISCHARGE IMMUNITY IN COMPUTER SYSTEMS	82	[185-189]
17517-20	MODELING OF EOS IN SILICON DEVICES	81	[132-138]
COMPUTERIZED ANALYSIS [DESIGN TOOLS & TECHNIQUES, SEMICONDUCTOR TECHNOLOGY]			
18172- 8	A PROGRAMMABLE EQUIPMENT FOR ELECTROSTATIC DISCHARGE TESTING TO HUMAN BODY MODELS	83	[48-55]
17515-19	AN ELECTROTHERMAL MODEL FOR CURRENT FILAMENTATION IN SECOND BREAKDOWN OF SILICON-ON-SAPPHIRE DIODES	79	[126-132]
COMPUTERIZED TECH [RELIABILITY MODELING TECHNIQUES, RELIABILITY MODELS/DATA/ANALYSIS]			
18172- 8	A PROGRAMMABLE EQUIPMENT FOR ELECTROSTATIC DISCHARGE TESTING TO HUMAN BODY MODELS	83	[48-55]
18172- 9	POWER FAILURE MODELING OF INTEGRATED CIRCUITS	83	[56-62]
18214-27	ELECTROSTATIC DISCHARGE IMMUNITY IN COMPUTER SYSTEMS	82	[185-189]
17515-16	DOPING PROFILES AND SECOND BREAKDOWN	79	[109-115]
17515-19	AN ELECTROTHERMAL MODEL FOR CURRENT FILAMENTATION IN SECOND BREAKDOWN OF SILICON-ON-SAPPHIRE DIODES	79	[126-132]
17515-20	MODELING OF ELECTRICAL OVERSTRESS IN SILICON DEVICES	79	[133-139]
CONDUCTIVE ESD PROTECTIVE MATERIAL [ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]			
18305-15	TESTING OF ELECTROSTATIC MATERIALS FED. STD. 101C, METHOD 4046.1	84	[97-103]
18214-16	DRASTIC LOSSES OF CONDUCTIVITY IN ANTISTATIC PLASTICS	82	[120-123]

EOS/ESD SYMPOSIUM INDEX

INDEX TERM-CATEGORY DOCUMENT-SEQUENCE NO.	TITLE	YEAR	PAGES
BULK CONDUCTIVE PLASTIC [ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]			
18305-12	AN EXPERIMENTAL STUDY OF THE ESD SCREENING EFFECTIVENESS OF ANTI-STATIC BAGS	84	[78-84]
17515- 9	THE DEFICIENCIES IN MILITARY SPECIFICATION MIL-B-81705: CONSIDERATIONS AND A SIMPLE MODEL FOR STATIC PROTECTION	79	[45-54]
CAPACITOR [PASSIVE DEVICE, COMPONENT TYPE]			
18214- 2	ELECTROSTATIC DISCHARGE (ESD) DAMAGE SUSCEPTIBILITY OF THIN FILM RESISTORS AND CAPACITORS	82	[13-18]
17517-25	PULSE POWER RESPONSE AND DAMAGE CHARACTERISTICS OF CAPACITORS	81	[174-191]
CCD [FIELD EFFECT,(FET), SEMICONDUCTOR TECHNOLOGY]			
18172-21	THE EFFECT OF ESD ON CCD RELIABILITY	83	[147-153]
CHARACTERIZATION [TEST TECHNIQUES FOR REL. ASSESSMENT, SEMICONDUCTOR TECHNOLOGY]			
18214- 9	THE FORWARD-BIAS CHARACTERISTIC AS A PREDICTOR AND SCREEN OF REVERSE-BIAS SECOND BREAKDOWN	82	[71-75]
18214-17	CHARACTERIZATION OF ESD SAFE REQUIREMENTS FOR FLOOR SURFACES	82	[124-130]
17516-23	AN OVERVIEW OF THE SOURCES AND EFFECTS OF ELECTRICAL OVERSTRESS	80	[154-160]
17516-27	MICROCIRCUIT ELECTRICAL OVERSTRESS TOLERANCE TESTING AND QUALIFICATION	80	[184-188]
17515-14	ELECTROSTATIC FAILURE OF X-BAND SILICON SCHOTTKY BARRIER DIODES	79	[97-103]
CHARGE DEVICE MODEL [ESD, DEVICE, TESTING METHODS]			
18305- 1	A REALISTIC AND SYSTEMATIC ESD CONTROL PLAN	84	[1-6]
18305-19	SECONDARY DISCHARGE: A NEW JEOPARDY AND A NEW TOOL	84	[131-135]
18172- 6	ESD BY STATIC INDUCTION	83	[29-36]
18172-19	ESD SENSITIVITY OF COMPLEX ICS	83	[128-133]
18172-21	THE EFFECT OF ESD ON CCD RELIABILITY	83	[147-153]
18214- 1	ESD SUSCEPTIBILITY TESTING OF ADVANCED SCHOTTKY TTL	82	[1-12]
18214- 2	ELECTROSTATIC DISCHARGE (ESD) DAMAGE SUSCEPTIBILITY OF THIN FILM RESISTORS AND CAPACITORS	82	[13-18]
17517-10	EVALUATION OF INTEGRATED CIRCUIT SHIPPING TUBES	81	[57-64]
17517-34	EVALUATION OF ELECTROSTATIC DISCHARGE TO 16K EPROMS	81	[236-241]
17516- 3	ESD DAMAGE FROM TRIBOELECTRICALLY CHARGED IC PINS	80	[17-22]
CHART/DIAGRAM [REFERENCE DOCUMENT]			
17515-13	FAILURE ANALYSIS OF MICROCIRCUITS SUBJECTED TO ELECTRICAL OVERSTRESS	79	[88-96]
CIRCUIT BOARD [NON-ELECTRONICS]			
18305- 4	ESD DAMAGE, DOES IT HAPPEN ON PCBS?	84	[22-23]
18305-19	SECONDARY DISCHARGE: A NEW JEOPARDY AND A NEW TOOL	84	[131-135]
18305-23	DEGRADATION BY ESD TRANSIENTS OF THE SUBSTRATE BIAS VOLTAGE OF NMOS 8085-TYPE MICROPROCESSORS	84	[165-178]
CIRCUIT BREAKER [CIRCUIT PROTECTION DEVICES, NON-ELECTRONICS]			
18214-28	ELECTRICAL GROUNDING IN LARGE INSTRUMENTATION SYSTEMS	82	[190-202]
CIRCUIT PROTECTION DEVICES [NON-ELECTRONICS]			
18172-13	PERMANENCE OF THE ANTISTATIC PROPERTY OF COMMERCIAL ANTISTATIC BAGS AND TOTE BOXES	83	[87-94]
18172-24	METAL OXIDE VARISTORS FOR TRANSIENT PROTECTION OF 3 TO 5-VOLT INTEGRATED CIRCUITS	83	[168-176]
18172-26	A SUMMARY OF MOST EFFECTIVE ELECTROSTATIC DISCHARGE PROTECTION CIRCUITS FOR MOS MEMORIES AND THEIR OBSERVED FAILURE MODES	83	[181-184]
18214-20	ESD IN I.C. ASSEMBLY (A BASE LINE SOLUTION)	82	[142-144]
18214-24	CIRCUIT DESIGN FOR EOS/ESD PROTECTION	82	[169-174]
17517-13	THE EFFECTS OF VLSI SCALING ON EOS/ESD FAILURE THRESHOLD	81	[85-89]

EOS/ESD SYMPOSIUM INDEX

INDEX TERM-CATEGORY DOCUMENT-SEQUENCE NO.	TITLE	YEAR	PAGES
AIR IONIZER [ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]			
18305- 2	HAZARDS OF STATIC CHARGES AND FIELDS AT THE WORK STATION	84	[7-19]
18305- 6	EFFECTS OF AIR IONS AND ELECTRIC FIELDS ON HEALTH AND PRODUCTIVITY	84	[34-39]
18305- 7	A ROOM IONIZATION SYSTEM FOR ELECTROSTATIC CHARGE AND DUST CONTROL	84	[40-44]
18172-11	THE ROOM AIR IONIZATION SYSTEM, A BETTER ALTERNATIVE THAN 40% RELATIVE HUMIDITY	83	[67-75]
18172-12	MEASURING EFFECTIVENESS OF AIR IONIZERS	83	[76-86]
18214-13	TEST METHODS FOR STATIC CONTROL PRODUCTS	82	[94-109]
17517- 2	QUANTITATIVE EFFECTS OF RELATIVE & ABSOLUTE HUMIDITY ON ESD GENERATION/ SUPPRESSION	81	[9-13]
17517- 5	THE ECONOMIC BENEFITS OF AN EFFECTIVE ESD AWARENESS AND CONTROL PROGRAM - AN EMPIRICAL ANALYSIS	81	[29-33]
17517- 7	A LOW-COST PROGRAM FOR EVALUATION OF ESD PROTECTIVE MATERIALS AND EQUIPMENT	81	[41-43]
17515- 2	CONTROLLING ELECTROSTATIC PROBLEMS IN THE FABRICATION AND HANDLING OF SPACECRAFT HARDWARE	79	[4-6]
ANTISTATIC GARMENTS [ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]			
18214-18	ESD AND CONTAMINATION FROM CLEAN ROOM GARMENTS - PROBLEMS AND SOLUTIONS	82	[131-135]
ANTISTATIC IMPREGNATED PLASTIC [ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]			
18172-13	PERMANENCE OF THE ANTISTATIC PROPERTY OF COMMERCIAL ANTISTATIC BAGS AND TOTE BOXES	83	[87-94]
APPLICATION FACTORS [DESIGN CONSIDERATIONS, SEMICONDUCTOR TECHNOLOGY]			
18172-11	THE ROOM AIR IONIZATION SYSTEM, A BETTER ALTERNATIVE THAN 40% RELATIVE HUMIDITY	83	[67-75]
18172-12	MEASURING EFFECTIVENESS OF AIR IONIZERS	83	[76-86]
18172-24	METAL OXIDE VARISTORS FOR TRANSIENT PROTECTION OF 3 TO 5-VOLT INTEGRATED CIRCUITS	83	[168-176]
18214-18	ESD AND CONTAMINATION FROM CLEAN ROOM GARMENTS - PROBLEMS AND SOLUTIONS	82	[131-135]
17517- 4	THE PERFECT "10" - CAN YOU REALLY HAVE ONE?	81	[21-27]
17517-14	ON CHIP PROTECTION OF HIGH DENSITY NMOS DEVICES	81	[90-96]
17517-15	INPUT PROTECTION DESIGN FOR THE 3-MICRON NMOS PROCESS	81	[97-100]
17515- 4	STATIC CONTROL USING TOPICAL ANTISTATS	79	[13-21]
17515-18	HUMAN FACTORS IN ELECTROSTATIC DISCHARGE PROTECTION	79	[122-125]
17515-29	STATISTICAL FAILURE ANALYSIS OF MILITARY SYSTEMS FOR HIGH-ALTITUDE EMP	79	[198-204]
ASSEMBLY & EQUIPMENT ESD CLASSIFICATION [ESD, DEVICE, TESTING METHODS]			
18305- 4	ESD DAMAGE, DOES IT HAPPEN ON PCBS?	84	[22-23]
17516-21	ASSESSING ELECTRICAL OVERSTRESS EFFECTS ON ELECTRONIC SYSTEMS	80	[140-148]
AVAILABILITY [SYSTEMS]			
18214-19	BASIC SPECIFICATION FOR ESD PROTECTION IN INDUSTRY	82	[136-141]
BIPOLAR [COMPONENT TYPE]			
18305-21	AN EVALUATION OF EOS FAILURE MODELS	84	[144-156]
17516-10	FAILURE THRESHOLD DISTRIBUTIONS IN BIPOLAR TRANSISTORS	80	[59-66]
17516-17	HIGH-FIELD PHENOMENA AND FAILURE MECHANISMS IN BIPOLAR TRANSISTORS	80	[112-116]
17516-18	SOME DESIGN CRITERIA FOR AVOIDING SECOND BREAKDOWN IN BIPOLAR DEVICES	80	[117-121]
17515- 7	MODULE ELECTROSTATIC DISCHARGE SIMULATOR	79	[36-40]
BIPOLAR & FET,(BIFET,BIMOS,ETC) [COMPONENT TYPE]			
17516-18	SOME DESIGN CRITERIA FOR AVOIDING SECOND BREAKDOWN IN BIPOLAR DEVICES	80	[117-121]
BOARD [LEVEL OF ASSEMBLY]			
18305- 4	ESD DAMAGE, DOES IT HAPPEN ON PCBS?	84	[22-23]
17515-30	THE ANALYSIS AND ELIMINATION OF EOS INDUCED SECONDARY FAILURE MECHANISMS	79	[205-209]

Section 2:

SUBJECT INDEX

ALPHABETICAL LISTING OF INDEX TERMS

<u>INDEX TERM</u>	<u>CATEGORIES</u>	<u>DOCUMENTS</u>
TEST TECHNIQUES	TESTING TOOLS & TECHNIQUES SEMICONDUCTOR TECHNOLOGY	6
TEST TECHNIQUES FOR REL. ASSESSMENT	SEMICONDUCTOR TECHNOLOGY	28
TESTING TOOLS & TECHNIQUES	SEMICONDUCTOR TECHNOLOGY	21
THEORY OF OPERATION	SEMICONDUCTOR TECHNOLOGY	6
THERMAL	TEST STRESS	4
THERMAL SECONDARY BREAKDOWN	ESD DEVICE FAILURE MODES	8
THERMAL STRESS/STRAIN	MECHANICAL & PHYSICAL FAILURE PHENOMENA SEMICONDUCTOR TECHNOLOGY	1
TOLERANCES	DESIGN CONSIDERATIONS SEMICONDUCTOR TECHNOLOGY	3
TOPICAL ANTISTATS	ESD MATERIALS AND EQUIPMENT PROTECTIVE	5
TRADE-OFFS	DESIGN CONSIDERATIONS SEMICONDUCTOR TECHNOLOGY	4
TRANSIENT SUPPRESSORS	ESD DEVICE PROTECTIVE DEVICES/INPUT PROTECTION	11
TRANSISTOR	DISCRETE SEMICONDUCTOR SEMICONDUCTOR DEVICE	13
TRIOBOELECTRIC CHARGING	ESD EOS/ESD PHYSICS	19
TTL	BIPOLAR COMPONENT TYPE	2
VOLUME RESISTIVITY	ESD MATERIALS AND EQUIPMENT TESTING	1
WEAPONS	EQUIPMENT TYPE/FUNCTION	1
WEIBULL	STATISTICAL ANALYSIS	2
WORKMANSHIP	FAILURE CAUSE FAILURE ANALYSIS SEMICONDUCTOR TECHNOLOGY	1
WRIST STRAP	ESD MATERIALS AND EQUIPMENT PROTECTIVE	6
WUNSCH BELL MODEL	ESD DEVICE TESTING METHODS	13

ALPHABETICAL LISTING OF INDEX TERMS

<u>INDEX TERM</u>	<u>CATEGORIES</u>	<u>DOCUMENTS</u>
QUALITY ASSURANCE	SYSTEMS	8
REFERENCE DOCUMENT		47
REL. STANDARDS	USER OF REL. PREDICTION MODELS	1
RELATIVE HUMIDITY	ESD MATERIALS AND EQUIPMENT PROTECTIVE TECHNIQUES	21
RELIABILITY	DESIGN CONSIDERATIONS SEMICONDUCTOR TECHNOLOGY	2
RELIABILITY	SYSTEMS	5
RELIABILITY MANAGEMENT TECH	USER OF REL. PREDICTION MODELS	1
RELIABILITY MODELING TECHNIQUES	RELIABILITY MODELS/DATA/ANALYSIS	4
RESISTOR	PASSIVE DEVICE COMPONENT TYPE	4
REVERSE BREAKDOWN	ELECTRICAL FAILURE PHENOMENA SEMICONDUCTOR TECHNOLOGY	1
SCREENING	TEST TECHNIQUES FOR REL. ASSESSMENT SEMICONDUCTOR TECHNOLOGY	2
SECONDARY BREAKDOWN	ELECTRICAL FAILURE PHENOMENA SEMICONDUCTOR TECHNOLOGY	15
SEMICONDUCTOR DEVICE		14
SENSITIVE ELECTRONIC DEVICE SYMBOLS	ESD MATERIALS AND EQUIPMENT PROTECTIVE	2
SILICON	SEMICONDUCTOR TECHNOLOGY	1
SPACE	APPLICATION ENVIRONMENT	1
SPECIFICATION/STANDARD	REFERENCE DOCUMENT	5
STATIC CONTROL	ESD MATERIALS AND EQUIPMENT PROTECTIVE TECHNIQUES	20
STATISTICAL ANALYSIS		2
STEP STRESS	TEST TECHNIQUES FOR REL. ASSESSMENT SEMICONDUCTOR TECHNOLOGY	5
SURFACE RESISTIVITY	ESD MATERIALS AND EQUIPMENT TESTING	15
SYSTEM	LEVEL OF ASSEMBLY	3
TEST EQUIPMENT	TESTING TOOLS & TECHNIQUES SEMICONDUCTOR TECHNOLOGY	8
TEST PROGRAM DEVELOPMENT	TESTING TOOLS & TECHNIQUES SEMICONDUCTOR TECHNOLOGY	8
TEST SPECIFICATION	TESTING TOOLS & TECHNIQUES SEMICONDUCTOR TECHNOLOGY	6

ALPHABETICAL LISTING OF INDEX TERMS

<u>INDEX TERM</u>	<u>CATEGORIES</u>	<u>DOCUMENTS</u>
MISC. FAILURE PHENOMENA	SEMICONDUCTOR TECHNOLOGY	2
MISSILE	APPLICATION ENVIRONMENT	1
MNOS	FIELD EFFECT, (FET) SEMICONDUCTOR TECHNOLOGY	1
MODELS/THEORY/EQUATIONS	RELIABILITY MODELING TECHNIQUES RELIABILITY MODELS/DATA/ANALYSIS	6
MOISTURE	TEST STRESS	1
MOSFET	FIELD EFFECT, (FET) SEMICONDUCTOR TECHNOLOGY	2
MOSFET C	FIELD EFFECT, (FET) SEMICONDUCTOR TECHNOLOGY	3
MOSFET N	FIELD EFFECT, (FET) SEMICONDUCTOR TECHNOLOGY	1
NONELECTRONICS		2
NOTICE/BULLETIN	REFERENCE DOCUMENT	1
OPERATIONAL TEST	TEST TECHNIQUES FOR REL. ASSESSMENT SEMICONDUCTOR TECHNOLOGY	2
OVERSTRESS	FAILURE CAUSE FAILURE ANALYSIS SEMICONDUCTOR TECHNOLOGY	45
OXIDATION	CHEMICAL FAILURE PHENOMENA SEMICONDUCTOR TECHNOLOGY	7
PACKAGE	SEMICONDUCTOR TECHNOLOGY	6
PKG BODY MATERIAL	PACKAGE SEMICONDUCTOR TECHNOLOGY	1
PKG ENCAPSULANT	PACKAGE SEMICONDUCTOR TECHNOLOGY	1
PKG LID OR COVER	PACKAGE SEMICONDUCTOR TECHNOLOGY	1
PROCESS CONTROL/SPECIFICATION	FABRICATION PROCESSES & TECHNIQUES SEMICONDUCTOR TECHNOLOGY	6
PROCESS DESIGN	DESIGN CONSIDERATIONS SEMICONDUCTOR TECHNOLOGY	3
PROCESS/WORKMANSHIP INDUCED	MISC. FAILURE PHENOMENA SEMICONDUCTOR TECHNOLOGY	1
PROCUREMENT CONTROLS	USER OF REL. PREDICTION MODELS	3
PROTECTED ESD AREA	ESD MATERIALS AND EQUIPMENT PROTECTIVE	12
PROTECTIVE BAGS	ESD MATERIALS AND EQUIPMENT PROTECTIVE	8
PROTECTIVE WORK BENCH SURFACE	ESD MATERIALS AND EQUIPMENT PROTECTIVE	6

ALPHABETICAL LISTING OF INDEX TERMS

<u>INDEX TERM</u>	<u>CATEGORIES</u>	<u>DOCUMENTS</u>
FMEA/FMECA, (FAILURE MODE EFFECTS)	RELIABILITY MODELING TECHNIQUES RELIABILITY MODELS/DATA/ANALYSIS	1
FUTURE TRENDS	SEMICONDUCTOR TECHNOLOGY	9
GEOMETRIES/LAYOUT	DESIGN CONSIDERATIONS SEMICONDUCTOR TECHNOLOGY	4
GRAPHICAL TECHNIQUES	RELIABILITY MODELING TECHNIQUES RELIABILITY MODELS/DATA/ANALYSIS	1
GROUNDING METHODS	ESD MATERIALS AND EQUIPMENT PROTECTIVE TECHNIQUES	6
GROUNDING STRAPS	ESD MATERIALS AND EQUIPMENT PROTECTIVE	6
GUIDE/PROCEDURE	REFERENCE DOCUMENT	24
HELICOPTOR	APPLICATION ENVIRONMENT	1
HUMAN BODY ESD MODEL	ESD DEVICE TESTING METHODS	21
HUMAN FACTORS	SYSTEMS	3
INDUCTIVE CHARGING	ESD EOS/ESD PHYSICS	3
INPUT PROTECTION	ESD DEVICE PROTECTIVE DEVICES/INPUT PROTECTION	16
JFET	FIELD EFFECT, (FET) SEMICONDUCTOR TECHNOLOGY	1
LATENT ESD FAILURE	ESD DEVICE FAILURE MODES	4
LIFE	TEST TECHNIQUES FOR REL. ASSESSMENT SEMICONDUCTOR TECHNOLOGY	4
LOGISTICS	SYSTEMS	1
MAINTAINABILITY TECHNIQUES	MAINTAINABILITY SYSTEMS	1
MATERIALS	DESIGN CONSIDERATIONS SEMICONDUCTOR TECHNOLOGY	11
MATHEMATICAL ANALYSIS		12
METALLIZATION MELT	ESD DEVICE FAILURE MODES	13
METALLURGICAL FAILURE PHENOMENA	SEMICONDUCTOR TECHNOLOGY	1
MICROCIRCUIT	SEMICONDUCTOR DEVICE	33
MICROWAVE	DISCRETE SEMICONDUCTOR SEMICONDUCTOR DEVICE	1

ALPHABETICAL LISTING OF INDEX TERMS

<u>INDEX TERM</u>	<u>CATEGORIES</u>	<u>DOCUMENTS</u>
ELECTROSTATIC SIMULATOR	ESD DEVICE TESTING METHODS	6
EMC - ELECTROMAGNETIC COMPATIBILITY	ESD EOS/ESD PHYSICS	1
EMI - ELECTROMAGNETIC INTERFACE	ESD EOS/ESD PHYSICS	10
EMP - ELECTROMAGNETIC PULSE	ESD EOS/ESD PHYSICS	17
ENVIRONMENTAL	TEST TECHNIQUES FOR REL. ASSESSMENT SEMICONDUCTOR TECHNOLOGY	2
EOS - ELECTRICAL OVERSTRESS	ESD EOS/ESD PHYSICS	23
EOS/ESD	SEMICONDUCTOR TECHNOLOGY	179
ESD CONTROL PROGRAM	ESD MATERIALS AND EQUIPMENT PROTECTIVE TECHNIQUES	20
ESD PROTECTIVE MATERIAL	ESD MATERIALS AND EQUIPMENT TESTING	20
ESD STD AND HANDBOOK	ESD STANDARDS, HANDBOOKS, MANUALS	21
ESD SUSCEPTIBILITY TESTING	ESD DEVICE TESTING METHODS	80
EVALUATION TEST	TEST TECHNIQUES FOR REL. ASSESSMENT SEMICONDUCTOR TECHNOLOGY	6
FABRICATION EQUIPMENT	FABRICATION PROCESSES & TECHNIQUES SEMICONDUCTOR TECHNOLOGY	2
FABRICATION PROCESSES & TECHNIQUES	SEMICONDUCTOR TECHNOLOGY	10
FAILURE ANALYSIS RESULTS	FAILURE ANALYSIS SEMICONDUCTOR TECHNOLOGY	16
FAILURE ANALYSIS TECHNIQUES	FAILURE ANALYSIS SEMICONDUCTOR TECHNOLOGY	2
FAILURE CAUSE	FAILURE ANALYSIS SEMICONDUCTOR TECHNOLOGY	3
FAILURE CHARACTERIZATION	SEMICONDUCTOR TECHNOLOGY	7
FAILURE INDICATOR	FAILURE ANALYSIS SEMICONDUCTOR TECHNOLOGY	2
FAILURE MODES	FAILURE ANALYSIS SEMICONDUCTOR TECHNOLOGY	8
FIELD EFFECT, (FET)	SEMICONDUCTOR TECHNOLOGY	2
FLOOR SURFACE	ESD MATERIALS AND EQUIPMENT PROTECTIVE	5

ALPHABETICAL LISTING OF INDEX TERMS

<u>INDEX TERM</u>	<u>CATEGORIES</u>	<u>DOCUMENTS</u>
COMPUTERIZED ANALYSIS	DESIGN TOOLS & TECHNIQUES SEMICONDUCTOR TECHNOLOGY	2
COMPUTERIZED TECH	RELIABILITY MODELING TECHNIQUES RELIABILITY MODELS/DATA/ANALYSIS	6
CONDUCTIVE ESD PROTECTIVE MATERIAL	ESD MATERIALS AND EQUIPMENT PROTECTIVE	7
CONDUCTIVE FOAM	ESD MATERIALS AND EQUIPMENT PROTECTIVE	2
CONTAMINATION	MISC. FAILURE PHENOMENA SEMICONDUCTOR TECHNOLOGY	2
CONTROL	EQUIPMENT TYPE/FUNCTION	3
COST	SYSTEMS	5
DATA COLLECTION SYS./TECHNIQUES	RELIABILITY MODELS/DATA/ANALYSIS	1
DECAY TIME	ESD MATERIALS AND EQUIPMENT TESTING	21
DESIGN CONSIDERATIONS	SEMICONDUCTOR TECHNOLOGY	12
DESIGN FOR TESTABILITY	DESIGN CONSIDERATIONS SEMICONDUCTOR TECHNOLOGY	16
DETECTOR/SENSOR	OPTOELECTRONIC SEMICONDUCTOR DEVICE	1
DEVELOPMENT PROGRAM	SEMICONDUCTOR TECHNOLOGY	12
DIELECTRIC BREAKDOWN	ESD DEVICE FAILURE MODES	8
DIGITAL LSI	MICROCIRCUIT SEMICONDUCTOR DEVICE	7
DIODE	DISCRETE SEMICONDUCTOR SEMICONDUCTOR DEVICE	7
DIP TUBE	ESD MATERIALS AND EQUIPMENT PROTECTIVE	3
DISCRETE SEMICONDUCTOR	SEMICONDUCTOR DEVICE	7
ELECTRICAL	TEST STRESS	4
ELECTRICAL FAILURE PHENOMENA	SEMICONDUCTOR TECHNOLOGY	4
ELECTRO-THERMOMIGRATION	ESD DEVICE FAILURE MODES	2
ELECTROSTATIC CHARGE DETECTOR	ESD MATERIALS AND EQUIPMENT PROTECTIVE	7
ELECTROSTATIC SHIELD	ESD EOS/ESD PHYSICS	3

ALPHABETICAL LISTING OF INDEX TERMS

<u>INDEX TERM</u>	<u>CATEGORIES</u>	<u>DOCUMENTS</u>
AIR IONIZER	ESD MATERIALS AND EQUIPMENT PROTECTIVE	10
ANTISTATIC GARMENTS	ESD MATERIALS AND EQUIPMENT PROTECTIVE	1
ANTISTATIC IMPREGNATED PLASTIC	ESD MATERIALS AND EQUIPMENT PROTECTIVE	1
APPLICATION FACTORS	DESIGN CONSIDERATIONS SEMICONDUCTOR TECHNOLOGY	10
ASSEMBLY & EQUIPMENT ESD CLASSIFICATION	ESD DEVICE TESTING METHODS	2
AVAILABILITY	SYSTEMS	1
BIPOLAR	COMPONENT TYPE	5
BIPOLAR & FET, (BIFET, BIMOS, ETC)	COMPONENT TYPE	1
BOARD	LEVEL OF ASSEMBLY	2
BULK CONDUCTIVE PLASTIC	ESD MATERIALS AND EQUIPMENT PROTECTIVE	2
CAPACITOR	PASSIVE DEVICE COMPONENT TYPE	2
CCD	FIELD EFFECT, (FET) SEMICONDUCTOR TECHNOLOGY	1
CHARACTERIZATION	TEST TECHNIQUES FOR REL. ASSESSMENT SEMICONDUCTOR TECHNOLOGY	5
CHARGE DEVICE MODEL	ESD DEVICE TESTING METHODS	10
CHART/DIAGRAM	REFERENCE DOCUMENT	1
CIRCUIT BOARD	NON-ELECTRONICS	3
CIRCUIT BREAKER	CIRCUIT PROTECTION DEVICES NON-ELECTRONICS	1
CIRCUIT PROTECTION DEVICES	NON-ELECTRONICS	15
CLEAN ROOM	ESD MATERIALS AND EQUIPMENT PROTECTIVE	1
COMPONENT	LEVEL OF ASSEMBLY	5
COMPUTATION	EQUIPMENT TYPE/FUNCTION	1
COMPUTER AIDED DESIGN, (CAD)	DESIGN TOOLS & TECHNIQUES SEMICONDUCTOR TECHNOLOGY	3
COMPUTERIZED	DATA COLLECTION SYS./TECHNIQUES RELIABILITY MODELS/DATA/ANALYSIS	3

Section 1:

ALPHABETICAL LISTING OF TERMS

EOS/ESD SYMPOSIUM INDEX

INDEX TERM-CATEGORY DOCUMENT-SEQUENCE NO.	TITLE	YEAR	PAGES
DEVELOPMENT PROGRAM [SEMICONDUCTOR TECHNOLOGY]			
17515-30	THE ANALYSIS AND ELIMINATION OF EOS INDUCED SECONDARY FAILURE MECHANISMS	79	[205-209]
DIELECTRIC BREAKDOWN [ESD, DEVICE, FAILURE MODES]			
18172-26	A SUMMARY OF MOST EFFECTIVE ELECTROSTATIC DISCHARGE PROTECTION CIRCUITS FOR MOS MEMORIES AND THEIR OBSERVED FAILURE MODES	83	[181-184]
18172-28	A STUDY OF ESD LATENT DEFECTS IN SEMICONDUCTORS	83	[198-204]
17517-13	THE EFFECTS OF VLSI SCALING ON EOS/ESD FAILURE THRESHOLD	81	[85-89]
17517-25	PULSE POWER RESPONSE AND DAMAGE CHARACTERISTICS OF CAPACITORS	81	[174-191]
17517-28	EOS THRESHOLD DETERMINATION OF ELECTRO-EXPLOSIVE DEVICES	81	[202-207]
17515-15	ESD SUSCEPTIBILITIES OF HIGH PERFORMANCE ANALOG INTEGRATED CIRCUITS	79	[104-108]
17515-20	MODELING OF ELECTRICAL OVERSTRESS IN SILICON DEVICES	79	[133-139]
17515-25	THE DIELECTRIC STRENGTH OF SiO ₂ IN A CMOS TRANSISTOR STRUCTURE	79	[176-182]
DIGITAL LSI [MICROCIRCUIT, SEMICONDUCTOR DEVICE]			
18172-27	ESD SENSITIVITY OF NMOS LSI CIRCUITS AND THEIR FAILURE CHARACTERISTICS	83	[185-197]
17517-18	ELECTRICAL OVERSTRESS INVESTIGATIONS IN MODERN INTEGRATED CIRCUIT TECHNOLOGIES	81	[114-119]
17517-34	EVALUATION OF ELECTROSTATIC DISCHARGE TO 16K EPROMS	81	[236-241]
17516-14	LSI DESIGN CONSIDERATIONS FOR ESD PROTECTION STRUCTURES RELATED TO PROCESS AND LAYOUT VARIATIONS	80	[87-94]
17515- 8	RELIABILITY OF EOS SCREENED GOLD DOPED 4002 CMOS DEVICES	79	[41-44]
17515-11	EFFECTS OF ELECTRICAL OVERSTRESS ON DIGITAL BIPOLAR MICROCIRCUITS AND ANALYSIS TECHNIQUES FOR FAILURE SITE LOCATION	79	[64-77]
17515-24	SUSCEPTIBILITY OF LSI MOS TO ELECTROSTATIC DISCHARGE AT ELEVATED TEMPERATURE	79	[168-175]
DIODE [DISCRETE SEMICONDUCTOR, SEMICONDUCTOR DEVICE]			
18172-15	CALCULATIONS OF SECOND BREAKDOWN IN SILICON DIODES AT MICROWAVE FREQUENCIES	83	[102-107]
18172-17	TEMPERATURE AT SECOND BREAKDOWN AT A WELL-DEFINED SITE	83	[118-121]
17516-19	EFFECT OF JUNCTION SPIKES AND DOPING LEVEL ON THE SECOND BREAKDOWN SUSCEPTIBILITY OF SILICON-ON-SAPPHIRE DIODES	80	[122-129]
17516-20	OSCILLATING VOLTAGE PULSES AND SECOND BREAKDOWN	80	[130-139]
17515-14	ELECTROSTATIC FAILURE OF X-BAND SILICON SCHOTTKY BARRIER DIODES	79	[97-103]
17515-16	DOPING PROFILES AND SECOND BREAKDOWN	79	[109-115]
17515-19	AN ELECTROTHERMAL MODEL FOR CURRENT FILAMENTATION IN SECOND BREAKDOWN OF SILICON-ON-SAPPHIRE DIODES	79	[126-132]
DIP TUBE [ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]			
18214-13	TEST METHODS FOR STATIC CONTROL PRODUCTS	82	[94-109]
17517-10	EVALUATION OF INTEGRATED CIRCUIT SHIPPING TUBES	81	[57-64]
17516- 3	ESD DAMAGE FROM TRIBOELECTRICALLY CHARGED IC PINS	80	[17-22]
DISCRETE SEMICONDUCTOR [SEMICONDUCTOR DEVICE]			
17517-19	AN OVERVIEW OF EOS EFFECTS ON SEMICONDUCTOR DEVICES	81	[120-131]
17517-21	SEMICONDUCTOR DEVICE FAILURE CRITERIA FOR SINUSOIDAL STRESSES	81	[139-144]
17517-23	EOS/ESD FAILURE THRESHOLD ANALYSIS ERRORS, THEIR SOURCE, SIZE AND CONTROL	81	[151-166]
17517-31	FAILURE ANALYSIS OF SEMICONDUCTOR DEVICES IN EOS/ESD TESTING	81	[219-224]
17517-35	NON-LINEAR KINETICS OF SEMICONDUCTOR JUNCTION THERMAL FAILURE	81	[242-245]
17516- 5	TRANSIENT PROTECTION WITH ZNO VARISTORS: TECHNICAL CONSIDERATIONS	80	[26-34]
17516- 6	PROTECTION LEVEL COMPARISONS FOR VOLTAGE TRANSIENT SUPPRESSORS (120 V, AC TYPE)	80	[35-43]
ELECTRICAL [TEST STRESS]			
18172- 9	POWER FAILURE MODELING OF INTEGRATED CIRCUITS	83	[56-62]
18172-24	METAL OXIDE VARISTORS FOR TRANSIENT PROTECTION OF 3 TO 5-VOLT INTEGRATED CIRCUITS	83	[168-176]
18214-10	MODELING OF CURRENT AND THERMAL MODE SECOND BREAKDOWN PHENOMENA	82	[76-81]
17516-27	MICROCIRCUIT ELECTRICAL OVERSTRESS TOLERANCE TESTING AND QUALIFICATION	80	[184-188]

EOS/ESD SYMPOSIUM INDEX

INDEX TERM-CATEGORY DOCUMENT-SEQUENCE NO.	TITLE	YEAR	PAGES
ELECTRICAL FAILURE PHENOMENA [SEMICONDUCTOR TECHNOLOGY]			
18305-17	DESIGNING TO AVOID STATIC - ESD TESTING OF DIGITAL DEVICES	84	[112-123]
17516-10	FAILURE THRESHOLD DISTRIBUTIONS IN BIPOLAR TRANSISTORS	80	[59-66]
17516-20	OSCILLATING VOLTAGE PULSES AND SECOND BREAKDOWN	80	[130-139]
17516-22	SOLAR CELL ELECTRICAL OVERSTRESS ANALYSIS	80	[149-153]
ELECTRO-THERMOMIGRATION [ESD, DEVICE, FAILURE MODES]			
18305-25	A FAILURE ANALYSIS METHODOLOGY FOR REVEALING ESD DAMAGE TO INTEGRATED CIRCUITS	84	[189-195]
17516-20	OSCILLATING VOLTAGE PULSES AND SECOND BREAKDOWN	80	[130-139]
ELECTROSTATIC CHARGE DETECTOR [ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]			
18305- 2	HAZARDS OF STATIC CHARGES AND FIELDS AT THE WORK STATION	84	[7-19]
18305- 3	TEST EQUIPMENT--A SOURCE OF ESD!!	84	[20-21]
18305- 5	ELECTROSTATIC MEASUREMENT FOR PROCESS CONTROL	84	[25-33]
18172- 7	CONSTRUCTION AND APPLICATION OF A TESTER FOR MEASURING EOS/ESD THRESHOLDS TO 15KV	83	[37-47]
18172-10	STATIC SURVEY METERS	83	[63-66]
17517-11	INCOMING INSPECTION OF ANTISTATIC PACKAGING MATERIALS	81	[65-74]
17516- 4	ELECTROSTATIC DISCHARGE (ESD) MONITOR DESIGN	80	[23-25]
ELECTROSTATIC SHIELD [ESD, EOS/ESD PHYSICS]			
18214-14	METALLOPLASTICS	82	[110-114]
17517-12	SELECTION OF PACKAGING MATERIALS FOR ESD SENSITIVE ITEMS	81	[75-84]
17515- 9	THE DEFICIENCIES IN MILITARY SPECIFICATION MIL-B-81705: CONSIDERATIONS AND A SIMPLE MODEL FOR STATIC PROTECTION	79	[45-54]
ELECTROSTATIC SIMULATOR [ESD, DEVICE, TESTING METHODS]			
18305-16	CRITICAL CONSIDERATIONS FOR ESD TESTING	84	[104-111]
18305-17	DESIGNING TO AVOID STATIC - ESD TESTING OF DIGITAL DEVICES	84	[112-123]
18305-20	PROTECTION OF COMPONENTS AGAINST ELECTRICAL OVERSTRESS (EOS) AND TRANSIENTS IN MONITORS	84	[136-143]
17516-27	MICROCIRCUIT ELECTRICAL OVERSTRESS TOLERANCE TESTING AND QUALIFICATION	80	[184-188]
17515- 5	THE GENERATION OF ELECTROSTATIC CHARGES IN SILICONE ENCAPSULANTS DURING CYCLIC GASEOUS PRESSURE TESTS	79	[22-26]
17515- 7	MODULE ELECTROSTATIC DISCHARGE SIMULATOR	79	[36-40]
EMC - ELECTROMAGNETIC COMPATIBILITY [ESD, EOS/ESD PHYSICS]			
17516-23	AN OVERVIEW OF THE SOURCES AND EFFECTS OF ELECTRICAL OVERSTRESS	80	[154-160]
EMI - ELECTROMAGNETIC INTERFACE [ESD, EOS/ESD PHYSICS]			
18305- 4	ESD DAMAGE, DOES IT HAPPEN ON PCBS?	84	[22-23]
18305-16	CRITICAL CONSIDERATIONS FOR ESD TESTING	84	[104-111]
18305-18	EMI CHARACTERISTICS OF ESD IN A SMALL AIR GAP --ARP GOVERNS THE EMI--	84	[124-130]
18172-11	THE ROOM AIR IONIZATION SYSTEM, A BETTER ALTERNATIVE THAN 40% RELATIVE HUMIDITY	83	[67-75]
18214- 6	A SURVEY OF EOS/ESD DATA SOURCES	82	[49-55]
18214-14	METALLOPLASTICS	82	[110-114]
17516- 6	PROTECTION LEVEL COMPARISONS FOR VOLTAGE TRANSIENT SUPPRESSORS (120 V, AC TYPE)	80	[35-43]
17516-23	AN OVERVIEW OF THE SOURCES AND EFFECTS OF ELECTRICAL OVERSTRESS	80	[154-160]
17516-29	FACILITY EVALUATION: ISOLATING ENVIRONMENTAL ESD PROBLEMS	80	[192-205]
17516-31	STATIC CONTROL SYSTEMS	80	[213-217]
EMP - ELECTROMAGNETIC PULSE [ESD, EOS/ESD PHYSICS]			
18305- 4	ESD DAMAGE, DOES IT HAPPEN ON PCBS?	84	[22-23]
18305-21	AN EVALUATION OF EOS FAILURE MODELS	84	[144-156]
18172- 9	POWER FAILURE MODELING OF INTEGRATED CIRCUITS	83	[56-62]
18172-16	MODELING AND TESTING FOR SECOND BREAKDOWN PHENOMENA	83	[108-117]
18214- 6	A SURVEY OF EOS/ESD DATA SOURCES	82	[49-55]

EOS/ESD SYMPOSIUM INDEX

INDEX TERM-CATEGORY DOCUMENT-SEQUENCE NO.	TITLE	YEAR	PAGES
EMP - ELECTROMAGNETIC PULSE [ESD, EOS/ESD PHYSICS]			
18214- 8	AN IMPROVED EOS CONDUCTION MODEL OF SEMICONDUCT DEVICES	82	[62-70]
18214-12	SECOND BREAKDOWN IN SWITCHING TRANSISTORS	82	[91-93]
17517-19	AN OVERVIEW OF EOS EFFECTS ON SEMICONDUCTOR DEVICES	81	[120-131]
17517-21	SEMICONDUCTOR DEVICE FAILURE CRITERIA FOR SINUSOIDAL STRESSES	81	[139-144]
17517-28	EOS THRESHOLD DETERMINATION OF ELECTRO-EXPLOSIVE DEVICES	81	[202-207]
17516-21	ASSESSING ELECTRICAL OVERSTRESS EFFECTS ON ELECTRONIC SYSTEMS	80	[140-148]
17516-23	AN OVERVIEW OF THE SOURCES AND EFFECTS OF ELECTRICAL OVERSTRESS	80	[154-160]
17516-27	MICROCIRCUIT ELECTRICAL OVERSTRESS TOLERANCE TESTING AND QUALIFICATION	80	[184-188]
17515-12	DYNAMIC WAVEFORM CHARACTERISTICS OF PERSONNEL ELECTROSTATIC DISCHARGE	79	[78-87]
17515-21	SQUARE PULSE AND RF PULSE OVERSTRESSING OF UHF TRANSISTORS	79	[140-146]
17515-23	DAMAGE RESPONSE OF SELECTED INTERFACE INTEGRATED CIRCUITS TO A SIMULATED EMP	79	[158-167]
17515-29	STATISTICAL FAILURE ANALYSIS OF MILITARY SYSTEMS FOR HIGH-ALTITUDE EMP	79	[198-204]
ENVIRONMENTAL [TEST TECHNIQUES FOR REL. ASSESSMENT, SEMICONDUCTOR TECHNOLOGY]			
17516- 2	THE EFFECTS OF HIGH HUMIDITY ENVIRONMENTS ON ELECTROSTATIC GENERATION AND DISCHARGE	80	[12-16]
17515- 5	THE GENERATION OF ELECTROSTATIC CHARGES IN SILICONE ENCAPSULANTS DURING CYCLIC CASEOUS PRESSURE TESTS	79	[22-26]
EOS - ELECTRICAL OVERSTRESS [ESD, EOS/ESD PHYSICS]			
18305- 5	ELECTROSTATIC MEASUREMENT FOR PROCESS CONTROL	84	[25-33]
18305-20	PROTECTION OF COMPONENTS AGAINST ELECTRICAL OVERSTRESS (EOS) AND TRANSIENTS IN MONITORS	84	[136-143]
18305-21	AN EVALUATION OF EOS FAILURE MODELS	84	[144-156]
18172- 7	CONSTRUCTION AND APPLICATION OF A TESTER FOR MEASURING EOS/ESD THRESHOLDS TO 15KV	83	[37-47]
18172-12	MEASURING EFFECTIVENESS OF AIR IONIZERS	83	[76-86]
18172-22	EOS OR ESD: CAN FAILURE ANALYSIS TELL THE DIFFERENCE?	83	[154-157]
18172-23	INVISIBLE EOS/ESD DAMAGE: HOW TO FIND IT	83	[158-167]
18214- 4	ELECTRICAL OVERSTRESS THRESHOLD TESTING	82	[34-40]
18214- 8	AN IMPROVED EOS CONDUCTION MODEL OF SEMICONDUCT DEVICES	82	[62-70]
18214-11	A PROBABILISTIC ESTIMATOR FOR BOUNDING TRANSISTOR EMITTER-BASE JUNCTION TRANSIENT-INDUCED FAILURES	82	[82-90]
18214-19	BASIC SPECIFICATION FOR ESD PROTECTION IN INDUSTRY	82	[136-141]
17517-19	AN OVERVIEW OF EOS EFFECTS ON SEMICONDUCTOR DEVICES	81	[120-131]
17517-20	MODELING OF EOS IN SILICON DEVICES	81	[132-138]
17517-23	EOS/ESD FAILURE THRESHOLD ANALYSIS ERRORS, THEIR SOURCE, SIZE AND CONTROL	81	[151-166]
17517-24	AN OVERVIEW OF EOS EFFECTS ON PASSIVE COMPONENTS	81	[167-173]
17517-28	EOS THRESHOLD DETERMINATION OF ELECTRO-EXPLOSIVE DEVICES	81	[202-207]
17517-31	FAILURE ANALYSIS OF SEMICONDUCTOR DEVICES IN EOS/ESD TESTING	81	[219-224]
17516-22	SOLAR CELL ELECTRICAL OVERSTRESS ANALYSIS	80	[149-153]
17516-23	AN OVERVIEW OF THE SOURCES AND EFFECTS OF ELECTRICAL OVERSTRESS	80	[154-160]
17516-27	MICROCIRCUIT ELECTRICAL OVERSTRESS TOLERANCE TESTING AND QUALIFICATION	80	[184-188]
17516-30	BASIC CONSIDERATIONS IN ELECTRO-THERMAL OVERSTRESS IN ELECTRONIC COMPONENTS	80	[206-212]
17515-13	FAILURE ANALYSIS OF MICROCIRCUITS SUBJECTED TO ELECTRICAL OVERSTRESS	79	[88-96]
17515-30	THE ANALYSIS AND ELIMINATION OF EOS INDUCED SECONDARY FAILURE MECHANISMS	79	[205-209]
EOS/ESD [SEMICONDUCTOR TECHNOLOGY]			
18305- 1	A REALISTIC AND SYSTEMATIC ESD CONTROL PLAN	84	[1-6]
18305- 2	HAZARDS OF STATIC CHARGES AND FIELDS AT THE WORK STATION	84	[7-19]
18305- 3	TEST EQUIPMENT--A SOURCE OF ESD!!	84	[20-21]
18305- 4	ESD DAMAGE, DOES IT HAPPEN ON PCBs?	84	[22-23]
18305- 5	ELECTROSTATIC MEASUREMENT FOR PROCESS CONTROL	84	[25-33]
18305- 6	EFFECTS OF AIR IONS AND ELECTRIC FIELDS ON HEALTH AND PRODUCTIVITY	84	[34-39]
18305- 7	A ROOM IONIZATION SYSTEM FOR ELECTROSTATIC CHARGE AND DUST CONTROL	84	[40-44]
18305- 8	STATIC-ELECTRIC CHARACTERIZATION OF SEMI-INSULATING MATERIALS	84	[45-49]
18305- 9	ESTIMATION OF DISCHARGE ENERGY RELEASED FROM CHARGED INSULATOR	84	[50-57]
18305-10	TRIBOELECTRIC TESTING FOR ELECTROSTATIC CHARGES ON MATERIALS AT KENNEDY SPACE CENTER	84	[58-63]
18305-11	TRIBOELECTRIC CHARGE: ITS ESD ABILITY AND A MEASUREMENT METHOD FOR ITS PROPENSITY ON PACKING MATERIALS	84	[64-77]

EOS/ESD SYMPOSIUM INDEX

INDEX TERM-CATEGORY DOCUMENT-SEQUENCE NO.	TITLE	YEAR	PAGES
EOS/ESD [SEMICONDUCTOR TECHNOLOGY]			
18305-12	AN EXPERIMENTAL STUDY OF THE ESD SCREENING EFFECTIVENESS OF ANTI-STATIC BAGS	84	[78-84]
18305-13	A MATERIAL EVALUATION PROGRAM FOR DECORATIVE STATIC CONTROL TABLE TOP LAMINATES	84	[85-93]
18305-14	A WRIST STRAP LIFE TEST PROGRAM	84	[94-96]
18305-15	TESTING OF ELECTROSTATIC MATERIALS FED. STD. 101C, METHOD 4046.1	84	[97-103]
18305-16	CRITICAL CONSIDERATIONS FOR ESD TESTING	84	[104-111]
18305-17	DESIGNING TO AVOID STATIC - ESD TESTING OF DIGITAL DEVICES	84	[112-123]
18305-18	EMI CHARACTERISTICS OF ESD IN A SMALL AIR GAP --ARP GOVERNS THE EMI--	84	[124-130]
18305-19	SECONDARY DISCHARGE: A NEW JEOPARDY AND A NEW TOOL	84	[131-135]
18305-20	PROTECTION OF COMPONENTS AGAINST ELECTRICAL OVERSTRESS (EOS) AND TRANSIENTS IN MONITORS	84	[136-143]
18305-21	AN EVALUATION OF EOS FAILURE MODELS	84	[144-156]
18305-22	DETERMINATION OF THRESHOLD ENERGIES AND DAMAGE MECHANISMS IN SEMICONDUCTOR DEVICES SUBJECTED TO VOLTAGE TRANSIENTS	84	[157-164]
18305-23	DEGRADATION BY ESD TRANSIENTS OF THE SUBSTRATE BIAS VOLTAGE OF NMOS 8085-TYPE MICROPROCESSORS	84	[165-178]
18305-24	DEVICE ESD SUSCEPTIBILITY TESTING AND DESIGN HARDENING	84	[179-188]
18305-25	A FAILURE ANALYSIS METHODOLOGY FOR REVEALING ESD DAMAGE TO INTEGRATED CIRCUITS	84	[189-195]
18305-26	ESD SENSITIVITY AND LATENCY EFFECTS OF SOME HCMOS INTEGRATED CIRCUITS	84	[196-201]
18305-27	A CMOS VLSI ESD INPUT PROTECTION DEVICE, DIFIDW	84	[202-209]
18172- 1	ESD-HOW OFTEN DOES IT HAPPEN?	83	[1-5]
18172- 2	ESD CONTROL IMPLEMENTATION AND COST AVOIDANCE ANALYSIS	83	[6-11]
18172- 3	THE PRODUCTION OPERATOR: WEAK LINK OR WARRIOR IN THE ESD BATTLE?	83	[12-16]
18172- 4	ANALYSIS OF ELECTROSTATIC CHARGE PROPENSITY OF FLOOR FINISHES	83	[17-20]
18172- 5	AIR FORCE MAINTENANCE PROGRAM FOR ELECTRICAL OVERSTRESS/ELECTROSTATIC DISCHARGE (EOS/ESD) CONTROL	83	[21-28]
18172- 6	ESD BY STATIC INDUCTION	83	[29-36]
18172- 7	CONSTRUCTION AND APPLICATION OF A TESTER FOR MEASURING EOS/ESD THRESHOLDS TO 15KV	83	[37-47]
18172- 8	A PROGRAMMABLE EQUIPMENT FOR ELECTROSTATIC DISCHARGE TESTING TO HUMAN BODY MODELS	83	[48-55]
18172- 9	POWER FAILURE MODELING OF INTEGRATED CIRCUITS	83	[56-62]
18172-10	STATIC SURVEY METERS	83	[63-66]
18172-11	THE ROOM AIR IONIZATION SYSTEM, A BETTER ALTERNATIVE THAN 40% RELATIVE HUMIDITY	83	[67-75]
18172-12	MEASURING EFFECTIVENESS OF AIR IONIZERS	83	[76-86]
18172-13	PERMANENCE OF THE ANTISTATIC PROPERTY OF COMMERCIAL ANTISTATIC BAGS AND TOTE BOXES	83	[87-94]
18172-14	COPLANAR TRIBOELECTRIFICATION OF SELECTED MATERIALS	83	[95-101]
18172-15	CALCULATIONS OF SECOND BREAKDOWN IN SILICON DIODES AT MICROWAVE FREQUENCIES	83	[102-107]
18172-16	MODELING AND TESTING FOR SECOND BREAKDOWN PHENOMENA	83	[108-117]
18172-17	TEMPERATURE AT SECOND BREAKDOWN AT A WELL-DEFINED SITE	83	[118-121]
18172-18	SEMICONDUCTOR JUNCTION NON-LINEAR FAILURE POWER THRESHOLDS: WUNSCH-BELL REVISITED	83	[122-127]
18172-19	ESD SENSITIVITY OF COMPLEX ICS	83	[128-133]
18172-20	ESD EVALUATION OF RADIATION-HARDENED, HIGH RELIABILITY CMOS AND MNOS ICS	83	[134-146]
18172-21	THE EFFECT OF ESD ON CCD RELIABILITY	83	[147-153]
18172-22	EOS OR ESD: CAN FAILURE ANALYSIS TELL THE DIFFERENCE?	83	[154-157]
18172-23	INVISIBLE EOS/ESD DAMAGE: HOW TO FIND IT	83	[158-167]
18172-24	METAL OXIDE VARISTORS FOR TRANSIENT PROTECTION OF 3 TO 5-VOLT INTEGRATED CIRCUITS	83	[168-176]
18172-25	USING SCR'S AS TRANSIENT PROTECTION STRUCTURES IN INTEGRATED CIRCUITS	83	[177-180]
18172-26	A SUMMARY OF MOST EFFECTIVE ELECTROSTATIC DISCHARGE PROTECTION CIRCUITS FOR MOS MEMORIES AND THEIR OBSERVED FAILURE MODES	83	[181-184]
18172-27	ESD SENSITIVITY OF NMOS LSI CIRCUITS AND THEIR FAILURE CHARACTERISTICS	83	[185-197]
18172-28	A STUDY OF ESD LATENT DEFECTS IN SEMICONDUCTORS	83	[198-204]
18214- 1	ESD SUSCEPTIBILITY TESTING OF ADVANCED SCHOTTKY TTL	82	[1-12]
18214- 2	ELECTROSTATIC DISCHARGE (ESD) DAMAGE SUSCEPTIBILITY OF THIN FILM RESISTORS AND CAPACITORS	82	[13-18]
18214- 3	LIMITATIONS IN MODELING ELECTRICAL OVERSTRESS FAILURE IN SEMICONDUCTOR DEVICES	82	[19-33]
18214- 4	ELECTRICAL OVERSTRESS THRESHOLD TESTING	82	[34-40]
18214- 5	LATENT ESD FAILURES	82	[41-48]
18214- 6	A SURVEY OF EOS/ESD DATA SOURCES	82	[49-55]
18214- 7	MODELING METALLIZATION BURNOUT OF INTEGRATED CIRCUITS	82	[56-61]
18214- 8	AN IMPROVED EOS CONDUCTION MODEL OF SEMICONDUCT DEVICES	82	[62-70]

EOS/ESD SYMPOSIUM INDEX

INDEX TERM-CATEGORY DOCUMENT-SEQUENCE NO.	TITLE	YEAR	PAGES
EOS/ESD [SEMICONDUCTOR TECHNOLOGY]			
18214- 9	THE FORWARD-BIAS CHARACTERISTIC AS A PREDICTOR AND SCREEN OF REVERSE-BIAS SECOND BREAKDOWN	82	[71-75]
18214-10	MODELING OF CURRENT AND THERMAL MODE SECOND BREAKDOWN PHENOMENA	82	[76-81]
18214-11	A PROBABILISTIC ESTIMATOR FOR BOUNDING TRANSISTOR EMITTER-BASE JUNCTION TRANSIENT-INDUCED FAILURES	82	[82-90]
18214-12	SECOND BREAKDOWN IN SWITCHING TRANSISTORS	82	[91-93]
18214-13	TEST METHODS FOR STATIC CONTROL PRODUCTS	82	[94-109]
18214-14	METALLOPLASTICS	82	[110-114]
18214-15	ELECTROACTIVE POLYMERS AS ALTERNATE ESD PROTECTIVE MATERIALS	82	[115-119]
18214-16	DRASTIC LOSSES OF CONDUCTIVITY IN ANTISTATIC PLASTICS	82	[120-123]
18214-17	CHARACTERIZATION OF ESD SAFE REQUIREMENTS FOR FLOOR SURFACES	82	[124-130]
18214-18	ESD AND CONTAMINATION FROM CLEAN ROOM GARMENTS - PROBLEMS AND SOLUTIONS	82	[131-135]
18214-19	BASIC SPECIFICATION FOR ESD PROTECTION IN INDUSTRY	82	[136-141]
18214-20	ESD IN I.C. ASSEMBLY (A BASE LINE SOLUTION)	82	[142-144]
18214-21	AN EFFECTIVE ELECTROSTATIC DISCHARGE PROTECTION PROGRAM	82	[145-156]
18214-22	ESD MINIMIZATION TECHNIQUE FOR MOS MANUFACTURING FINAL TEST AREA	82	[157-164]
18214-23	UNIFORM ESD PROTECTION IN A LARGE MULTI-DEPARTMENT ASSEMBLY PLANT	82	[165-168]
18214-24	CIRCUIT DESIGN FOR EOS/ESD PROTECTION	82	[169-174]
18214-25	IN-CIRCUIT ANALYSIS OF ESD DAMAGED DEVICES	82	[175-178]
18214-26	ELECTROSTATIC DISCHARGE AT THE PRODUCT LEVEL	82	[179-184]
18214-27	ELECTROSTATIC DISCHARGE IMMUNITY IN COMPUTER SYSTEMS	82	[185-189]
18214-28	ELECTRICAL GROUNDING IN LARGE INSTRUMENTATION SYSTEMS	82	[190-202]
17517- 1	A CLOSER LOOK AT THE HUMAN ESD EVENT	81	[1-8]
17517- 2	QUANTITATIVE EFFECTS OF RELATIVE & ABSOLUTE HUMIDITY ON ESD GENERATION/ SUPPRESSION	81	[9-13]
17517- 3	ANALYSIS OF ESD FAILURES	81	[14-20]
17517- 4	THE PERFECT "10" - CAN YOU REALLY HAVE ONE?	81	[21-27]
17517- 5	THE ECONOMIC BENEFITS OF AN EFFECTIVE ESD AWARENESS AND CONTROL PROGRAM - AN EMPIRICAL ANALYSIS	81	[29-33]
17517- 6	A PRAGMATIC APPROACH TO ESD PROBLEM SOLVING IN THE MANUFACTURING ENVIRONMENT A CASE HISTORY	81	[34-39]
17517- 7	A LOW-COST PROGRAM FOR EVALUATION OF ESD PROTECTIVE MATERIALS AND EQUIPMENT	81	[41-43]
17517- 8	AN ANALYSIS OF ANTISTATIC CUSHIONING MATERIALS	81	[44-48]
17517- 9	CHO-TRAP, A NOVEL VOLTAGE TRANSIENT PROTECTION PACKAGING MATERIAL	81	[49-56]
17517-10	EVALUATION OF INTEGRATED CIRCUIT SHIPPING TUBES	81	[57-64]
17517-11	INCOMING INSPECTION OF ANTISTATIC PACKAGING MATERIALS	81	[65-74]
17517-12	SELECTION OF PACKAGING MATERIALS FOR ESD SENSITIVE ITEMS	81	[75-84]
17517-13	THE EFFECTS OF VLSI SCALING ON EOS/ESD FAILURE THRESHOLD	81	[85-89]
17517-14	ON CHIP PROTECTION OF HIGH DENSITY NMOS DEVICES	81	[90-96]
17517-15	INPUT PROTECTION DESIGN FOR THE 3-MICRON NMOS PROCESS	81	[97-100]
17517-16	DIAGNOSIS AND ANALYSIS OF EMITTER-BASE JUNCTION OVERSTRESS DAMAGE	81	[101-105]
17517-17	SUSCEPTIBILITY OF ICS IN ESD STEP-STRESS TESTS	81	[106-113]
17517-18	ELECTRICAL OVERSTRESS INVESTIGATIONS IN MODERN INTEGRATED CIRCUIT TECHNOLOGIES	81	[114-119]
17517-19	AN OVERVIEW OF EOS EFFECTS ON SEMICONDUCTOR DEVICES	81	[120-131]
17517-20	MODELING OF EOS IN SILICON DEVICES	81	[132-138]
17517-21	SEMICONDUCTOR DEVICE FAILURE CRITERIA FOR SINUSOIDAL STRESSES	81	[139-144]
17517-22	DETERMINING AN EMITTER-BASE FAILURE THRESHOLD DISTRIBUTION OF NPN TRANSISTORS	81	[145-150]
17517-23	EOS/ESD FAILURE THRESHOLD ANALYSIS ERRORS, THEIR SOURCE, SIZE AND CONTROL	81	[151-166]
17517-24	AN OVERVIEW OF EOS EFFECTS ON PASSIVE COMPONENTS	81	[167-173]
17517-25	PULSE POWER RESPONSE AND DAMAGE CHARACTERISTICS OF CAPACITORS	81	[174-191]
17517-26	PREDICTION OF THIN-FILM RESISTOR BURNOUT	81	[192-197]
17517-27	BEHAVIOR OF THICK-FILM POWER RESISTORS SUBJECTED TO LARGE MOMENTARY OVERLOADS	81	[198-201]
17517-28	EOS THRESHOLD DETERMINATION OF ELECTRO-EXPLOSIVE DEVICES	81	[202-207]
17517-29	POTENTIAL ESD HAZARDS ASSOCIATED WITH EXPLOSIVE PRIMERS	81	[208-211]
17517-30	LIGHTNING PROTECTION FOR COMPUTER DATA LINES	81	[212-218]
17517-31	FAILURE ANALYSIS OF SEMICONDUCTOR DEVICES IN EOS/ESD TESTING	81	[219-224]
17517-32	TIME-RELATED IMPROVEMENTS OF ELECTRICAL CHARACTERISTICS IN ELECTROSTATICALLY DAMAGED OPERATIONAL AMPLIFIERS	81	[225-228]
17517-33	EOS DAMAGE IN SILICON SOLAR CELLS	81	[209-235]
17517-34	EVALUATION OF ELECTROSTATIC DISCHARGE TO 16K EPROMS	81	[236-241]
17517-35	NON-LINEAR KINETICS OF SEMICONDUCTOR JUNCTION THERMAL FAILURE	81	[242-245]
17516- 1	PASSIVE STATIC PROTECTION: THEORY AND PRACTICE	80	[1-11]
17516- 2	THE EFFECTS OF HIGH HUMIDITY ENVIRONMENTS ON ELECTROSTATIC GENERATION AND DISCHARGE	80	[12-16]

EOS/ESD SYMPOSIUM INDEX

INDEX TERM-CATEGORY DOCUMENT-SEQUENCE NO.	TITLE	YEAR	PAGES
EOS/ESD [SEMICONDUCTOR TECHNOLOGY]			
17516- 3	ESD DAMAGE FROM TRIBOELECTRICALLY CHARGED IC PINS	80	[17-22]
17516- 4	ELECTROSTATIC DISCHARGE (ESD) MONITOR DESIGN	80	[23-25]
17516- 5	TRANSIENT PROTECTION WITH ZNO VARISTORS: TECHNICAL CONSIDERATIONS	80	[26-34]
17516- 6	PROTECTION LEVEL COMPARISONS FOR VOLTAGE TRANSIENT SUPPRESSORS (120 V, AC TYPE)	80	[35-43]
17516- 7	GAS TUBE SURGE ARRESTERS FOR CONTROL OF TRANSIENT VOLTAGES	80	[44-53]
17516- 8	IDENTIFICATION OF LATENT ESD FAILURES	80	[54-57]
17516- 9	STUDY OF EFFECTS OF ELECTRO-STATIC DISCHARGE ON SOLID-STATE DEVICES	80	[58]
17516-10	FAILURE THRESHOLD DISTRIBUTIONS IN BIPOLAR TRANSISTORS	80	[59-66]
17516-11	ANALYSIS OF ESD DAMAGE IN JFET PREAMPLIFIERS	80	[67-72]
17516-12	PROTECTION OF MOS INTEGRATED CIRCUITS FROM DESTRUCTION BY ELECTROSTATIC DISCHARGE	80	[73-80]
17516-13	SOS PROTECTION: THE DESIGN PROBLEM	80	[81-86]
17516-14	LSI DESIGN CONSIDERATIONS FOR ESD PROTECTION STRUCTURES RELATED TO PROCESS AND LAYOUT VARIATIONS	80	[87-94]
17516-15	ELECTROSTATIC SENSITIVITY OF VARIOUS INPUT PROTECTION NETWORKS	80	[95-103]
17516-16	SURPRISING PATTERNS OF CMOS SUSCEPTIBILITY TO ESD AND IMPLICATIONS ON LONG-TERM RELIABILITY	80	[104-111]
17516-17	HIGH-FIELD PHENOMENA AND FAILURE MECHANISMS IN BIPOLAR TRANSISTORS	80	[112-116]
17516-18	SOME DESIGN CRITERIA FOR AVOIDING SECOND BREAKDOWN IN BIPOLAR DEVICES	80	[117-121]
17516-19	EFFECT OF JUNCTION SPIKES AND DOPING LEVEL ON THE SECOND BREAKDOWN SUSCEPTIBILITY OF SILICON-ON-SAPPHIRE DIODES	80	[122-129]
17516-20	OSCILLATING VOLTAGE PULSES AND SECOND BREAKDOWN	80	[130-139]
17516-21	ASSESSING ELECTRICAL OVERSTRESS EFFECTS ON ELECTRONIC SYSTEMS	80	[140-148]
17516-22	SCALAR CELL ELECTRICAL OVERSTRESS ANALYSIS	80	[149-153]
17516-23	AN OVERVIEW OF THE SOURCES AND EFFECTS OF ELECTRICAL OVERSTRESS	80	[154-160]
17516-24	TEST WAVEFORMS AND TECHNIQUES TO ASSESS THE THREAT TO ELECTRONIC DEVICES OF LIGHTNING-INDUCED TRANSIENTS	80	[161-166]
17516-25	LIGHTNING PROTECTION DESIGN FOR A PHOTOVOLTAIC CONCENTRATOR	80	[167-175]
17516-26	SURGE TESTS ON PLUG-IN TRANSFORMERS	80	[176-183]
17516-27	MICROCIRCUIT ELECTRICAL OVERSTRESS TOLERANCE TESTING AND QUALIFICATION	80	[184-188]
17516-28	AN EFFECTIVE ESD AWARENESS TRAINING PROGRAM	80	[189-191]
17516-29	FACILITY EVALUATION: ISOLATING ENVIRONMENTAL ESD PROBLEMS	80	[192-205]
17516-30	BASIC CONSIDERATIONS IN ELECTRO-THERMAL OVERSTRESS IN ELECTRONIC COMPONENTS	80	[206-212]
17516-31	STATIC CONTROL SYSTEMS	80	[213-217]
17516-32	AN EVALUATION OF WRIST STRAP PARAMETERS	80	[218-224]
17516-33	MEASUREMENT OF FAST TRANSIENTS AND APPLICATION TO HUMAN ESD	80	[225-230]
17515- 1	AN EFFECTIVE ESD AWARENESS TRAINING PROGRAM	79	[1-3]
17515- 2	CONTROLLING ELECTROSTATIC PROBLEMS IN THE FABRICATION AND HANDLING OF SPACECRAFT HARDWARE	79	[4-6]
17515- 3	ELECTROSTATIC CONDUCTIVITY CHARACTERISTICS OF WORKBENCH-TOP SURFACE MATERIALS	79	[7-12]
17515- 4	STATIC CONTROL USING TOPICAL ANTISTATS	79	[13-21]
17515- 5	THE GENERATION OF ELECTROSTATIC CHARGES IN SILICONE ENCAPSULANTS DURING CYCLIC GASEOUS PRESSURE TESTS	79	[22-26]
17515- 6	PROPOSED MIL-STD AND MIL-HDBK FOR AN ELECTROSTATIC DISCHARGE CONTROL PROGRAM - BACKGROUND AND STATUS	79	[27-35]
17515- 7	MODULE ELECTROSTATIC DISCHARGE SIMULATOR	79	[36-40]
17515- 8	RELIABILITY OF EOS SCREENED GOLD DOPED 4002 CMOS DEVICES	79	[41-44]
17515- 9	THE DEFICIENCIES IN MILITARY SPECIFICATION MIL-B-81705: CONSIDERATIONS AND A SIMPLE MODEL FOR STATIC PROTECTION	79	[45-54]
17515-10	ELECTRO-STATIC DISCHARGE AND CMOS LOGIC	79	[55-63]
17515-11	EFFECTS OF ELECTRICAL OVERSTRESS ON DIGITAL BIPOLAR MICROCIRCUITS AND ANALYSIS TECHNIQUES FOR FAILURE SITE LOCATION	79	[64-77]
17515-12	DYNAMIC WAVEFORM CHARACTERISTICS OF PERSONNEL ELECTROSTATIC DISCHARGE	79	[78-87]
17515-13	FAILURE ANALYSIS OF MICROCIRCUITS SUBJECTED TO ELECTRICAL OVERSTRESS	79	[88-96]
17515-14	ELECTROSTATIC FAILURE OF X-BAND SILICON SCHOTTKY BARRIER DIODES	79	[97-103]
17515-15	ESD SUSCEPTIBILITIES OF HIGH PERFORMANCE ANALOG INTEGRATED CIRCUITS	79	[104-108]
17515-16	DOPING PROFILES AND SECOND BREAKDOWN	79	[109-115]
17515-17	REVERSE-BIAS SECOND BREAKDOWN IN POWER TRANSISTORS	79	[116-121]
17515-18	HUMAN FACTORS IN ELECTROSTATIC DISCHARGE PROTECTION	79	[122-125]
17515-19	AN ELECTROTHERMAL MODEL FOR CURRENT FILAMENTATION IN SECOND BREAKDOWN OF SILICON-ON-SAPPHIRE DIODES	79	[126-132]
17515-20	MODELING OF ELECTRICAL OVERSTRESS IN SILICON DEVICES	79	[133-139]
17515-21	SQUARE PULSE AND RF PULSE OVERSTRESSING OF UHF TRANSISTORS	79	[140-146]

EOS/ESD SYMPOSIUM INDEX

INDEX TERM-CATEGORY DOCUMENT-SEQUENCE NO.	TITLE	YEAR	PAGES
EOS/ESD [SEMICONDUCTOR TECHNOLOGY]			
17515-22	MICROWAVE NANOSECOND PULSE BURNOUT PROPERTIES OF ONE MICRON MESFETS	79	[147-157]
17515-23	DAMAGE RESPONSE OF SELECTED INTERFACE INTEGRATED CIRCUITS TO A SIMULATED EMP	79	[158-167]
17515-24	SUSCEPTIBILITY OF LSI MOS TO ELECTROSTATIC DISCHARGE AT ELEVATED TEMPERATURE	79	[168-175]
17515-25	THE DIELECTRIC STRENGTH OF SiO ₂ IN A CMOS TRANSISTOR STRUCTURE	79	[176-182]
17515-26	ELECTRICAL OVERSTRESS VERSUS DEVICE GEOMETRY	79	[183-187]
17515-27	THE PHANTOM EMITTER-AN ESD-RESISTANT BIPOLAR TRANSISTOR DESIGN AND ITS APPLICATIONS TO LINEAR INTEGRATED CIRCUITS	79	[188-192]
17515-28	ELECTROSTATIC DISCHARGE PROTECTION USING SILICON TRANSIENT SUPPRESSORS	79	[193-197]
17515-29	STATISTICAL FAILURE ANALYSIS OF MILITARY SYSTEMS FOR HIGH-ALTITUDE EMP	79	[198-204]
17515-30	THE ANALYSIS AND ELIMINATION OF EOS INDUCED SECONDARY FAILURE MECHANISMS	79	[205-209]
ESD CONTROL PROGRAM [ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]			
18305- 1	A REALISTIC AND SYSTEMATIC ESD CONTROL PLAN	84	[1-6]
18172- 1	ESD-HOW OFTEN DOES IT HAPPEN?	83	[1-5]
18172- 2	ESD CONTROL IMPLEMENTATION AND COST AVOIDANCE ANALYSIS	83	[6-11]
18172- 3	THE PRODUCTION OPERATOR: WEAK LINK OR WARRIOR IN THE ESD BATTLE?	83	[12-16]
18172- 5	AIR FORCE MAINTENANCE PROGRAM FOR ELECTRICAL OVERSTRESS/ELECTROSTATIC DISCHARGE (EOS/ESD) CONTROL	83	[21-28]
18214-23	UNIFORM ESD PROTECTION IN A LARGE MULTI-DEPARTMENT ASSEMBLY PLANT	82	[165-168]
18214-25	IN-CIRCUIT ANALYSIS OF ESD DAMAGED DEVICES	82	[175-178]
18214-26	ELECTROSTATIC DISCHARGE AT THE PRODUCT LEVEL	82	[179-184]
18214-27	ELECTROSTATIC DISCHARGE IMMUNITY IN COMPUTER SYSTEMS	82	[185-189]
17517- 4	THE PERFECT "10" - CAN YOU REALLY HAVE ONE?	81	[21-27]
17517- 5	THE ECONOMIC BENEFITS OF AN EFFECTIVE ESD AWARENESS AND CONTROL PROGRAM - AN EMPIRICAL ANALYSIS	81	[29-33]
17516- 1	PASSIVE STATIC PROTECTION: THEORY AND PRACTICE	80	[1-11]
17516- 2	THE EFFECTS OF HIGH HUMIDITY ENVIRONMENTS ON ELECTROSTATIC GENERATION AND DISCHARGE	80	[12-16]
17516- 4	ELECTROSTATIC DISCHARGE (ESD) MONITOR DESIGN	80	[23-25]
17516-28	AN EFFECTIVE ESD AWARENESS TRAINING PROGRAM	80	[189-191]
17516-29	FACILITY EVALUATION: ISOLATING ENVIRONMENTAL ESD PROBLEMS	80	[192-205]
17515- 1	AN EFFECTIVE ESD AWARENESS TRAINING PROGRAM	79	[1-3]
17515- 2	CONTROLLING ELECTROSTATIC PROBLEMS IN THE FABRICATION AND HANDLING OF SPACECRAFT HARDWARE	79	[4-6]
17515- 6	PROPOSED MIL-STD AND MIL-HDBK FOR AN ELECTROSTATIC DISCHARGE CONTROL PROGRAM - BACKGROUND AND STATUS	79	[27-35]
17515-18	HUMAN FACTORS IN ELECTROSTATIC DISCHARGE PROTECTION	79	[122-125]
ESD PROTECTIVE MATERIAL [ESD, MATERIALS AND EQUIPMENT, TESTING]			
18305- 2	HAZARDS OF STATIC CHARGES AND FIELDS AT THE WORK STATION	84	[7-19]
18305- 8	STATIC-ELECTRIC CHARACTERIZATION OF SEMI-INSULATING MATERIALS	84	[45-49]
18305-15	TESTING OF ELECTROSTATIC MATERIALS FED. STD. 101C, METHOD 4046.1	84	[97-103]
18172- 2	ESD CONTROL IMPLEMENTATION AND COST AVOIDANCE ANALYSIS	83	[6-11]
18172- 6	ESD BY STATIC INDUCTION	83	[29-36]
18172-13	PERMANENCE OF THE ANTISTATIC PROPERTY OF COMMERCIAL ANTISTATIC BAGS AND TOTE BOXES	83	[87-94]
18172-14	COPLANAR TRIBOELECTRIFICATION OF SELECTED MATERIALS	83	[95-101]
18214-13	TEST METHODS FOR STATIC CONTROL PRODUCTS	82	[94-109]
18214-15	ELECTROACTIVE POLYMERS AS ALTERNATE ESD PROTECTIVE MATERIALS	82	[115-119]
18214-19	BASIC SPECIFICATION FOR ESD PROTECTION IN INDUSTRY	82	[136-141]
17517- 5	THE ECONOMIC BENEFITS OF AN EFFECTIVE ESD AWARENESS AND CONTROL PROGRAM - AN EMPIRICAL ANALYSIS	81	[29-33]
17517- 7	A LOW-COST PROGRAM FOR EVALUATION OF ESD PROTECTIVE MATERIALS AND EQUIPMENT	81	[41-43]
17517- 9	CHO-TRAP, A NOVEL VOLTAGE TRANSIENT PROTECTION PACKAGING MATERIAL	81	[49-56]
17517-12	SELECTION OF PACKAGING MATERIALS FOR ESD SENSITIVE ITEMS	81	[75-84]
17516-28	AN EFFECTIVE ESD AWARENESS TRAINING PROGRAM	80	[189-191]
17516-29	FACILITY EVALUATION: ISOLATING ENVIRONMENTAL ESD PROBLEMS	80	[192-205]
17515- 2	CONTROLLING ELECTROSTATIC PROBLEMS IN THE FABRICATION AND HANDLING OF SPACECRAFT HARDWARE	79	[4-6]
17515- 3	ELECTROSTATIC CONDUCTIVITY CHARACTERISTICS OF WORKBENCH-TOP SURFACE MATERIALS	79	[7-12]
17515- 6	PROPOSED MIL-STD AND MIL-HDBK FOR AN ELECTROSTATIC DISCHARGE CONTROL PROGRAM - BACKGROUND AND STATUS	79	[27-35]

EOS/ESD SYMPOSIUM INDEX

INDEX TERM-CATEGORY DOCUMENT-SEQUENCE NO.	TITLE	YEAR	PAGES
ESD PROTECTIVE MATERIAL [ESD, MATERIALS AND EQUIPMENT, TESTING]			
17515- 9	THE DEFICIENCIES IN MILITARY SPECIFICATION MIL-B-81705: CONSIDERATIONS AND A SIMPLE MODEL FOR STATIC PROTECTION	79	[45-54]
ESD STD AND HANDBOOK [ESD, STANDARDS, HANDBOOKS, MANUALS]			
18305- 3	TEST EQUIPMENT--A SOURCE OF ESD!!	84	[20-21]
18305-15	TESTING OF ELECTROSTATIC MATERIALS FED. STD. 101C, METHOD 4046.1	84	[97-103]
18305-23	DEGRADATION BY ESD TRANSIENTS OF THE SUBSTRATE BIAS VOLTAGE OF NMOS 8085-TYPE MICROPROCESSORS	84	[165-178]
18172- 5	AIR FORCE MAINTENANCE PROGRAM FOR ELECTRICAL OVERSTRESS/ELECTROSTATIC DISCHARGE (EOS/ESD) CONTROL	83	[21-28]
18172-13	PERMANENCE OF THE ANTISTATIC PROPERTY OF COMMERCIAL ANTISTATIC BAGS AND TOTE BOXES	83	[87-94]
18172-20	ESD EVALUATION OF RADIATION-HARDENED, HIGH RELIABILITY CMOS AND MNOS ICS	83	[134-146]
18172-21	THE EFFECT OF ESD ON CCD RELIABILITY	83	[147-153]
18214- 1	ESD SUSCEPTIBILITY TESTING OF ADVANCED SCHOTTKY TTL	82	[1-12]
18214- 5	LATENT ESD FAILURES	82	[41-48]
18214- 6	A SURVEY OF EOS/ESD DATA SOURCES	82	[49-55]
18214-13	TEST METHODS FOR STATIC CONTROL PRODUCTS	82	[94-109]
17517- 7	A LOW-COST PROGRAM FOR EVALUATION OF ESD PROTECTIVE MATERIALS AND EQUIPMENT	81	[41-43]
17517- 8	AN ANALYSIS OF ANTISTATIC CUSHIONING MATERIALS	81	[44-48]
17517-12	SELECTION OF PACKAGING MATERIALS FOR ESD SENSITIVE ITEMS	81	[75-84]
17517-19	AN OVERVIEW OF EOS EFFECTS ON SEMICONDUCTOR DEVICES	81	[120-131]
17517-32	TIME-RELATED IMPROVEMENTS OF ELECTRICAL CHARACTERISTICS IN ELECTROSTATICALLY DAMAGED OPERATIONAL AMPLIFIERS	81	[225-228]
17516- 1	PASSIVE STATIC PROTECTION: THEORY AND PRACTICE	80	[1-11]
17516-23	AN OVERVIEW OF THE SOURCES AND EFFECTS OF ELECTRICAL OVERSTRESS	80	[154-160]
17515- 6	PROPOSED MIL-STD AND MIL-HDBK FOR AN ELECTROSTATIC DISCHARGE CONTROL PROGRAM - BACKGROUND AND STATUS	79	[27-35]
17515- 8	RELIABILITY OF EOS SCREENED GOLD DOPED 4002 CMOS DEVICES	79	[41-44]
17515- 9	THE DEFICIENCIES IN MILITARY SPECIFICATION MIL-B-81705: CONSIDERATIONS AND A SIMPLE MODEL FOR STATIC PROTECTION	79	[45-54]
ESD SUSCEPTIBILITY TESTING [ESD, DEVICE, TESTING METHODS]			
18305-22	DETERMINATION OF THRESHOLD ENERGIES AND DAMAGE MECHANISMS IN SEMICONDUCTOR DEVICES SUBJECTED TO VOLTAGE TRANSIENTS	84	[157-164]
18305-23	DEGRADATION BY ESD TRANSIENTS OF THE SUBSTRATE BIAS VOLTAGE OF NMOS 8085-TYPE MICROPROCESSORS	84	[165-178]
18305-24	DEVICE ESD SUSCEPTIBILITY TESTING AND DESIGN HARDENING	84	[179-188]
18305-25	A FAILURE ANALYSIS METHODOLOGY FOR REVEALING ESD DAMAGE TO INTEGRATED CIRCUITS	84	[189-195]
18305-26	ESD SENSITIVITY AND LATENCY EFFECTS OF SOME HCMOS INTEGRATED CIRCUITS	84	[196-201]
18172- 1	ESD-HOW OFTEN DOES IT HAPPEN?	83	[1-5]
18172- 9	POWER FAILURE MODELING OF INTEGRATED CIRCUITS	83	[56-62]
18172-16	MODELING AND TESTING FOR SECOND BREAKDOWN PHENOMENA	83	[108-117]
18172-18	SEMICONDUCTOR JUNCTION NON-LINEAR FAILURE POWER THRESHOLDS: WUNSCH-BELL REVISITED	83	[122-127]
18172-19	ESD SENSITIVITY OF COMPLEX ICS	83	[128-133]
18172-20	ESD EVALUATION OF RADIATION-HARDENED, HIGH RELIABILITY CMOS AND MNOS ICS	83	[134-146]
18172-27	ESD SENSITIVITY OF NMOS LSI CIRCUITS AND THEIR FAILURE CHARACTERISTICS	83	[185-197]
18214- 1	ESD SUSCEPTIBILITY TESTING OF ADVANCED SCHOTTKY TTL	82	[1-12]
18214- 2	ELECTROSTATIC DISCHARGE (ESD) DAMAGE SUSCEPTIBILITY OF THIN FILM RESISTORS AND CAPACITORS	82	[13-18]
18214- 3	LIMITATIONS IN MODELING ELECTRICAL OVERSTRESS FAILURE IN SEMICONDUCTOR DEVICES	82	[19-33]
18214- 4	ELECTRICAL OVERSTRESS THRESHOLD TESTING	82	[34-40]
18214- 5	LATENT ESD FAILURES	82	[41-48]
18214- 7	MODELING METALLIZATION BURNOUT OF INTEGRATED CIRCUITS	82	[56-61]
18214- 9	THE FORWARD-BIAS CHARACTERISTIC AS A PREDICTOR AND SCREEN OF REVERSE-BIAS SECOND BREAKDOWN	82	[71-75]
18214-10	MODELING OF CURRENT AND THERMAL MODE SECOND BREAKDOWN PHENOMENA	82	[76-81]
18214-11	A PROBABILISTIC ESTIMATOR FOR BOUNDING TRANSISTOR EMITTER-BASE JUNCTION TRANSIENT-INDUCED FAILURES	82	[82-90]
18214-21	AN EFFECTIVE ELECTROSTATIC DISCHARGE PROTECTION PROGRAM	82	[145-156]

EOS/ESD SYMPOSIUM INDEX

INDEX TERM-CATEGORY DOCUMENT-SEQUENCE NO.	TITLE	YEAR	PAGES
ESD SUSCEPTIBILITY TESTING [ESD, DEVICE, TESTING METHODS]			
18214-22	ESD MINIMIZATION TECHNIQUE FOR MOS MANUFACTURING FINAL TEST AREA	82	[157-164]
18214-25	IN-CIRCUIT ANALYSIS OF ESD DAMAGED DEVICES	82	[175-178]
17517- 3	ANALYSIS OF ESD FAILURES	81	[14-20]
17517- 4	THE PERFECT "10" - CAN YOU REALLY HAVE ONE?	81	[21-27]
17517- 9	CHO-TRAP, A NOVEL VOLTAGE TRANSIENT PROTECTION PACKAGING MATERIAL	81	[49-56]
17517-13	THE EFFECTS OF VLSI SCALING ON EOS/ESD FAILURE THRESHOLD	81	[85-89]
17517-14	ON CHIP PROTECTION OF HIGH DENSITY NMOS DEVICES	81	[90-96]
17517-16	DIAGNOSIS AND ANALYSIS OF EMITTER-BASE JUNCTION OVERSTRESS DAMAGE	81	[101-105]
17517-17	SUSCEPTIBILITY OF ICS IN ESD STEP-STRESS TESTS	81	[106-113]
17517-18	ELECTRICAL OVERSTRESS INVESTIGATIONS IN MODERN INTEGRATED CIRCUIT TECHNOLOGIES	81	[114-119]
17517-19	AN OVERVIEW OF EOS EFFECTS ON SEMICONDUCTOR DEVICES	81	[120-131]
17517-21	SEMICONDUCTOR DEVICE FAILURE CRITERIA FOR SINUSOIDAL STRESSES	81	[139-144]
17517-22	DETERMINING AN EMITTER-BASE FAILURE THRESHOLD DISTRIBUTION OF NPN TRANSISTORS	81	[145-150]
17517-23	EOS/ESD FAILURE THRESHOLD ANALYSIS ERRORS, THEIR SOURCE, SIZE AND CONTROL	81	[151-166]
17517-24	AN OVERVIEW OF EOS EFFECTS ON PASSIVE COMPONENTS	81	[167-173]
17517-25	PULSE POWER RESPONSE AND DAMAGE CHARACTERISTICS OF CAPACITORS	81	[174-191]
17517-26	PREDICTION OF THIN-FILM RESISTOR BURNOUT	81	[192-197]
17517-27	BEHAVIOR OF THICK-FILM POWER RESISTORS SUBJECTED TO LARGE MOMENTARY OVERLOADS	81	[198-201]
17517-31	FAILURE ANALYSIS OF SEMICONDUCTOR DEVICES IN EOS/ESD TESTING	81	[219-224]
17517-32	TIME-RELATED IMPROVEMENTS OF ELECTRICAL CHARACTERISTICS IN ELECTROSTATICALLY DAMAGED OPERATIONAL AMPLIFIERS	81	[225-228]
17517-33	EOS DAMAGE IN SILICON SOLAR CELLS	81	[209-235]
17517-34	EVALUATION OF ELECTROSTATIC DISCHARGE TO 16K EPROMS	81	[236-241]
17517-35	NON-LINEAR KINETICS OF SEMICONDUCTOR JUNCTION THERMAL FAILURE	81	[242-245]
17516- 3	ESD DAMAGE FROM TRIBOELECTRICALLY CHARGED IC PINS	80	[17-22]
17516- 9	STUDY OF EFFECTS OF ELECTRO-STATIC DISCHARGE ON SOLID-STATE DEVICES	80	[58]
17516-10	FAILURE THRESHOLD DISTRIBUTIONS IN BIPOLAR TRANSISTORS	80	[59-66]
17516-11	ANALYSIS OF ESD DAMAGE IN JFET PREAMPLIFIERS	80	[67-72]
17516-12	PROTECTION OF MOS INTEGRATED CIRCUITS FROM DESTRUCTION BY ELECTROSTATIC DISCHARGE	80	[73-80]
17516-14	LSI DESIGN CONSIDERATIONS FOR ESD PROTECTION STRUCTURES RELATED TO PROCESS AND LAYOUT VARIATIONS	80	[87-94]
17516-15	ELECTROSTATIC SENSITIVITY OF VARIOUS INPUT PROTECTION NETWORKS	80	[95-103]
17516-16	SUPRISING PATTERNS OF CMOS SUSCEPTIBILITY TO ESD AND IMPLICATIONS ON LONG-TERM RELIABILITY	80	[104-111]
17516-17	HIGH-FIELD PHENOMENA AND FAILURE MECHANISMS IN BIPOLAR TRANSISTORS	80	[112-116]
17516-18	SOME DESIGN CRITERIA FOR AVOIDING SECOND BREAKDOWN IN BIPOLAR DEVICES	80	[117-121]
17516-19	EFFECT OF JUNCTION SPIKES AND DOPING LEVEL ON THE SECOND BREAKDOWN SUSCEPTIBILITY OF SILICON-ON-SAPPHIRE DIODES	80	[122-129]
17516-20	OSCILLATING VOLTAGE PULSES AND SECOND BREAKDOWN	80	[130-139]
17516-21	ASSESSING ELECTRICAL OVERSTRESS EFFECTS ON ELECTRONIC SYSTEMS	80	[140-148]
17516-22	SOLAR CELL ELECTRICAL OVERSTRESS ANALYSIS	80	[149-153]
17516-23	AN OVERVIEW OF THE SOURCES AND EFFECTS OF ELECTRICAL OVERSTRESS	80	[154-160]
17516-27	MICROCIRCUIT ELECTRICAL OVERSTRESS TOLERANCE TESTING AND QUALIFICATION	80	[184-188]
17515- 5	THE GENERATION OF ELECTROSTATIC CHARGES IN SILICONE ENCAPSULANTS DURING CYCLIC GASEOUS PRESSURE TESTS	79	[22-26]
17515- 6	PROPOSED MIL-STD AND MIL-HDBK FOR AN ELECTROSTATIC DISCHARGE CONTROL PROGRAM - BACKGROUND AND STATUS	79	[27-35]
17515- 8	RELIABILITY OF EOS SCREENED GOLD DOPED 4002 CMOS DEVICES	79	[41-44]
17515- 9	THE DEFICIENCIES IN MILITARY SPECIFICATION MIL-B-81705: CONSIDERATIONS AND A SIMPLE MODEL FOR STATIC PROTECTION	79	[45-54]
17515-10	ELECTRO-STATIC DISCHARGE AND CMOS LOGIC	79	[55-63]
17515-11	EFFECTS OF ELECTRICAL OVERSTRESS ON DIGITAL BIPOLAR MICROCIRCUITS AND ANALYSIS TECHNIQUES FOR FAILURE SITE LOCATION	79	[64-77]
17515-12	DYNAMIC WAVEFORM CHARACTERISTICS OF PERSONNEL ELECTROSTATIC DISCHARGE	79	[78-87]
17515-14	ELECTROSTATIC FAILURE OF X-BAND SILICON SCHOTTKY BARRIER DIODES	79	[97-103]
17515-15	ESD SUSCEPTIBILITIES OF HIGH PERFORMANCE ANALOG INTEGRATED CIRCUITS	79	[104-108]
17515-16	DOPING PROFILES AND SECOND BREAKDOWN	79	[109-115]
17515-17	REVERSE-BIAS SECOND BREAKDOWN IN POWER TRANSISTORS	79	[116-121]
17515-21	SQUARE PULSE AND RF PULSE OVERSTRESSING OF UHF TRANSISTORS	79	[140-146]
17515-22	MICROWAVE NANOSECOND PULSE BURNOUT PROPERTIES OF ONE MICRON MESFETS	79	[147-157]
17515-23	DAMAGE RESPONSE OF SELECTED INTERFACE INTEGRATED CIRCUITS TO A SIMULATED EMP	79	[158-167]
17515-24	SUSCEPTIBILITY OF LSI MOS TO ELECTROSTATIC DISCHARGE AT ELEVATED TEMPERATURE	79	[168-175]

EOS/ESD SYMPOSIUM INDEX

INDEX TERM-CATEGORY DOCUMENT-SEQUENCE NO.

TITLE

YEAR PAGES

ESD SUSCEPTIBILITY TESTING [ESD, DEVICE, TESTING METHODS]

17515-25	THE DIELECTRIC STRENGTH OF SIO ₂ IN A CMOS TRANSISTOR STRUCTURE	79	[176-182]
17515-27	THE PHANTOM EMITTER-AN ESD-RESISTANT BIPOLAR TRANSISTOR DESIGN AND ITS APPLICATIONS TO LINEAR INTEGRATED CIRCUITS	79	[188-192]
17515-29	STATISTICAL FAILURE ANALYSIS OF MILITARY SYSTEMS FOR HIGH-ALTITUDE EMP	79	[198-204]
17515-30	THE ANALYSIS AND ELIMINATION OF EOS INDUCED SECONDARY FAILURE MECHANISMS	79	[205-209]

EVALUATION TEST [TEST TECHNIQUES FOR REL. ASSESSMENT, SEMICONDUCTOR TECHNOLOGY]

18172-20	ESD EVALUATION OF RADIATION-HARDENED, HIGH RELIABILITY CMOS AND MNOS ICS	83	[134-146]
18214-16	DRASTIC LOSSES OF CONDUCTIVITY IN ANTISTATIC PLASTICS	82	[120-123]
17517-11	INCOMING INSPECTION OF ANTISTATIC PACKAGING MATERIALS	81	[65-74]
17517-12	SELECTION OF PACKAGING MATERIALS FOR ESD SENSITIVE ITEMS	81	[75-84]
17515- 4	STATIC CONTROL USING TOPICAL ANTISTATS	79	[13-21]
17515-16	DOPING PROFILES AND SECOND BREAKDOWN	79	[109-115]

FABRICATION EQUIPMENT [FABRICATION PROCESSES & TECHNIQUES, SEMICONDUCTOR TECHNOLOGY]

18305- 2	HAZARDS OF STATIC CHARGES AND FIELDS AT THE WORK STATION	84	[7-19]
17515- 7	MODULE ELECTROSTATIC DISCHARGE SIMULATOR	79	[36-40]

FABRICATION PROCESSES & TECHNIQUES [SEMICONDUCTOR TECHNOLOGY]

18305- 2	HAZARDS OF STATIC CHARGES AND FIELDS AT THE WORK STATION	84	[7-19]
18305- 6	EFFECTS OF AIR IONS AND ELECTRIC FIELDS ON HEALTH AND PRODUCTIVITY	84	[34-39]
18172-13	PERMANENCE OF THE ANTISTATIC PROPERTY OF COMMERCIAL ANTISTATIC BAGS AND TOTE BOXES	83	[87-94]
18214-11	A PROBABILISTIC ESTIMATOR FOR BOUNDING TRANSISTOR EMITTER-BASE JUNCTION TRANSIENT-INDUCED FAILURES	82	[82-90]
18214-14	METALLOPLASTICS	82	[110-114]
17517-13	THE EFFECTS OF VLSI SCALING ON EOS/ESD FAILURE THRESHOLD	81	[85-89]
17515- 3	ELECTROSTATIC CONDUCTIVITY CHARACTERISTICS OF WORKBENCH-TOP SURFACE MATERIALS	79	[7-12]
17515-12	DYNAMIC WAVEFORM CHARACTERISTICS OF PERSONNEL ELECTROSTATIC DISCHARGE	79	[78-87]
17515-25	THE DIELECTRIC STRENGTH OF SIO ₂ IN A CMOS TRANSISTOR STRUCTURE	79	[176-182]
17515-26	ELECTRICAL OVERSTRESS VERSUS DEVICE GEOMETRY	79	[183-187]

FAILURE ANALYSIS RESULTS [FAILURE ANALYSIS, SEMICONDUCTOR TECHNOLOGY]

18172-19	ESD SENSITIVITY OF COMPLEX ICS	83	[128-133]
18172-20	ESD EVALUATION OF RADIATION-HARDENED, HIGH RELIABILITY CMOS AND MNOS ICS	83	[134-146]
18172-21	THE EFFECT OF ESD ON CCD RELIABILITY	83	[147-153]
18172-22	EOS OR ESD: CAN FAILURE ANALYSIS TELL THE DIFFERENCE?	83	[154-157]
18172-23	INVISIBLE EOS/ESD DAMAGE: HOW TO FIND IT	83	[158-167]
18172-26	A SUMMARY OF MOST EFFECTIVE ELECTROSTATIC DISCHARGE PROTECTION CIRCUITS FOR MOS MEMORIES AND THEIR OBSERVED FAILURE MODES	83	[181-184]
18172-27	ESD SENSITIVITY OF NMOS LSI CIRCUITS AND THEIR FAILURE CHARACTERISTICS	83	[185-197]
17517- 3	ANALYSIS OF ESD FAILURES	81	[14-20]
17517-12	SELECTION OF PACKAGING MATERIALS FOR ESD SENSITIVE ITEMS	81	[75-84]
17517-31	FAILURE ANALYSIS OF SEMICONDUCTOR DEVICES IN EOS/ESD TESTING	81	[219-224]
17516-11	ANALYSIS OF ESD DAMAGE IN JFET PREAMPLIFIERS	80	[67-72]
17516-22	SOLAR CELL ELECTRICAL OVERSTRESS ANALYSIS	80	[149-153]
17515-23	DAMAGE RESPONSE OF SELECTED INTERFACE INTEGRATED CIRCUITS TO A SIMULATED EMP	79	[158-167]
17515-24	SUSCEPTIBILITY OF LSI MOS TO ELECTROSTATIC DISCHARGE AT ELEVATED TEMPERATURE	79	[168-175]
17515-29	STATISTICAL FAILURE ANALYSIS OF MILITARY SYSTEMS FOR HIGH-ALTITUDE EMP	79	[198-204]
17515-30	THE ANALYSIS AND ELIMINATION OF EOS INDUCED SECONDARY FAILURE MECHANISMS	79	[205-209]

FAILURE ANALYSIS TECHNIQUES [FAILURE ANALYSIS, SEMICONDUCTOR TECHNOLOGY]

18305-24	DEVICE ESD SUSCEPTIBILITY TESTING AND DESIGN HARDENING	84	[179-188]
17517-22	DETERMINING AN EMITTER-BASE FAILURE THRESHOLD DISTRIBUTION OF NPN TRANSISTORS	81	[145-150]

FAILURE CAUSE [FAILURE ANALYSIS, SEMICONDUCTOR TECHNOLOGY]

17517-16	DIAGNOSIS AND ANALYSIS OF EMITTER-BASE JUNCTION OVERSTRESS DAMAGE	81	[101-105]
----------	---	----	-----------

EOS/ESD SYMPOSIUM INDEX

DEX TERM-CATEGORY CUMENT-SEQUENCE NO.	TITLE	YEAR	PAGES
ILURE CAUSE [FAILURE ANALYSIS, SEMICONDUCTOR TECHNOLOGY]			
7517-29	POTENTIAL ESD HAZARDS ASSOCIATED WITH EXPLOSIVE PRIMERS	81	[208-211]
7515-29	STATISTICAL FAILURE ANALYSIS OF MILITARY SYSTEMS FOR HIGH-ALTITUDE EMP	79	[198-204]
ILURE CHARACTERIZATION [SEMICONDUCTOR TECHNOLOGY]			
8172-16	MODELING AND TESTING FOR SECOND BREAKDOWN PHENOMENA	83	[108-117]
8172-27	ESD SENSITIVITY OF NMOS LSI CIRCUITS AND THEIR FAILURE CHARACTERISTICS	83	[185-197]
8214- 6	A SURVEY OF EOS/ESD DATA SOURCES	82	[49-55]
7517-21	SEMICONDUCTOR DEVICE FAILURE CRITERIA FOR SINUSOIDAL STRESSES	81	[139-144]
7517-24	AN OVERVIEW OF EOS EFFECTS ON PASSIVE COMPONENTS	81	[167-173]
7517-28	EOS THRESHOLD DETERMINATION OF ELECTRO-EXPLOSIVE DEVICES	81	[202-207]
7516-17	HIGH-FIELD PHENOMENA AND FAILURE MECHANISMS IN BIPOLAR TRANSISTORS	80	[112-116]
ILURE INDICATOR [FAILURE ANALYSIS, SEMICONDUCTOR TECHNOLOGY]			
8172-22	EOS OR ESD: CAN FAILURE ANALYSIS TELL THE DIFFERENCE?	83	[154-157]
8172-23	INVISIBLE EOS/ESD DAMAGE: HOW TO FIND IT	83	[158-167]
ILURE MODES [FAILURE ANALYSIS, SEMICONDUCTOR TECHNOLOGY]			
8305-24	DEVICE ESD SUSCEPTIBILITY TESTING AND DESIGN HARDENING	84	[179-188]
8172-26	A SUMMARY OF MOST EFFECTIVE ELECTROSTATIC DISCHARGE PROTECTION CIRCUITS FOR MOS MEMORIES AND THEIR OBSERVED FAILURE MODES	83	[181-184]
8214- 5	LATENT ESD FAILURES	82	[41-48]
17517-19	AN OVERVIEW OF EOS EFFECTS ON SEMICONDUCTOR DEVICES	81	[120-131]
17516- 3	ESD DAMAGE FROM TRIBOELECTRICALLY CHARGED IC PINS	80	[17-22]
17516- 8	IDENTIFICATION OF LATENT ESD FAILURES	80	[54-57]
17515-22	MICROWAVE NANOSECOND PULSE BURNOUT PROPERTIES OF ONE MICRON MESFETS	79	[147-157]
17515-25	THE DIELECTRIC STRENGTH OF SiO2 IN A CMOS TRANSISTOR STRUCTURE	79	[176-182]
IELD EFFECT,(FET) [SEMICONDUCTOR TECHNOLOGY]			
17515- 7	MODULE ELECTROSTATIC DISCHARGE SIMULATOR	79	[36-40]
17515-22	MICROWAVE NANOSECOND PULSE BURNOUT PROPERTIES OF ONE MICRON MESFETS	79	[147-157]
LOOR SURFACE [ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]			
18172- 4	ANALYSIS OF ELECTROSTATIC CHARGE PROPENSITY OF FLOOR FINISHES	83	[17-20]
18214-17	CHARACTERIZATION OF ESD SAFE REQUIREMENTS FOR FLOOR SURFACES	82	[124-130]
18214-21	AN EFFECTIVE ELECTROSTATIC DISCHARGE PROTECTION PROGRAM	82	[145-156]
17517- 2	QUANTITATIVE EFFECTS OF RELATIVE & ABSOLUTE HUMIDITY ON ESD GENERATION/ SUPPRESSION	81	[9-13]
17516- 2	THE EFFECTS OF HIGH HUMIDITY ENVIRONMENTS ON ELECTROSTATIC GENERATION AND DISCHARGE	80	[12-16]
MEA/FMECA,(FAILURE MODE EFFECTS) [RELIABILITY MODELING TECHNIQUES, RELIABILITY MODELS/DATA/ANALYSIS]			
17515-13	FAILURE ANALYSIS OF MICROCIRCUITS SUBJECTED TO ELECTRICAL OVERSTRESS	79	[88-96]
UTURE TRENDS [SEMICONDUCTOR TECHNOLOGY]			
18214-20	FSD IN I.C. ASSEMBLY (A BASE LINE SOLUTION)	82	[142-144]
18214-21	AN EFFECTIVE ELECTROSTATIC DISCHARGE PROTECTION PROGRAM	82	[145-156]
18214-24	CIRCUIT DESIGN FOR EOS/ESD PROTECTION	82	[169-174]
18214-25	IN-CIRCUIT ANALYSIS OF ESD DAMAGED DEVICES	82	[175-178]
18214-27	ELECTROSTATIC DISCHARGE IMMUNITY IN COMPUTER SYSTEMS	82	[185-189]
17517-18	ELECTRICAL OVERSTRESS INVESTIGATIONS IN MODERN INTEGRATED CIRCUIT TECHNOLOGIES	81	[114-119]
17515- 2	CONTROLLING ELECTROSTATIC PROBLEMS IN THE FABRICATION AND HANDLING OF SPACECRAFT HARDWARE	79	[4-6]
17515- 7	MODULE ELECTROSTATIC DISCHARGE SIMULATOR	79	[36-40]
17515-28	ELECTROSTATIC DISCHARGE PROTECTION USING SILICON TRANSIENT SUPPRESSORS	79	[193-197]

EOS/ESD SYMPOSIUM INDEX

DEX TERM-CATEGORY CUMENT-SEQUENCE NO.	TITLE	YEAR	PAGES
OMETRIES/LAYOUT [DESIGN CONSIDERATIONS, SEMICONDUCTOR TECHNOLOGY]			
8172- 8	A PROGRAMMABLE EQUIPMENT FOR ELECTROSTATIC DISCHARGE TESTING TO HUMAN BODY MODELS	83	[48-55]
7516-15	ELECTROSTATIC SENSITIVITY OF VARIOUS INPUT PROTECTION NETWORKS	80	[95-103]
7515-26	ELECTRICAL OVERSTRESS VERSUS DEVICE GEOMETRY	79	[183-187]
7515-27	THE PHANTOM EMITTER-AN ESD-RESISTANT BIPOLAR TRANSISTOR DESIGN AND ITS APPLICATIONS TO LINEAR INTEGRATED CIRCUITS	79	[188-192]
APHICAL TECHNIQUES [RELIABILITY MODELING TECHNIQUES, RELIABILITY MODELS/DATA/ANALYSIS]			
7515-16	DOPING PROFILES AND SECOND BREAKDOWN	79	[109-115]
OUNDING METHODS [ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]			
8305-13	A MATERIAL EVALUATION PROGRAM FOR DECORATIVE STATIC CONTROL TABLE TOP LAMINATES	84	[85-93]
8214-20	ESD IN I.C. ASSEMBLY (A BASE LINE SOLUTION)	82	[142-144]
8214-28	ELECTRICAL GROUNDING IN LARGE INSTRUMENTATION SYSTEMS	82	[190-202]
7516- 1	PASSIVE STATIC PROTECTION: THEORY AND PRACTICE	80	[1-11]
7516-25	LIGHTNING PROTECTION DESIGN FOR A PHOTOVOLTAIC CONCENTRATOR	80	[167-175]
7515- 3	ELECTROSTATIC CONDUCTIVITY CHARACTERISTICS OF WORKBENCH-TOP SURFACE MATERIALS	79	[7-12]
OUNDING STRAPS [ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]			
8305-14	A WRIST STRAP LIFE TEST PROGRAM	84	[94-96]
17517- 5	THE ECONOMIC BENEFITS OF AN EFFECTIVE ESD AWARENESS AND CONTROL PROGRAM - AN EMPIRICAL ANALYSIS	81	[29-33]
17517- 6	A PRAGMATIC APPROACH TO ESD PROBLEM SOLVING IN THE MANUFACTURING ENVIRONMENT A CASE HISTORY	81	[34-39]
17516-29	FACILITY EVALUATION: ISOLATING ENVIRONMENTAL ESD PROBLEMS	80	[192-205]
17516-32	AN EVALUATION OF WRIST STRAP PARAMETERS	80	[218-224]
17515- 2	CONTROLLING ELECTROSTATIC PROBLEMS IN THE FABRICATION AND HANDLING OF SPACECRAFT HARDWARE	79	[4-6]
UIDE/PROCEDURE [REFERENCE DOCUMENT]			
18172- 2	ESD CONTROL IMPLEMENTATION AND COST AVOIDANCE ANALYSIS	83	[6-11]
18172- 4	ANALYSIS OF ELECTROSTATIC CHARGE PROPENSITY OF FLOOR FINISHES	83	[17-20]
18172- 5	AIR FORCE MAINTENANCE PROGRAM FOR ELECTRICAL OVERSTRESS/ELECTROSTATIC DISCHARGE (EOS/ESD) CONTROL	83	[21-28]
18172- 9	POWER FAILURE MODELING OF INTEGRATED CIRCUITS	83	[56-62]
18172-13	PERMANENCE OF THE ANTISTATIC PROPERTY OF COMMERCIAL ANTISTATIC BAGS AND TOTE BOXES	83	[87-94]
18172-24	METAL OXIDE VARISTORS FOR TRANSIENT PROTECTION OF 3 TO 5-VOLT INTEGRATED CIRCUITS	83	[168-176]
18172-25	USING SCR'S AS TRANSIENT PROTECTION STRUCTURES IN INTEGRATED CIRCUITS	83	[177-180]
18172-26	A SUMMARY OF MOST EFFECTIVE ELECTROSTATIC DISCHARGE PROTECTION CIRCUITS FOR MOS MEMORIES AND THEIR OBSERVED FAILURE MODES	83	[181-184]
18172-28	A STUDY OF ESD LATENT DEFECTS IN SEMICONDUCTORS	83	[198-204]
18214-27	ELECTROSTATIC DISCHARGE IMMUNITY IN COMPUTER SYSTEMS	82	[185-189]
17517- 7	A LOW-COST PROGRAM FOR EVALUATION OF ESD PROTECTIVE MATERIALS AND EQUIPMENT	81	[41-43]
17517-10	EVALUATION OF INTEGRATED CIRCUIT SHIPPING TUBES	81	[57-64]
17517-11	INCOMING INSPECTION OF ANTISTATIC PACKAGING MATERIALS	81	[65-74]
17517-17	SUSCEPTIBILITY OF ICS IN ESD STEP-STRESS TESTS	81	[106-113]
17515- 1	AN EFFECTIVE ESD AWARENESS TRAINING PROGRAM	79	[1-3]
17515- 2	CONTROLLING ELECTROSTATIC PROBLEMS IN THE FABRICATION AND HANDLING OF SPACECRAFT HARDWARE	79	[4-6]
17515- 3	ELECTROSTATIC CONDUCTIVITY CHARACTERISTICS OF WORKBENCH-TOP SURFACE MATERIALS	79	[7-12]
17515- 4	STATIC CONTROL USING TOPICAL ANTISTATS	79	[13-21]
17515-18	HUMAN FACTORS IN ELECTROSTATIC DISCHARGE PROTECTION	79	[122-125]
17515-19	AN ELECTROTHERMAL MODEL FOR CURRENT FILAMENTATION IN SECOND BREAKDOWN OF SILICON-ON-SAPPHIRE DIODES	79	[126-132]
17515-21	SQUARE PULSE AND RF PULSE OVERSTRESSING OF UHF TRANSISTORS	79	[140-146]
17515-24	SUSCEPTIBILITY OF LSI MOS TO ELECTROSTATIC DISCHARGE AT ELEVATED TEMPERATURE	79	[168-175]
17515-26	ELECTRICAL OVERSTRESS VERSUS DEVICE GEOMETRY	79	[183-187]

EOS/ESD SYMPOSIUM INDEX

TERM-CATEGORY MENT-SEQUENCE NO.	TITLE	YEAR	PAGES
E/PROCEDURE [REFERENCE DOCUMENT]			
15-30	THE ANALYSIS AND ELIMINATION OF EOS INDUCED SECONDARY FAILURE MECHANISMS	79	[205-209]
O/COPTOR [APPLICATION ENVIRONMENT]			
15-18	HUMAN FACTORS IN ELECTROSTATIC DISCHARGE PROTECTION	79	[122-125]
N BODY ESD MODEL [ESD, DEVICE, TESTING METHODS]			
05- 1	A REALISTIC AND SYSTEMATIC ESD CONTROL PLAN	84	[1-6]
05- 5	ELECTROSTATIC MEASUREMENT FOR PROCESS CONTROL	84	[25-33]
05-16	CRITICAL CONSIDERATIONS FOR ESD TESTING	84	[104-111]
05-17	DESIGNING TO AVOID STATIC - ESD TESTING OF DIGITAL DEVICES	84	[112-123]
05-23	DEGRADATION BY ESD TRANSIENTS OF THE SUBSTRATE BIAS VOLTAGE OF NMOS 8085-TYPE MICROPROCESSORS	84	[165-178]
05-25	A FAILURE ANALYSIS METHODOLOGY FOR REVEALING ESD DAMAGE TO INTEGRATED CIRCUITS	84	[189-195]
72- 1	ESD-HOW OFTEN DOES IT HAPPEN?	83	[1-5]
72- 8	A PROGRAMMABLE EQUIPMENT FOR ELECTROSTATIC DISCHARGE TESTING TO HUMAN BODY MODELS	83	[48-55]
72-20	ESD EVALUATION OF RADIATION-HARDENED, HIGH RELIABILITY CMOS AND MNOS ICS	83	[134-146]
72-27	ESD SENSITIVITY OF NMOS LSI CIRCUITS AND THEIR FAILURE CHARACTERISTICS	83	[185-197]
14- 2	ELECTROSTATIC DISCHARGE (ESD) DAMAGE SUSCEPTIBILITY OF THIN FILM RESISTORS AND CAPACITORS	82	[13-18]
14-24	CIRCUIT DESIGN FOR EOS/ESD PROTECTION	82	[169-174]
17- 1	A CLOSER LOOK AT THE HUMAN ESD EVENT	81	[1-8]
17- 9	CHO-TRAP, A NOVEL VOLTAGE TRANSIENT PROTECTION PACKAGING MATERIAL	81	[49-56]
17-10	EVALUATION OF INTEGRATED CIRCUIT SHIPPING TUBES	81	[57-64]
17-29	POTENTIAL ESD HAZARDS ASSOCIATED WITH EXPLOSIVE PRIMERS	81	[208-211]
17-32	TIME-RELATED IMPROVEMENTS OF ELECTRICAL CHARACTERISTICS IN ELECTROSTATICALLY DAMAGED OPERATIONAL AMPLIFIERS	81	[225-228]
17-34	EVALUATION OF ELECTROSTATIC DISCHARGE TO 16K EPROMS	81	[236-241]
16-12	PROTECTION OF MOS INTEGRATED CIRCUITS FROM DESTRUCTION BY ELECTROSTATIC DISCHARGE	80	[73-80]
15- 7	MODULE ELECTROSTATIC DISCHARGE SIMULATOR	79	[36-40]
15-15	ESD SUSCEPTIBILITIES OF HIGH PERFORMANCE ANALOG INTEGRATED CIRCUITS	79	[104-108]
N FACTORS [SYSTEMS]			
72- 3	THE PRODUCTION OPERATOR: WEAK LINK OR WARRIOR IN THE ESD BATTLE?	83	[12-16]
72- 5	AIR FORCE MAINTENANCE PROGRAM FOR ELECTRICAL OVERSTRESS/ELECTROSTATIC DISCHARGE (EOS/ESD) CONTROL	83	[21-28]
14-21	AN EFFECTIVE ELECTROSTATIC DISCHARGE PROTECTION PROGRAM	82	[145-156]
CTIVE CHARGING [ESD, EOS/ESD PHYSICS]			
05- 9	ESTIMATION OF DISCHARGE ENERGY RELEASED FROM CHARGED INSULATOR	84	[50-57]
72- 6	ESD BY STATIC INDUCTION	83	[29-36]
16-33	MEASUREMENT OF FAST TRANSIENTS AND APPLICATION TO HUMAN ESD	80	[225-230]
T PROTECTION [ESD, DEVICE, PROTECTIVE DEVICES/INPUT PROTECTION]			
05-27	A CMOS VLSI ESD INPUT PROTECTION DEVICE, DIFIDW	84	[202-209]
14-24	CIRCUIT DESIGN FOR EOS/ESD PROTECTION	82	[169-174]
17-13	THE EFFECTS OF VLSI SCALING ON EOS/ESD FAILURE THRESHOLD	81	[85-89]
17-14	ON CHIP PROTECTION OF HIGH DENSITY NMOS DEVICES	81	[90-96]
17-15	INPUT PROTECTION DESIGN FOR THE 3-MICRON NMOS PROCESS	81	[97-100]
17-18	ELECTRICAL OVERSTRESS INVESTIGATIONS IN MODERN INTEGRATED CIRCUIT TECHNOLOGIES	81	[114-119]
16- 5	TRANSIENT PROTECTION WITH ZNO VARISTORS: TECHNICAL CONSIDERATIONS	80	[26-34]
16- 6	PROTECTION LEVEL COMPARISONS FOR VOLTAGE TRANSIENT SUPPRESSORS (120 V, AC TYPE)	80	[35-43]
16- 7	GAS TUBE SURGE ARRESTERS FOR CONTROL OF TRANSIENT VOLTAGES	80	[44-53]
16- 9	STUDY OF EFFECTS OF ELECTRO-STATIC DISCHARGE ON SOLID-STATE DEVICES	80	[58]
16-13	SOS PROTECTION: THE DESIGN PROBLEM	80	[81-86]
16-15	ELECTROSTATIC SENSITIVITY OF VARIOUS INPUT PROTECTION NETWORKS	80	[95-103]
16-26	SURGE TESTS ON PLUG-IN TRANSFORMERS	80	[176-183]

EOS/ESD SYMPOSIUM INDEX

TERM-CATEGORY IDENT-SEQUENCE NO.	TITLE	YEAR	PAGES
[PROTECTION [ESD, DEVICE, PROTECTIVE DEVICES/INPUT PROTECTION]			
15-13	FAILURE ANALYSIS OF MICROCIRCUITS SUBJECTED TO ELECTRICAL OVERSTRESS	79	[88-96]
15-18	HUMAN FACTORS IN ELECTROSTATIC DISCHARGE PROTECTION	79	[122-125]
15-26	ELECTRICAL OVERSTRESS VERSUS DEVICE GEOMETRY	79	[183-187]
[FIELD EFFECT,(FET), SEMICONDUCTOR TECHNOLOGY]			
16-11	ANALYSIS OF ESD DAMAGE IN JFET PREAMPLIFIERS	80	[67-72]
NT ESD FAILURE [ESD, DEVICE, FAILURE MODES]			
72-28	A STUDY OF ESD LATENT DEFECTS IN SEMICONDUCTORS	83	[198-204]
14- 5	LATENT ESD FAILURES	82	[41-48]
16- 8	IDENTIFICATION OF LATENT ESD FAILURES	80	[54-57]
15-10 ELECTRO-STATIC DISCHARGE AND CMOS LOGIC			
79		[55-63]	
[TEST TECHNIQUES FOR REL. ASSESSMENT, SEMICONDUCTOR TECHNOLOGY]			
05-13	A MATERIAL EVALUATION PROGRAM FOR DECORATIVE STATIC CONTROL TABLE TOP LAMINATES	84	[85-93]
72-21	THE EFFECT OF ESD ON CCD RELIABILITY	83	[147-153]
72-28	A STUDY OF ESD LATENT DEFECTS IN SEMICONDUCTORS	83	[198-204]
14- 5	LATENT ESD FAILURES	82	[41-48]
STICS [SYSTEMS]			
05-11	TRIBOELECTRIC CHARGE: ITS ESD ABILITY AND A MEASUREMENT METHOD FOR ITS PROPENSITY ON PACKING MATERIALS	84	[64-77]
MAINTAINABILITY TECHNIQUES [MAINTAINABILITY, SYSTEMS]			
72- 5	AIR FORCE MAINTENANCE PROGRAM FOR ELECTRICAL OVERSTRESS/ELECTROSTATIC DISCHARGE (EOS/ESD) CONTROL	83	[21-28]
TRIALS [DESIGN CONSIDERATIONS, SEMICONDUCTOR TECHNOLOGY]			
72- 4	ANALYSIS OF ELECTROSTATIC CHARGE PROPENSITY OF FLOOR FINISHES	83	[17-20]
72-13	PERMANENCE OF THE ANTISTATIC PROPERTY OF COMMERCIAL ANTISTATIC BAGS AND TOTE BOXES	83	[87-94]
14-15	ELECTROACTIVE POLYMERS AS ALTERNATE ESD PROTECTIVE MATERIALS	82	[115-119]
14-16	DRASTIC LOSSES OF CONDUCTIVITY IN ANTISTATIC PLASTICS	82	[120-123]
14-18	ESD AND CONTAMINATION FROM CLEAN ROOM GARMENTS - PROBLEMS AND SOLUTIONS	82	[131-135]
17- 2	QUANTITATIVE EFFECTS OF RELATIVE & ABSOLUTE HUMIDITY ON ESD GENERATION/SUPPRESSION	81	[9-13]
17- 8	AN ANALYSIS OF ANTISTATIC CUSHIONING MATERIALS	81	[44-48]
17-11	INCOMING INSPECTION OF ANTISTATIC PACKAGING MATERIALS	81	[65-74]
17-12	SELECTION OF PACKAGING MATERIALS FOR ESD SENSITIVE ITEMS	81	[75-84]
16-30	BASIC CONSIDERATIONS IN ELECTRO-THERMAL OVERSTRESS IN ELECTRONIC COMPONENTS	80	[206-212]
15- 3	ELECTROSTATIC CONDUCTIVITY CHARACTERISTICS OF WORKBENCH-TOP SURFACE MATERIALS	79	[7-12]
THERMAL ANALYSIS			
72-17	TEMPERATURE AT SECOND BREAKDOWN AT A WELL-DEFINED SITE	83	[118-121]
72-18	SEMICONDUCTOR JUNCTION NON-LINEAR FAILURE POWER THRESHOLDS: WUNSCH-BELL REVISITED	83	[122-127]
14- 7	MODELING METALLIZATION BURNOUT OF INTEGRATED CIRCUITS	82	[56-61]
14- 8	AN IMPROVED EOS CONDUCTION MODEL OF SEMICONDUCT DEVICES	82	[62-70]
14- 9	THE FORWARD-BIAS CHARACTERISTIC AS A PREDICTOR AND SCREEN OF REVERSE-BIAS SECOND BREAKDOWN	82	[71-75]
14-10	MODELING OF CURRENT AND THERMAL MODE SECOND BREAKDOWN PHENOMENA	82	[76-81]
17-21	SEMICONDUCTOR DEVICE FAILURE CRITERIA FOR SINUSOIDAL STRESSES	81	[139-144]
17-26	PREDICTION OF THIN-FILM RESISTOR BURNOUT	81	[192-197]

EOS/ESD SYMPOSIUM INDEX

FORM-CATEGORY -SEQUENCE NO.	TITLE	YEAR	PAGES
RAP [ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]			
12	AN EVALUATION OF WRIST STRAP PARAMETERS	80	[218-224]
2	CONTROLLING ELECTROSTATIC PROBLEMS IN THE FABRICATION AND HANDLING OF SPACECRAFT HARDWARE	79	[4-6]
BELL MODEL [ESD, DEVICE, TESTING METHODS]			
18	SEMICONDUCTOR JUNCTION NON-LINEAR FAILURE POWER THRESHOLDS: WUNSCH-BELL REVISITED	83	[122-127]
2	ELECTROSTATIC DISCHARGE (ESD) DAMAGE SUSCEPTIBILITY OF THIN FILM RESISTORS AND CAPACITORS	82	[13-18]
3	LIMITATIONS IN MODELING ELECTRICAL OVERSTRESS FAILURE IN SEMICONDUCTOR DEVICES	82	[19-33]
8	AN IMPROVED EOS CONDUCTION MODEL OF SEMICONDUCTOR DEVICES	82	[62-70]
18	ELECTRICAL OVERSTRESS INVESTIGATIONS IN MODERN INTEGRATED CIRCUIT TECHNOLOGIES	81	[114-119]
19	AN OVERVIEW OF EOS EFFECTS ON SEMICONDUCTOR DEVICES	81	[120-131]
20	MODELING OF EOS IN SILICON DEVICES	81	[132-138]
22	DETERMINING AN EMITTER-BASE FAILURE THRESHOLD DISTRIBUTION OF NPN TRANSISTORS	81	[145-150]
35	NON-LINEAR KINETICS OF SEMICONDUCTOR JUNCTION THERMAL FAILURE	81	[242-245]
3	ESD DAMAGE FROM TRIBOELECTRICALLY CHARGED IC PINS	80	[17-22]
18	SOME DESIGN CRITERIA FOR AVOIDING SECOND BREAKDOWN IN BIPOLAR DEVICES	80	[117-121]
22	SOLAR CELL ELECTRICAL OVERSTRESS ANALYSIS	80	[149-153]
13	FAILURE ANALYSIS OF MICROCIRCUITS SUBJECTED TO ELECTRICAL OVERSTRESS	79	[88-96]

EOS/ESD SYMPOSIUM INDEX

ERM-CATEGORY

[SEQUENCE NO.]

TITLE

YEAR

PAGES

FOR [DISCRETE SEMICONDUCTOR, SEMICONDUCTOR DEVICE]

10	FAILURE THRESHOLD DISTRIBUTIONS IN BIPOLAR TRANSISTORS	80	[59-66]
17	HIGH-FIELD PHENOMENA AND FAILURE MECHANISMS IN BIPOLAR TRANSISTORS	80	[112-116]
17	REVERSE-BIAS SECOND BREAKDOWN IN POWER TRANSISTORS	79	[116-121]
21	SQUARE PULSE AND RF PULSE OVERSTRESSING OF UHF TRANSISTORS	79	[140-146]
25	THE DIELECTRIC STRENGTH OF SiO ₂ IN A CMOS TRANSISTOR STRUCTURE	79	[176-182]
27	THE PHANTOM EMITTER-AN ESD-RESISTANT BIPOLAR TRANSISTOR DESIGN AND ITS APPLICATIONS TO LINEAR INTEGRATED CIRCUITS	79	[188-192]

LECTRIC CHARGING [ESD, EOS/ESD PHYSICS]

5	ELECTROSTATIC MEASUREMENT FOR PROCESS CONTROL	84	[25-33]
10	TRIBOELECTRIC TESTING FOR ELECTROSTATIC CHARGES ON MATERIALS AT KENNEDY SPACE CENTER	84	[58-63]
11	TRIBOELECTRIC CHARGE: ITS ESD ABILITY AND A MEASUREMENT METHOD FOR ITS PROPENSITY ON PACKING MATERIALS	84	[64-77]
12	AN EXPERIMENTAL STUDY OF THE ESD SCREENING EFFECTIVENESS OF ANTI-STATIC BAGS	84	[78-84]
15	TESTING OF ELECTROSTATIC MATERIALS FED. STD. 101C, METHOD 4046.1	84	[97-103]
19	SECONDARY DISCHARGE: A NEW JEOPARDY AND A NEW TOOL	84	[131-135]
13	PERMANENCE OF THE ANTISTATIC PROPERTY OF COMMERCIAL ANTISTATIC BAGS AND TOTE BOXES	83	[87-94]
14	COPLANAR TRIBOELECTRIFICATION OF SELECTED MATERIALS	93	[95-101]
13	TEST METHODS FOR STATIC CONTROL PRODUCTS	82	[94-109]
16	DRASTIC LOSSES OF CONDUCTIVITY IN ANTISTATIC PLASTICS	82	[120-123]
17	CHARACTERIZATION OF ESD SAFE REQUIREMENTS FOR FLOOR SURFACES	82	[124-130]
22	ESD MINIMIZATION TECHNIQUE FOR MOS MANUFACTURING FINAL TEST AREA	82	[157-164]
8	AN ANALYSIS OF ANTISTATIC CUSHIONING MATERIALS	81	[44-48]
10	EVALUATION OF INTEGRATED CIRCUIT SHIPPING TUBES	81	[57-64]
29	POTENTIAL ESD HAZARDS ASSOCIATED WITH EXPLOSIVE PRIMERS	81	[208-211]
3	ESD DAMAGE FROM TRIBOELECTRICALLY CHARGED IC PINS	80	[17-22]
4	STATIC CONTROL USING TOPICAL ANTISTATS	79	[13-21]
5	THE GENERATION OF ELECTROSTATIC CHARGES IN SILICONE ENCAPSULANTS DURING CYCLIC GASEOUS PRESSURE TESTS	79	[22-26]
9	THE DEFICIENCIES IN MILITARY SPECIFICATION MIL-B-81705: CONSIDERATIONS AND A SIMPLE MODEL FOR STATIC PROTECTION	79	[45-54]

IPOLAR, COMPONENT TYPE]

1	ESD SUSCEPTIBILITY TESTING OF ADVANCED SCHOTTKY TTL	82	[1-12]
9	STUDY OF EFFECTS OF ELECTRO-STATIC DISCHARGE ON SOLID-STATE DEVICES	80	[58]

RESISTIVITY [ESD, MATERIALS AND EQUIPMENT, TESTING]

11	INCOMING INSPECTION OF ANTISTATIC PACKAGING MATERIALS	81	[65-74]
	[EQUIPMENT TYPE/FUNCTION]		
29	POTENTIAL ESD HAZARDS ASSOCIATED WITH EXPLOSIVE PRIMERS	81	[208-211]
	[STATISTICAL ANALYSIS]		
22	DETERMINING AN EMITTER-BASE FAILURE THRESHOLD DISTRIBUTION OF NPN TRANSISTORS	81	[145-150]
10	ELECTRO-STATIC DISCHARGE AND CMOS LOGIC	79	[55-63]

SHIP [FAILURE CAUSE, FAILURE ANALYSIS, SEMICONDUCTOR TECHNOLOGY]

4	THE PERFECT "10" - CAN YOU REALLY HAVE ONE?	81	[21-27]
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TRAP [ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]

2	HAZARDS OF STATIC CHARGES AND FIELDS AT THE WORK STATION	84	[7-19]
14	A WRIST STRAP LIFE TEST PROGRAM	84	[94-96]
13	TEST METHODS FOR STATIC CONTROL PRODUCTS	82	[94-109]
21	AN EFFECTIVE ELECTROSTATIC DISCHARGE PROTECTION PROGRAM	82	[145-156]

EOS/ESD SYMPOSIUM INDEX

INDEX TERM-CATEGORY DOCUMENT-SEQUENCE NO.	TITLE	YEAR	PAGES
THERMAL SECONDARY BREAKDOWN [ESD, DEVICE, FAILURE MODES]			
8172-17	TEMPERATURE AT SECOND BREAKDOWN AT A WELL-DEFINED SITE	83	[118-121]
8214- 3	LIMITATIONS IN MODELING ELECTRICAL OVERSTRESS FAILURE IN SEMICONDUCTOR DEVICES	82	[19-33]
8214-10	MODELING OF CURRENT AND THERMAL MODE SECOND BREAKDOWN PHENOMENA	82	[76-81]
7517-31	FAILURE ANALYSIS OF SEMICONDUCTOR DEVICES IN EOS/ESD TESTING	81	[219-224]
7516-18	SOME DESIGN CRITERIA FOR AVOIDING SECOND BREAKDOWN IN BIPOLAR DEVICES	80	[117-121]
7516-19	EFFECT OF JUNCTION SPIKES AND DOPING LEVEL ON THE SECOND BREAKDOWN SUSCEPTIBILITY OF SILICON-ON-SAPPHIRE DIODES	80	[122-129]
7516-22	SOLAR CELL ELECTRICAL OVERSTRESS ANALYSIS	80	[149-153]
7515-17	REVERSE-BIAS SECOND BREAKDOWN IN POWER TRANSISTORS	79	[116-121]
THERMAL STRESS/STRAIN [MECHANICAL & PHYSICAL FAILURE PHENOMENA, SEMICONDUCTOR TECHNOLOGY]			
8172-17	TEMPERATURE AT SECOND BREAKDOWN AT A WELL-DEFINED SITE	83	[118-121]
TOLERANCES [DESIGN CONSIDERATIONS, SEMICONDUCTOR TECHNOLOGY]			
8305-16	CRITICAL CONSIDERATIONS FOR ESD TESTING	84	[104-111]
8172-12	MEASURING EFFECTIVENESS OF AIR IONIZERS	83	[76-86]
8214-15	ELECTROACTIVE POLYMERS AS ALTERNATE ESD PROTECTIVE MATERIALS	82	[115-119]
TYPICAL ANTISTATS [ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]			
7517- 8	AN ANALYSIS OF ANTISTATIC CUSHIONING MATERIALS	81	[44-48]
7517-12	SELECTION OF PACKAGING MATERIALS FOR ESD SENSITIVE ITEMS	81	[75-84]
7516-29	FACILITY EVALUATION: ISOLATING ENVIRONMENTAL ESD PROBLEMS	80	[192-205]
7515- 3	ELECTROSTATIC CONDUCTIVITY CHARACTERISTICS OF WORKBENCH-TOP SURFACE MATERIALS	79	[7-12]
7515- 4	STATIC CONTROL USING TOPICAL ANTISTATS	79	[13-21]
TYPICAL OFFS [DESIGN CONSIDERATIONS, SEMICONDUCTOR TECHNOLOGY]			
8172-10	STATIC SURVEY METERS	83	[63-66]
8172-13	PERMANENCE OF THE ANTISTATIC PROPERTY OF COMMERCIAL ANTISTATIC BAGS AND TOTE BOXES	83	[87-94]
8214-13	TEST METHODS FOR STATIC CONTROL PRODUCTS	82	[94-109]
7515- 5	THE GENERATION OF ELECTROSTATIC CHARGES IN SILICONE ENCAPSULANTS DURING CYCLIC GASEOUS PRESSURE TESTS	79	[22-26]
TRANSIENT SUPPRESSORS [ESD, DEVICE, PROTECTIVE DEVICES/INPUT PROTECTION]			
8172-24	METAL OXIDE VARISTORS FOR TRANSIENT PROTECTION OF 3 TO 5-VOLT INTEGRATED CIRCUITS	83	[168-176]
8172-25	USING SCR'S AS TRANSIENT PROTECTION STRUCTURES IN INTEGRATED CIRCUITS	83	[177-180]
7517-30	LIGHTNING PROTECTION FOR COMPUTER DATA LINES	81	[212-218]
7516- 5	TRANSIENT PROTECTION WITH ZNO VARISTORS: TECHNICAL CONSIDERATIONS	80	[26-34]
7516- 6	PROTECTION LEVEL COMPARISONS FOR VOLTAGE TRANSIENT SUPPRESSORS (120 V, AC TYPE)	80	[35-43]
7516- 7	GAS TUBE SURGE ARRESTERS FOR CONTROL OF TRANSIENT VOLTAGES	80	[44-53]
7516-24	TEST WAVEFORMS AND TECHNIQUES TO ASSESS THE THREAT TO ELECTRONIC DEVICES OF LIGHTNING-INDUCED TRANSIENTS	80	[161-166]
7516-25	LIGHTNING PROTECTION DESIGN FOR A PHOTOVOLTAIC CONCENTRATOR	80	[167-175]
7516-26	SURGE TESTS ON PLUG-IN TRANSFORMERS	80	[176-183]
7516-30	BASIC CONSIDERATIONS IN ELECTRO-THERMAL OVERSTRESS IN ELECTRONIC COMPONENTS	80	[206-212]
7515-28	ELECTROSTATIC DISCHARGE PROTECTION USING SILICON TRANSIENT SUPPRESSORS	79	[193-197]
TRANSISTOR [DISCRETE SEMICONDUCTOR, SEMICONDUCTOR DEVICE]			
8305-21	AN EVALUATION OF EOS FAILURE MODELS	84	[144-156]
8172-16	MODELING AND TESTING FOR SECOND BREAKDOWN PHENOMENA	83	[108-117]
8214-11	A PROBABILISTIC ESTIMATOR FOR BOUNDING TRANSISTOR EMITTER-BASE JUNCTION TRANSIENT-INDUCED FAILURES	82	[82-90]
8214-12	SECOND BREAKDOWN IN SWITCHING TRANSISTORS	82	[91-93]
7517-16	DIAGNOSIS AND ANALYSIS OF EMITTER-BASE JUNCTION OVERSTRESS DAMAGE	81	[101-105]
7517-22	DETERMINING AN EMITTER-BASE FAILURE THRESHOLD DISTRIBUTION OF NPN TRANSISTORS	81	[145-150]
7516- 9	STUDY OF EFFECTS OF ELECTRO-STATIC DISCHARGE ON SOLID-STATE DEVICES	80	[58]

EOS/ESD SYMPOSIUM INDEX

DEX TERM-CATEGORY CUMENT-SEQUENCE NO.	TITLE	YEAR	PAGES
ST TECHNIQUES FOR REL. ASSESSMENT [SEMICONDUCTOR TECHNOLOGY]			
8214-28	ELECTRICAL GROUNDING IN LARGE INSTRUMENTATION SYSTEMS	82	[190-202]
7517-16	DIAGNOSIS AND ANALYSIS OF EMITTER-BASE JUNCTION OVERSTRESS DAMAGE	81	[101-105]
7517-18	ELECTRICAL OVERSTRESS INVESTIGATIONS IN MODERN INTEGRATED CIRCUIT TECHNOLOGIES	81	[114-119]
7517-31	FAILURE ANALYSIS OF SEMICONDUCTOR DEVICES IN EOS/ESD TESTING	81	[219-224]
7517-34	EVALUATION OF ELECTROSTATIC DISCHARGE TO 16K EPROMS	81	[236-241]
7516- 6	PROTECTION LEVEL COMPARISONS FOR VOLTAGE TRANSIENT SUPPRESSORS (120 V, AC TYPE)	80	[35-43]
7516-10	FAILURE THRESHOLD DISTRIBUTIONS IN BIPOLAR TRANSISTORS	80	[59-66]
7516-16	SUPRISING PATTERNS OF CMOS SUSCEPTIBILITY TO ESD AND IMPLICATIONS ON LONG-TERM RELIABILITY	80	[104-111]
7516-26	SURGE TESTS ON PLUG-IN TRANSFORMERS	80	[176-183]
7515- 1	AN EFFECTIVE ESD AWARENESS TRAINING PROGRAM	79	[1-3]
7515- 4	STATIC CONTROL USING TOPICAL ANTISTATS	79	[13-21]
7515-10	ELECTRO-STATIC DISCHARGE AND CMOS LOGIC	79	[55-63]
7515-12	DYNAMIC WAVEFORM CHARACTERISTICS OF PERSONNEL ELECTROSTATIC DISCHARGE	79	[78-87]
7515-13	FAILURE ANALYSIS OF MICROCIRCUITS SUBJECTED TO ELECTRICAL OVERSTRESS	79	[88-96]
7515-15	ESD SUSCEPTIBILITIES OF HIGH PERFORMANCE ANALOG INTEGRATED CIRCUITS	79	[104-108]
7515-17	REVERSE-BIAS SECOND BREAKDOWN IN POWER TRANSISTORS	79	[116-121]
7515-18	HUMAN FACTORS IN ELECTROSTATIC DISCHARGE PROTECTION	79	[122-125]
7515-23	DAMAGE RESPONSE OF SELECTED INTERFACE INTEGRATED CIRCUITS TO A SIMULATED EMP	79	[158-167]
ESTING TOOLS & TECHNIQUES [SEMICONDUCTOR TECHNOLOGY]			
18305- 7	A ROOM IONIZATION SYSTEM FOR ELECTROSTATIC CHARGE AND DUST CONTROL	84	[40-44]
18305- 9	ESTIMATION OF DISCHARGE ENERGY RELEASED FROM CHARGED INSULATOR	84	[50-57]
18305-13	A MATERIAL EVALUATION PROGRAM FOR DECORATIVE STATIC CONTROL TABLE TOP LAMINATES	84	[85-93]
18305-14	A WRIST STRAP LIFE TEST PROGRAM	84	[94-96]
18305-15	TESTING OF ELECTROSTATIC MATERIALS FED. STD. 101C, METHOD 4046.1	84	[97-103]
18305-18	EMI CHARACTERISTICS OF ESD IN A SMALL AIR GAP --ARP GOVERNS THE EMI--	84	[124-130]
18172-27	ESD SENSITIVITY OF NMOS LSI CIRCUITS AND THEIR FAILURE CHARACTERISTICS	83	[185-197]
18214- 1	ESD SUSCEPTIBILITY TESTING OF ADVANCED SCHOTTKY TTL	82	[1-12]
18214- 4	ELECTRICAL OVERSTRESS THRESHOLD TESTING	82	[34-40]
18214- 6	A SUREY OF EOS/ESD DATA SOURCES	82	[49-55]
18214-17	CHARACTERIZATION OF ESD SAFE REQUIREMENTS FOR FLOOR SURFACES	82	[124-130]
17517- 1	A CLOSER LOOK AT THE HUMAN ESD EVENT	81	[1-8]
17516- 2	THE EFFECTS OF HIGH HUMIDITY ENVIRONMENTS ON ELECTROSTATIC GENERATION AND DISCHARGE	80	[12-16]
17516- 3	ESD DAMAGE FROM TRIBOELECTRICALLY CHARGED IC PINS	80	[17-22]
17516- 4	ELECTROSTATIC DISCHARGE (ESD) MONITOR DESIGN	80	[23-25]
17516- 8	IDENTIFICATION OF LATENT ESD FAILURES	80	[54-57]
17516-24	TEST WAVEFORMS AND TECHNIQUES TO ASSESS THE THREAT TO ELECTRONIC DEVICES OF LIGHTNING-INDUCED TRANSIENTS	80	[161-166]
17515-21	SQUARE PULSE AND RF PULSE OVERSTRESSING OF UHF TRANSISTORS	79	[140-146]
17515-22	MICROWAVE NANOSECOND PULSE BURNOUT PROPERTIES OF ONE MICRON MESFETS	79	[147-157]
17515-26	ELECTRICAL OVERSTRESS VERSUS DEVICE GEOMETRY	79	[183-187]
17515-27	THE PHANTOM EMITTER-AN ESD-RESISTANT BIPOLAR TRANSISTOR DESIGN AND ITS APPLICATIONS TO LINEAR INTEGRATED CIRCUITS	79	[188-192]
HEORY OF OPERATION [SEMICONDUCTOR TECHNOLOGY]			
18172- 6	ESD BY STATIC INDUCTION	83	[29-36]
18172-12	MEASURING EFFECTIVENESS OF AIR IONIZERS	83	[76-86]
18172-14	COPLANAR TRIBOELECTRIFICATION OF SELECTED MATERIALS	83	[95-101]
17517- 1	A CLOSER LOOK AT THE HUMAN ESD EVENT	81	[1-8]
17517- 2	QUANTITATIVE EFFECTS OF RELATIVE & ABSOLUTE HUMIDITY ON ESD GENERATION/ SUPPRESSION	81	[9-13]
17516- 1	PASSIVE STATIC PROTECTION: THEORY AND PRACTICE	80	[1-11]
HERMAL [TEST STRESS]			
18172-17	TEMPERATURE AT SECOND BREAKDOWN AT A WELL-DEFINED SITE	83	[118-121]
18214-10	MODELING OF CURRENT AND THERMAL MODE SECOND BREAKDOWN PHENOMENA	82	[76-81]
18214-12	SECOND BREAKDOWN IN SWITCHING TRANSISTORS	82	[91-93]
17516-30	BASIC CONSIDERATIONS IN ELECTRO-THERMAL OVERSTRESS IN ELECTRONIC COMPONENTS	80	[206-212]

EOS/ESD SYMPOSIUM INDEX

INDEX TERM-CATEGORY DOCUMENT-SEQUENCE NO.	TITLE	YEAR	PAGES
SYSTEM [LEVEL OF ASSEMBLY]			
17516-21	ASSESSING ELECTRICAL OVERSTRESS EFFECTS ON ELECTRONIC SYSTEMS	80	[140-148]
TEST EQUIPMENT [TESTING TOOLS & TECHNIQUES, SEMICONDUCTOR TECHNOLOGY]			
18305- 3	TEST EQUIPMENT--A SOURCE OF ESD!!	84	[20-21]
18305- 5	ELECTROSTATIC MEASUREMENT FOR PROCESS CONTROL	84	[25-33]
18172- 2	ESD CONTROL IMPLEMENTATION AND COST AVOIDANCE ANALYSIS	83	[6-11]
18172-10	STATIC SURVEY METERS	83	[63-66]
18172-13	PERMANENCE OF THE ANTISTATIC PROPERTY OF COMMERCIAL ANTISTATIC BAGS AND TOTE BOXES	83	[87-94]
18214- 5	LATENT ESD FAILURES	82	[41-48]
17516-31	STATIC CONTROL SYSTEMS	80	[213-217]
17516-32	AN EVALUATION OF WRIST STRAP PARAMETERS	80	[218-224]
TEST PROGRAM DEVELOPMENT [TESTING TOOLS & TECHNIQUES, SEMICONDUCTOR TECHNOLOGY]			
18172- 2	ESD CONTROL IMPLEMENTATION AND COST AVOIDANCE ANALYSIS	83	[6-11]
18172- 3	THE PRODUCTION OPERATOR: WEAK LINK OR WARRIOR IN THE ESD BATTLE?	83	[12-16]
18172- 4	ANALYSIS OF ELECTROSTATIC CHARGE PROPENSITY OF FLOOR FINISHES	83	[17-20]
18172- 9	POWER FAILURE MODELING OF INTEGRATED CIRCUITS	83	[56-62]
18172-13	PERMANENCE OF THE ANTISTATIC PROPERTY OF COMMERCIAL ANTISTATIC BAGS AND TOTE BOXES	83	[87-94]
18214-26	ELECTROSTATIC DISCHARGE AT THE PRODUCT LEVEL	82	[179-184]
17517- 8	AN ANALYSIS OF ANTISTATIC CUSHIONING MATERIALS	81	[44-48]
17515- 7	MODULE ELECTROSTATIC DISCHARGE SIMULATOR	79	[36-40]
TEST SPECIFICATION [TESTING TOOLS & TECHNIQUES, SEMICONDUCTOR TECHNOLOGY]			
18172- 8	A PROGRAMMABLE EQUIPMENT FOR ELECTROSTATIC DISCHARGE TESTING TO HUMAN BODY MODELS	83	[48-55]
18172-19	ESD SENSITIVITY OF COMPLEX ICS	83	[128-133]
18172-28	A STUDY OF ESD LATENT DEFECTS IN SEMICONDUCTORS	83	[198-204]
17517-15	INPUT PROTECTION DESIGN FOR THE 3-MICRON NMOS PROCESS	81	[97-100]
17515- 9	THE DEFICIENCIES IN MILITARY SPECIFICATION MIL-B-81705: CONSIDERATIONS AND A SIMPLE MODEL FOR STATIC PROTECTION	79	[45-54]
17515-26	ELECTRICAL OVERSTRESS VERSUS DEVICE GEOMETRY	79	[183-187]
TEST TECHNIQUES [TESTING TOOLS & TECHNIQUES, SEMICONDUCTOR TECHNOLOGY]			
18305- 5	ELECTROSTATIC MEASUREMENT FOR PROCESS CONTROL	84	[25-33]
18172- 1	ESD-HOW OFTEN DOES IT HAPPEN?	83	[1-5]
18172- 7	CONSTRUCTION AND APPLICATION OF A TESTER FOR MEASURING EOS/ESD THRESHOLDS TO 15KV	83	[37-47]
18172-13	PERMANENCE OF THE ANTISTATIC PROPERTY OF COMMERCIAL ANTISTATIC BAGS AND TOTE BOXES	83	[87-94]
18172-20	ESD EVALUATION OF RADIATION-HARDENED, HIGH RELIABILITY CMOS AND MNOS ICS	83	[134-146]
17517-14	ON CHIP PROTECTION OF HIGH DENSITY NMOS DEVICES	81	[90-96]
TEST TECHNIQUES FOR REL. ASSESSMENT [SEMICONDUCTOR TECHNOLOGY]			
18172- 7	CONSTRUCTION AND APPLICATION OF A TESTER FOR MEASURING EOS/ESD THRESHOLDS TO 15KV	83	[37-47]
18172- 8	A PROGRAMMABLE EQUIPMENT FOR ELECTROSTATIC DISCHARGE TESTING TO HUMAN BODY MODELS	83	[48-55]
18172-11	THE ROOM AIR IONIZATION SYSTEM, A BETTER ALTERNATIVE THAN 40% RELATIVE HUMIDITY	83	[67-75]
18172-12	MEASURING EFFECTIVENESS OF AIR IONIZERS	83	[76-86]
18172-13	PERMANENCE OF THE ANTISTATIC PROPERTY OF COMMERCIAL ANTISTATIC BAGS AND TOTE BOXES	83	[87-94]
18214- 1	ESD SUSCEPTIBILITY TESTING OF ADVANCED SCHOTTKY TTL	82	[1-12]
18214- 3	LIMITATIONS IN MODELING ELECTRICAL OVERSTRESS FAILURE IN SEMICONDUCTOR DEVICES	82	[19-33]
18214-13	TEST METHODS FOR STATIC CONTROL PRODUCTS	82	[94-109]
18214-17	CHARACTERIZATION OF ESD SAFE REQUIREMENTS FOR FLOOR SURFACES	82	[124-130]
18214-22	ESD MINIMIZATION TECHNIQUE FOR MOS MANUFACTURING FINAL TEST AREA	82	[157-164]

EOS/ESD SYMPOSIUM INDEX

INDEX TERM-CATEGORY DOCUMENT-SEQUENCE NO.	TITLE	YEAR	PAGES
STATIC CONTROL [ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]			
18305- 1	A REALISTIC AND SYSTEMATIC ESD CONTROL PLAN	84	[1-6]
18305- 6	EFFECTS OF AIR IONS AND ELECTRIC FIELDS ON HEALTH AND PRODUCTIVITY	84	[34-39]
18172- 2	ESD CONTROL IMPLEMENTATION AND COST AVOIDANCE ANALYSIS	83	[6-11]
18214-18	ESD AND CONTAMINATION FROM CLEAN ROOM GARMENTS - PROBLEMS AND SOLUTIONS	82	[131-135]
18214-20	ESD IN I.C. ASSEMBLY (A BASE LINE SOLUTION)	82	[142-144]
18214-21	AN EFFECTIVE ELECTROSTATIC DISCHARGE PROTECTION PROGRAM	82	[145-156]
18214-22	ESD MINIMIZATION TECHNIQUE FOR MOS MANUFACTURING FINAL TEST AREA	82	[157-164]
18214-23	UNIFORM ESD PROTECTION IN A LARGE MULTI-DEPARTMENT ASSEMBLY PLANT	82	[165-168]
18214-27	ELECTROSTATIC DISCHARGE IMMUNITY IN COMPUTER SYSTEMS	82	[185-189]
17517- 2	QUANTITATIVE EFFECTS OF RELATIVE & ABSOLUTE HUMIDITY ON ESD GENERATION/ SUPPRESSION	81	[9-13]
17517- 5	THE ECONOMIC BENEFITS OF AN EFFECTIVE ESD AWARENESS AND CONTROL PROGRAM - AN EMPIRICAL ANALYSIS	81	[29-33]
17516- 1	PASSIVE STATIC PROTECTION: THEORY AND PRACTICE	80	[1-11]
17516- 5	TRANSIENT PROTECTION WITH ZNO VARISTORS: TECHNICAL CONSIDERATIONS	80	[26-34]
17516- 7	GAS TUBE SURGE ARRESTERS FOR CONTROL OF TRANSIENT VOLTAGES	80	[44-53]
17516-28	AN EFFECTIVE ESD AWARENESS TRAINING PROGRAM	80	[189-191]
17516-29	FACILITY EVALUATION: ISOLATING ENVIRONMENTAL ESD PROBLEMS	80	[192-205]
17516-31	STATIC CONTROL SYSTEMS	80	[213-217]
17515- 1	AN EFFECTIVE ESD AWARENESS TRAINING PROGRAM	79	[1-3]
17515- 6	PROPOSED MIL-STD AND MIL-HDBK FOR AN ELECTROSTATIC DISCHARGE CONTROL PROGRAM - BACKGROUND AND STATUS	79	[27-35]
17515-18	HUMAN FACTORS IN ELECTROSTATIC DISCHARGE PROTECTION	79	[122-125]
STATISTICAL ANALYSIS			
18172-18	SEMICONDUCTOR JUNCTION NON-LINEAR FAILURE POWER THRESHOLDS: WUNSCH-BELL REVISITED	83	[122-127]
17517-31	FAILURE ANALYSIS OF SEMICONDUCTOR DEVICES IN EOS/ESD TESTING	81	[219-224]
STEP STRESS [TEST TECHNIQUES FOR REL. ASSESSMENT, SEMICONDUCTOR TECHNOLOGY]			
18305-26	ESD SENSITIVITY AND LATENCY EFFECTS OF SOME HCMOS INTEGRATED CIRCUITS	84	[196-201]
18214- 1	ESD SUSCEPTIBILITY TESTING OF ADVANCED SCHOTTKY TTL	82	[1-12]
17517-17	SUSCEPTIBILITY OF ICS IN ESD STEP-STRESS TESTS	81	[106-113]
17517-18	ELECTRICAL OVERSTRESS INVESTIGATIONS IN MODERN INTEGRATED CIRCUIT TECHNOLOGIES	81	[114-119]
17515-24	SUSCEPTIBILITY OF LSI MOS TO ELECTROSTATIC DISCHARGE AT ELEVATED TEMPERATURE	79	[168-175]
SURFACE RESISTIVITY [ESD, MATERIALS AND EQUIPMENT, TESTING]			
18305- 2	HAZARDS OF STATIC CHARGES AND FIELDS AT THE WORK STATION	84	[7-19]
18305- 8	STATIC-ELECTRIC CHARACTERIZATION OF SEMI-INSULATING MATERIALS	84	[45-49]
18305-10	TRIBOELECTRIC TESTING FOR ELECTROSTATIC CHARGES ON MATERIALS AT KENNEDY SPACE CENTER	84	[58-63]
18305-11	TRIBOELECTRIC CHARGE: ITS ESD ABILITY AND A MEASUREMENT METHOD FOR ITS PROPENSITY ON PACKING MATERIALS	84	[64-77]
18305-13	A MATERIAL EVALUATION PROGRAM FOR DECORATIVE STATIC CONTROL TABLE TOP LAMINATES	84	[85-93]
18305-15	TESTING OF ELECTROSTATIC MATERIALS FED. STD. 101C, METHOD 4046.1	84	[97-103]
18172-13	PERMANENCE OF THE ANTISTATIC PROPERTY OF COMMERCIAL ANTISTATIC BAGS AND TOTE BOXES	83	[87-94]
18214-13	TEST METHODS FOR STATIC CONTROL PRODUCTS	82	[94-109]
18214-15	ELECTROACTIVE POLYMERS AS ALTERNATE ESD PROTECTIVE MATERIALS	82	[115-119]
18214-16	DRASTIC LOSSES OF CONDUCTIVITY IN ANTISTATIC PLASTICS	82	[120-123]
18214-18	ESD AND CONTAMINATION FROM CLEAN ROOM GARMENTS - PROBLEMS AND SOLUTIONS	82	[131-135]
17517- 7	A LOW-COST PROGRAM FOR EVALUATION OF ESD PROTECTIVE MATERIALS AND EQUIPMENT	81	[41-43]
17517- 8	AN ANALYSIS OF ANTISTATIC CUSHIONING MATERIALS	81	[44-48]
17517-11	INCOMING INSPECTION OF ANTISTATIC PACKAGING MATERIALS	81	[65-74]
17516- 1	PASSIVE STATIC PROTECTION: THEORY AND PRACTICE	80	[1-11]
SYSTEM [LEVEL OF ASSEMBLY]			
18214-26	ELECTROSTATIC DISCHARGE AT THE PRODUCT LEVEL	82	[179-184]
18214-28	ELECTRICAL GROUNDING IN LARGE INSTRUMENTATION SYSTEMS	82	[190-202]

EOS/ESD SYMPOSIUM INDEX

INDEX TERM-CATEGORY DOCUMENT-SEQUENCE NO.	TITLE	YEAR	PAGES
SECONDARY BREAKDOWN [ELECTRICAL FAILURE PHENOMENA, SEMICONDUCTOR TECHNOLOGY]			
18172-16	MODELING AND TESTING FOR SECOND BREAKDOWN PHENOMENA	83	[108-117]
18172-17	TEMPERATURE AT SECOND BREAKDOWN AT A WELL-DEFINED SITE	83	[118-121]
18214- 5	LATENT ESD FAILURES	82	[41-48]
18214- 9	THE FORWARD-BIAS CHARACTERISTIC AS A PREDICTOR AND SCREEN OF REVERSE-BIAS SECOND BREAKDOWN	82	[71-75]
18214-10	MODELING OF CURRENT AND THERMAL MODE SECOND BREAKDOWN PHENOMENA	82	[76-81]
18214-12	SECOND BREAKDOWN IN SWITCHING TRANSISTORS	82	[91-93]
17517-23	EOS/ESD FAILURE THRESHOLD ANALYSIS ERRORS, THEIR SOURCE, SIZE AND CONTROL	81	[151-166]
17516-17	HIGH-FIELD PHENOMENA AND FAILURE MECHANISMS IN BIPOLAR TRANSISTORS	80	[112-116]
17516-19	EFFECT OF JUNCTION SPIKES AND DOPING LEVEL ON THE SECOND BREAKDOWN SUSCEPTIBILITY OF SILICON-ON-SAPPHIRE DIODES	80	[122-129]
17516-20	OSCILLATING VOLTAGE PULSES AND SECOND BREAKDOWN	80	[130-139]
17515-16	DOPING PROFILES AND SECOND BREAKDOWN	79	[109-115]
17515-17	REVERSE-BIAS SECOND BREAKDOWN IN POWER TRANSISTORS	79	[116-121]
17515-19	AN ELECTROTHERMAL MODEL FOR CURRENT FILAMENTATION IN SECOND BREAKDOWN OF SILICON-ON-SAPPHIRE DIODES	79	[126-132]
17515-30	THE ANALYSIS AND ELIMINATION OF EOS INDUCED SECONDARY FAILURE MECHANISMS	79	[205-209]
SEMICONDUCTOR DEVICE			
18172-18	SEMICONDUCTOR JUNCTION NON-LINEAR FAILURE POWER THRESHOLDS: WUNSCH-BELL REVISITED	83	[122-127]
18172-25	USING SCR'S AS TRANSIENT PROTECTION STRUCTURES IN INTEGRATED CIRCUITS	83	[177-180]
18172-28	A STUDY OF ESD LATENT DEFECTS IN SEMICONDUCTORS	83	[198-204]
18214- 3	LIMITATIONS IN MODELING ELECTRICAL OVERSTRESS FAILURE IN SEMICONDUCTOR DEVICES	82	[19-33]
18214- 8	AN IMPROVED EOS CONDUCTION MODEL OF SEMICONDUCT DEVICES	82	[62-70]
18214-20	ESD IN I.C. ASSEMBLY (A BASE LINE SOLUTION)	82	[142-144]
18214-21	AN EFFECTIVE ELECTROSTATIC DISCHARGE PROTECTION PROGRAM	82	[145-156]
17517- 4	THE PERFECT "10" - CAN YOU REALLY HAVE ONE?	81	[21-27]
17517-10	EVALUATION OF INTEGRATED CIRCUIT SHIPPING TUBES	81	[57-64]
17517-14	ON CHIP PROTECTION OF HIGH DENSITY NMOS DEVICES	81	[90-96]
17517-15	INPUT PROTECTION DESIGN FOR THE 3-MICRON NMOS PROCESS	81	[97-100]
17516-23	AN OVERVIEW OF THE SOURCES AND EFFECTS OF ELECTRICAL OVERSTRESS	80	[154-160]
17515- 6	PROPOSED MIL-STD AND MIL-HDBK FOR AN ELECTROSTATIC DISCHARGE CONTROL PROGRAM - BACKGROUND AND STATUS	79	[27-35]
17515-20	MODELING OF ELECTRICAL OVERSTRESS IN SILICON DEVICES	79	[133-139]
SENSITIVE ELECTRONIC DEVICE SYMBOLS [ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]			
17517- 5	THE ECONOMIC BENEFITS OF AN EFFECTIVE ESD AWARENESS AND CONTROL PROGRAM - AN EMPIRICAL ANALYSIS	81	[29-33]
17515- 2	CONTROLLING ELECTROSTATIC PROBLEMS IN THE FABRICATION AND HANDLING OF SPACECRAFT HARDWARE	79	[4-6]
SILICON [SEMICONDUCTOR TECHNOLOGY]			
17517-20	MODELING OF EOS IN SILICON DEVICES	81	[132-138]
SPACE [APPLICATION ENVIRONMENT]			
17515- 2	CONTROLLING ELECTROSTATIC PROBLEMS IN THE FABRICATION AND HANDLING OF SPACECRAFT HARDWARE	79	[4-6]
SPECIFICATION/STANDARD [REFERENCE DOCUMENT]			
18172- 5	AIR FORCE MAINTENANCE PROGRAM FOR ELECTRICAL OVERSTRESS/ELECTROSTATIC DISCHARGE (EOS/ESD) CONTROL	83	[21-28]
18172- 8	A PROGRAMMABLE EQUIPMENT FOR ELECTROSTATIC DISCHARGE TESTING TO HUMAN BODY MODELS	83	[48-55]
18214-19	BASIC SPECIFICATION FOR ESD PROTECTION IN INDUSTRY	82	[136-141]
17515- 6	PROPOSED MIL-STD AND MIL-HDBK FOR AN ELECTROSTATIC DISCHARGE CONTROL PROGRAM - BACKGROUND AND STATUS	79	[27-35]
17515- 9	THE DEFICIENCIES IN MILITARY SPECIFICATION MIL-B-81705: CONSIDERATIONS AND A SIMPLE MODEL FOR STATIC PROTECTION	79	[45-54]

EOS/ESD SYMPOSIUM INDEX

INDEX TERM-CATEGORY DOCUMENT-SEQUENCE NO.	TITLE	YEAR	PAGES
RELATIVE HUMIDITY [ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]			
18214-19	BASIC SPECIFICATION FOR ESD PROTECTION IN INDUSTRY	82	[136-141]
18214-20	ESD IN I.C. ASSEMBLY (A BASE LINE SOLUTION)	82	[142-144]
18214-22	ESD MINIMIZATION TECHNIQUE FOR MOS MANUFACTURING FINAL TEST AREA	82	[157-164]
17517- 2	QUANTITATIVE EFFECTS OF RELATIVE & ABSOLUTE HUMIDITY ON ESD GENERATION/ SUPPRESSION	81	[9-13]
17517- 6	A PRAGMATIC APPROACH TO ESD PROBLEM SOLVING IN THE MANUFACTURING ENVIRONMENT A CASE HISTORY	81	[34-39]
17517- 8	AN ANALYSIS OF ANTISTATIC CUSHIONING MATERIALS	81	[44-48]
17517-11	INCOMING INSPECTION OF ANTISTATIC PACKAGING MATERIALS	81	[65-74]
17517-12	SELECTION OF PACKAGING MATERIALS FOR ESD SENSITIVE ITEMS	81	[75-84]
17517-17	SUSCEPTIBILITY OF ICS IN ESD STEP-STRESS TESTS	81	[106-113]
17516- 2	THE EFFECTS OF HIGH HUMIDITY ENVIRONMENTS ON ELECTROSTATIC GENERATION AND DISCHARGE	80	[12-16]
17515- 3	ELECTROSTATIC CONDUCTIVITY CHARACTERISTICS OF WORKBENCH-TOP SURFACE MATERIALS	79	[7-12]
17515- 4	STATIC CONTROL USING TOPICAL ANTISTATS	79	[13-21]
RELIABILITY [DESIGN CONSIDERATIONS, SEMICONDUCTOR TECHNOLOGY]			
18214- 5	LATENT ESD FAILURES	82	[41-48]
17517-18	ELECTRICAL OVERSTRESS INVESTIGATIONS IN MODERN INTEGRATED CIRCUIT TECHNOLOGIES	81	[114-119]
RELIABILITY [SYSTEMS]			
18214-13	TEST METHODS FOR STATIC CONTROL PRODUCTS	82	[94-109]
17517-24	AN OVERVIEW OF EOS EFFECTS ON PASSIVE COMPONENTS	81	[167-173]
17516-21	ASSESSING ELECTRICAL OVERSTRESS EFFECTS ON ELECTRONIC SYSTEMS	80	[140-148]
17516-23	AN OVERVIEW OF THE SOURCES AND EFFECTS OF ELECTRICAL OVERSTRESS	80	[154-160]
17516-29	FACILITY EVALUATION: ISOLATING ENVIRONMENTAL ESD PROBLEMS	80	[192-205]
RELIABILITY MANAGEMENT TECH [USER OF REL. PREDICTION MODELS]			
17515- 1	AN EFFECTIVE ESD AWARENESS TRAINING PROGRAM	79	[1-3]
RELIABILITY MODELING TECHNIQUES [RELIABILITY MODELS/DATA/ANALYSIS]			
18172- 8	A PROGRAMMABLE EQUIPMENT FOR ELECTROSTATIC DISCHARGE TESTING TO HUMAN BODY MODELS	83	[48-55]
17517-20	MODELING OF EOS IN SILICON DEVICES	81	[132-138]
17517-23	EOS/ESD FAILURE THRESHOLD ANALYSIS ERRORS, THEIR SOURCE, SIZE AND CONTROL	81	[151-166]
17517-33	EOS DAMAGE IN SILICON SOLAR CELLS	81	[209-235]
RESISTOR [PASSIVE DEVICE, COMPONENT TYPE]			
18214- 2	ELECTROSTATIC DISCHARGE (ESD) DAMAGE SUSCEPTIBILITY OF THIN FILM RESISTORS AND CAPACITORS	82	[13-18]
17517-24	AN OVERVIEW OF EOS EFFECTS ON PASSIVE COMPONENTS	81	[167-173]
17517-26	PREDICTION OF THIN-FILM RESISTOR BURNOUT	81	[192-197]
17517-27	BEHAVIOR OF THICK-FILM POWER RESISTORS SUBJECTED TO LARGE MOMENTARY OVERLOADS	81	[198-201]
REVERSE BREAKDOWN [ELECTRICAL FAILURE PHENOMENA, SEMICONDUCTOR TECHNOLOGY]			
18214- 9	THE FORWARD-BIAS CHARACTERISTIC AS A PREDICTOR AND SCREEN OF REVERSE-BIAS SECOND BREAKDOWN	82	[71-75]
SCREENING [TEST TECHNIQUES FOR REL. ASSESSMENT, SEMICONDUCTOR TECHNOLOGY]			
17515- 8	RELIABILITY OF EOS SCREENED GOLD DOPED 4002 CMOS DEVICES	79	[41-44]
17515-11	EFFECTS OF ELECTRICAL OVERSTRESS ON DIGITAL BIPOLAR MICROCIRCUITS AND ANALYSIS TECHNIQUES FOR FAILURE SITE LOCATION	79	[64-77]
SECONDARY BREAKDOWN [ELECTRICAL FAILURE PHENOMENA, SEMICONDUCTOR TECHNOLOGY]			
18172-15	CALCULATIONS OF SECOND BREAKDOWN IN SILICON DIODES AT MICROWAVE FREQUENCIES	83	[102-107]

EOS/ESD SYMPOSIUM INDEX

INDEX TERM-CATEGORY DOCUMENT-SEQUENCE NO.	TITLE	YEAR	PAGES
REFERENCE DOCUMENT			
18172-11	THE ROOM AIR IONIZATION SYSTEM, A BETTER ALTERNATIVE THAN 40% RELATIVE HUMIDITY	83	[67-75]
18172-12	MEASURING EFFECTIVENESS OF AIR IONIZERS	83	[76-86]
18172-14	COPLANAR TRIBOELECTRIFICATION OF SELECTED MATERIALS	83	[95-101]
18172-17	TEMPERATURE AT SECOND BREAKDOWN AT A WELL-DEFINED SITE	83	[118-121]
18172-20	ESD EVALUATION OF RADIATION-HARDED, HIGH RELIABILITY CMOS AND MNOS ICS	83	[134-146]
18172-21	THE EFFECT OF ESD ON CCD RELIABILITY	83	[147-153]
18172-22	EOS OR ESD: CAN FAILURE ANALYSIS TELL THE DIFFERENCE?	83	[154-157]
18172-23	INVISIBLE EOS/ESD DAMAGE: HOW TO FIND IT	83	[158-167]
18172-27	ESD SENSITIVITY OF NMOS LSI CIRCUITS AND THEIR FAILURE CHARACTERISTICS	83	[185-197]
18214- 5	LATENT ESD FAILURES	82	[41-48]
18214- 8	AN IMPROVED EOS CONDUCTION MODEL OF SEMICONDUCTOR DEVICES	82	[62-70]
18214-23	UNIFORM ESD PROTECTION IN A LARGE MULTI-DEPARTMENT ASSEMBLY PLANT	82	[165-168]
18214-24	CIRCUIT DESIGN FOR EOS/ESD PROTECTION	82	[169-174]
18214-28	ELECTRICAL GROUNDING IN LARGE INSTRUMENTATION SYSTEMS	82	[190-202]
17517- 3	ANALYSIS OF ESD FAILURES	81	[14-20]
17517- 4	THE PERFECT "10" - CAN YOU REALLY HAVE ONE?	81	[21-27]
17517- 5	THE ECONOMIC BENEFITS OF AN EFFECTIVE ESD AWARENESS AND CONTROL PROGRAM - AN EMPIRICAL ANALYSIS	81	[29-33]
17517- 6	A PRAGMATIC APPROACH TO ESD PROBLEM SOLVING IN THE MANUFACTURING ENVIRONMENT A CASE HISTORY	81	[34-39]
17517- 8	AN ANALYSIS OF ANTISTATIC CUSHIONING MATERIALS	81	[44-48]
17517- 9	CHO-TRAP, A NOVEL VOLTAGE TRANSIENT PROTECTION PACKAGING MATERIAL	81	[49-56]
17517-12	SELECTION OF PACKAGING MATERIALS FOR ESD SENSITIVE ITEMS	81	[75-84]
17517-13	THE EFFECTS OF VLSI SCALING ON EOS/ESD FAILURE THRESHOLD	81	[85-89]
17517-14	ON CHIP PROTECTION OF HIGH DENSITY NMOS DEVICES	81	[90-96]
17517-15	INPUT PROTECTION DESIGN FOR THE 3-MICRON NMOS PROCESS	81	[97-100]
17517-16	DIAGNOSIS AND ANALYSIS OF EMITTER-BASE JUNCTION OVERSTRESS DAMAGE	81	[101-105]
17517-19	AN OVERVIEW OF EOS EFFECTS ON SEMICONDUCTOR DEVICES	81	[120-131]
17517-24	AN OVERVIEW OF EOS EFFECTS ON PASSIVE COMPONENTS	81	[167-173]
17517-25	PULSE POWER RESPONSE AND DAMAGE CHARACTERISTICS OF CAPACITORS	81	[174-191]
17517-26	PREDICTION OF THIN-FILM RESISTOR BURNOUT	81	[192-197]
17517-27	BEHAVIOR OF THICK-FILM POWER RESISTORS SUBJECTED TO LARGE MOMENTARY OVERLOADS	81	[198-201]
17517-29	POTENTIAL ESD HAZARDS ASSOCIATED WITH EXPLOSIVE PRIMERS	81	[208-211]
17517-30	LIGHTNING PROTECTION FOR COMPUTER DATA LINES	81	[212-218]
17516-28	AN EFFECTIVE ESD AWARENESS TRAINING PROGRAM	80	[189-191]
17515- 5	THE GENERATION OF ELECTROSTATIC CHARGES IN SILICONE ENCAPSULANTS DURING CYCLIC GASEOUS PRESSURE TESTS	79	[22-26]
17515-10	ELECTRO-STATIC DISCHARGE AND CMOS LOGIC	79	[55-63]
17515-14	ELECTROSTATIC FAILURE OF X-BAND SILICON SCHOTTKY BARRIER DIODES	79	[97-103]
17515-22	MICROWAVE NANOSECOND PULSE BURNOUT PROPERTIES OF ONE MICRON MESFETS	79	[147-157]
17515-23	DAMAGE RESPONSE OF SELECTED INTERFACE INTEGRATED CIRCUITS TO A SIMULATED EMP	79	[158-167]
17515-25	THE DIELECTRIC STRENGTH OF SIO2 IN A CMOS TRANSISTOR STRUCTURE	79	[176-182]
17515-27	THE PHANTOM EMITTER-AN ESD-RESISTANT BIPOLAR TRANSISTOR DESIGN AND ITS APPLICATIONS TO LINEAR INTEGRATED CIRCUITS	79	[188-192]
17515-28	ELECTROSTATIC DISCHARGE PROTECTION USING SILICON TRANSIENT SUPPRESSORS	79	[193-197]
REL. STANDARDS [USER OF REL. PREDICTION MODELS]			
17515- 6	PROPOSED MIL-STD AND MIL-HDBK FOR AN ELECTROSTATIC DISCHARGE CONTROL PROGRAM - BACKGROUND AND STATUS	79	[27-35]
RELATIVE HUMIDITY [ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]			
18305-10	TRIBOELECTRIC TESTING FOR ELECTROSTATIC CHARGES ON MATERIALS AT KENNEDY SPACE CENTER	84	[58-63]
18305-16	CRITICAL CONSIDERATIONS FOR ESD TESTING	84	[104-111]
18305-19	SECONDARY DISCHARGE: A NEW JEOPARDY AND A NEW TOOL	84	[131-135]
18172- 4	ANALYSIS OF ELECTROSTATIC CHARGE PROPENSITY OF FLOOR FINISHES	83	[17-20]
18172-11	THE ROOM AIR IONIZATION SYSTEM, A BETTER ALTERNATIVE THAN 40% RELATIVE HUMIDITY	83	[67-75]
18172-12	MEASURING EFFECTIVENESS OF AIR IONIZERS	83	[76-86]
18172-14	COPLANAR TRIBOELECTRIFICATION OF SELECTED MATERIALS	83	[95-101]
18214-13	TEST METHODS FOR STATIC CONTROL PRODUCTS	82	[94-109]
18214-18	ESD AND CONTAMINATION FROM CLEAN ROOM GARMENTS - PROBLEMS AND SOLUTIONS	82	[131-135]

EOS/ESD SYMPOSIUM INDEX

INDEX TERM-CATEGORY DOCUMENT-SEQUENCE NO.	TITLE	YEAR	PAGES
PROTECTED ESD AREA [ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]			
18305- 2	HAZARDS OF STATIC CHARGES AND FIELDS AT THE WORK STATION	84	[7-19]
18172- 2	ESD CONTROL IMPLEMENTATION AND COST AVOIDANCE ANALYSIS	83	[6-11]
18172- 5	AIR FORCE MAINTENANCE PROGRAM FOR ELECTRICAL OVERSTRESS/ELECTROSTATIC DISCHARGE (EOS/ESD) CONTROL	83	[21-28]
18214-19	BASIC SPECIFICATION FOR ESD PROTECTION IN INDUSTRY	82	[136-141]
18214-21	AN EFFECTIVE ELECTROSTATIC DISCHARGE PROTECTION PROGRAM	82	[145-156]
17517- 4	THE PERFECT "10" - CAN YOU REALLY HAVE ONE?	81	[21-27]
17517- 5	THE ECONOMIC BENEFITS OF AN EFFECTIVE ESD AWARENESS AND CONTROL PROGRAM - AN EMPIRICAL ANALYSIS	81	[29-33]
17517- 6	A PRAGMATIC APPROACH TO ESD PROBLEM SOLVING IN THE MANUFACTURING ENVIRONMENT A CASE HISTORY	81	[34-39]
17516- 1	PASSIVE STATIC PROTECTION: THEORY AND PRACTICE	80	[1-11]
17515- 2	CONTROLLING ELECTROSTATIC PROBLEMS IN THE FABRICATION AND HANDLING OF SPACECRAFT HARDWARE	79	[4-6]
17515- 3	ELECTROSTATIC CONDUCTIVITY CHARACTERISTICS OF WORKBENCH-TOP SURFACE MATERIALS	79	[7-12]
17515- 6	PROPOSED MIL-STD AND MIL-HDBK FOR AN ELECTROSTATIC DISCHARGE CONTROL PROGRAM - BACKGROUND AND STATUS	79	[27-35]
PROTECTIVE BAGS [ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]			
18305- 2	HAZARDS OF STATIC CHARGES AND FIELDS AT THE WORK STATION	84	[7-19]
18305-11	TRIBOELECTRIC CHARGE: ITS ESD ABILITY AND A MEASUREMENT METHOD FOR ITS PROPENSITY ON PACKING MATERIALS	84	[64-77]
18305-12	AN EXPERIMENTAL STUDY OF THE ESD SCREENING EFFECTIVENESS OF ANTI-STATIC BAGS	84	[78-84]
18172-13	PERMANENCE OF THE ANTISTATIC PROPERTY OF COMMERCIAL ANTISTATIC BAGS AND TOTE BOXES	83	[87-94]
18214-16	DRASTIC LOSSES OF CONDUCTIVITY IN ANTISTATIC PLASTICS	82	[120-123]
17517-12	SELECTION OF PACKAGING MATERIALS FOR ESD SENSITIVE ITEMS	81	[75-84]
17516- 1	PASSIVE STATIC PROTECTION: THEORY AND PRACTICE	80	[1-11]
17515- 9	THE DEFICIENCIES IN MILITARY SPECIFICATION MIL-B-81705: CONSIDERATIONS AND A SIMPLE MODEL FOR STATIC PROTECTION	79	[45-54]
PROTECTIVE WORK BENCH SURFACE [ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]			
18305-13	A MATERIAL EVALUATION PROGRAM FOR DECORATIVE STATIC CONTROL TABLE TOP LAMINATES	84	[85-93]
18305-19	SECONDARY DISCHARGE: A NEW JEOPARDY AND A NEW TOOL	84	[131-135]
18214-22	ESD MINIMIZATION TECHNIQUE FOR MOS MANUFACTURING FINAL TEST AREA	82	[157-164]
17517- 6	A PRAGMATIC APPROACH TO ESD PROBLEM SOLVING IN THE MANUFACTURING ENVIRONMENT A CASE HISTORY	81	[34-39]
17516- 1	PASSIVE STATIC PROTECTION: THEORY AND PRACTICE	80	[1-11]
17515- 3	ELECTROSTATIC CONDUCTIVITY CHARACTERISTICS OF WORKBENCH-TOP SURFACE MATERIALS	79	[7-12]
QUALITY ASSURANCE [SYSTEMS]			
18305- 1	A REALISTIC AND SYSTEMATIC ESD CONTROL PLAN	84	[1-6]
18305- 2	HAZARDS OF STATIC CHARGES AND FIELDS AT THE WORK STATION	84	[7-19]
18172- 5	AIR FORCE MAINTENANCE PROGRAM FOR ELECTRICAL OVERSTRESS/ELECTROSTATIC DISCHARGE (EOS/ESD) CONTROL	83	[21-28]
18214-13	TEST METHODS FOR STATIC CONTROL PRODUCTS	82	[94-109]
18214-18	ESD AND CONTAMINATION FROM CLEAN ROOM GARMENTS - PROBLEMS AND SOLUTIONS	82	[131-135]
18214-21	AN EFFECTIVE ELECTROSTATIC DISCHARGE PROTECTION PROGRAM	82	[145-156]
17517- 4	THE PERFECT "10" - CAN YOU REALLY HAVE ONE?	81	[21-27]
17517-11	INCOMING INSPECTION OF ANTISTATIC PACKAGING MATERIALS	81	[65-74]
REFERENCE DOCUMENT			
18172- 1	ESD-HOW OFTEN DOES IT HAPPEN?	83	[1-5]
18172- 2	ESD CONTROL IMPLEMENTATION AND COST AVOIDANCE ANALYSIS	83	[6-11]
18172- 3	THE PRODUCTION OPERATOR: WEAK LINK OR WARRIOR IN THE ESD BATTLE?	83	[12-16]
18172- 6	ESD BY STATIC INDUCTION	83	[29-36]
18172- 7	CONSTRUCTION AND APPLICATION OF A TESTER FOR MEASURING EOS/ESD THRESHOLDS TO 15KV	83	[37-47]
18172-10	STATIC SURVEY METERS	83	[63-66]

EOS/ESD SYMPOSIUM INDEX

<u>INDEX TERM-CATEGORY</u> <u>DOCUMENT-SEQUENCE NO.</u>	<u>TITLE</u>	<u>YEAR</u>	<u>PAGES</u>
OXIDATION [CHEMICAL FAILURE PHENOMENA, SEMICONDUCTOR TECHNOLOGY]			
18305-24	DEVICE ESD SUSCEPTIBILITY TESTING AND DESIGN HARDENING	84	[179-188]
17517-14	ON CHIP PROTECTION OF HIGH DENSITY NMOS DEVICES	81	[90-96]
17517-19	AN OVERVIEW OF EOS EFFECTS ON SEMICONDUCTOR DEVICES	81	[120-131]
17516-12	PROTECTION OF MOS INTEGRATED CIRCUITS FROM DESTRUCTION BY ELECTROSTATIC DISCHARGE	80	[73-80]
17516-14	LSI DESIGN CONSIDERATIONS FOR ESD PROTECTION STRUCTURES RELATED TO PROCESS AND LAYOUT VARIATIONS	80	[87-94]
17516-15	ELECTROSTATIC SENSITIVITY OF VARIOUS INPUT PROTECTION NETWORKS	80	[95-103]
17516-16	SUPRISING PATTERNS OF CMOS SUSCEPTIBILITY TO ESD AND IMPLICATIONS ON LONG-TERM RELIABILITY	80	[104-111]
PACKAGE [SEMICONDUCTOR TECHNOLOGY]			
18305-10	TRIBOELECTRIC TESTING FOR ELECTROSTATIC CHARGES ON MATERIALS AT KENNEDY SPACE CENTER	84	[58-63]
18305-18	EMI CHARACTERISTICS OF ESD IN A SMALL AIR GAP --ARP GOVERNS THE EMI--	84	[124-130]
18214-15	ELECTROACTIVE POLYMERS AS ALTERNATE ESD PROTECTIVE MATERIALS	82	[115-119]
17517-10	EVALUATION OF INTEGRATED CIRCUIT SHIPPING TUBES	81	[57-64]
17517-11	INCOMING INSPECTION OF ANTISTATIC PACKAGING MATERIALS	81	[65-74]
17517-12	SELECTION OF PACKAGING MATERIALS FOR ESD SENSITIVE ITEMS	81	[75-84]
PKG BODY MATERIAL [PACKAGE, SEMICONDUCTOR TECHNOLOGY]			
18172-13	PERMANENCE OF THE ANTISTATIC PROPERTY OF COMMERCIAL ANTISTATIC BAGS AND TOTE BOXES	83	[87-94]
PKG ENCAPSULANT [PACKAGE, SEMICONDUCTOR TECHNOLOGY]			
17515- 5	THE GENERATION OF ELECTROSTATIC CHARGES IN SILICONE ENCAPSULANTS DURING CYCLIC GASEOUS PRESSURE TESTS	79	[22-26]
PKG LID OR COVER [PACKAGE, SEMICONDUCTOR TECHNOLOGY]			
17516- 3	ESD DAMAGE FROM TRIBOELECTRICALLY CHARGED IC PINS	80	[17-22]
PROCESS CONTROL/SPECIFICATION [FABRICATION PROCESSES & TECHNIQUES, SEMICONDUCTOR TECHNOLOGY]			
18305- 5	ELECTROSTATIC MEASUREMENT FOR PROCESS CONTROL	84	[25-33]
18214-19	BASIC SPECIFICATION FOR ESD PROTECTION IN INDUSTRY	82	[136-141]
18214-20	ESD IN I.C. ASSEMBLY (A BASE LINE SOLUTION)	82	[142-144]
18214-25	IN-CIRCUIT ANALYSIS OF ESD DAMAGED DEVICES	82	[175-178]
17515- 6	PROPOSED MIL-STD AND MIL-HDBK FOR AN ELECTROSTATIC DISCHARGE CONTROL PROGRAM - BACKGROUND AND STATUS	79	[27-35]
17515- 9	THE DEFICIENCIES IN MILITARY SPECIFICATION MIL-B-81705: CONSIDERATIONS AND A SIMPLE MODEL FOR STATIC PROTECTION	79	[45-54]
PROCESS DESIGN [DESIGN CONSIDERATIONS, SEMICONDUCTOR TECHNOLOGY]			
18214-14	METALLOPLASTICS	82	[110-114]
17517-17	SUSCEPTIBILITY OF ICS IN ESD STEP-STRESS TESTS	81	[106-113]
17515-28	ELECTROSTATIC DISCHARGE PROTECTION USING SILICON TRANSIENT SUPPRESSORS	79	[193-197]
PROCESS/WORKMANSHIP INDUCED [MISC. FAILURE PHENOMENA, SEMICONDUCTOR TECHNOLOGY]			
18214-22	ESD MINIMIZATION TECHNIQUE FOR MOS MANUFACTURING FINAL TEST AREA	82	[157-164]
PROCUREMENT CONTROLS [USER OF REL. PREDICTION MODELS]			
18214-26	ELECTROSTATIC DISCHARGE AT THE PRODUCT LEVEL	82	[179-184]
17515- 8	RELIABILITY OF EOS SCREENED GOLD DOPED 4002 CMOS DEVICES	79	[41-44]
17515-18	HUMAN FACTORS IN ELECTROSTATIC DISCHARGE PROTECTION	79	[122-125]

EOS/ESD SYMPOSIUM INDEX

INDEX TERM-CATEGORY DOCUMENT-SEQUENCE NO.	TITLE	YEAR	PAGES
NOTICE/BULLETIN [REFERENCE DOCUMENT]			
17515-12	DYNAMIC WAVEFORM CHARACTERISTICS OF PERSONNEL ELECTROSTATIC DISCHARGE	79	[78-87]
OPERATIONAL TEST [TEST TECHNIQUES FOR REL. ASSESSMENT, SEMICONDUCTOR TECHNOLOGY]			
18172-21	THE EFFECT OF ESD ON CCD RELIABILITY	83	[147-153]
18172-28	A STUDY OF ESD LATENT DEFECTS IN SEMICONDUCTORS	83	[198-204]
OVERSTRESS [FAILURE CAUSE, FAILURE ANALYSIS, SEMICONDUCTOR TECHNOLOGY]			
18172- 5	AIR FORCE MAINTENANCE PROGRAM FOR ELECTRICAL OVERSTRESS/ELECTROSTATIC DISCHARGE (EOS/ESD) CONTROL	83	[21-28]
18172-22	EOS OR ESD: CAN FAILURE ANALYSIS TELL THE DIFFERENCE?	83	[154-157]
18172-23	INVISIBLE EOS/ESD DAMAGE: HOW TO FIND IT	83	[158-167]
18172-28	A STUDY OF ESD LATENT DEFECTS IN SEMICONDUCTORS	83	[198-204]
18214- 2	ELECTROSTATIC DISCHARGE (ESD) DAMAGE SUSCEPTIBILITY OF THIN FILM RESISTORS AND CAPACITORS	82	[13-18]
18214- 3	LIMITATIONS IN MODELING ELECTRICAL OVERSTRESS FAILURE IN SEMICONDUCTOR DEVICES	82	[19-33]
18214- 4	ELECTRICAL OVERSTRESS THRESHOLD TESTING	82	[34-40]
18214- 5	LATENT ESD FAILURES	82	[41-48]
18214-11	A PROBABILISTIC ESTIMATOR FOR BOUNDING TRANSISTOR EMITTER-BASE JUNCTION TRANSIENT-INDUCED FAILURES	82	[82-90]
18214-21	AN EFFECTIVE ELECTROSTATIC DISCHARGE PROTECTION PROGRAM	82	[145-156]
18214-22	ESD MINIMIZATION TECHNIQUE FOR MOS MANUFACTURING FINAL TEST AREA	82	[157-164]
18214-24	CIRCUIT DESIGN FOR EOS/ESD PROTECTION	82	[169-174]
18214-25	IN-CIRCUIT ANALYSIS OF ESD DAMAGED DEVICES	82	[175-178]
18214-26	ELECTROSTATIC DISCHARGE AT THE PRODUCT LEVEL	82	[179-184]
17517- 3	ANALYSIS OF ESD FAILURES	81	[14-20]
17517- 4	THE PERFECT "10" - CAN YOU REALLY HAVE ONE?	81	[21-27]
17517- 5	THE ECONOMIC BENEFITS OF AN EFFECTIVE ESD AWARENESS AND CONTROL PROGRAM - AN EMPIRICAL ANALYSIS	81	[29-33]
17517-10	EVALUATION OF INTEGRATED CIRCUIT SHIPPING TUBES	81	[57-64]
17517-13	THE EFFECTS OF VLSI SCALING ON EOS/ESD FAILURE THRESHOLD	81	[85-89]
17517-14	ON CHIP PROTECTION OF HIGH DENSITY NMOS DEVICES	81	[90-96]
17517-15	INPUT PROTECTION DESIGN FOR THE 3-MICRON NMOS PROCESS	81	[97-100]
17517-17	SUSCEPTIBILITY OF ICS IN ESD STEP-STRESS TESTS	81	[106-113]
17517-18	ELECTRICAL OVERSTRESS INVESTIGATIONS IN MODERN INTEGRATED CIRCUIT TECHNOLOGIES	81	[114-119]
17517-19	AN OVERVIEW OF EOS EFFECTS ON SEMICONDUCTOR DEVICES	81	[120-131]
17517-25	PULSE POWER RESPONSE AND DAMAGE CHARACTERISTICS OF CAPACITORS	81	[174-191]
17517-27	BEHAVIOR OF THICK-FILM POWER RESISTORS SUBJECTED TO LARGE MOMENTARY OVERLOADS	81	[198-201]
17517-32	TIME-RELATED IMPROVEMENTS OF ELECTRICAL CHARACTERISTICS IN ELECTROSTATICALLY DAMAGED OPERATIONAL AMPLIFIERS	81	[225-228]
17517-33	EOS DAMAGE IN SILICON SOLAR CELLS	81	[209-235]
17517-34	EVALUATION OF ELECTROSTATIC DISCHARGE TO 16K EPROMS	81	[236-241]
17517-35	NON-LINEAR KINETICS OF SEMICONDUCTOR JUNCTION THERMAL FAILURE	81	[242-245]
17515- 6	PROPOSED MIL-STD AND MIL-HDBK FOR AN ELECTROSTATIC DISCHARGE CONTROL PROGRAM - BACKGROUND AND STATUS	79	[27-35]
17515- 7	MODULE ELECTROSTATIC DISCHARGE SIMULATOR	79	[36-40]
17515- 8	RELIABILITY OF EOS SCREENED GOLD DOPED 4002 CMOS DEVICES	79	[41-44]
17515-10	ELECTRO-STATIC DISCHARGE AND CMOS LOGIC	79	[55-63]
17515-11	EFFECTS OF ELECTRICAL OVERSTRESS ON DIGITAL BIPOLAR MICROCIRCUITS AND ANALYSIS TECHNIQUES FOR FAILURE SITE LOCATION	79	[64-77]
17515-12	DYNAMIC WAVEFORM CHARACTERISTICS OF PERSONNEL ELECTROSTATIC DISCHARGE	79	[78-87]
17515-13	FAILURE ANALYSIS OF MICROCIRCUITS SUBJECTED TO ELECTRICAL OVERSTRESS	79	[88-96]
17515-14	ELECTROSTATIC FAILURE OF X-BAND SILICON SCHOTTKY BARRIER DIODES	79	[97-103]
17515-15	ESD SUSCEPTIBILITIES OF HIGH PERFORMANCE ANALOG INTEGRATED CIRCUITS	79	[104-108]
17515-20	MODELING OF ELECTRICAL OVERSTRESS IN SILICON DEVICES	79	[133-139]
17515-21	SQUARE PULSE AND RF PULSE OVERSTRESSING OF UHF TRANSISTORS	79	[140-146]
17515-22	MICROWAVE NANOSECOND PULSE BURNOUT PROPERTIES OF ONE MICRON MESFETS	79	[147-157]
17515-24	SUSCEPTIBILITY OF LSI MOS TO ELECTROSTATIC DISCHARGE AT ELEVATED TEMPERATURE	79	[168-175]
17515-27	THE PHANTOM EMITTER-AN ESD-RESISTANT BIPOLAR TRANSISTOR DESIGN AND ITS APPLICATIONS TO LINEAR INTEGRATED CIRCUITS	79	[188-192]
17515-30	THE ANALYSIS AND ELIMINATION OF EOS INDUCED SECONDARY FAILURE MECHANISMS	79	[205-209]

EOS/ESD SYMPOSIUM INDEX

INDEX TERM-CATEGORY DOCUMENT-SEQUENCE NO.	TITLE	YEAR	PAGES
MICROCIRCUIT [SEMICONDUCTOR DEVICE]			
17516-27	MICROCIRCUIT ELECTRICAL OVERSTRESS TOLERANCE TESTING AND QUALIFICATION	80	[184-188]
17515-10	ELECTRO-STATIC DISCHARGE AND CMOS LOGIC	79	[55-63]
17515-13	FAILURE ANALYSIS OF MICROCIRCUITS SUBJECTED TO ELECTRICAL OVERSTRESS	79	[88-96]
17515-15	ESD SUSCEPTIBILITIES OF HIGH PERFORMANCE ANALOG INTEGRATED CIRCUITS	79	[104-108]
17515-23	DAMAGE RESPONSE OF SELECTED INTERFACE INTEGRATED CIRCUITS TO A SIMULATED EMP	79	[158-167]
17515-27	THE PHANTOM EMITTER-AN ESD-RESISTANT BIPOLAR TRANSISTOR DESIGN AND ITS APPLICATIONS TO LINEAR INTEGRATED CIRCUITS	79	[188-192]
MICROWAVE [DISCRETE SEMICONDUCTOR, SEMICONDUCTOR DEVICE]			
18172-15	CALCULATIONS OF SECOND BREAKDOWN IN SILICON DIODES AT MICROWAVE FREQUENCIES	83	[102-107]
MISC. FAILURE PHENOMENA [SEMICONDUCTOR TECHNOLOGY]			
18214-16	DRASTIC LOSSES OF CONDUCTIVITY IN ANTISTATIC PLASTICS	82	[120-123]
18214-18	ESD AND CONTAMINATION FROM CLEAN ROOM GARMENTS - PROBLEMS AND SOLUTIONS	82	[131-135]
MISSILE [APPLICATION ENVIRONMENT]			
17517-28	EOS THRESHOLD DETERMINATION OF ELECTRO-EXPLOSIVE DEVICES	81	[202-207]
MNOS [FIELD EFFECT,(FET), SEMICONDUCTOR TECHNOLOGY]			
17516-16	SUPRISING PATTERNS OF CMOS SUSCEPTIBILITY TO ESD AND IMPLICATIONS ON LONG-TERM RELIABILITY	80	[104-111]
MODELS/THEORY/EQUATIONS [RELIABILITY MODELING TECHNIQUES, RELIABILITY MODELS/DATA/ANALYSIS]			
18305-20	PROTECTION OF COMPONENTS AGAINST ELECTRICAL OVERSTRESS (EOS) AND TRANSIENTS IN MONITORS	84	[136-143]
18214- 3	LIMITATIONS IN MODELING ELECTRICAL OVERSTRESS FAILURE IN SEMICONDUCTOR DEVICES	82	[19-33]
18214- 7	MODELING METALLIZATION BURNOUT OF INTEGRATED CIRCUITS	82	[56-61]
18214- 8	AN IMPROVED EOS CONDUCTION MODEL OF SEMICONDUCT DEVICES	82	[62-70]
18214-10	MODELING OF CURRENT AND THERMAL MODE SECOND BREAKDOWN PHENOMENA	82	[76-81]
17515-20	MODELING OF ELECTRICAL OVERSTRESS IN SILICON DEVICES	79	[133-139]
MOISTURE [TEST STRESS]			
17516- 2	THE EFFECTS OF HIGH HUMIDITY ENVIRONMENTS ON ELECTROSTATIC GENERATION AND DISCHARGE	80	[12-16]
MOSFET [FIELD EFFECT,(FET), SEMICONDUCTOR TECHNOLOGY]			
18305- 2	HAZARDS OF STATIC CHARGES AND FIELDS AT THE WORK STATION	84	[7-19]
17516-13	SOS PROTECTION: THE DESIGN PROBLEM	80	[81-86]
MOSFET C [FIELD EFFECT,(FET), SEMICONDUCTOR TECHNOLOGY]			
18305-21	AN EVALUATION OF EOS FAILURE MODELS	84	[144-156]
18305-25	A FAILURE ANALYSIS METHODOLOGY FOR REVEALING ESD DAMAGE TO INTEGRATED CIRCUITS	84	[189-195]
18305-26	ESD SENSITIVITY AND LATENCY EFFECTS OF SOME HCMOS INTEGRATED CIRCUITS	84	[196-201]
MOSFET N [FIELD EFFECT,(FET), SEMICONDUCTOR TECHNOLOGY]			
18305-22	DETERMINATION OF THRESHOLD ENERGIES AND DAMAGE MECHANISMS IN SEMICONDUCTOR DEVICES SUBJECTED TO VOLTAGE TRANSIENTS	84	[157-164]
NONELECTRONICS			
18305- 7	A ROOM IONIZATION SYSTEM FOR ELECTROSTATIC CHARGE AND DUST CONTROL	84	[40-44]
18305-19	SECONDARY DISCHARGE: A NEW JEOPARDY AND A NEW TOOL	84	[131-135]

EOS/ESD SYMPOSIUM INDEX

INDEX TERM-CATEGORY DOCUMENT-SEQUENCE NO.	TITLE	YEAR	PAGES
MATHEMATICAL ANALYSIS			
17517-33	EOS DAMAGE IN SILICON SOLAR CELLS	81	[209-235]
17517-35	NON-LINEAR KINETICS OF SEMICONDUCTOR JUNCTION THERMAL FAILURE	81	[242-245]
17515-19	AN ELECTROTHERMAL MODEL FOR CURRENT FILAMENTATION IN SECOND BREAKDOWN OF SILICON-ON-SAPPHIRE DIODES	79	[126-132]
17515-24	SUSCEPTIBILITY OF LSI MOS TO ELECTROSTATIC DISCHARGE AT ELEVATED TEMPERATURE	79	[168-175]
METALLIZATION MELT [ESD, DEVICE, FAILURE MODES]			
18305-23	DEGRADATION BY ESD TRANSIENTS OF THE SUBSTRATE BIAS VOLTAGE OF NMOS 8085-TYPE MICROPROCESSORS	84	[165-178]
18214- 7	MODELING METALLIZATION BURNOUT OF INTEGRATED CIRCUITS	82	[56-61]
17517-13	THE EFFECTS OF VLSI SCALING ON EOS/ESD FAILURE THRESHOLD	81	[85-89]
17517-17	SUSCEPTIBILITY OF ICS IN ESD STEP-STRESS TESTS	81	[106-113]
17517-19	AN OVERVIEW OF EOS EFFECTS ON SEMICONDUCTOR DEVICES	81	[120-131]
17517-33	EOS DAMAGE IN SILICON SOLAR CELLS	81	[209-235]
17516- 9	STUDY OF EFFECTS OF ELECTRO-STATIC DISCHARGE ON SOLID-STATE DEVICES	80	[58]
17516-11	ANALYSIS OF ESD DAMAGE IN JFET PREAMPLIFIERS	80	[67-72]
17516-22	SOLAR CELL ELECTRICAL OVERSTRESS ANALYSIS	80	[149-153]
17515-11	EFFECTS OF ELECTRICAL OVERSTRESS ON DIGITAL BIPOLAR MICROCIRCUITS AND ANALYSIS TECHNIQUES FOR FAILURE SITE LOCATION	79	[64-77]
17515-14	ELECTROSTATIC FAILURE OF X-BAND SILICON SCHOTTKY BARRIER DIODES	79	[97-103]
17515-22	MICROWAVE NANOSECOND PULSE BURNOUT PROPERTIES OF ONE MICRON MESFETS	79	[147-157]
17515-24	SUSCEPTIBILITY OF LSI MOS TO ELECTROSTATIC DISCHARGE AT ELEVATED TEMPERATURE	79	[168-175]
METALLURGICAL FAILURE PHENOMENA [SEMICONDUCTOR TECHNOLOGY]			
18214- 7	MODELING METALLIZATION BURNOUT OF INTEGRATED CIRCUITS	82	[56-61]
MICROCIRCUIT [SEMICONDUCTOR DEVICE]			
18305- 3	TEST EQUIPMENT--A SOURCE OF ESD!!	84	[20-21]
18305- 4	ESD DAMAGE, DOES IT HAPPEN ON PCBs?	84	[22-23]
18305- 6	EFFECTS OF AIR IONS AND ELECTRIC FIELDS ON HEALTH AND PRODUCTIVITY	84	[34-39]
18305-10	TRIBOELECTRIC TESTING FOR ELECTROSTATIC CHARGES ON MATERIALS AT KENNEDY SPACE CENTER	84	[58-63]
18305-18	EMI CHARACTERISTICS OF ESD IN A SMALL AIR GAP --ARP GOVERNS THE EMI--	84	[124-130]
18305-19	SECONDARY DISCHARGE: A NEW JEOPARDY AND A NEW TOOL	84	[131-135]
18305-21	AN EVALUATION OF EOS FAILURE MODELS	84	[144-156]
18305-22	DETERMINATION OF THRESHOLD ENERGIES AND DAMAGE MECHANISMS IN SEMICONDUCTOR DEVICES SUBJECTED TO VOLTAGE TRANSIENTS	84	[157-164]
18305-23	DEGRADATION BY ESD TRANSIENTS OF THE SUBSTRATE BIAS VOLTAGE OF NMOS 8085-TYPE MICROPROCESSORS	84	[165-178]
18305-24	DEVICE ESD SUSCEPTIBILITY TESTING AND DESIGN HARDENING	84	[179-188]
18305-25	A FAILURE ANALYSIS METHODOLOGY FOR REVEALING ESD DAMAGE TO INTEGRATED CIRCUITS	84	[189-195]
18305-26	ESD SENSITIVITY AND LATENCY EFFECTS OF SOME HCMOS INTEGRATED CIRCUITS	84	[196-201]
18172- 9	POWER FAILURE MODELING OF INTEGRATED CIRCUITS	83	[56-62]
18172-19	ESD SENSITIVITY OF COMPLEX ICS	83	[128-133]
18172-20	ESD EVALUATION OF RADIATION-HARDENED, HIGH RELIABILITY CMOS AND MNOS ICS	83	[134-146]
18172-24	METAL OXIDE VARISTORS FOR TRANSIENT PROTECTION OF 3 TO 5-VOLT INTEGRATED CIRCUITS	83	[168-176]
18172-25	USING SCR'S AS TRANSIENT PROTECTION STRUCTURES IN INTEGRATED CIRCUITS	83	[177-180]
18172-26	A SUMMARY OF MOST EFFECTIVE ELECTROSTATIC DISCHARGE PROTECTION CIRCUITS FOR MOS MEMORIES AND THEIR OBSERVED FAILURE MODES	83	[181-184]
18214- 1	ESD SUSCEPTIBILITY TESTING OF ADVANCED SCHOTTKY TTL	82	[1-12]
18214- 7	MODELING METALLIZATION BURNOUT OF INTEGRATED CIRCUITS	82	[56-61]
18214- 8	AN IMPROVED EOS CONDUCTION MODEL OF SEMICONDUCT DEVICES	82	[62-70]
18214-22	ESD MINIMIZATION TECHNIQUE FOR MOS MANUFACTURING FINAL TEST AREA	82	[157-164]
18214-25	IN-CIRCUIT ANALYSIS OF ESD DAMAGED DEVICES	82	[175-178]
17517- 3	ANALYSIS OF ESD FAILURES	81	[14-20]
17517-17	SUSCEPTIBILITY OF ICS IN ESD STEP-STRESS TESTS	81	[106-113]
17516-12	PROTECTION OF MOS INTEGRATED CIRCUITS FROM DESTRUCTION BY ELECTROSTATIC DISCHARGE	80	[73-80]
17516-16	SURPRISING PATTERNS OF CMOS SUSCEPTIBILITY TO ESD AND IMPLICATIONS ON LONG-TERM RELIABILITY	80	[104-111]

Section 3:

AUTHOR INDEX

AUTHOR INDEX

<u>AUTHOR</u> <u>DOCUMENT-SEQUENCE NO.</u>	<u>TITLE</u>	<u>YEAR</u>	<u>PAGES</u>
ADAMS, O. E.			
18214- 3	LIMITATIONS IN MODELING ELECTRICAL OVERSTRESS FAILURE IN SEMICONDUCTOR DEVICES	82	[19-33]
ALEXANDER, D. R.			
17517-18	ELECTRICAL OVERSTRESS INVESTIGATIONS IN MODERN INTEGRATED CIRCUIT TECHNOLOGIES	81	[114-119]
ANAND, Y.			
17515-14	ELECTROSTATIC FAILURE OF X-BAND SILICON SCHOTTKY BARRIER DIODES	79	[97-103]
ANDERSON, W. E.			
18305- 2	HAZARDS OF STATIC CHARGES AND FIELDS AT THE WORK STATION	84	[7-19]
18172-13	PERMANENCE OF THE ANTISTATIC PROPERTY OF COMMERCIAL ANTISTATIC BAGS AND TOTE BOXES	83	[87-94]
17517-12	SELECTION OF PACKAGING MATERIALS FOR ESD SENSITIVE ITEMS	81	[75-84]
ANTINONE, R. J.			
17516-27	MICROCIRCUIT ELECTRICAL OVERSTRESS TOLERANCE TESTING AND QUALIFICATION	80	[184-188]
ANTONEVICH, J. N.			
18172-12	MEASURING EFFECTIVENESS OF AIR IONIZERS	83	[76-86]
ARMENDARIZ, M. G.			
17516-16	SUPRISING PATTERNS OF CMOS SUSCEPTIBILITY TO ESD AND IMPLICATIONS ON LONG-TERM RELIABILITY	80	[104-111]
ASH, M. S.			
18172-18	SEMICONDUCTOR JUNCTION NON-LINEAR FAILURE POWER THRESHOLDS: WUNSCH-BELL REVISITED	83	[122-127]
17517-35	NON-LINEAR KINETICS OF SEMICONDUCTOR JUNCTION THERMAL FAILURE	81	[242-245]
AVERY, L. R.			
18172-25	USING SCR'S AS TRANSIENT PROTECTION STRUCTURES IN INTEGRATED CIRCUITS	83	[177-180]
BAKER, R. P.			
17516-16	SUPRISING PATTERNS OF CMOS SUSCEPTIBILITY TO ESD AND IMPLICATIONS ON LONG-TERM RELIABILITY	80	[104-111]
BARNUM, J.			
17517-33	EOS DAMAGE IN SILICON SOLAR CELLS	81	[209-235]
BARUAH, A.			
17515-19	AN ELECTROTHERMAL MODEL FOR CURRENT FILAMENTATION IN SECOND BREAKDOWN OF SILICON-ON-SAPPHIRE DIODES	79	[126-132]
BAUMGARTNER, G.			
18305-15	TESTING OF ELECTROSTATIC MATERIALS FED. STD. 101C, METHOD 4046.1	84	[97-103]
18305- 5	ELECTROSTATIC MEASUREMENT FOR PROCESS CONTROL	84	[25-33]
BAZARIAN, A.			
17516- 7	GAS TUBE SURGE ARRESTERS FOR CONTROL OF TRANSIENT VOLTAGES	80	[44-53]

AUTHOR INDEX

<u>AUTHOR</u>	<u>DOCUMENT-SEQUENCE NO.</u>	<u>TITLE</u>	<u>YEAR</u>	<u>PAGES</u>
BEALL, J.				
	18172-28	A STUDY OF ESD LATENT DEFECTS IN SEMICONDUCTORS	83	[198-204]
BERBECO, G. R.				
	18214-17	CHARACTERIZATION OF ESD SAFE REQUIREMENTS FOR FLOOR SURFACES	82	[124-130]
	17516- 1	PASSIVE STATIC PROTECTION: THEORY AND PRACTICE	80	[1-11]
BERNETT, M. K.				
	18214-15	ELECTROACTIVE POLYMERS AS ALTERNATE ESD PROTECTIVE MATERIALS	82	[115-119]
BERNING, D. W.				
	17515-17	REVERSE-BIAS SECOND BREAKDOWN IN POWER TRANSISTORS	79	[116-121]
BHAR, T. N.				
	17515- 6	PROPOSED MIL-STD AND MIL-HDBK FOR AN ELECTROSTATIC DISCHARGE CONTROL PROGRAM - BACKGROUND AND STATUS	79	[27-35]
BLACKBURN, D. L.				
	17515-17	REVERSE-BIAS SECOND BREAKDOWN IN POWER TRANSISTORS	79	[116-121]
BLINDE, D. R.				
	18172-11	THE ROOM AIR IONIZATION SYSTEM, A BETTER ALTERNATIVE THAN 40% RELATIVE HUMIDITY	83	[67-75]
	17517- 2	QUANTITATIVE EFFECTS OF RELATIVE & ABSOLUTE HUMIDITY ON ESD GENERATION/ SUPPRESSION	81	[9-13]
BLITSHTEYN, M.				
	18172-12	MEASURING EFFECTIVENESS OF AIR IONIZERS	83	[76-86]
BLORE, R. A.				
	17515- 8	RELIABILITY OF EOS SCREENED GOLD DOPED 4002 CMOS DEVICES	79	[41-44]
BOLASNY, R. E.				
	17516-31	STATIC CONTROL SYSTEMS	80	[213-217]
BOSSARD, P. R.				
	18305- 7	A ROOM IONIZATION SYSTEM FOR ELECTROSTATIC CHARGE AND DUST CONTROL	84	[40-44]
	18172- 6	ESD BY STATIC INDUCTION	83	[29-36]
	17517-10	EVALUATION OF INTEGRATED CIRCUIT SHIPPING TUBES	81	[57-64]
	17516- 3	ESD DAMAGE FROM TRIBOELECTRICALLY CHARGED IC PINS	80	[17-22]
BOWERS, J.				
	18172-28	A STUDY OF ESD LATENT DEFECTS IN SEMICONDUCTORS	83	[198-204]
BRANBERG, G.				
	17515-10	ELECTRO-STATIC DISCHARGE AND CMOS LOGIC	79	[55-63]
BRENNAN, T. F.				
	18172-23	INVISIBLE EOS/ESD DAMAGE: HOW TO FIND IT	83	[158-167]

AUTHOR INDEX

<u>AUTHOR</u>	<u>DOCUMENT-SEQUENCE NO.</u>	<u>TITLE</u>	<u>YEAR</u>	<u>PAGES</u>
BRIGGS, C.				
	17515-	3 ELECTROSTATIC CONDUCTIVITY CHARACTERISTICS OF WORKBENCH-TOP SURFACE MATERIALS	79	[7-12]
BUDEN, B. N.				
	18172-	9 POWER FAILURE MODELING OF INTEGRATED CIRCUITS	83	[56-62]
BUDENSTEIN, P. P.				
	17516-	19 EFFECT OF JUNCTION SPIKES AND DOPING LEVEL ON THE SECOND BREAKDOWN SUSCEPTIBILITY OF SILICON-ON-SAPPHIRE DIODES	80	[122-129]
	17515-	19 AN ELECTROTHERMAL MODEL FOR CURRENT FILAMENTATION IN SECOND BREAKDOWN OF SILICON-ON-SAPPHIRE DIODES	79	[126-132]
BURNETT, E. S.				
	18214-	18 ESD AND CONTAMINATION FROM CLEAN ROOM GARMENTS - PROBLEMS AND SOLUTIONS	82	[131-135]
BURROUGHS, J. E.				
	18214-	27 ELECTROSTATIC DISCHARGE IMMUNITY IN COMPUTER SYSTEMS	82	[185-189]
CABAYAN, H. S.				
	17515-	29 STATISTICAL FAILURE ANALYSIS OF MILITARY SYSTEMS FOR HIGH-ALTITUDE EMP	79	[198-204]
CAIDERBANK, J. M.				
	17516-	2 THE EFFECTS OF HIGH HUMIDITY ENVIRONMENTS ON ELECTROSTATIC GENERATION AND DISCHARGE	80	[12-16]
CALVIN, H.				
	17517-	1 A CLOSER LOOK AT THE HUMAN ESD EVENT	81	[1-8]
	17516-	33 MEASUREMENT OF FAST TRANSIENTS AND APPLICATION TO HUMAN ESD	80	[225-230]
CARLTON, R. M.				
	18305-	6 EFFECTS OF AIR IONS AND ELECTRIC FIELDS ON HEALTH AND PRODUCTIVITY	84	[34-39]
CASTLE, G. S. P.				
	17516-	11 ANALYSIS OF ESD DAMAGE IN JFET PREAMPLIFIERS	80	[67-72]
CHASE, E. W.				
	18214-	2 ELECTROSTATIC DISCHARGE (ESD) DAMAGE SUSCPETIBILITY OF THIN FILM RESISTORS AND CAPACITORS	82	[13-18]
	17517-	34 EVALUATION OF ELECTROSTATIC DISCHARGE TO 16K EPROMS	81	[236-241]
CHEMELLI, R. G.				
	18305-	7 A ROOM IONIZATION SYSTEM FOR ELECTROSTATIC CHARGE AND DUST CONTROL	84	[40-44]
	18172-	6 ESD BY STATIC INDUCTION	83	[29-36]
	17517-	10 EVALUATION OF INTEGRATED CIRCUIT SHIPPING TUBES	81	[57-64]
	17516-	3 ESD DAMAGE FROM TRIBOELECTRICALLY CHARGED IC PINS	80	[17-22]
CHI, K.				
	18305-	27 A CMOS VLSI ESD INPUT PROTECTION DEVICE, DIFIDW	84	[202-209]
CLARK, O. M.				
	17517-	30 LIGHTNING PROTECTION FOR COMPUTER DATA LINES	81	[212-218]

AUTHOR INDEX

<u>AUTHOR</u> <u>DOCUMENT-SEQUENCE NO.</u>	<u>TITLE</u>	<u>YEAR</u>	<u>PAGES</u>
CLARK, O. M.			
17515-28	ELECTROSTATIC DISCHARGE PROTECTION USING SILICON TRANSIENT SUPPRESSORS	79	[193-197]
CROCKETT, R. G. M.			
18305-26	ESD SENSITIVITY AND LATENCY EFFECTS OF SOME HCMOS INTEGRATED CIRCUITS	84	[196-201]
CROUCH, K. E.			
17516-25	LIGHTNING PROTECTION DESIGN FOR A PHOTOVOLTAIC CONCENTRATOR	80	[167-175]
DANGELMAYER, G. T.			
18305-	1 A REALISTIC AND SYSTEMATIC ESD CONTROL PLAN	84	[1-6]
18172-	1 ESD-HOW OFTEN DOES IT HAPPEN?	83	[1-5]
DASH, G. R.			
18305-17	DESIGNING TO AVOID STATIC - ESD TESTING OF DIGITAL DEVICES	84	[112-123]
DAVENPORT, D. E.			
18214-14	METALLOPLASTICS	82	[110-114]
DEADRICK, F. J.			
17515-29	STATISTICAL FAILURE ANALYSIS OF MILITARY SYSTEMS FOR HIGH-ALTITUDE EMP	79	[198-204]
DECHIARO, L. F.			
18305-24	DEVICE ESD SUSCEPTIBILITY TESTING AND DESIGN HARDENING	84	[179-188]
DENSON, W. K.			
18214-	1 ESD SUSCEPTIBILITY TESTING OF ADVANCED SCHOTTKY TTL	82	[1-12]
DERMARDESIAN, A.			
17515-	5 THE GENERATION OF ELECTROSTATIC CHARGES IN SILICONE ENCAPSULANTS DURING CYCLIC GASEOUS PRESSURE TESTS	79	[22-26]
DEY, K. A.			
18214-	1 ESD SUSCEPTIBILITY TESTING OF ADVANCED SCHOTTKY TTL	82	[1-12]
DODSON, G. A.			
17515-27	THE PHANTOM EMITTER-AN ESD-RESISTANT BIPOLAR TRANSISTOR DESIGN AND ITS APPLICATIONS TO LINEAR INTEGRATED CIRCUITS	79	[188-192]
DOMINGOS, H.			
18214-24	CIRCUIT DESIGN FOR EOS/ESD PROTECTION	82	[169-174]
17516-30	BASIC CONSIDERATIONS IN ELECTRO-THERMAL OVERSTRESS IN ELECTRONIC COMPONENTS	80	[206-212]
17515-21	SQUARE PULSE AND RF PULSE OVERSTRESSING OF UHF TRANSISTORS	79	[140-146]
DOWNING, M. H.			
18172-	2 ESD CONTROL IMPLEMENTATION AND COST AVOIDANCE ANALYSIS	83	[6-11]
DREIBELBIS, D. H.			
18172-22	EOS OR ESD: CAN FAILURE ANALYSIS TELL THE DIFFERENCE?	83	[154-157]

AUTHOR INDEX

<u>AUTHOR</u>	<u>DOCUMENT-SEQUENCE NO.</u>	<u>TITLE</u>	<u>YEAR</u>	<u>PAGES</u>
DURGIN, D. L.				
	18214- 6	A SUREY OF EOS/ESD DATA SOURCES	82	[49-55]
	17517-19	AN OVERVIEW OF EOS EFFECTS ON SEMICONDUCTOR DEVICES	81	[120-131]
	17516-23	AN OVERVIEW OF THE SOURCES AND EFFECTS OF ELECTRICAL OVERSTRESS	80	[154-160]
DUVVURY, C.				
	18172-26	A SUMMARY OF MOST EFFECTIVE ELECTROSTATIC DISCHARGE PROTECTION CIRCUITS FOR MOS MEMORIES AND THEIR OBSERVED FAILURE MODES	83	[181-184]
ELLIS, E. B.				
	18214-26	ELECTROSTATIC DISCHARGE AT THE PRODUCT LEVEL	82	[179-184]
ENDERS, J.				
	17517-17	SUSCEPTIBILITY OF ICS IN ESD STEP-STRESS TESTS	81	[106-113]
ENLOW, E. W.				
	18172- 9	POWER FAILURE MODELING OF INTEGRATED CIRCUITS	83	[56-62]
	17517-22	DETERMINING AN EMITTER-BASE FAILURE THRESHOLD DISTRIBUTION OF NPN TRANSISTORS	81	[145-150]
	17516-10	FAILURE THRESHOLD DISTRIBUTIONS IN BIPOLAR TRANSISTORS	80	[59-66]
ENOCH, R. D.				
	18305-23	DEGRADATION BY ESD TRANSIENTS OF THE SUBSTRATE BIAS VOLTAGE OF NMOS 8085-TYPE MICROPROCESSORS	84	[165-178]
	18172- 8	A PROGRAMMABLE EQUIPMENT FOR ELECTROSTATIC DISCHARGE TESTING TO HUMAN BODY MODELS	83	[48-55]
	18172-27	ESD SENSITIVITY OF NMOS LSI CIRCUITS AND THEIR FAILURE CHARACTERISTICS	83	[185-197]
EUKER, R.				
	18214-20	ESD IN I.C. ASSEMBLY (A BASE LINE SOLUTION)	82	[142-144]
FEASEY, P. R.				
	18305-25	A FAILURE ANALYSIS METHODOLOGY FOR REVEALING ESD DAMAGE TO INTEGRATED CIRCUITS	84	[189-195]
FELT, F. S.				
	18172-14	COPLANAR TRIBOELECTRIFICATION OF SELECTED MATERIALS	83	[95-101]
FOERSTER, G.				
	18305-20	PROTECTION OF COMPONENTS AGAINST ELECTRICAL OVERSTRESS (EOS) AND TRANSIENTS IN MONITORS	84	[136-143]
FORMANEK, V. C.				
	17515-23	DAMAGE RESPONSE OF SELECTED INTERFACE INTEGRATED CIRCUITS TO A SIMULATED EMP	79	[158-167]
FRANK, D. E.				
	17517- 4	THE PERFECT "10" - CAN YOU REALLY HAVE ONE?	81	[21-27]
GIERI, V. A.				
	18172- 9	POWER FAILURE MODELING OF INTEGRATED CIRCUITS	83	[56-62]
GOMPF, R. H.				
	18305-10	TRIBOELECTRIC TESTING FOR ELECTROSTATIC CHARGES ON MATERIALS AT KENNEDY SPACE CENTER	84	[58-63]

AUTHOR INDEX

<u>AUTHOR</u> <u>DOCUMENT-SEQUENCE NO.</u>	<u>TITLE</u>	<u>YEAR</u>	<u>PAGES</u>
GRUCHALLA, M.			
18214-28	ELECTRICAL GROUNDING IN LARGE INSTRUMENTATION SYSTEMS	82	[190-202]
GUAY, R. H.			
17517-27	BEHAVIOR OF THICK-FILM POWER RESISTORS SUBJECTED TO LARGE MOMENTARY OVERLOADS	81	[198-201]
HALPERIN, S. A.			
17516-29	FACILITY EVALUATION: ISOLATING ENVIRONMENTAL ESD PROBLEMS	80	[192-205]
17515- 4	STATIC CONTROL USING TOPICAL ANTISTATS	79	[13-21]
HANSEL, G. E.			
18172- 3	THE PRODUCTION OPERATOR: WEAK LINK OR WARRIOR IN THE ESD BATTLE?	83	[12-16]
HART, A. R.			
17516-14	LSI DESIGN CONSIDERATIONS FOR ESD PROTECTION STRUCTURES RELATED TO PROCESS AND LAYOUT VARIATIONS	80	[87-94]
17515-24	SUSCEPTIBILITY OF LSI MOS TO ELECTROSTATIC DISCHARGE AT ELEVATED TEMPERATURE	79	[168-175]
HARTDEGEN, N.			
18214-22	ESD MINIMIZATION TECHNIQUE FOR MOS MANUFACTURING FINAL TEST AREA	82	[157-164]
HARTMANN, H. C.			
17517- 8	AN ANALYSIS OF ANTISTATIC CUSHIONING MATERIALS	81	[44-48]
HAVERMANN, R.			
18305-15	TESTING OF ELECTROSTATIC MATERIALS FED. STD. 101C, METHOD 4046.1	84	[97-103]
HAYS, R. A.			
18214- 4	ELECTRICAL OVERSTRESS THRESHOLD TESTING	82	[34-40]
17517-28	EOS THRESHOLD DETERMINATION OF ELECTRO-EXPLOSIVE DEVICES	81	[202-207]
HEAD, G. O.			
18214-16	DRASTIC LOSSES OF CONDUCTIVITY IN ANTISTATIC PLASTICS	82	[120-123]
17517-32	TIME-RELATED IMPROVEMENTS OF ELECTRICAL CHARACTERISTICS IN ELECTROSTATICALLY DAMAGED OPERATIONAL AMPLIFIERS	81	[225-228]
17517- 7	A LOW-COST PROGRAM FOR EVALUATION OF ESD PROTECTIVE MATERIALS AND EQUIPMENT	81	[41-43]
HESS, R. F.			
17 16-24	TEST WAVEFORMS AND TECHNIQUES TO ASSESS THE THREAT TO ELECTRONIC DEVICES OF LIGHTNING-INDUCED TRANSIENTS	80	[161-166]
HIBBERT, D. R.			
17516-11	ANALYSIS OF ESD DAMAGE IN JFET PREAMPLIFIERS	80	[67-72]
HOHL, A. P.			
18305-14	A WRIST STRAP LIFE TEST PROGRAM	84	[94-96]
HOLMES, G. C.			
18305-12	AN EXPERIMENTAL STUDY OF THE ESD SCREENING EFFECTIVENESS OF ANTI-STATIC BAGS	84	[78-84]

AUTHOR INDEX

<u>AUTHOR</u>	<u>DOCUMENT-SEQUENCE NO.</u>	<u>TITLE</u>	<u>YEAR</u>	<u>PAGES</u>
HOLT, V. E.				
	18172-	4 ANALYSIS OF ELECTROSTATIC CHARGE PROPENSITY OF FLOOR FINISHES	83	[17-20]
HONDA, M.				
	18305-	18 EMI CHARACTERISTICS OF ESD IN A SMALL AIR GAP --ARP GOVERNS THE EMI--	84	[124-130]
HOPKINS, D. C.				
	17516-	6 PROTECTION LEVEL COMPARISONS FOR VOLTAGE TRANSIENT SUPPRESSORS (120 V, AC TYPE)	80	[35-43]
HORGAN, E. L.				
	18214-	3 LIMITATIONS IN MODELING ELECTRICAL OVERSTRESS FAILURE IN SEMICONDUCTOR DEVICES	82	[19-33]
	17517-	31 FAILURE ANALYSIS OF SEMICONDUCTOR DEVICES IN EOS/ESD TESTING	81	[219-224]
	17517-	23 EOS/ESD FAILURE THRESHOLD ANALYSIS ERRORS, THEIR SOURCE, SIZE AND CONTROL	81	[151-166]
	17516-	21 ASSESSING ELECTRICAL OVERSTRESS EFFECTS ON ELECTRONIC SYSTEMS	80	[140-148]
HOWER, P. L.				
	17516-	17 HIGH-FIELD PHENOMENA AND FAILURE MECHANISMS IN BIPOLAR TRANSISTORS	80	[112-116]
HUFF, P. J.				
	18305-	12 AN EXPERIMENTAL STUDY OF THE ESD SCREENING EFFECTIVENESS OF ANTI-STATIC BAGS	84	[78-84]
HUGHES, J. F.				
	18305-	26 ESD SENSITIVITY AND LATENCY EFFECTS OF SOME HCMOS INTEGRATED CIRCUITS	84	[196-201]
HULETT, T. V.				
	17517-	14 ON CHIP PROTECTION OF HIGH DENSITY NMOS DEVICES	81	[90-96]
HUNTSMAN, J. R.				
	18305-	11 TRIBOELECTRIC CHARGE: ITS ESD ABILITY AND A MEASUREMENT METHOD FOR ITS PROPENSITY ON PACKING MATERIALS	84	[64-77]
	18214-	13 TEST METHODS FOR STATIC CONTROL PRODUCTS	82	[94-109]
	17515-	9 THE DEFICIENCIES IN MILITARY SPECIFICATION MIL-B-81705: CONSIDERATIONS AND A SIMPLE MODEL FOR STATIC PROTECTION	79	[45-54]
HYATT, H.				
	17516-	33 MEASUREMENT OF FAST TRANSIENTS AND APPLICATION TO HUMAN ESD	80	[225-230]
HYATT, H. M.				
	18305-	16 CRITICAL CONSIDERATIONS FOR ESD TESTING	84	[104-111]
	17517-	1 A CLOSER LOOK AT THE HUMAN ESD EVENT	81	[1-8]
JENSEN, M. C.				
	17517-	16 DIAGNOSIS AND ANALYSIS OF EMITTER-BASE JUNCTION OVERSTRESS DAMAGE	81	[101-105]
JOHNSON, M. A.				
	17517-	8 AN ANALYSIS OF ANTISTATIC CUSHIONING MATERIALS	81	[44-48]
JOHNSON, R. L.				
	18305-	12 AN EXPERIMENTAL STUDY OF THE ESD SCREENING EFFECTIVENESS OF ANTI-STATIC BAGS	84	[78-84]

AUTHOR INDEX

AUTHOR DOCUMENT-SEQUENCE NO.	TITLE	YEAR	PAGES
JONASSEN, N.			
18305- 8	STATIC-ELECTRIC CHARACTERIZATION OF SEMI-INSULATING MATERIALS	84	[45-49]
KARASKIEWICZ, R. J.			
17517-18	ELECTRICAL OVERSTRESS INVESTIGATIONS IN MODERN INTEGRATED CIRCUIT TECHNOLOGIES	81	[114-119]
17516-10	FAILURE THRESHOLD DISTRIBUTIONS IN BIPOLAR TRANSISTORS	80	[59-66]
KAWAMURA, T.			
18305-18	EMI CHARACTERISTICS OF ESD IN A SMALL AIR GAP --ARP GOVERNS THE EMI--	84	[124-130]
KELAIDIS, M. J.			
18172- 5	AIR FORCE MAINTENANCE PROGRAM FOR ELECTRICAL OVERSTRESS/ELECTROSTATIC DISCHARGE (EOS/ESD) CONTROL	83	[21-28]
KELLER, J. K.			
17516-12	PROTECTION OF MOS INTEGRATED CIRCUITS FROM DESTRUCTION BY ELECTROSTATIC DISCHARGE	80	[73-80]
KING, M. W.			
17515-12	DYNAMIC WAVEFORM CHARACTERISTICS OF PERSONNEL ELECTROSTATIC DISCHARGE	79	[78-87]
KIRK, W. J.			
18214-23	UNIFORM ESD PROTECTION IN A LARGE MULTI-DEPARTMENT ASSEMBLY PLANT	82	[165-168]
KNIGHT, E. R.			
17516-19	EFFECT OF JUNCTION SPIKES AND DOPING LEVEL ON THE SECOND BREAKDOWN SUSCEPTIBILITY OF SILICON-ON-SAPPHIRE DIODES	80	[122-129]
KOLYER, J. M.			
18305- 2	HAZARDS OF STATIC CHARGES AND FIELDS AT THE WORK STATION	84	[7-19]
18172-13	PERMANENCE OF THE ANTISTATIC PROPERTY OF COMMERCIAL ANTISTATIC BAGS AND TOTE BOXES	83	[87-94]
17517-12	SELECTION OF PACKAGING MATERIALS FOR ESD SENSITIVE ITEMS	81	[75-84]
KORN, S. R.			
18172-24	METAL OXIDE VARISTORS FOR TRANSIENT PROTECTION OF 3 TO 5-VOLT INTEGRATED CIRCUITS	83	[168-176]
KRESSLER, D. R.			
17516-26	SURGE TESTS ON PLUG-IN TRANSFORMERS	80	[176-183]
KUSENEZOV, N.			
17515-20	MODELING OF ELECTRICAL OVERSTRESS IN SILICON DEVICES	79	[133-139]
KUSNEZOV, N.			
17517-20	MODELING OF EOS IN SILICON DEVICES	81	[132-138]
LAFFERTY, D.			
18305-19	SECONDARY DISCHARGE: A NEW JEOPARDY AND A NEW TOOL	84	[131-135]

AUTHOR INDEX

<u>AUTHOR</u> <u>DOCUMENT-SEQUENCE NO.</u>	<u>TITLE</u>	<u>YEAR</u>	<u>PAGES</u>
LANE, C. H.			
17515- 8	RELIABILITY OF EOS SCREENED GOLD DOPED 4002 CMOS DEVICES	79	[41-44]
LAVOIE, L.			
17517- 2	QUANTITATIVE EFFECTS OF RELATIVE & ABSOLUTE HUMIDITY ON ESD GENERATION/ SUPPRESSION	81	[9-13]
LEE, T. W.			
18172- 7	CONSTRUCTION AND APPLICATION OF A TESTER FOR MEASURING EOS/ESD THRESHOLDS TO 15KV	83	[37-47]
LEVINSON, L. M.			
17516- 5	TRANSIENT PROTECTION WITH ZNO VARISTORS: TECHNICAL CONSIDERATIONS	80	[26-34]
LIN, T. S.			
17517-31	FAILURE ANALYSIS OF SEMICONDUCTOR DEVICES IN EOS/ESD TESTING	81	[219-224]
LINGOUSKY, J. E.			
18172- 4	ANALYSIS OF ELECTROSTATIC CHARGE PROPENSITY OF FLOOR FINISHES	83	[17-20]
LITTAU, W. R.			
17517-26	PREDICTION OF THIN-FILM RESISTOR BURNOUT	81	[192-197]
LONBORG, J. O.			
18172-10	STATIC SURVEY METERS	83	[63-66]
LUCAS, G. H.			
17517- 6	A PRAGMATIC APPROACH TO ESD PROBLEM SOLVING IN THE MANUFACTURING ENVIRONMENT A CASE HISTORY	81	[34-39]
LUISI, J. A.			
17516-13	SOS PROTECTION: THE DESIGN PROBLEM	80	[81-86]
LYNCH, J. T.			
18172-21	THE EFFECT OF ESD ON CCD RELIABILITY	83	[147-153]
MADISON, J. A.			
17515-30	THE ANALYSIS AND ELIMINATION OF EOS INDUCED SECONDARY FAILURE MECHANISMS	79	[205-209]
MADZY, T. M.			
17515- 7	MODULE ELECTROSTATIC DISCHARGE SIMULATOR	79	[36-40]
MALINARIC, P.			
17517- 9	CHO-TRAP, A NOVEL VOLTAGE TRANSIENT PROTECTION PACKAGING MATERIAL	81	[49-56]
MARTIN, L. C.			
18172-16	MODELING AND TESTING FOR SECOND BREAKDOWN PHENOMENA	83	[108-117]
18214-10	MODELING OF CURRENT AND THERMAL MODE SECOND BREAKDOWN PHENOMENA	82	[76-81]
17515-29	STATISTICAL FAILURE ANALYSIS OF MILITARY SYSTEMS FOR HIGH-ALTITUDE EMP	79	[198-204]

AUTHOR INDEX

<u>OR</u> <u>IDENT-SEQUENCE NO.</u>	<u>TITLE</u>	<u>YEAR</u>	<u>PAGES</u>
I, R. M.			
14-11	A PROBABILISTIC ESTIMATOR FOR BOUNDING TRANSISTOR EMITTER-BASE JUNCTION TRANSIENT-INDUCED FAILURES	82	[82-90]
EWS, D.			
16-18	SOME DESIGN CRITERIA FOR AVOIDING SECOND BREAKDOWN IN BIPOLAR DEVICES	80	[117-121]
JURIN, J.			
17-27	BEHAVIOR OF THICK-FILM POWER RESISTORS SUBJECTED TO LARGE MOMENTARY OVERLOADS	81	[198-201]
J. E.			
72-24	METAL OXIDE VARISTORS FOR TRANSIENT PROTECTION OF 3 TO 5-VOLT INTEGRATED CIRCUITS	83	[168-176]
ULLOUGH, D. T.			
15- 8	RELIABILITY OF EOS SCREENED GOLD DOPED 4002 CMOS DEVICES	79	[41-44]
AHON, E. J.			
15- 6	PROPOSED MIL-STD AND MIL-HDBK FOR AN ELECTROSTATIC DISCHARGE CONTROL PROGRAM - BACKGROUND AND STATUS	79	[27-35]
EER, R. E.			
17- 6	A PRAGMATIC APPROACH TO ESD PROBLEM SOLVING IN THE MANUFACTURING ENVIRONMENT A CASE HISTORY	81	[34-39]
EER, O. J.			
14- 5	LATENT ESD FAILURES	82	[41-48]
17- 3	ANALYSIS OF ESD FAILURES	81	[14-20]
16-28	AN EFFECTIVE ESD AWARENESS TRAINING PROGRAM	80	[189-191]
15- 1	AN EFFECTIVE ESD AWARENESS TRAINING PROGRAM	79	[1-3]
NALD, A.			
17- 6	A PRAGMATIC APPROACH TO ESD PROBLEM SOLVING IN THE MANUFACTURING ENVIRONMENT A CASE HISTORY	81	[34-39]
RLAND, W. Y.			
17- 5	THE ECONOMIC BENEFITS OF AN EFFECTIVE ESD AWARENESS AND CONTROL PROGRAM - AN EMPIRICAL ANALYSIS	81	[29-33]
NNA, A.			
15-24	SUSCEPTIBILITY OF LSI MOS TO ELECTROSTATIC DISCHARGE AT ELEVATED TEMPERATURE	79	[168-175]
BERG, H.			
17- 1	A CLOSER LOOK AT THE HUMAN ESD EVENT	81	[1-8]
16-33	MEASUREMENT OF FAST TRANSIENTS AND APPLICATION TO HUMAN ESD	80	[225-230]
URN, R. T.			
17-16	DIAGNOSIS AND ANALYSIS OF EMITTER-BASE JUNCTION OVERSTRESS DAMAGE	81	[101-105]
HAM, J. R.			
05-13	A MATERIAL EVALUATION PROGRAM FOR DECORATIVE STATIC CONTROL TABLE TOP LAMINATES	84	[85-93]

AUTHOR INDEX

<u>IR</u> <u>IDENT-SEQUENCE NO.</u>	<u>TITLE</u>	<u>YEAR</u>	<u>PAGES</u>
IR, R. L.			
5-27	THE PHANTOM EMITTER-AN ESD-RESISTANT BIPOLAR TRANSISTOR DESIGN AND ITS APPLICATIONS TO LINEAR INTEGRATED CIRCUITS	79	[188-192]
II, S.			
15-13	FAILURE ANALYSIS OF MICROCIRCUITS SUBJECTED TO ELECTRICAL OVERSTRESS	79	[88-96]
M. G.			
15-15	ESD SUSCEPTIBILITIES OF HIGH PERFORMANCE ANALOG INTEGRATED CIRCUITS	79	[104-108]
IS, S.			
16-15	ELECTROSTATIC SENSITIVITY OF VARIOUS INPUT PROTECTION NETWORKS	80	[95-103]
INEN, C. F.			
72-11	THE ROOM AIR IONIZATION SYSTEM, A BETTER ALTERNATIVE THAN 40% RELATIVE HUMIDITY	83	[67-75]
17-29	POTENTIAL ESD HAZARDS ASSOCIATED WITH EXPLOSIVE PRIMERS	81	[208-211]
P. H.			
72-22	EOS OR ESD: CAN FAILURE ANALYSIS TELL THE DIFFERENCE?	83	[154-157]
C. L.			
72- 5	AIR FORCE MAINTENANCE PROGRAM FOR ELECTRICAL OVERSTRESS/ELECTROSTATIC DISCHARGE (EOS/ESD) CONTROL	83	[21-28]
I, T.			
15- 6	PROPOSED MIL-STD AND MIL-HDBK FOR AN ELECTROSTATIC DISCHARGE CONTROL PROGRAM - BACKGROUND AND STATUS	79	[27-35]
S, W. J.			
72-16	MODELING AND TESTING FOR SECOND BREAKDOWN PHENOMENA	83	[108-117]
14-10	MODELING OF CURRENT AND THERMAL MODE SECOND BREAKDOWN PHENOMENA	82	[76-81]
BAY, D. E.			
16- 2	THE EFFECTS OF HIGH HUMIDITY ENVIRONMENTS ON ELECTROSTATIC GENERATION AND DISCHARGE	80	[12-16]
HOLY, R. K.			
17-13	THE EFFECTS OF VLSI SCALING ON EOS/ESD FAILURE THRESHOLD	81	[85-89]
ISE, E. D.			
16- 4	ELECTROSTATIC DISCHARGE (ESD) MONITOR DESIGN	80	[23-25]
REK, R. A.			
72-20	ESD EVALUATION OF RADIATION-HARDENED, HIGH RELIABILITY CMOS AND NMOS ICS	83	[134-146]
E, R. L.			
17-33	EOS DAMAGE IN SILICON SOLAR CELLS	81	[209-235]
LLA, J.			
17- 9	CHO-TRAP, A NOVEL VOLTAGE TRANSIENT PROTECTION PACKAGING MATERIAL	81	[49-56]

AUTHOR INDEX

<u>I-SEQUENCE NO.</u>	<u>TITLE</u>	<u>YEAR</u>	<u>PAGES</u>
.M.			
6	A SURVEY OF EOS/ESD DATA SOURCES	82	[49-55]
F,J.			
21	AN EVALUATION OF EOS FAILURE MODELS	84	[144-156]
,J.F.			
11	EFFECTS OF ELECTRICAL OVERSTRESS ON DIGITAL BIPOLAR MICROCIRCUITS AND ANALYSIS TECHNIQUES FOR FAILURE SITE LOCATION	79	[64-77]
O,C.J.			
26	ELECTRICAL OVERSTRESS VERSUS DEVICE GEOMETRY	79	[183-187]
,H.R.			
5	TRANSIENT PROTECTION WITH ZNO VARISTORS: TECHNICAL CONSIDERATIONS	80	[26-34]
S,L.P.			
19	BASIC SPECIFICATION FOR ESD PROTECTION IN INDUSTRY	82	[136-141]
D.G.			
21	AN EVALUATION OF EOS FAILURE MODELS	84	[144-156]
11	A PROBABILISTIC ESTIMATOR FOR BOUNDING TRANSISTOR EMITTER-BASE JUNCTION TRANSIENT-INDUCED FAILURES	82	[82-90]
7	MODELING METALLIZATION BURNOUT OF INTEGRATED CIRCUITS	82	[56-61]
19	AN OVERVIEW OF EOS EFFECTS ON SEMICONDUCTOR DEVICES	81	[120-131]
,W.M.			
17	TEMPERATURE AT SECOND BREAKDOWN AT A WELL-DEFINED SITE	83	[118-121]
12	SECOND BREAKDOWN IN SWITCHING TRANSISTORS	82	[91-93]
.A.			
7	MODULE ELECTROSTATIC DISCHARGE SIMULATOR	79	[36-40]
N,R.			
24	CIRCUIT DESIGN FOR EOS/ESD PROTECTION	82	[169-174]
NO,E.			
22	MICROWAVE NANOSECOND PULSE BURNOUT PROPERTIES OF ONE MICRON MESFETS	79	[147-157]
H.			
15	ELECTROACTIVE POLYMERS AS ALTERNATE ESD PROTECTIVE MATERIALS	82	[115-119]
SON,L.			
27	A CMOS VLSI ESD INPUT PROTECTION DEVICE, DIFIDW	84	[202-209]
,L.			
5	THE GENERATION OF ELECTROSTATIC CHARGES IN SILICONE ENCAPSULANTS DURING CYCLIC GASEOUS PRESSURE TESTS	79	[22-26]

AUTHOR INDEX

<u>T-SEQUENCE NO.</u>	<u>TITLE</u>	<u>YEAR</u>	<u>PAGES</u>
,B.C.			
22	DETERMINATION OF THRESHOLD ENERGIES AND DAMAGE MECHANISMS IN SEMICONDUCTOR DEVICES SUBJECTED TO VOLTAGE TRANSIENTS	84	[157-164]
.			
28	A STUDY OF ESD LATENT DEFECTS IN SEMICONDUCTORS	83	[198-204]
,E,R.N.			
26	A SUMMARY OF MOST EFFECTIVE ELECTROSTATIC DISCHARGE PROTECTION CIRCUITS FOR MOS MEMORIES AND THEIR OBSERVED FAILURE MODES	83	[181-184]
,I.H.			
3	LIMITATIONS IN MODELING ELECTRICAL OVERSTRESS FAILURE IN SEMICONDUCTOR DEVICES	82	[19-33]
23	EOS/ESD FAILURE THRESHOLD ANALYSIS ERRORS, THEIR SOURCE, SIZE AND CONTROL	81	[151-166]
,ORD,D.H.			
11	EFFECTS OF ELECTRICAL OVERSTRESS ON DIGITAL BIPOLAR MICROCIRCUITS AND ANALYSIS TECHNIQUES FOR FAILURE SITE LOCATION	79	[64-77]
,N.I.			
13	A MATERIAL EVALUATION PROGRAM FOR DECORATIVE STATIC CONTROL TABLE TOP LAMINATES	84	[85-93]
,J.P.			
3	TEST EQUIPMENT--A SOURCE OF ESD!!	84	[20-21]
25	IN-CIRCUIT ANALYSIS OF ESD DAMAGED DEVICES	82	[175-178]
,ER,T.R.			
18	HUMAN FACTORS IN ELECTROSTATIC DISCHARGE PROTECTION	79	[122-125]
,J.R.			
16	SUPRISING PATTERNS OF CMOS SUSCEPTIBILITY TO ESD AND IMPLICATIONS ON LONG-TERM RELIABILITY	80	[104-111]
.			
22	ESD MINIMIZATION TECHNIQUE FOR MOS MANUFACTURING FINAL TEST AREA	82	[157-164]
,N.			
23	DEGRADATION BY ESD TRANSIENTS OF THE SUBSTRATE BIAS VOLTAGE OF NMOS 8085-TYPE MICROPROCESSORS	84	[165-178]
8	A PROGRAMMABLE EQUIPMENT FOR ELECTROSTATIC DISCHARGE TESTING TO HUMAN BODY MODELS	83	[48-55]
27	ESD SENSITIVITY OF NMOS LSI CIRCUITS AND THEIR FAILURE CHARACTERISTICS	83	[185-197]
,D.K.			
27	ELECTROSTATIC DISCHARGE IMMUNITY IN COMPUTER SYSTEMS	82	[185-189]
,W.L.			
21	AN EVALUATION OF EOS FAILURE MODELS	84	[144-156]
,R.			
27	A CMOS VLSI ESD INPUT PROTECTION DEVICE, DIFIDW	84	[202-209]

Section 5:

KEYWORD IN TITLE INDEX

CORPORATE INDEX

<u>SEQUENCE NO.</u>	<u>TITLE</u>	<u>YEAR</u>	<u>PAGES</u>
ELECTRIC COMPANY, INC.			
	ESD-HOW OFTEN DOES IT HAPPEN?	83	[1-5]
	THE ECONOMIC BENEFITS OF AN EFFECTIVE ESD AWARENESS AND CONTROL PROGRAM - AN EMPIRICAL ANALYSIS	81	[29-33]
USE			
	LATENT ESD FAILURES	82	[41-48]
	ANALYSIS OF ESD FAILURES	81	[14-20]
	HIGH-FIELD PHENOMENA AND FAILURE MECHANISMS IN BIPOLAR TRANSISTORS	80	[112-116]
	AN EFFECTIVE ESD AWARENESS TRAINING PROGRAM	80	[189-191]
	AN EFFECTIVE ESD AWARENESS TRAINING PROGRAM	79	[1-3]
	THE ANALYSIS AND ELIMINATION OF EOS INDUCED SECONDARY FAILURE MECHANISMS	79	[205-209]

CORPORATE INDEX

<u>RATION</u> <u>ENT-SEQUENCE NO.</u>	<u>TITLE</u>	<u>YEAR</u>	<u>PAGES</u>
Y UNIVAC			
4-21	AN EFFECTIVE ELECTROSTATIC DISCHARGE PROTECTION PROGRAM	82	[145-156]
ARD ELECTRIK LORENZ AG			
7-17	SUSCEPTIBILITY OF ICS IN ESD STEP-STRESS TESTS	81	[106-113]
AT BUFFALO			
5-21	SQUARE PULSE AND RF PULSE OVERSTRESSING OF UHF TRANSISTORS	79	[140-146]
5-22	MICROWAVE NANOSECOND PULSE BURNOUT PROPERTIES OF ONE MICRON MESFETS	79	[147-157]
ICAL UNIVERSITY OF DENMARK			
15- 8	STATIC-ELECTRIC CHARACTERIZATION OF SEMI-INSULATING MATERIALS	84	[45-49]
IONIX			
16- 9	STUDY OF EFFECTS OF ELECTRO-STATIC DISCHARGE ON SOLID-STATE DEVICES	80	[58]
; INSTRUMENTS (TI)			
72-26	A SUMMARY OF MOST EFFECTIVE ELECTROSTATIC DISCHARGE PROTECTION CIRCUITS FOR MOS MEMORIES AND THEIR OBSERVED FAILURE MODES	83	[181-184]
17- 6	A PRAGMATIC APPROACH TO ESD PROBLEM SOLVING IN THE MANUFACTURING ENVIRONMENT A CASE HISTORY	81	[34-39]
S TECH UNIVERSITY			
72-17	TEMPERATURE AT SECOND BREAKDOWN AT A WELL-DEFINED SITE	83	[118-121]
14-12	SECOND BREAKDOWN IN SWITCHING TRANSISTORS	82	[91-93]
OR MBA			
14-14	METALLOPLASTICS	82	[110-114]
72-18 SEMICONDUCTOR JUNCTION NON-LINEAR FAILURE POWER THRESHOLDS: WUNSCH-BELL REVISITED			
14- 3	LIMITATIONS IN MODELING ELECTRICAL OVERSTRESS FAILURE IN SEMICONDUCTOR DEVICES	82	[19-33]
14- 8	AN IMPROVED EOS CONDUCTION MODEL OF SEMICONDUCT DEVICES	82	[62-70]
17-23	EOS/ESD FAILURE THRESHOLD ANALYSIS ERRORS, THEIR SOURCE, SIZE AND CONTROL	81	[151-166]
17-31	FAILURE ANALYSIS OF SEMICONDUCTOR DEVICES IN EOS/ESD TESTING	81	[219-224]
17-35	NON-LINEAR KINETICS OF SEMICONDUCTOR JUNCTION THERMAL FAILURE	81	[242-245]
16-21	ASSESSING ELECTRICAL OVERSTRESS EFFECTS ON ELECTRONIC SYSTEMS	80	[140-148]
AIR FORCE			
05- 4	ESD DAMAGE, DOES IT HAPPEN ON PCBS?	84	[22-23]
72- 5	AIR FORCE MAINTENANCE PROGRAM FOR ELECTRICAL OVERSTRESS/ELECTROSTATIC DISCHARGE (EOS/ESD) CONTROL	83	[21-28]
14- 4	ELECTRICAL OVERSTRESS THRESHOLD TESTING	82	[34-40]
17-28	EOS THRESHOLD DETERMINATION OF ELECTRO-EXPLOSIVE DEVICES	81	[202-207]
ARMY			
16-18	SOME DESIGN CRITERIA FOR AVOIDING SECOND BREAKDOWN IN BIPOLAR DEVICES	80	[117-121]
ERSITY OF SOUTHAMPTON			
05-26	ESD SENSITIVITY AND LATENCY EFFECTS OF SOME HCMOS INTEGRATED CIRCUITS	84	[196-201]

CORPORATE INDEX

<u>ORATION</u> <u>MENT-SEQUENCE NO.</u>	<u>TITLE</u>	<u>YEAR</u>	<u>PAGES</u>
SEY			
72-21	THE EFFECT OF ESD ON CCD RELIABILITY	83	[147-153]
HEON			
15- 5	THE GENERATION OF ELECTROSTATIC CHARGES IN SILICONE ENCAPSULANTS DURING CYCLIC GASEOUS PRESSURE TESTS	79	[22-26]
15-11	EFFECTS OF ELECTRICAL OVERSTRESS ON DIGITAL BIPOLAR MICROCIRCUITS AND ANALYSIS TECHNIQUES FOR FAILURE SITE LOCATION	79	[64-77]
05-14	A WRIST STRAP LIFE TEST PROGRAM	84	[94-96]
05-20	PROTECTION OF COMPONENTS AGAINST ELECTRICAL OVERSTRESS (EOS) AND TRANSIENTS IN MONITORS	84	[136-143]
72-25	USING SCR'S AS TRANSIENT PROTECTION STRUCTURES IN INTEGRATED CIRCUITS	83	[177-180]
15-26	ELECTRICAL OVERSTRESS VERSUS DEVICE GEOMETRY	79	[183-187]
ABILITY SCIENCES, INC.			
15- 6	PROPOSED MIL-STD AND MIL-HDBK FOR AN ELECTROSTATIC DISCHARGE CONTROL PROGRAM - BACKGROUND AND STATUS	79	[27-35]
WELL			
05- 2	HAZARDS OF STATIC CHARGES AND FIELDS AT THE WORK STATION	84	[7-19]
72-13	PERMANENCE OF THE ANTISTATIC PROPERTY OF COMMERCIAL ANTISTATIC BAGS AND TOTE BOXES	83	[87-94]
17-12	SELECTION OF PACKAGING MATERIALS FOR ESD SENSITIVE ITEMS	81	[75-84]
17-13	THE EFFECTS OF VLSI SCALING ON EOS/ESD FAILURE THRESHOLD	81	[85-89]
16-13	SOS PROTECTION: THE DESIGN PROBLEM	80	[81-86]
AIR DEVELOPMENT CENTER (RADC)			
15- 8	RELIABILITY OF EOS SCREENED GOLD DOPED 4002 CMOS DEVICES	79	[41-44]
IA LABORATORIES			
72-20	ESD EVALUATION OF RADIATION-HARDENED, HIGH RELIABILITY CMOS AND MNOS ICS	83	[134-146]
16-10	FAILURE THRESHOLD DISTRIBUTIONS IN BIPOLAR TRANSISTORS	80	[59-66]
16-16	SUPRISING PATTERNS OF CMOS SUSCEPTIBILITY TO ESD AND IMPLICATIONS ON LONG-TERM RELIABILITY	80	[104-111]
15-25	THE DIELECTRIC STRENGTH OF SIO2 IN A CMOS TRANSISTOR STRUCTURE	79	[176-182]
NTIFIC ENTERPRISES, INC.			
16-31	STATIC CONTROL SYSTEMS	80	[213-217]
O COMPANY			
72-12	MEASURING EFFECTIVENESS OF AIR IONIZERS	83	[76-86]
LDING FIBRE COMPANY, INC.			
05-13	A MATERIAL EVALUATION PROGRAM FOR DECORATIVE STATIC CONTROL TABLE TOP LAMINATES	84	[85-93]
RY CORPORATION			
72-23	INVISIBLE EOS/ESD DAMAGE: HOW TO FIND IT	83	[158-167]
16-24	TEST WAVEFORMS AND TECHNIQUES TO ASSESS THE THREAT TO ELECTRONIC DEVICES OF LIGHTNING-INDUCED TRANSIENTS	80	[161-166]

CORPORATE INDEX

<u>PORTION</u> <u>UMENT-SEQUENCE NO.</u>	<u>TITLE</u>	<u>YEAR</u>	<u>PAGES</u>
KHEED			
172- 2	ESD CONTROL IMPLEMENTATION AND COST AVOIDANCE ANALYSIS	83	[6-11]
517-20	MODELING OF EOS IN SILICON DEVICES	81	[132-138]
517-26	PREDICTION OF THIN-FILM RESISTOR BURNOUT	81	[192-197]
515-20	MODELING OF ELECTRICAL OVERSTRESS IN SILICON DEVICES	79	[133-139]
NAVOX			
305- 3	TEST EQUIPMENT--A SOURCE OF ESD!!	84	[20-21]
214-25	IN-CIRCUIT ANALYSIS OF ESD DAMAGED DEVICES	82	[175-178]
TIN MARIETTA			
172-14	COPLANAR TRIBOELECTRIFICATION OF SELECTED MATERIALS	83	[95-101]
172-19	ESD SENSITIVITY OF COMPLEX ICS	83	[128-133]
172-28	A STUDY OF ESD LATENT DEFECTS IN SEMICONDUCTORS	83	[198-204]
ROWAVE ASSOCIATES, INC.			
515-14	ELECTROSTATIC FAILURE OF X-BAND SILICON SCHOTTKY BARRIER DIODES	79	[97-103]
ISTORY OF LABOUR			
1305- 9	ESTIMATION OF DISCHARGE ENERGY RELEASED FROM CHARGED INSULATOR	84	[50-57]
ISION RESEARCH CORPORATION			
517-33	EOS DAMAGE IN SILICON SOLAR CELLS	81	[209-235]
516-22	SOLAR CELL ELECTRICAL OVERSTRESS ANALYSIS	80	[149-153]
ITEK			
1214-22	ESD MINIMIZATION TECHNIQUE FOR MOS MANUFACTURING FINAL TEST AREA	82	[157-164]
517-15	INPUT PROTECTION DESIGN FOR THE 3-MICRON NMOS PROCESS	81	[97-100]
516-15	ELECTROSTATIC SENSITIVITY OF VARIOUS INPUT PROTECTION NETWORKS	80	[95-103]
OROLA			
1172- 3	THE PRODUCTION OPERATOR: WEAK LINK OR WARRIOR IN THE ESD BATTLE?	83	[12-16]
1172- 7	CONSTRUCTION AND APPLICATION OF A TESTER FOR MEASURING EOS/ESD THRESHOLDS TO 15KV	83	[37-47]
517-14	ON CHIP PROTECTION OF HIGH DENSITY NMOS DEVICES	81	[90-96]
517-16	DIAGNOSIS AND ANALYSIS OF EMITTER-BASE JUNCTION OVERSTRESS DAMAGE	81	[101-105]
TIONAL BUREAU OF STANDARDS (NBS)			
515-17	REVERSE-BIAS SECOND BREAKDOWN IN POWER TRANSISTORS	79	[116-121]
AL RESEARCH LABORATORY (NRL)			
1214-15	ELECTROACTIVE POLYMERS AS ALTERNATE ESD PROTECTIVE MATERIALS	82	[115-119]
PON UNIVAC KAISHA, LTD.			
1305-18	EMI CHARACTERISTICS OF ESD IN A SMALL AIR GAP --ARP GOVERNS THE EMI--	84	[124-130]
THERN TELECOM			
516-11	ANALYSIS OF ESD DAMAGE IN JPET PREAMPLIFIERS	80	[67-72]
KAGING INDUSTRIES OF CALIFORNIA			
517- 8	AN ANALYSIS OF ANTISTATIC CUSHIONING MATERIALS	81	[44-48]

CORPORATE INDEX

<u>CORPORATION</u> <u>DOCUMENT-SEQUENCE NO.</u>	<u>TITLE</u>	<u>YEAR</u>	<u>PAGES</u>
HEWLETT PACKARD			
17516-14	LSI DESIGN CONSIDERATIONS FOR ESD PROTECTION STRUCTURES RELATED TO PROCESS AND LAYOUT VARIATIONS	80	[87-94]
17515-10	ELECTRO-STATIC DISCHARGE AND CMOS LOGIC	79	[55-63]
17515-24	SUSCEPTIBILITY OF LSI MOS TO ELECTROSTATIC DISCHARGE AT ELEVATED TEMPERATURE	79	[168-175]
MITSUBISHI			
17515-13	FAILURE ANALYSIS OF MICROCIRCUITS SUBJECTED TO ELECTRICAL OVERSTRESS	79	[88-96]
DOWNEYWELL			
18172-11	THE ROOM AIR IONIZATION SYSTEM, A BETTER ALTERNATIVE THAN 40% RELATIVE HUMIDITY	83	[67-75]
18214-27	ELECTROSTATIC DISCHARGE IMMUNITY IN COMPUTER SYSTEMS	82	[185-189]
17517- 2	QUANTITATIVE EFFECTS OF RELATIVE & ABSOLUTE HUMIDITY ON ESD GENERATION/ SUPPRESSION	81	[9-13]
17517-29	POTENTIAL ESD HAZARDS ASSOCIATED WITH EXPLOSIVE PRIMERS	81	[208-211]
17516-32	AN EVALUATION OF WRIST STRAP PARAMETERS	80	[218-224]
IBM CORPORATION			
18172-22	EOS OR ESD: CAN FAILURE ANALYSIS TELL THE DIFFERENCE?	83	[154-157]
17516- 4	ELECTROSTATIC DISCHARGE (ESD) MONITOR DESIGN	80	[23-25]
17515- 7	MODULE ELECTROSTATIC DISCHARGE SIMULATOR	79	[36-40]
MIT RESEARCH INSTITUTE			
18214- 1	ESD SUSCEPTIBILITY TESTING OF ADVANCED SCHOTTKY TTL	82	[1-12]
17516- 8	IDENTIFICATION OF LATENT ESD FAILURES	80	[54-57]
17515-23	DAMAGE RESPONSE OF SELECTED INTERFACE INTEGRATED CIRCUITS TO A SIMULATED EMP	79	[158-167]
INTEL			
18305-19	SECONDARY DISCHARGE: A NEW JEOPARDY AND A NEW TOOL	84	[131-135]
JET PROPULSION LABORATORY (JPL)			
18172-10	STATIC SURVEY METERS	83	[63-66]
AMMAN SCIENCES CORPORATION			
17517-21	SEMICONDUCTOR DEVICE FAILURE CRITERIA FOR SINUSOIDAL STRESSES	81	[139-144]
LAWRENCE LIVERMORE NATIONAL LABORATORY			
18172-16	MODELING AND TESTING FOR SECOND BREAKDOWN PHENOMENA	83	[108-117]
18214-10	MODELING OF CURRENT AND THERMAL MODE SECOND BREAKDOWN PHENOMENA	82	[76-81]
17515-29	STATISTICAL FAILURE ANALYSIS OF MILITARY SYSTEMS FOR HIGH-ALTITUDE EMP	79	[198-204]
EAR SIEGLER, INC.			
18214-16	DRASTIC LOSSES OF CONDUCTIVITY IN ANTISTATIC PLASTICS	82	[120-123]
17517- 7	A LOW-COST PROGRAM FOR EVALUATION OF ESD PROTECTIVE MATERIALS AND EQUIPMENT	81	[41-43]
17517-32	TIME-RELATED IMPROVEMENTS OF ELECTRICAL CHARACTERISTICS IN ELECTROSTATICALLY DAMAGED OPERATIONAL AMPLIFIERS	81	[225-228]
LIGHTNING TECHNOLOGIES			
17516-25	LIGHTNING PROTECTION DESIGN FOR A PHOTOVOLTAIC CONCENTRATOR	80	[167-175]
DICKHEED			
18305- 5	ELECTROSTATIC MEASUREMENT FOR PROCESS CONTROL	84	[25-33]
18305-15	TESTING OF ELECTROSTATIC MATERIALS FED. STD. 101C, METHOD 4046.1	84	[97-103]

CORPORATE INDEX

<u>CORPORATION</u> <u>DOCUMENT-SEQUENCE NO.</u>	<u>TITLE</u>	<u>YEAR</u>	<u>PAGES</u>
E-SYSTEMS, INC.			
17516- 2	THE EFFECTS OF HIGH HUMIDITY ENVIRONMENTS ON ELECTROSTATIC GENERATION AND DISCHARGE	80	[12-16]
EG&G WASC, INC.			
18214-28	ELECTRICAL GROUNDING IN LARGE INSTRUMENTATION SYSTEMS	82	[190-202]
EPITEK ELECTRONIC, LTD.			
17517-27	BEHAVIOR OF THICK-FILM POWER RESISTORS SUBJECTED TO LARGE MOMENTARY OVERLOADS	81	[198-201]
ERA TECHNOLOGY, LTD.			
18305-22	DETERMINATION OF THRESHOLD ENERGIES AND DAMAGE MECHANISMS IN SEMICONDUCTOR DEVICES SUBJECTED TO VOLTAGE TRANSIENTS	84	[157-164]
EXPERIMENTAL PHYSICS CORPORATION			
18305-16	CRITICAL CONSIDERATIONS FOR ESD TESTING	84	[104-111]
17517- 1	A CLOSER LOOK AT THE HUMAN ESD EVENT	81	[1-8]
17516-33	MEASUREMENT OF FAST TRANSIENTS AND APPLICATION TO HUMAN ESD	80	[225-230]
GARRETT MANUFACTURING, LTD.			
18214-19	BASIC SPECIFICATION FOR ESD PROTECTION IN INDUSTRY	82	[136-141]
GENERAL ELECTRIC			
18172-24	METAL OXIDE VARISTORS FOR TRANSIENT PROTECTION OF 3 TO 5-VOLT INTEGRATED CIRCUITS	83	[168-176]
17517-25	PULSE POWER RESPONSE AND DAMAGE CHARACTERISTICS OF CAPACITORS	81	[174-191]
17516- 5	TRANSIENT PROTECTION WITH ZNO VARISTORS: TECHNICAL CONSIDERATIONS	80	[26-34]
17516- 6	PROTECTION LEVEL COMPARISONS FOR VOLTAGE TRANSIENT SUPPRESSORS (120 V, AC TYPE)	80	[35-43]
GENERAL INSTRUMENT			
17516- 7	GAS TUBE SURGE ARRESTERS FOR CONTROL OF TRANSIENT VOLTAGES	80	[44-53]
GENERAL SEMICONDUCTOR INDUSTRIES			
17517-30	LIGHTNING PROTECTION FOR COMPUTER DATA LINES	81	[212-218]
17515-28	ELECTROSTATIC DISCHARGE PROTECTION USING SILICON TRANSIENT SUPPRESSORS	79	[193-197]
GOULD			
17515-18	HUMAN FACTORS IN ELECTROSTATIC DISCHARGE PROTECTION	79	[122-125]
HARRIS			
17515-15	ESD SUSCEPTIBILITIES OF HIGH PERFORMANCE ANALOG INTEGRATED CIRCUITS	79	[104-108]
HARRY DIAMOND LAB (HDL)			
18172-15	CALCULATIONS OF SECOND BREAKDOWN IN SILICON DIODES AT MICROWAVE FREQUENCIES	83	[102-107]
18214- 9	THE FORWARD-BIAS CHARACTERISTIC AS A PREDICTOR AND SCREEN OF REVERSE-BIAS SECOND BREAKDOWN	82	[71-75]
17516-20	OSCILLATING VOLTAGE PULSES AND SECOND BREAKDOWN	80	[130-139]
17515-16	DOPING PROFILES AND SECOND BREAKDOWN	79	[109-115]
HEWLETT PACKARD			
18214-20	ESD IN I.C. ASSEMBLY (A BASE LINE SOLUTION)	82	[142-144]
18214-26	ELECTROSTATIC DISCHARGE AT THE PRODUCT LEVEL	82	[179-184]

CORPORATE INDEX

<u>CORPORATION</u> <u>DOCUMENT-SEQUENCE NO.</u>	<u>TITLE</u>	<u>YEAR</u>	<u>PAGES</u>
BENDIX			
18214-23	UNIFORM ESD PROTECTION IN A LARGE MULTI-DEPARTMENT ASSEMBLY PLANT	82	[165-168]
BOOZ, ALLEN & HAMILTON			
18305-21	AN EVALUATION OF EOS FAILURE MODELS	84	[144-156]
18214- 6	A SURVEY OF EOS/ESD DATA SOURCES	82	[49-55]
18214- 7	MODELING METALLIZATION BURNOUT OF INTEGRATED CIRCUITS	82	[56-61]
18214-11	A PROBABILISTIC ESTIMATOR FOR BOUNDING TRANSISTOR EMITTER-BASE JUNCTION TRANSIENT-INDUCED FAILURES	82	[82-90]
17517-19	AN OVERVIEW OF EOS EFFECTS ON SEMICONDUCTOR DEVICES	81	[120-131]
17516-23	AN OVERVIEW OF THE SOURCES AND EFFECTS OF ELECTRICAL OVERSTRESS	80	[154-160]
BRITISH TELECOM			
18305-12	AN EXPERIMENTAL STUDY OF THE ESD SCREENING EFFECTIVENESS OF ANTI-STATIC BAGS	84	[78-84]
18305-23	DEGRADATION BY ESD TRANSIENTS OF THE SUBSTRATE BIAS VOLTAGE OF NMOS 8085-TYPE MICROPROCESSORS	84	[165-178]
18305-25	A FAILURE ANALYSIS METHODOLOGY FOR REVEALING ESD DAMAGE TO INTEGRATED CIRCUITS	84	[189-195]
18172- 8	A PROGRAMMABLE EQUIPMENT FOR ELECTROSTATIC DISCHARGE TESTING TO HUMAN BODY MODELS	83	[48-55]
18172-27	ESD SENSITIVITY OF NMOS LSI CIRCUITS AND THEIR FAILURE CHARACTERISTICS	83	[185-197]
CHARLES STARK DRAPER LABORATORIES			
17515- 3	ELECTROSTATIC CONDUCTIVITY CHARACTERISTICS OF WORKBENCH-TOP SURFACE MATERIALS	79	[7-12]
CHARLESWATERS PRODUCT, INC.			
18214-17	CHARACTERIZATION OF ESD SAFE REQUIREMENTS FOR FLOOR SURFACES	82	[124-130]
17516- 1	PASSIVE STATIC PROTECTION: THEORY AND PRACTICE	80	[1-11]
CHOMERIC, INC.			
17517- 9	CHO-TRAP, A NOVEL VOLTAGE TRANSIENT PROTECTION PACKAGING MATERIAL	81	[49-56]
CLARKSON COLLEGE			
18214-24	CIRCUIT DESIGN FOR EOS/ESD PROTECTION	82	[169-174]
17516-30	BASIC CONSIDERATIONS IN ELECTRO-THERMAL OVERSTRESS IN ELECTRONIC COMPONENTS	80	[206-212]
CONSULTANT			
18305-10	TRIBOELECTRIC TESTING FOR ELECTROSTATIC CHARGES ON MATERIALS AT KENNEDY SPACE CENTER	84	[58-63]
17515-12	DYNAMIC WAVEFORM CHARACTERISTICS OF PERSONNEL ELECTROSTATIC DISCHARGE	79	[78-87]
DASH, STRAUS, & GOODHUE, INC.			
18305-17	DESIGNING TO AVOID STATIC - ESD TESTING OF DIGITAL DEVICES	84	[112-123]
DIGITAL EQUIPMENT CORPORATION (DEC)			
18305-27	A CMOS VLSI ESD INPUT PROTECTION DEVICE, DIFIDW	84	[202-209]
DOUGLAS AIRCRAFT			
17517- 4	THE PERFECT "10" - CAN YOU REALLY HAVE ONE?	81	[21-27]
DU PONT			
17517-11	INCOMING INSPECTION OF ANTISTATIC PACKAGING MATERIALS	81	[65-74]

CORPORATE INDEX

<u>CORPORATION</u>	<u>DOCUMENT-SEQUENCE NO.</u>	<u>TITLE</u>	<u>YEAR</u>	<u>PAGES</u>
3M				
	18305-11	TRIBOELECTRIC CHARGE: ITS ESD ABILITY AND A MEASUREMENT METHOD FOR ITS PROPENSITY ON PACKING MATERIALS	84	[64-77]
	18214-13	TEST METHODS FOR STATIC CONTROL PRODUCTS	82	[94-109]
	17515- 9	THE DEFICIENCIES IN MILITARY SPECIFICATION MIL-B-81705: CONSIDERATIONS AND A SIMPLE MODEL FOR STATIC PROTECTION	79	[45-54]
AEROSPACE CORPORATION				
	17515- 2	CONTROLLING ELECTROSTATIC PROBLEMS IN THE FABRICATION AND HANDLING OF SPACECRAFT HARDWARE	79	[4-6]
AMERICAN INSTITUTE OF MEDICAL CLIMATOLOGY (AIMC)				
	18305- 6	EFFECTS OF AIR IONS AND ELECTRIC FIELDS ON HEALTH AND PRODUCTIVITY	84	[34-39]
ANALYTICAL CHEMICAL LABORATORY				
	17516-29	FACILITY EVALUATION: ISOLATING ENVIRONMENTAL ESD PROBLEMS	80	[192-205]
	17515- 4	STATIC CONTROL USING TOPICAL ANTISTATS	79	[13-21]
ARATEX				
	18214-18	ESD AND CONTAMINATION FROM CLEAN ROOM GARMENTS - PROBLEMS AND SOLUTIONS	82	[131-135]
ATT				
	18305- 1	A REALISTIC AND SYSTEMATIC ESD CONTROL PLAN	84	[1-6]
AUBURN UNIVERSITY				
	17516-19	EFFECT OF JUNCTION SPIKES AND DOPING LEVEL ON THE SECOND BREAKDOWN SUSCEPTIBILITY OF SILICON-ON-SAPPHIRE DIODES	80	[122-129]
	17515-19	AN ELECTROTHERMAL MODEL FOR CURRENT FILAMENTATION IN SECOND BREAKDOWN OF SILICON-ON-SAPPHIRE DIODES	79	[126-132]
BDM CORPORATION				
	18172- 9	POWER FAILURE MODELING OF INTEGRATED CIRCUITS	83	[56-62]
	17517-18	ELECTRICAL OVERSTRESS INVESTIGATIONS IN MODERN INTEGRATED CIRCUIT TECHNOLOGIES	81	[114-119]
	17517-22	DETERMINING AN EMITTER-BASE FAILURE THRESHOLD DISTRIBUTION OF NPN TRANSISTORS	81	[145-150]
	17517-24	AN OVERVIEW OF EOS EFFECTS ON PASSIVE COMPONENTS	81	[167-173]
	17516-27	MICROCIRCUIT ELECTRICAL OVERSTRESS TOLERANCE TESTING AND QUALIFICATION	80	[184-188]
BELL COMMUNICATIONS RESEARCH, INC.				
	18305- 7	A ROOM IONIZATION SYSTEM FOR ELECTROSTATIC CHARGE AND DUST CONTROL	84	[40-44]
BELL LABORATORIES				
	18305-24	DEVICE ESD SUSCEPTIBILITY TESTING AND DESIGN HARDENING	84	[179-188]
	18172- 4	ANALYSIS OF ELECTROSTATIC CHARGE PROPENSITY OF FLOOR FINISHES	83	[17-20]
	18172- 6	ESD BY STATIC INDUCTION	83	[29-36]
	18214- 2	ELECTROSTATIC DISCHARGE (ESD) DAMAGE SUSCEPTIBILITY OF THIN FILM RESISTORS AND CAPACITORS	82	[13-18]
	17517-10	EVALUATION OF INTEGRATED CIRCUIT SHIPPING TUBES	81	[57-64]
	17517-34	EVALUATION OF ELECTROSTATIC DISCHARGE TO 16K EPROMS	81	[236-241]
	17516- 3	ESD DAMAGE FROM TRIBOELECTRICALLY CHARGED IC PINS	80	[17-22]
	17516-12	PROTECTION OF MOS INTEGRATED CIRCUITS FROM DESTRUCTION BY ELECTROSTATIC DISCHARGE	80	[73-80]
	17516-26	SURGE TESTS ON PLUG-IN TRANSFORMERS	80	[176-183]
	17515-27	THE PHANTOM EMITTER-AN ESD-RESISTANT BIPOLAR TRANSISTOR DESIGN AND ITS APPLICATIONS TO LINEAR INTEGRATED CIRCUITS	79	[188-192]

Section 4:

CORPORATE INDEX

AUTHOR INDEX

<u>AUTHOR</u> <u>DOCUMENT-SEQUENCE NO.</u>	<u>TITLE</u>	<u>YEAR</u>	<u>PAGES</u>
WUNSCH, D. C.			
17517-24	AN OVERVIEW OF EOS EFFECTS ON PASSIVE COMPONENTS	81	[167-173]
YEE, J. H.			
18172-16	MODELING AND TESTING FOR SECOND BREAKDOWN PHENOMENA	83	[108-117]
18214-10	MODELING OF CURRENT AND THERMAL MODE SECOND BREAKDOWN PHENOMENA	82	[76-81]
YENNI, D. M.			
18214-13	TEST METHODS FOR STATIC CONTROL PRODUCTS	82	[94-109]
17515- 9	THE DEFICIENCIES IN MILITARY SPECIFICATION MIL-B-81705: CONSIDERATIONS AND A SIMPLE MODEL FOR STATIC PROTECTION	79	[45-54]
YOUN, S. Y.			
18214-22	ESD MINIMIZATION TECHNIQUE FOR MOS MANUFACTURING FINAL TEST AREA	82	[157-164]
YOUNG, P. A.			
17517-18	ELECTRICAL OVERSTRESS INVESTIGATIONS IN MODERN INTEGRATED CIRCUIT TECHNOLOGIES	81	[114-119]
ZAJAC, H.			
17516- 9	STUDY OF EFFECTS OF ELECTRO-STATIC DISCHARGE ON SOLID-STATE DEVICES	80	[58]

AUTHOR INDEX

<u>AUTHOR</u> <u>DOCUMENT-SEQUENCE NO.</u>	<u>TITLE</u>	<u>YEAR</u>	<u>PAGES</u>
VAN LINT, V. A. J.			
17516-22	SOLAR CELL ELECTRICAL OVERSTRESS ANALYSIS	80	[149-153]
VOLMERANGE, H.			
18214- 8	AN IMPROVED EOS CONDUCTION MODEL OF SEMICONDUCT DEVICES	82	[62-70]
VULIET, W.			
17517-33	EOS DAMAGE IN SILICON SOLAR CELLS	81	[209-235]
WALKER, R. C.			
18214- 5	LATENT ESD FAILURES	82	[41-48]
17516- 8	IDENTIFICATION OF LATENT ESD FAILURES	80	[54-57]
WARD, A. L.			
18172-15	CALCULATIONS OF SECOND BREAKDOWN IN SILICON DIODES AT MICROWAVE FREQUENCIES	83	[102-107]
18214- 9	THE FORWARD-BIAS CHARACTERISTIC AS A PREDICTOR AND SCREEN OF REVERSE-BIAS SECOND BREAKDOWN	82	[71-75]
17516-20	OSCILLATING VOLTAGE PULSES AND SECOND BREAKDOWN	80	[130-139]
17515-16	DOPING PROFILES AND SECOND BREAKDOWN	79	[109-115]
WATSON, D. E.			
18305- 2	HAZARDS OF STATIC CHARGES AND FIELDS AT THE WORK STATION	84	[7-19]
WEBER, D. C.			
18214-15	ELECTROACTIVE POLYMERS AS ALTERNATE ESD PROTECTIVE MATERIALS	82	[115-119]
WEIGHT, M. E.			
18214-21	AN EFFECTIVE ELECTROSTATIC DISCHARGE PROTECTION PROGRAM	82	[145-156]
WHALEN, J. J.			
17515-22	MICROWAVE NANOSECOND PULSE BURNOUT PROPERTIES OF ONE MICRON MESFETS	79	[147-157]
17515-21	SQUARE PULSE AND RF PULSE OVERSTRESSING OF UHF TRANSISTORS	79	[140-146]
WHITE, L. S.			
18172-26	A SUMMARY OF MOST EFFECTIVE ELECTROSTATIC DISCHARGE PROTECTION CIRCUITS FOR MOS MEMORIES AND THEIR OBSERVED FAILURE MODES	83	[181-184]
WHITEHEAD, A. P.			
18172-21	THE EFFECT OF ESD ON CCD RELIABILITY	83	[147-153]
WILSON, D.			
18172-19	ESD SENSITIVITY OF COMPLEX ICS	83	[128-133]
WOODHOUSE, J.			
18305-25	A FAILURE ANALYSIS METHODOLOGY FOR REVEALING ESD DAMAGE TO INTEGRATED CIRCUITS	84	[189-195]
WU, C.			
17516- 4	ELECTROSTATIC DISCHARGE (ESD) MONITOR DESIGN	80	[23-25]

AUTHOR INDEX

<u>AUTHOR</u>	<u>DOCUMENT-SEQUENCE NO.</u>	<u>TITLE</u>	<u>YEAR</u>	<u>PAGES</u>
TEMPLAR, L. C.				
	17517-23	EOS/ESD FAILURE THRESHOLD ANALYSIS ERRORS, THEIR SOURCE, SIZE AND CONTROL	81	[151-166]
TENG, T.				
	17516-14	LSI DESIGN CONSIDERATIONS FOR ESD PROTECTION STRUCTURES RELATED TO PROCESS AND LAYOUT VARIATIONS	80	[87-94]
	17515-24	SUSCEPTIBILITY OF LSI MOS TO ELECTROSTATIC DISCHARGE AT ELEVATED TEMPERATURE	79	[168-175]
TENZER, F. D.				
	17517- 8	AN ANALYSIS OF ANTISTATIC CUSHIONING MATERIALS	81	[44-48]
THOMAS, R. E.				
	17517-21	SEMICONDUCTOR DEVICE FAILURE CRITERIA FOR SINUSOIDAL STRESSES	81	[139-144]
THOMAS, R. M.				
	17517-27	BEHAVIOR OF THICK-FILM POWER RESISTORS SUBJECTED TO LARGE MOMENTARY OVERLOADS	81	[198-201]
THOMPSON, W. H.				
	18305- 4	ESD DAMAGE, DOES IT HAPPEN ON PCBS?	84	[22-23]
	18172- 5	AIR FORCE MAINTENANCE PROGRAM FOR ELECTRICAL OVERSTRESS/ELECTROSTATIC DISCHARGE (EOS/ESD) CONTROL	83	[21-28]
	18214- 6	A SURVEY OF EOS/ESD DATA SOURCES	82	[49-55]
THORN, M. L.				
	17515-22	MICROWAVE NANOSECOND PULSE BURNOUT PROPERTIES OF ONE MICRON MESFETS	79	[147-157]
TOPOLSKI, A. S.				
	17517-11	INCOMING INSPECTION OF ANTISTATIC PACKAGING MATERIALS	81	[65-74]
TURNER, T. E.				
	17516-15	ELECTROSTATIC SENSITIVITY OF VARIOUS INPUT PROTECTION NETWORKS	80	[95-103]
TWEET, A.				
	18214-21	AN EFFECTIVE ELECTROSTATIC DISCHARGE PROTECTION PROGRAM	82	[145-156]
TWIST, R. E.				
	18214- 5	LATENT ESD FAILURES	82	[41-48]
	17517- 3	ANALYSIS OF ESD FAILURES	81	[14-20]
UETSUKI, T.				
	17515-13	FAILURE ANALYSIS OF MICROCIRCUITS SUBJECTED TO ELECTRICAL OVERSTRESS	79	[88-96]
UNGER, B.				
	17517-10	EVALUATION OF INTEGRATED CIRCUIT SHIPPING TUBES	81	[57-64]
UNGER, B. A.				
	18305- 7	A ROOM IONIZATION SYSTEM FOR ELECTROSTATIC CHARGE AND DUST CONTROL	84	[40-44]
	18172- 6	ESD BY STATIC INDUCTION	83	[29-36]
	17516- 3	ESD DAMAGE FROM TRIBOELECTRICALLY CHARGED IC PINS	80	[17-22]

AUTHOR INDEX

<u>AUTHOR</u>	<u>DOCUMENT-SEQUENCE NO.</u>	<u>TITLE</u>	<u>YEAR</u>	<u>PAGES</u>
SKELTON, D. J.				
	18214-12	SECOND BREAKDOWN IN SWITCHING TRANSISTORS	82	[91-93]
SMITH, J. G.				
	18305-26	ESD SENSITIVITY AND LATENCY EFFECTS OF SOME HCMOS INTEGRATED CIRCUITS	84	[196-201]
SMITH, J. S.				
	17517-20	MODELING OF EOS IN SILICON DEVICES	81	[132-138]
	17517-26	PREDICTION OF THIN-FILM RESISTOR BURNOUT	81	[192-197]
	17515-20	MODELING OF ELECTRICAL OVERSTRESS IN SILICON DEVICES	79	[133-139]
SMYTH, J. B.				
	17516-22	SOLAR CELL ELECTRICAL OVERSTRESS ANALYSIS	80	[149-153]
SNYOER, H. Z.				
	17516- 2	THE EFFECTS OF HIGH HUMIDITY ENVIRONMENTS ON ELECTROSTATIC GENERATION AND DISCHARGE	80	[12-16]
SODEN, J. M.				
	18172-20	ESD EVALUATION OF RADIATION-HARDENED, HIGH RELIABILITY CMOS AND MNOS ICS	83	[134-146]
	17515-25	THE DIELECTRIC STRENGTH OF SIO2 IN A CMOS TRANSISTOR STRUCTURE	79	[176-182]
SOHL, J. E.				
	17516-32	AN EVALUATION OF WRIST STRAP PARAMETERS	80	[218-224]
STEWART, H. D.				
	18172-20	ESD EVALUATION OF RADIATION-HARDENED, HIGH RELIABILITY CMOS AND MNOS ICS	83	[134-146]
STORM, D. C.				
	17515- 2	CONTROLLING ELECTROSTATIC PROBLEMS IN THE FABRICATION AND HANDLING OF SPACECRAFT HARDWARE	79	[4-6]
STOTTS, L. J.				
	18172-17	TEMPERATURE AT SECOND BREAKDOWN AT A WELL-DEFINED SITE	83	[118-121]
STRAND, C. J.				
	18214-21	AN EFFECTIVE ELECTROSTATIC DISCHARGE PROTECTION PROGRAM	82	[145-156]
TABATA, Y.				
	18305- 9	ESTIMATION OF DISCHARGE ENERGY RELEASED FROM CHARGED INSULATOR	84	[50-57]
TASCA, D. M.				
	17517-25	PULSE POWER RESPONSE AND DAMAGE CHARACTERISTICS OF CAPACITORS	81	[174-191]
TAYLOR, R. G.				
	18305-25	A FAILURE ANALYSIS METHODOLOGY FOR REVEALING ESD DAMAGE TO INTEGRATED CIRCUITS	84	[189-195]
	18305-23	DEGRADATION BY ESD TRANSIENTS OF THE SUBSTRATE BIAS VOLTAGE OF NMOS 8085-TYPE MICROPROCESSORS	84	[165-178]
	18172-27	ESD SENSITIVITY OF NMOS LSI CIRCUITS AND THEIR FAILURE CHARACTERISTICS	84	[185-197]
	17517-15	INPUT PROTECTION DESIGN FOR THE 3-MICRON NMOS PROCESS	81	[97-100]

KEYWORD IN TITLE INDEX

KEYWORD DOCUMENT-SEQUENCE NO.	TITLE	YEAR	PAGES
ANALYSIS			
18305-25	A FAILURE ANALYSIS METHODOLOGY FOR REVEALING ESD DAMAGE TO INTEGRATED CIRCUITS	84	[189-195]
18172- 2	ESD CONTROL IMPLEMENTATION AND COST AVOIDANCE ANALYSIS	83	[6-11]
18172- 4	ANALYSIS OF ELECTROSTATIC CHARGE PROPENSITY OF FLOOR FINISHES	83	[17-20]
18172-22	EOS OR ESD: CAN FAILURE ANALYSIS TELL THE DIFFERENCE?	83	[154-157]
18214-25	IN-CIRCUIT ANALYSIS OF ESD DAMAGED DEVICES	82	[175-178]
17517- 3	ANALYSIS OF ESD FAILURES	81	[14-20]
17517- 5	THE ECONOMIC BENEFITS OF AN EFFECTIVE ESD AWARENESS AND CONTROL PROGRAM - AN EMPIRICAL ANALYSIS	81	[29-33]
17517- 8	AN ANALYSIS OF ANTISTATIC CUSHIONING MATERIALS	81	[44-48]
17517-16	DIAGNOSIS AND ANALYSIS OF EMITTER-BASE JUNCTION OVERSTRESS DAMAGE	81	[101-105]
17517-23	EOS/ESD FAILURE THRESHOLD ANALYSIS ERRORS, THEIR SOURCE, SIZE AND CONTROL	81	[151-166]
17517-31	FAILURE ANALYSIS OF SEMICONDUCTOR DEVICES IN EOS/ESD TESTING	81	[219-224]
17516-11	ANALYSIS OF ESD DAMAGE IN JFET PREAMPLIFIERS	80	[67-72]
17516-22	SOLAR CELL ELECTRICAL OVERSTRESS ANALYSIS	80	[149-153]
17515-11	EFFECTS OF ELECTRICAL OVERSTRESS ON DIGITAL BIPOLAR MICROCIRCUITS AND ANALYSIS TECHNIQUES FOR FAILURE SITE LOCATION	79	[64-77]
17515-13	FAILURE ANALYSIS OF MICROCIRCUITS SUBJECTED TO ELECTRICAL OVERSTRESS	79	[88-96]
17515-29	STATISTICAL FAILURE ANALYSIS OF MILITARY SYSTEMS FOR HIGH-ALTITUDE EMP	79	[198-204]
17515-30	THE ANALYSIS AND ELIMINATION OF EOS INDUCED SECONDARY FAILURE MECHANISMS	79	[205-209]
ANTI-STATIC			
18305-12	AN EXPERIMENTAL STUDY OF THE ESD SCREENING EFFECTIVENESS OF ANTI-STATIC BAGS	84	[78-84]
ANTISTATIC			
18172-13	PERMANENCE OF THE ANTISTATIC PROPERTY OF COMMERCIAL ANTISTATIC BAGS AND TOTE BOXES	83	[87-94]
18214-16	DRASTIC LOSSES OF CONDUCTIVITY IN ANTISTATIC PLASTICS	82	[120-123]
17517- 8	AN ANALYSIS OF ANTISTATIC CUSHIONING MATERIALS	81	[44-48]
17517-11	INCOMING INSPECTION OF ANTISTATIC PACKAGING MATERIALS	81	[65-74]
BAG			
18305-12	AN EXPERIMENTAL STUDY OF THE ESD SCREENING EFFECTIVENESS OF ANTI-STATIC BAGS	84	[78-84]
18172-13	PERMANENCE OF THE ANTISTATIC PROPERTY OF COMMERCIAL ANTISTATIC BAGS AND TOTE BOXES	83	[87-94]
BARRIER			
17515-14	ELECTROSTATIC FAILURE OF X-BAND SILICON SCHOTTKY BARRIER DIODES	79	[97-103]
BIPOLAR			
17516-10	FAILURE THRESHOLD DISTRIBUTIONS IN BIPOLAR TRANSISTORS	80	[59-66]
17516-17	HIGH-FIELD PHENOMENA AND FAILURE MECHANISMS IN BIPOLAR TRANSISTORS	80	[112-116]
17516-18	SOME DESIGN CRITERIA FOR AVOIDING SECOND BREAKDOWN IN BIPOLAR DEVICES	80	[117-121]
17515-11	EFFECTS OF ELECTRICAL OVERSTRESS ON DIGITAL BIPOLAR MICROCIRCUITS AND ANALYSIS TECHNIQUES FOR FAILURE SITE LOCATION	79	[64-77]
17515-27	THE PHANTOM EMITTER-AN ESD-RESISTANT BIPOLAR TRANSISTOR DESIGN AND ITS APPLICATIONS TO LINEAR INTEGRATED CIRCUITS	79	[188-192]
BOX			
18172-13	PERMANENCE OF THE ANTISTATIC PROPERTY OF COMMERCIAL ANTISTATIC BAGS AND TOTE BOXES	83	[87-94]
BREAKDOWN			
18172-15	CALCULATIONS OF SECOND BREAKDOWN IN SILICON DIODES AT MICROWAVE FREQUENCIES	83	[102-107]
18172-16	MODELING AND TESTING FOR SECOND BREAKDOWN PHENOMENA	83	[108-117]
18172-17	TEMPERATURE AT SECOND BREAKDOWN AT A WELL-DEFINED SITE	83	[118-121]
18214- 9	THE FORWARD-BIAS CHARACTERISTIC AS A PREDICTOR AND SCREEN OF REVERSE-BIAS SECOND BREAKDOWN	82	[71-75]

KEYWORD IN TITLE INDEX

KEYWORD DOCUMENT-SEQUENCE NO.	TITLE	YEAR	PAGES
BREAKDOWN			
18214-10	MODELING OF CURRENT AND THERMAL MODE SECOND BREAKDOWN PHENOMENA	82	[76-81]
18214-12	SECOND BREAKDOWN IN SWITCHING TRANSISTORS	82	[91-93]
17516-18	SOME DESIGN CRITERIA FOR AVOIDING SECOND BREAKDOWN IN BIPOLAR DEVICES	80	[117-121]
17516-19	EFFECT OF JUNCTION SPIKES AND DOPING LEVEL ON THE SECOND BREAKDOWN SUSCEPTIBILITY OF SILICON-ON-SAPPHIRE DIODES	80	[122-129]
17516-20	OSCILLATING VOLTAGE PULSES AND SECOND BREAKDOWN	80	[130-139]
17515-16	DOPING PROFILES AND SECOND BREAKDOWN	79	[109-115]
17515-17	REVERSE-BIAS SECOND BREAKDOWN IN POWER TRANSISTORS	79	[116-121]
17515-19	AN ELECTROTHERMAL MODEL FOR CURRENT FILAMENTATION IN SECOND BREAKDOWN OF SILICON-ON-SAPPHIRE DIODES	79	[126-132]
BURNOUT			
18214- 7	MODELING METALLIZATION BURNOUT OF INTEGRATED CIRCUITS	82	[56-61]
17517-26	PREDICTION OF THIN-FILM RESISTOR BURNOUT	81	[192-197]
17515-22	MICROWAVE NANOSECOND PULSE BURNOUT PROPERTIES OF ONE MICRON MESFETS	79	[147-157]
CALCULATION			
18172-15	CALCULATIONS OF SECOND BREAKDOWN IN SILICON DIODES AT MICROWAVE FREQUENCIES	83	[102-107]
CAPACITOR			
18214- 2	ELECTROSTATIC DISCHARGE (ESD) DAMAGE SUSCPTIBILITY OF THIN FILM RESISTORS AND CAPACITORS	82	[13-18]
17517-25	PULSE POWER RESPONSE AND DAMAGE CHARACTERISTICS OF CAPACITORS	81	[174-191]
CCD			
18172-21	THE EFFECT OF ESD ON CCD RELIABILITY	83	[147-153]
CELL			
17517-33	EOS DAMAGE IN SILICON SOLAR CELLS	81	[209-235]
17516-22	SOLAR CELL ELECTRICAL OVERSTRESS ANALYSIS	80	[149-153]
CHARACTERIZATION			
18305- 8	STATIC-ELECTRIC CHARACTERIZATION OF SEMI-INSULATING MATERIALS	84	[45-49]
18214-17	CHARACTERIZATION OF ESD SAFE REQUIREMENTS FOR FLOOR SURFACES	82	[124-130]
CHIP			
17517-14	ON CHIP PROTECTION OF HIGH DENSITY NMOS DEVICES	81	[90-96]
CLEAN			
18214-18	ESD AND CONTAMINATION FROM CLEAN ROOM GARMENTS - PROBLEMS AND SOLUTIONS	82	[131-135]
CMOS			
18305-27	A CMOS VLSI ESD INPUT PROTECTION DEVICE, DIFIDW	84	[202-209]
18172-20	ESD EVALUATION OF RADIATION-HARDENED, HIGH RELIABILITY CMOS AND MNOS ICS	83	[134-146]
17516-16	SUPRISING PATTERNS OF CMOS SUSCEPTIBILITY TO ESD AND IMPLICATIONS ON LONG-TERM RELIABILITY	80	[104-111]
17515- 8	RELIABILITY OF EOS SCREENED GOLD DOPED 4002 CMOS DEVICES	79	[41-44]
17515-10	ELECTRO-STATIC DISCHARGE AND CMOS LOGIC	79	[55-63]
17515-25	THE DIELECTRIC STRENGTH OF SiO2 IN A CMOS TRANSISTOR STRUCTURE	79	[176-182]
COMPLEX			
18172-19	ESD SENSITIVITY OF COMPLEX ICS	83	[128-133]

KEYWORD IN TITLE INDEX

KEYWORD DOCUMENT-SEQUENCE NO.	TITLE	YEAR	PAGES
COMPONENT			
18305-20	PROTECTION OF COMPONENTS AGAINST ELECTRICAL OVERSTRESS (EOS) AND TRANSIENTS IN MONITORS	84	[136-143]
17517-24	AN OVERVIEW OF EOS EFFECTS ON PASSIVE COMPONENTS	81	[167-173]
17516-30	BASIC CONSIDERATIONS IN ELECTRO-THERMAL OVERSTRESS IN ELECTRONIC COMPONENTS	80	[206-212]
CONDUCTIVITY			
18214-16	DRASTIC LOSSES OF CONDUCTIVITY IN ANTISTATIC PLASTICS	82	[120-123]
17515- 3	ELECTROSTATIC CONDUCTIVITY CHARACTERISTICS OF WORKBENCH-TOP SURFACE MATERIALS	79	[7-12]
CONTAMINATION			
18214-18	ESD AND CONTAMINATION FROM CLEAN ROOM GARMENTS - PROBLEMS AND SOLUTIONS	82	[131-135]
CONTROL			
18305- 1	A REALISTIC AND SYSTEMATIC ESD CONTROL PLAN	84	[1-6]
18305- 5	ELECTROSTATIC MEASUREMENT FOR PROCESS CONTROL	84	[25-33]
18305- 7	A ROOM IONIZATION SYSTEM FOR ELECTROSTATIC CHARGE AND DUST CONTROL	84	[40-44]
18305-13	A MATERIAL EVALUATION PROGRAM FOR DECORATIVE STATIC CONTROL TABLE TOP LAMINATES	84	[85-93]
18172- 2	ESD CONTROL IMPLEMENTATION AND COST AVOIDANCE ANALYSIS	83	[6-11]
18172- 5	AIR FORCE MAINTENANCE PROGRAM FOR ELECTRICAL OVERSTRESS/ELECTROSTATIC DISCHARGE (EOS/ESD) CONTROL	83	[21-28]
18214-13	TEST METHODS FOR STATIC CONTROL PRODUCTS	82	[94-109]
17517- 5	THE ECONOMIC BENEFITS OF AN EFFECTIVE ESD AWARENESS AND CONTROL PROGRAM - AN EMPIRICAL ANALYSIS	81	[29-33]
17517-23	EOS/ESD FAILURE THRESHOLD ANALYSIS ERRORS, THEIR SOURCE, SIZE AND CONTROL	81	[151-166]
17516- 7	GAS TUBE SURGE ARRESTERS FOR CONTROL OF TRANSIENT VOLTAGES	80	[44-53]
17516-31	STATIC CONTROL SYSTEMS	80	[213-217]
17515- 2	CONTROLLING ELECTROSTATIC PROBLEMS IN THE FABRICATION AND HANDLING OF SPACECRAFT HARDWARE	79	[4-6]
17515- 4	STATIC CONTROL USING TOPICAL ANTISTATS	79	[13-21]
17515- 6	PROPOSED MIL-STD AND MIL-HDBK FOR AN ELECTROSTATIC DISCHARGE CONTROL PROGRAM - BACKGROUND AND STATUS	79	[27-35]
COST			
18172- 2	ESD CONTROL IMPLEMENTATION AND COST AVOIDANCE ANALYSIS	83	[6-11]
CURRENT			
18214-10	MODELING OF CURRENT AND THERMAL MODE SECOND BREAKDOWN PHENOMENA	82	[76-81]
17515-19	AN ELECTROTHERMAL MODEL FOR CURRENT FILAMENTATION IN SECOND BREAKDOWN OF SILICON-ON-SAPPHIRE DIODES	79	[126-132]
DEFECT			
18172-28	A STUDY OF ESD LATENT DEFECTS IN SEMICONDUCTORS	83	[198-204]
DEGRADATION			
18305-23	DEGRADATION BY ESD TRANSIENTS OF THE SUBSTRATE BIAS VOLTAGE OF NMOS 8085-TYPE MICROPROCESSORS	84	[165-178]
DESIGN			
18305-17	DESIGNING TO AVOID STATIC - ESD TESTING OF DIGITAL DEVICES	84	[112-123]
18305-24	DEVICE ESD SUSCEPTIBILITY TESTING AND DESIGN HARDENING	84	[179-188]
18214-24	CIRCUIT DESIGN FOR EOS/ESD PROTECTION	82	[169-174]
17517-15	INPUT PROTECTION DESIGN FOR THE 3-MICRON NMOS PROCESS	81	[97-100]
17516- 4	ELECTROSTATIC DISCHARGE (ESD) MONITOR DESIGN	80	[23-25]
17516-13	SOS PROTECTION: THE DESIGN PROBLEM	80	[81-86]
17516-14	LSI DESIGN CONSIDERATIONS FOR ESD PROTECTION STRUCTURES RELATED TO PROCESS AND LAYOUT VARIATIONS	80	[87-94]

KEYWORD IN TITLE INDEX

KEYWORD			
DOCUMENT-SEQUENCE NO.	TITLE	YEAR	PAGES
DESIGN			
17516-18	SOME DESIGN CRITERIA FOR AVOIDING SECOND BREAKDOWN IN BIPOLAR DEVICES	80	[117-121]
17516-25	LIGHTNING PROTECTION DESIGN FOR A PHOTOVOLTAIC CONCENTRATOR	80	[167-175]
17515-27	THE PHANTOM EMITTER-AN ESD-RESISTANT BIPOLAR TRANSISTOR DESIGN AND ITS APPLICATIONS TO LINEAR INTEGRATED CIRCUITS	79	[188-192]
DIAGNOSIS			
17517-16	DIAGNOSIS AND ANALYSIS OF EMITTER-BASE JUNCTION OVERSTRESS DAMAGE	81	[101-105]
DIELECTRIC			
17515-25	THE DIELECTRIC STRENGTH OF SIO2 IN A CMOS TRANSISTOR STRUCTURE	79	[176-182]
DIODE			
18172-15	CALCULATIONS OF SECOND BREAKDOWN IN SILICON DIODES AT MICROWAVE FREQUENCIES	83	[102-107]
17516-19	EFFECT OF JUNCTION SPIKES AND DOPING LEVEL ON THE SECOND BREAKDOWN SUSCEPTIBILITY OF SILICON-ON-SAPPHIRE DIODES	80	[122-129]
17515-14	ELECTROSTATIC FAILURE OF X-BAND SILICON SCHOTTKY BARRIER DIODES	79	[97-103]
17515-19	AN ELECTROTHERMAL MODEL FOR CURRENT FILAMENTATION IN SECOND BREAKDOWN OF SILICON-ON-SAPPHIRE DIODES	79	[126-132]
DYNAMIC			
17515-12	DYNAMIC WAVEFORM CHARACTERISTICS OF PERSONNEL ELECTROSTATIC DISCHARGE	79	[78-87]
ELECTRO-THERMAL			
17516-30	BASIC CONSIDERATIONS IN ELECTRO-THERMAL OVERSTRESS IN ELECTRONIC COMPONENTS	80	[206-212]
ELECTRONIC			
17516-21	ASSESSING ELECTRICAL OVERSTRESS EFFECTS ON ELECTRONIC SYSTEMS	80	[140-148]
17516-24	TEST WAVEFORMS AND TECHNIQUES TO ASSESS THE THREAT TO ELECTRONIC DEVICES OF LIGHTNING-INDUCED TRANSIENTS	80	[161-166]
17516-30	BASIC CONSIDERATIONS IN ELECTRO-THERMAL OVERSTRESS IN ELECTRONIC COMPONENTS	80	[206-212]
ELECTROSTATIC			
18305- 5	ELECTROSTATIC MEASUREMENT FOR PROCESS CONTROL	84	[25-33]
18305- 7	A ROOM IONIZATION SYSTEM FOR ELECTROSTATIC CHARGE AND DUST CONTROL	84	[40-44]
18305-10	TRIBOELECTRIC TESTING FOR ELECTROSTATIC CHARGES ON MATERIALS AT KENNEDY SPACE CENTER	84	[58-63]
18305-15	TESTING OF ELECTROSTATIC MATERIALS FED. STD. 101C, METHOD 4046.1	84	[97-103]
18172- 4	ANALYSIS OF ELECTROSTATIC CHARGE PROPENSITY OF FLOOR FINISHES	83	[17-20]
18172- 8	A PROGRAMMABLE EQUIPMENT FOR ELECTROSTATIC DISCHARGE TESTING TO HUMAN BODY MODELS	83	[48-55]
18172-26	A SUMMARY OF MOST EFFECTIVE ELECTROSTATIC DISCHARGE PROTECTION CIRCUITS FOR MOS MEMORIES AND THEIR OBSERVED FAILURE MODES	83	[181-184]
18214- 2	ELECTROSTATIC DISCHARGE (ESD) DAMAGE SUSCPETIBILITY OF THIN FILM RESISTORS AND CAPACITORS	82	[13-18]
18214-21	AN EFFECTIVE ELECTROSTATIC DISCHARGE PROTECTION PROGRAM	82	[145-156]
18214-26	ELECTROSTATIC DISCHARGE AT THE PRODUCT LEVEL	82	[179-184]
18214-27	ELECTROSTATIC DISCHARGE IMMUNITY IN COMPUTER SYSTEMS	82	[185-189]
17517-32	TIME-RELATED IMPROVEMENTS OF ELECTRICAL CHARACTERISTICS IN ELECTROSTATICALLY DAMAGED OPERATIONAL AMPLIFIERS	81	[225-228]
17517-34	EVALUATION OF ELECTROSTATIC DISCHARGE TO 16K EPROMS	81	[236-241]
17516- 2	THE EFFECTS OF HIGH HUMIDITY ENVIRONMENTS ON ELECTROSTATIC GENERATION AND DISCHARGE	80	[12-16]
17516- 4	ELECTROSTATIC DISCHARGE (ESD) MONITOR DESIGN	80	[23-25]
17516-12	PROTECTION OF MOS INTEGRATED CIRCUITS FROM DESTRUCTION BY ELECTROSTATIC DISCHARGE	80	[73-80]
17516-15	ELECTROSTATIC SENSITIVITY OF VARIOUS INPUT PROTECTION NETWORKS	80	[95-103]

KEYWORD IN TITLE INDEX

KEYWORD DOCUMENT-SEQUENCE NO.	TITLE	YEAR	PAGES
ELECTROSTATIC			
17515- 2	CONTROLLING ELECTROSTATIC PROBLEMS IN THE FABRICATION AND HANDLING OF SPACECRAFT HARDWARE	79	[4-6]
17515- 3	ELECTROSTATIC CONDUCTIVITY CHARACTERISTICS OF WORKBENCH-TOP SURFACE MATERIALS	79	[7-12]
17515- 5	THE GENERATION OF ELECTROSTATIC CHARGES IN SILICONE ENCAPSULANTS DURING CYCLIC GASEOUS PRESSURE TESTS	79	[22-26]
17515- 6	PROPOSED MIL-STD AND MIL-HDBK FOR AN ELECTROSTATIC DISCHARGE CONTROL PROGRAM - BACKGROUND AND STATUS	79	[27-35]
17515- 7	MODULE ELECTROSTATIC DISCHARGE SIMULATOR	79	[36-40]
17515-12	DYNAMIC WAVEFORM CHARACTERISTICS OF PERSONNEL ELECTROSTATIC DISCHARGE	79	[78-87]
17515-14	ELECTROSTATIC FAILURE OF X-BAND SILICON SCHOTTKY BARRIER DIODES	79	[97-103]
17515-18	HUMAN FACTORS IN ELECTROSTATIC DISCHARGE PROTECTION	79	[122-125]
17515-24	SUSCEPTIBILITY OF LSI MOS TO ELECTROSTATIC DISCHARGE AT ELEVATED TEMPERATURE	79	[168-175]
17515-28	ELECTROSTATIC DISCHARGE PROTECTION USING SILICON TRANSIENT SUPPRESSORS	79	[193-197]
EMP			
17515-23	DAMAGE RESPONSE OF SELECTED INTERFACE INTEGRATED CIRCUITS TO A SIMULATED EMP	79	[158-167]
17515-29	STATISTICAL FAILURE ANALYSIS OF MILITARY SYSTEMS FOR HIGH-ALTITUDE EMP	79	[198-204]
EMPIRICAL			
17517- 5	THE ECONOMIC BENEFITS OF AN EFFECTIVE ESD AWARENESS AND CONTROL PROGRAM - AN EMPIRICAL ANALYSIS	81	[29-33]
EPROM			
17517-34	EVALUATION OF ELECTROSTATIC DISCHARGE TO 16K EPROMS	81	[236-241]
EQUIPMENT			
18305- 3	TEST EQUIPMENT--A SOURCE OF ESD!!	84	[20-21]
18172- 8	A PROGRAMMABLE EQUIPMENT FOR ELECTROSTATIC DISCHARGE TESTING TO HUMAN BODY MODELS	83	[48-55]
17517- 7	A LOW-COST PROGRAM FOR EVALUATION OF ESD PROTECTIVE MATERIALS AND EQUIPMENT	81	[41-43]
ESD			
18305- 1	A REALISTIC AND SYSTEMATIC ESD CONTROL PLAN	84	[1-6]
18305- 3	TEST EQUIPMENT--A SOURCE OF ESD!!	84	[20-21]
18305- 4	ESD DAMAGE, DOES IT HAPPEN ON PCBS?	84	[22-23]
18305-11	TRIBOELECTRIC CHARGE: ITS ESD ABILITY AND A MEASUREMENT METHOD FOR ITS PROPENSITY ON PACKING MATERIALS	84	[64-77]
18305-12	AN EXPERIMENTAL STUDY OF THE ESD SCREENING EFFECTIVENESS OF ANTI-STATIC BAGS	84	[78-84]
18305-16	CRITICAL CONSIDERATIONS FOR ESD TESTING	84	[104-111]
18305-17	DESIGNING TO AVOID STATIC - ESD TESTING OF DIGITAL DEVICES	84	[112-123]
18305-18	EMI CHARACTERISTICS OF ESD IN A SMALL AIR GAP --ARP GOVERNS THE EMI--	84	[124-130]
18305-23	DEGRADATION BY ESD TRANSIENTS OF THE SUBSTRATE BIAS VOLTAGE OF NMOS 8085-TYPE MICROPROCESSORS	84	[165-178]
18305-24	DEVICE ESD SUSCEPTIBILITY TESTING AND DESIGN HARDENING	84	[179-188]
18305-25	A FAILURE ANALYSIS METHODOLOGY FOR REVEALING ESD DAMAGE TO INTEGRATED CIRCUITS	84	[189-195]
18305-26	ESD SENSITIVITY AND LATENCY EFFECTS OF SOME HCMOS INTEGRATED CIRCUITS	84	[196-201]
18305-27	A CMOS VLSI ESD INPUT PROTECTION DEVICE, DIP16W	84	[202-209]
18172- 1	ESD-HOW OFTEN DOES IT HAPPEN?	83	[1-5]
18172- 2	ESD CONTROL IMPLEMENTATION AND COST AVOIDANCE ANALYSIS	83	[6-11]
18172- 3	THE PRODUCTION OPERATOR: WEAK LINK OR WARRIOR IN THE ESD BATTLE?	83	[12-16]
18172- 6	ESD BY STATIC INDUCTION	83	[29-36]
18172-19	ESD SENSITIVITY OF COMPLEX ICS	83	[128-133]
18172-20	ESD EVALUATION OF RADIATION-HARDENED, HIGH RELIABILITY CMOS AND MNOS ICS	83	[134-146]
18172-21	THE EFFECT OF ESD ON CCD RELIABILITY	83	[147-153]
18172-22	EOS OR ESD: CAN FAILURE ANALYSIS TELL THE DIFFERENCE?	83	[154-157]
18172-27	ESD SENSITIVITY OF MNOS LSI CIRCUITS AND THEIR FAILURE CHARACTERISTICS	83	[185-197]
18172-28	A STUDY OF ESD LATENT DEFECTS IN SEMICONDUCTORS	83	[198-204]
18214- 1	ESD SUSCEPTIBILITY TESTING OF ADVANCED SCHOTTKY TTL	82	[1-12]

KEYWORD IN TITLE INDEX

KEYWORD DOCUMENT-SEQUENCE NO.	TITLE	YEAR	PAGES
ESD			
18214- 5	LATENT ESD FAILURES	82	[41-48]
18214-15	ELECTROACTIVE POLYMERS AS ALTERNATE ESD PROTECTIVE MATERIALS	82	[115-119]
18214-17	CHARACTERIZATION OF ESD SAFE REQUIREMENTS FOR FLOOR SURFACES	82	[124-130]
18214-18	ESD AND CONTAMINATION FROM CLEAN ROOM GARMENTS - PROBLEMS AND SOLUTIONS	82	[131-135]
18214-19	BASIC SPECIFICATION FOR ESD PROTECTION IN INDUSTRY	82	[136-141]
18214-20	ESD IN I.C. ASSEMBLY (A BASE LINE SOLUTION)	82	[142-144]
18214-22	ESD MINIMIZATION TECHNIQUE FOR MOS MANUFACTURING FINAL TEST AREA	82	[157-164]
18214-23	UNIFORM ESD PROTECTION IN A LARGE MULTI-DEPARTMENT ASSEMBLY PLANT	82	[165-168]
18214-25	IN-CIRCUIT ANALYSIS OF ESD DAMAGED DEVICES	82	[175-178]
17517- 1	A CLOSER LOOK AT THE HUMAN ESD EVENT	81	[1-8]
17517- 2	QUANTITATIVE EFFECTS OF RELATIVE & ABSOLUTE HUMIDITY ON ESD GENERATION/ SUPPRESSION	81	[9-13]
17517- 3	ANALYSIS OF ESD FAILURES	81	[14-20]
17517- 5	THE ECONOMIC BENEFITS OF AN EFFECTIVE ESD AWARENESS AND CONTROL PROGRAM - AN EMPIRICAL ANALYSIS	81	[29-33]
17517- 6	A PRAGMATIC APPROACH TO ESD PROBLEM SOLVING IN THE MANUFACTURING ENVIRONMENT A CASE HISTORY	81	[34-39]
17517- 7	A LOW-COST PROGRAM FOR EVALUATION OF ESD PROTECTIVE MATERIALS AND EQUIPMENT	81	[41-43]
17517-12	SELECTION OF PACKAGING MATERIALS FOR ESD SENSITIVE ITEMS	81	[75-84]
17517-17	SUSCEPTIBILITY OF ICS IN ESD STEP-STRESS TESTS	81	[106-113]
17517-29	POTENTIAL ESD HAZARDS ASSOCIATED WITH EXPLOSIVE PRIMERS	81	[208-211]
17516- 3	ESD DAMAGE FROM TRIBOELECTRICALLY CHARGED IC PINS	80	[17-22]
17516- 8	IDENTIFICATION OF LATENT ESD FAILURES	80	[54-57]
17516-11	ANALYSIS OF ESD DAMAGE IN JFET PREAMPLIFIERS	80	[67-72]
17516-14	LSI DESIGN CONSIDERATIONS FOR ESD PROTECTION STRUCTURES RELATED TO PROCESS AND LAYOUT VARIATIONS	80	[87-94]
17516-16	SUPRISING PATTERNS OF CMOS SUSCEPTIBILITY TO ESD AND IMPLICATIONS ON LONG-TERM RELIABILITY	80	[104-111]
17516-28	AN EFFECTIVE ESD AWARENESS TRAINING PROGRAM	80	[189-191]
17516-29	FACILITY EVALUATION: ISOLATING ENVIRONMENTAL ESD PROBLEMS	80	[192-205]
17516-33	MEASUREMENT OF FAST TRANSIENTS AND APPLICATION TO HUMAN ESD	80	[225-230]
17515- 1	AN EFFECTIVE ESD AWARENESS TRAINING PROGRAM	79	[1-3]
17515-15	ESD SUSCEPTIBILITIES OF HIGH PERFORMANCE ANALOG INTEGRATED CIRCUITS	79	[104-108]
17515-27	THE PHANTOM EMITTER-AN ESD-RESISTANT BIPOLAR TRANSISTOR DESIGN AND ITS APPLICATIONS TO LINEAR INTEGRATED CIRCUITS	79	[188-192]
EVALUATION			
18305-13	A MATERIAL EVALUATION PROGRAM FOR DECORATIVE STATIC CONTROL TABLE TOP LAMINATES	84	[85-93]
18305-21	AN EVALUATION OF EOS FAILURE MODELS	84	[144-156]
18172-20	ESD EVALUATION OF RADIATION-HARDENED, HIGH RELIABILITY CMOS AND MNOS ICS	83	[134-146]
17517- 7	A LOW-COST PROGRAM FOR EVALUATION OF ESD PROTECTIVE MATERIALS AND EQUIPMENT	81	[41-43]
17517-10	EVALUATION OF INTEGRATED CIRCUIT SHIPPING TUBES	81	[57-64]
17517-34	EVALUATION OF ELECTROSTATIC DISCHARGE TO 16K EPROMS	81	[236-241]
17516-29	FACILITY EVALUATION: ISOLATING ENVIRONMENTAL ESD PROBLEMS	80	[192-205]
17516-32	AN EVALUATION OF WRIST STRAP PARAMETERS	80	[218-224]
FAILURE			
18305-21	AN EVALUATION OF EOS FAILURE MODELS	84	[144-156]
18305-25	A FAILURE ANALYSIS METHODOLOGY FOR REVEALING ESD DAMAGE TO INTEGRATED CIRCUITS	84	[189-195]
18172- 9	POWER FAILURE MODELING OF INTEGRATED CIRCUITS	83	[56-62]
18172-18	SEMICONDUCTOR JUNCTION NON-LINEAR FAILURE POWER THRESHOLDS: WUNSCH-BELL REVISITED	83	[122-127]
18172-22	EOS OR ESD: CAN FAILURE ANALYSIS TELL THE DIFFERENCE?	83	[154-157]
18172-26	A SUMMARY OF MOST EFFECTIVE ELECTROSTATIC DISCHARGE PROTECTION CIRCUITS FOR MOS MEMORIES AND THEIR OBSERVED FAILURE MODES	83	[181-184]
18172-27	ESD SENSITIVITY OF NMOS LSI CIRCUITS AND THEIR FAILURE CHARACTERISTICS	83	[185-197]
18214- 3	LIMITATIONS IN MODELING ELECTRICAL OVERSTRESS FAILURE IN SEMICONDUCTOR DEVICES	82	[19-33]
18214- 5	LATENT ESD FAILURES	82	[41-48]
18214-11	A PROBABILISTIC ESTIMATOR FOR BOUNDING TRANSISTOR EMITTER-BASE JUNCTION TRANSIENT-INDUCED FAILURES	82	[82-90]
17517- 3	ANALYSIS OF ESD FAILURES	81	[14-20]

KEYWORD IN TITLE INDEX

KEYWORD DOCUMENT-SEQUENCE NO.	TITLE	YEAR	PAGES
FAILURE			
17517-13	THE EFFECTS OF VLSI SCALING ON EOS/ESD FAILURE THRESHOLD	81	[85-89]
17517-21	SEMICONDUCTOR DEVICE FAILURE CRITERIA FOR SINUSOIDAL STRESSES	81	[139-144]
17517-22	DETERMINING AN EMITTER-BASE FAILURE THRESHOLD DISTRIBUTION OF NPN TRANSISTORS	81	[145-150]
17517-23	EOS/ESD FAILURE THRESHOLD ANALYSIS ERRORS, THEIR SOURCE, SIZE AND CONTROL	81	[151-166]
17517-31	FAILURE ANALYSIS OF SEMICONDUCTOR DEVICES IN EOS/ESD TESTING	81	[219-224]
17517-35	NON-LINEAR KINETICS OF SEMICONDUCTOR JUNCTION THERMAL FAILURE	81	[242-245]
17516- 8	IDENTIFICATION OF LATENT ESD FAILURES	80	[54-57]
17516-10	FAILURE THRESHOLD DISTRIBUTIONS IN BIPOLAR TRANSISTORS	80	[59-66]
17516-17	HIGH-FIELD PHENOMENA AND FAILURE MECHANISMS IN BIPOLAR TRANSISTORS	80	[112-116]
17515-11	EFFECTS OF ELECTRICAL OVERSTRESS ON DIGITAL BIPOLAR MICROCIRCUITS AND ANALYSIS TECHNIQUES FOR FAILURE SITE LOCATION	79	[64-77]
17515-13	FAILURE ANALYSIS OF MICROCIRCUITS SUBJECTED TO ELECTRICAL OVERSTRESS	79	[88-96]
17515-14	ELECTROSTATIC FAILURE OF X-BAND SILICON SCHOTTKY BARRIER DIODES	79	[97-103]
17515-29	STATISTICAL FAILURE ANALYSIS OF MILITARY SYSTEMS FOR HIGH-ALTITUDE EMP	79	[198-204]
17515-30	THE ANALYSIS AND ELIMINATION OF EOS INDUCED SECONDARY FAILURE MECHANISMS	79	[205-209]
FIELD			
18305- 2	HAZARDS OF STATIC CHARGES AND FIELDS AT THE WORK STATION	84	[7-19]
18305- 6	EFFECTS OF AIR IONS AND ELECTRIC FIELDS ON HEALTH AND PRODUCTIVITY	84	[34-39]
FLOOR			
18172- 4	ANALYSIS OF ELECTROSTATIC CHARGE PROPENSITY OF FLOOR FINISHES	83	[17-20]
18214-17	CHARACTERIZATION OF ESD SAFE REQUIREMENTS FOR FLOOR SURFACES	82	[124-130]
GAS			
17516- 7	GAS TUBE SURGE ARRESTERS FOR CONTROL OF TRANSIENT VOLTAGES	80	[44-53]
17515- 5	THE GENERATION OF ELECTROSTATIC CHARGES IN SILICONE ENCAPSULANTS DURING CYCLIC GASEOUS PRESSURE TESTS	79	[22-26]
GEOMETRY			
17515-26	ELECTRICAL OVERSTRESS VERSUS DEVICE GEOMETRY	79	[183-187]
GOLD			
17515- 8	RELIABILITY OF EOS SCREENED GOLD DOPED 4002 CMOS DEVICES	79	[41-44]
HCMOS			
18305-26	ESD SENSITIVITY AND LATENCY EFFECTS OF SOME HCMOS INTEGRATED CIRCUITS	84	[196-201]
HUMAN			
18172- 8	A PROGRAMMABLE EQUIPMENT FOR ELECTROSTATIC DISCHARGE TESTING TO HUMAN BODY MODELS	83	[48-55]
17517- 1	A CLOSER LOOK AT THE HUMAN ESD EVENT	81	[1-8]
17516-33	MEASUREMENT OF FAST TRANSIENTS AND APPLICATION TO HUMAN ESD	80	[225-230]
17515-18	HUMAN FACTORS IN ELECTROSTATIC DISCHARGE PROTECTION	79	[122-125]
HUMIDITY			
18172-11	THE ROOM AIR IONIZATION SYSTEM, A BETTER ALTERNATIVE THAN 40% RELATIVE HUMIDITY	83	[67-75]
17517- 2	QUANTITATIVE EFFECTS OF RELATIVE & ABSOLUTE HUMIDITY ON ESD GENERATION/SUPPRESSION	81	[9-13]
17516- 2	THE EFFECTS OF HIGH HUMIDITY ENVIRONMENTS ON ELECTROSTATIC GENERATION AND DISCHARGE	80	[12-16]
INDUCED			
17515-30	THE ANALYSIS AND ELIMINATION OF EOS INDUCED SECONDARY FAILURE MECHANISMS	79	[205-209]

KEYWORD IN TITLE INDEX

KEYWORD			
DOCUMENT-SEQUENCE NO.	TITLE	YEAR	PAGES
INPUT			
18305-27	A CMOS VLSI ESD INPUT PROTECTION DEVICE, DIFIDW	84	[202-209]
17517-15	INPUT PROTECTION DESIGN FOR THE 3-MICRON NMOS PROCESS	81	[97-100]
17516-15	ELECTROSTATIC SENSITIVITY OF VARIOUS INPUT PROTECTION NETWORKS	80	[95-103]
INSPECTION			
17517-11	INCOMING INSPECTION OF ANTISTATIC PACKAGING MATERIALS	81	[65-74]
INSTRUMENTATION			
18214-28	ELECTRICAL GROUNDING IN LARGE INSTRUMENTATION SYSTEMS	82	[190-202]
INSULATOR			
18305- 9	ESTIMATION OF DISCHARGE ENERGY RELEASED FROM CHARGED INSULATOR	84	[50-57]
INTEGRATED			
18305-25	A FAILURE ANALYSIS METHODOLOGY FOR REVEALING ESD DAMAGE TO INTEGRATED CIRCUITS	84	[189-195]
18305-26	ESD SENSITIVITY AND LATENCY EFFECTS OF SOME HCMOS INTEGRATED CIRCUITS	84	[196-201]
18172- 9	POWER FAILURE MODELING OF INTEGRATED CIRCUITS	83	[56-62]
18172-24	METAL OXIDE VARISTORS FOR TRANSIENT PROTECTION OF 3 TO 5-VOLT INTEGRATED CIRCUITS	83	[168-176]
18172-25	USING SCR'S AS TRANSIENT PROTECTION STRUCTURES IN INTEGRATED CIRCUITS	83	[177-180]
18214- 7	MODELING METALLIZATION BURNOUT OF INTEGRATED CIRCUITS	82	[56-61]
17517-10	EVALUATION OF INTEGRATED CIRCUIT SHIPPING TUBES	81	[57-64]
17517-18	ELECTRICAL OVERSTRESS INVESTIGATIONS IN MODERN INTEGRATED CIRCUIT TECHNOLOGIES	81	[114-119]
17516-12	PROTECTION OF MOS INTEGRATED CIRCUITS FROM DESTRUCTION BY ELECTROSTATIC DISCHARGE	80	[73-80]
17515-15	ESD SUSCEPTIBILITIES OF HIGH PERFORMANCE ANALOG INTEGRATED CIRCUITS	79	[104-108]
17515-23	DAMAGE RESPONSE OF SELECTED INTERFACE INTEGRATED CIRCUITS TO A SIMULATED EMP	79	[158-167]
17515-27	THE PHANTOM EMITTER-AN ESD-RESISTANT BIPOLAR TRANSISTOR DESIGN AND ITS APPLICATIONS TO LINEAR INTEGRATED CIRCUITS	79	[188-192]
INTERFACE			
17515-23	DAMAGE RESPONSE OF SELECTED INTERFACE INTEGRATED CIRCUITS TO A SIMULATED EMP	79	[158-167]
INVESTIGATION			
17517-18	ELECTRICAL OVERSTRESS INVESTIGATIONS IN MODERN INTEGRATED CIRCUIT TECHNOLOGIES	81	[114-119]
ION			
18305- 6	EFFECTS OF AIR IONS AND ELECTRIC FIELDS ON HEALTH AND PRODUCTIVITY	84	[34-39]
18172-12	MEASURING EFFECTIVENESS OF AIR IONIZERS	83	[76-86]
IONIZATION			
18305- 7	A ROOM IONIZATION SYSTEM FOR ELECTROSTATIC CHARGE AND DUST CONTROL	84	[40-44]
18172-11	THE ROOM AIR IONIZATION SYSTEM, A BETTER ALTERNATIVE THAN 40% RELATIVE HUMIDITY	83	[67-75]
JUNCTION			
18172-18	SEMICONDUCTOR JUNCTION NON-LINEAR FAILURE POWER THRESHOLDS: WUNSCH-BELL REVISITED	83	[122-127]
18214-11	A PROBABILISTIC ESTIMATOR FOR BOUNDING TRANSISTOR EMITTER-BASE JUNCTION TRANSIENT-INDUCED FAILURES	82	[82-90]
17517-16	DIAGNOSIS AND ANALYSIS OF EMITTER-BASE JUNCTION OVERSTRESS DAMAGE	81	[101-105]
17517-35	NON-LINEAR KINETICS OF SEMICONDUCTOR JUNCTION THERMAL FAILURE	81	[242-245]
17516-19	EFFECT OF JUNCTION SPIKES AND DOPING LEVEL ON THE SECOND BREAKDOWN SUSCEPTIBILITY OF SILICON-ON-SAPPHIRE DIODES	80	[122-129]

KEYWORD IN TITLE INDEX

WORD				
DOCUMENT-SEQUENCE NO.	TITLE	YEAR	PAGES	
FENT				
8172-28	A STUDY OF ESD LATENT DEFECTS IN SEMICONDUCTORS	83	[198-204]	
8214- 5	LATENT ESD FAILURES	82	[41-48]	
7516- 8	IDENTIFICATION OF LATENT ESD FAILURES	80	[54-57]	
FE				
8305-14	A WRIST STRAP LIFE TEST PROGRAM	84	[94-96]	
GHTNING				
7517-30	LIGHTNING PROTECTION FOR COMPUTER DATA LINES	81	[212-218]	
7516-24	TEST WAVEFORMS AND TECHNIQUES TO ASSESS THE THREAT TO ELECTRONIC DEVICES OF LIGHTNING-INDUCED TRANSIENTS	80	[161-166]	
7516-25	LIGHTNING PROTECTION DESIGN FOR A PHOTOVOLTAIC CONCENTRATOR	80	[167-175]	
I				
8172-27	ESD SENSITIVITY OF NMOS LSI CIRCUITS AND THEIR FAILURE CHARACTERISTICS	83	[185-197]	
7516-14	LSI DESIGN CONSIDERATIONS FOR ESD PROTECTION STRUCTURES RELATED TO PROCESS AND LAYOUT VARIATIONS	80	[87-94]	
7515-24	SUSCEPTIBILITY OF LSI MOS TO ELECTROSTATIC DISCHARGE AT ELEVATED TEMPERATURE	79	[168-175]	
TERIAL				
8305- 8	STATIC-ELECTRIC CHARACTERIZATION OF SEMI-INSULATING MATERIALS	84	[45-49]	
8305-10	TRIBOELECTRIC TESTING FOR ELECTROSTATIC CHARGES ON MATERIALS AT KENNEDY SPACE CENTER	84	[58-63]	
8305-11	TRIBOELECTRIC CHARGE: ITS ESD ABILITY AND A MEASUREMENT METHOD FOR ITS PROPENSITY ON PACKING MATERIALS	84	[64-77]	
8305-13	A MATERIAL EVALUATION PROGRAM FOR DECORATIVE STATIC CONTROL TABLE TOP LAMINATES	84	[85-93]	
8305-15	TESTING OF ELECTROSTATIC MATERIALS FED. STD. 101C, METHOD 4046.1	84	[97-103]	
8172-14	COPLANAR TRIBOELECTRIFICATION OF SELECTED MATERIALS	83	[95-101]	
8214-15	ELECTROACTIVE POLYMERS AS ALTERNATE ESD PROTECTIVE MATERIALS	82	[115-119]	
7517- 7	A LOW-COST PROGRAM FOR EVALUATION OF ESD PROTECTIVE MATERIALS AND EQUIPMENT	81	[41-43]	
7517- 8	AN ANALYSIS OF ANTISTATIC CUSHIONING MATERIALS	81	[44-48]	
7517- 9	CHO-TRAP, A NOVEL VOLTAGE TRANSIENT PROTECTION PACKAGING MATERIAL	81	[49-56]	
7517-11	INCOMING INSPECTION OF ANTISTATIC PACKAGING MATERIALS	81	[65-74]	
7517-12	SELECTION OF PACKAGING MATERIALS FOR ESD SENSITIVE ITEMS	81	[75-84]	
7515- 3	ELECTROSTATIC CONDUCTIVITY CHARACTERISTICS OF WORKBENCH-TOP SURFACE MATERIALS	79	[7-12]	
MEASUREMENT				
8305- 5	ELECTROSTATIC MEASUREMENT FOR PROCESS CONTROL	84	[25-33]	
8305-11	TRIBOELECTRIC CHARGE: ITS ESD ABILITY AND A MEASUREMENT METHOD FOR ITS PROPENSITY ON PACKING MATERIALS	84	[64-77]	
7516-33	MEASUREMENT OF FAST TRANSIENTS AND APPLICATION TO HUMAN ESD	80	[225-230]	
MECHANISM				
8305-22	DETERMINATION OF THRESHOLD ENERGIES AND DAMAGE MECHANISMS IN SEMICONDUCTOR DEVICES SUBJECTED TO VOLTAGE TRANSIENTS	84	[157-164]	
7516-17	HIGH-FIELD PHENOMENA AND FAILURE MECHANISMS IN BIPOLAR TRANSISTORS	80	[112-116]	
7515-30	THE ANALYSIS AND ELIMINATION OF EOS INDUCED SECONDARY FAILURE MECHANISMS	79	[205-209]	
MEMORIES				
8172-26	A SUMMARY OF MOST EFFECTIVE ELECTROSTATIC DISCHARGE PROTECTION CIRCUITS FOR MOS MEMORIES AND THEIR OBSERVED FAILURE MODES	83	[181-184]	
MESFET				
7515-22	MICROWAVE NANOSECOND PULSE BURNOUT PROPERTIES OF ONE MICRON MESFETS	79	[147-157]	

KEYWORD IN TITLE INDEX

<u>WORD</u> <u>IDENT-SEQUENCE NO.</u>	<u>TITLE</u>	<u>YEAR</u>	<u>PAGES</u>
72-24	METAL OXIDE VARISTORS FOR TRANSIENT PROTECTION OF 3 TO 5-VOLT INTEGRATED CIRCUITS	83	[168-176]
14-14	METALLOPLASTICS	82	[110-114]
	METALLIZATION		
14- 7	MODELING METALLIZATION BURNOUT OF INTEGRATED CIRCUITS	82	[56-61]
	STATIC SURVEY METERS	83	[63-66]
	TRIBOELECTRIC CHARGE: ITS ESD ABILITY AND A MEASUREMENT METHOD FOR ITS PROPENSITY ON PACKING MATERIALS	84	[64-77]
05-15	TESTING OF ELECTROSTATIC MATERIALS FED. STD. 101C, METHOD 4046.1	84	[97-103]
05-25	A FAILURE ANALYSIS METHODOLOGY FOR REVEALING ESD DAMAGE TO INTEGRATED CIRCUITS	84	[189-195]
14-13	TEST METHODS FOR STATIC CONTROL PRODUCTS	82	[94-109]
	MICROCIRCUIT		
16-27	MICROCIRCUIT ELECTRICAL OVERSTRESS TOLERANCE TESTING AND QUALIFICATION	80	[184-188]
15-11	EFFECTS OF ELECTRICAL OVERSTRESS ON DIGITAL BIPOLAR MICROCIRCUITS AND ANALYSIS TECHNIQUES FOR FAILURE SITE LOCATION	79	[64-77]
15-13	FAILURE ANALYSIS OF MICROCIRCUITS SUBJECTED TO ELECTRICAL OVERSTRESS	79	[88-96]
	MICROWAVE		
72-15	CALCULATIONS OF SECOND BREAKDOWN IN SILICON DIODES AT MICROWAVE FREQUENCIES	83	[102-107]
15-22	MICROWAVE NANOSECOND PULSE BURNOUT PROPERTIES OF ONE MICRON MESFETS	79	[147-157]
72-20	ESD EVALUATION OF RADIATION-HARDENED, HIGH RELIABILITY CMOS AND MNOS ICS	83	[134-146]
72-26	A SUMMARY OF MOST EFFECTIVE ELECTROSTATIC DISCHARGE PROTECTION CIRCUITS FOR MOS MEMORIES AND THEIR OBSERVED FAILURE MODES	83	[181-184]
14-10	MODELING OF CURRENT AND THERMAL MODE SECOND BREAKDOWN PHENOMENA	82	[76-81]
	MONITORS		
05-20	PROTECTION OF COMPONENTS AGAINST ELECTRICAL OVERSTRESS (EOS) AND TRANSIENTS IN MONITORS	84	[136-143]
16- 4	ELECTROSTATIC DISCHARGE (ESD) MONITOR DESIGN	80	[23-25]
72-26	A SUMMARY OF MOST EFFECTIVE ELECTROSTATIC DISCHARGE PROTECTION CIRCUITS FOR MOS MEMORIES AND THEIR OBSERVED FAILURE MODES	83	[181-184]
14-22	ESD MINIMIZATION TECHNIQUE FOR MOS MANUFACTURING FINAL TEST AREA	82	[157-164]
16-12	PROTECTION OF MOS INTEGRATED CIRCUITS FROM DESTRUCTION BY ELECTROSTATIC DISCHARGE	80	[73-80]
15-24	SUSCEPTIBILITY OF LSI MOS TO ELECTROSTATIC DISCHARGE AT ELEVATED TEMPERATURE	79	[168-175]
05-23	DEGRADATION BY ESD TRANSIENTS OF THE SUBSTRATE BIAS VOLTAGE OF NMOS 8085-TYPE MICROPROCESSORS	84	[165-178]
72-27	ESD SENSITIVITY OF NMOS LSI CIRCUITS AND THEIR FAILURE CHARACTERISTICS	83	[185-197]
17-14	ON CHIP PROTECTION OF HIGH DENSITY NMOS DEVICES	81	[90-96]

KEYWORD IN TITLE INDEX

RD ENT-SEQUENCE NO.	TITLE	YEAR	PAGES
7-15	INPUT PROTECTION DESIGN FOR THE 3-MICRON NMOS PROCESS	81	[97-100]
TRESS			
5-20	PROTECTION OF COMPONENTS AGAINST ELECTRICAL OVERSTRESS (EOS) AND TRANSIENTS IN MONITORS	84	[136-143]
2- 5	AIR FORCE MAINTENANCE PROGRAM FOR ELECTRICAL OVERSTRESS/ELECTROSTATIC DISCHARGE (EOS/ESD) CONTROL	83	[21-28]
4- 3	LIMITATIONS IN MODELING ELECTRICAL OVERSTRESS FAILURE IN SEMICONDUCTOR DEVICES	82	[19-33]
4- 4	ELECTRICAL OVERSTRESS THRESHOLD TESTING	82	[34-40]
7-16	DIAGNOSIS AND ANALYSIS OF EMITTER-BASE JUNCTION OVERSTRESS DAMAGE	81	[101-105]
7-18	ELECTRICAL OVERSTRESS INVESTIGATIONS IN MODERN INTEGRATED CIRCUIT TECHNOLOGIES	81	[114-119]
6-21	ASSESSING ELECTRICAL OVERSTRESS EFFECTS ON ELECTRONIC SYSTEMS	80	[140-148]
6-22	SOLAR CELL ELECTRICAL OVERSTRESS ANALYSIS	80	[149-153]
6-23	AN OVERVIEW OF THE SOURCES AND EFFECTS OF ELECTRICAL OVERSTRESS	80	[154-160]
6-27	MICROCIRCUIT ELECTRICAL OVERSTRESS TOLERANCE TESTING AND QUALIFICATION	80	[184-188]
6-30	BASIC CONSIDERATIONS IN ELECTRO-THERMAL OVERSTRESS IN ELECTRONIC COMPONENTS	80	[206-212]
5-11	EFFECTS OF ELECTRICAL OVERSTRESS ON DIGITAL BIPOLAR MICROCIRCUITS AND ANALYSIS TECHNIQUES FOR FAILURE SITE LOCATION	79	[64-77]
5-13	FAILURE ANALYSIS OF MICROCIRCUITS SUBJECTED TO ELECTRICAL OVERSTRESS	79	[88-96]
5-20	MODELING OF ELECTRICAL OVERSTRESS IN SILICON DEVICES	79	[133-139]
5-21	SQUARE PULSE AND RF PULSE OVERSTRESSING OF UHF TRANSISTORS	79	[140-146]
5-26	ELECTRICAL OVERSTRESS VERSUS DEVICE GEOMETRY	79	[183-187]
E			
72-24	METAL OXIDE VARISTORS FOR TRANSIENT PROTECTION OF 3 TO 5-VOLT INTEGRATED CIRCUITS	83	[168-176]
AGING			
17- 9	CHO-TRAP, A NOVEL VOLTAGE TRANSIENT PROTECTION PACKAGING MATERIAL	81	[49-56]
17-11	INCOMING INSPECTION OF ANTISTATIC PACKAGING MATERIALS	81	[65-74]
17-12	SELECTION OF PACKAGING MATERIALS FOR ESD SENSITIVE ITEMS	81	[75-84]
METER			
16-32	AN EVALUATION OF WRIST STRAP PARAMETERS	80	[218-224]
IVE			
17-24	AN OVERVIEW OF EOS EFFECTS ON PASSIVE COMPONENTS	81	[167-173]
16- 1	PASSIVE STATIC PROTECTION: THEORY AND PRACTICE	80	[1-11]
ERN			
16-16	SUPRISING PATTERNS OF CMOS SUSCEPTIBILITY TO ESD AND IMPLICATIONS ON LONG-TERM RELIABILITY	80	[104-111]
VOLTAIC			
16-25	LIGHTNING PROTECTION DESIGN FOR A PHOTOVOLTAIC CONCENTRATOR	80	[167-175]
PIC			
14-16	DRASTIC LOSSES OF CONDUCTIVITY IN ANTISTATIC PLASTICS	82	[120-123]
MER			
14-15	ELECTROACTIVE POLYMERS AS ALTERNATE ESD PROTECTIVE MATERIALS	82	[115-119]

KEYWORD IN TITLE INDEX

<u>SEQUENCE NO.</u>	<u>TITLE</u>	<u>YEAR</u>	<u>PAGES</u>
9	POWER FAILURE MODELING OF INTEGRATED CIRCUITS	83	[56-62]
8	SEMICONDUCTOR JUNCTION NON-LINEAR FAILURE POWER THRESHOLDS: WUNSCH-BELL REVISITED	83	[122-127]
15	PULSE POWER RESPONSE AND DAMAGE CHARACTERISTICS OF CAPACITORS	81	[174-191]
17	BEHAVIOR OF THICK-FILM POWER RESISTORS SUBJECTED TO LARGE MOMENTARY OVERLOADS	81	[198-201]
17	REVERSE-BIAS SECOND BREAKDOWN IN POWER TRANSISTORS	79	[116-121]
ION			
16	PREDICTION OF THIN-FILM RESISTOR BURNOUT	81	[192-197]
5	ELECTROSTATIC MEASUREMENT FOR PROCESS CONTROL	84	[25-33]
15	INPUT PROTECTION DESIGN FOR THE 3-MICRON NMOS PROCESS	81	[97-100]
14	LSI DESIGN CONSIDERATIONS FOR ESD PROTECTION STRUCTURES RELATED TO PROCESS AND LAYOUT VARIATIONS	80	[87-94]
ION			
10	PROTECTION OF COMPONENTS AGAINST ELECTRICAL OVERSTRESS (EOS) AND TRANSIENTS IN MONITORS	84	[136-143]
17	A CMOS VLSI ESD INPUT PROTECTION DEVICE, DIFIDW	84	[202-209]
14	METAL OXIDE VARISTORS FOR TRANSIENT PROTECTION OF 3 TO 5-VOLT INTEGRATED CIRCUITS	83	[168-176]
15	USING SCR'S AS TRANSIENT PROTECTION STRUCTURES IN INTEGRATED CIRCUITS	83	[177-180]
16	A SUMMARY OF MOST EFFECTIVE ELECTROSTATIC DISCHARGE PROTECTION CIRCUITS FOR MOS MEMORIES AND THEIR OBSERVED FAILURE MODES	83	[181-184]
19	BASIC SPECIFICATION FOR ESD PROTECTION IN INDUSTRY	82	[136-141]
11	AN EFFECTIVE ELECTROSTATIC DISCHARGE PROTECTION PROGRAM	82	[145-156]
13	UNIFORM ESD PROTECTION IN A LARGE MULTI-DEPARTMENT ASSEMBLY PLANT	82	[165-168]
14	CIRCUIT DESIGN FOR EOS/ESD PROTECTION	82	[169-174]
9	CHO-TRAP, A NOVEL VOLTAGE TRANSIENT PROTECTION PACKAGING MATERIAL	81	[49-56]
14	ON CHIP PROTECTION OF HIGH DENSITY NMOS DEVICES	81	[90-96]
15	INPUT PROTECTION DESIGN FOR THE 3-MICRON NMOS PROCESS	81	[97-100]
10	LIGHTNING PROTECTION FOR COMPUTER DATA LINES	81	[212-218]
1	PASSIVE STATIC PROTECTION: THEORY AND PRACTICE	80	[1-11]
5	TRANSIENT PROTECTION WITH ZNO VARISTORS: TECHNICAL CONSIDERATIONS	80	[26-34]
6	PROTECTION LEVEL COMPARISONS FOR VOLTAGE TRANSIENT SUPPRESSORS (120 V, AC TYPE)	80	[35-43]
12	PROTECTION OF MOS INTEGRATED CIRCUITS FROM DESTRUCTION BY ELECTROSTATIC DISCHARGE	80	[73-80]
13	SOS PROTECTION: THE DESIGN PROBLEM	80	[81-86]
14	LSI DESIGN CONSIDERATIONS FOR ESD PROTECTION STRUCTURES RELATED TO PROCESS AND LAYOUT VARIATIONS	80	[87-94]
15	ELECTROSTATIC SENSITIVITY OF VARIOUS INPUT PROTECTION NETWORKS	80	[95-103]
15	LIGHTNING PROTECTION DESIGN FOR A PHOTOVOLTAIC CONCENTRATOR	80	[167-175]
9	THE DEFICIENCIES IN MILITARY SPECIFICATION MIL-B-81705: CONSIDERATIONS AND A SIMPLE MODEL FOR STATIC PROTECTION	79	[45-54]
18	HUMAN FACTORS IN ELECTROSTATIC DISCHARGE PROTECTION	79	[122-125]
18	ELECTROSTATIC DISCHARGE PROTECTION USING SILICON TRANSIENT SUPPRESSORS	79	[193-197]
15	PULSE POWER RESPONSE AND DAMAGE CHARACTERISTICS OF CAPACITORS	81	[174-191]
10	OSCILLATING VOLTAGE PULSES AND SECOND BREAKDOWN	80	[130-139]
11	SQUARE PULSE AND RF PULSE OVERSTRESSING OF UHF TRANSISTORS	79	[140-146]
12	MICROWAVE NANOSECOND PULSE BURNOUT PROPERTIES OF ONE MICRON MESFETS	79	[147-157]
ON			
10	ESD EVALUATION OF RADIATION-HARDENED, HIGH RELIABILITY CMOS AND MNOS ICS	83	[134-146]

KEYWORD IN TITLE INDEX

<u>SEQUENCE NO.</u>	<u>TITLE</u>	<u>YEAR</u>	<u>PAGES</u>
1			
	ESD EVALUATION OF RADIATION-HARDENED, HIGH RELIABILITY CMOS AND MNOS ICS	83	[134-146]
	THE EFFECT OF ESD ON CCD RELIABILITY	83	[147-153]
	SUPRISING PATTERNS OF CMOS SUSCEPTIBILITY TO ESD AND IMPLICATIONS ON LONG-TERM RELIABILITY	80	[104-111]
	RELIABILITY OF EOS SCREENED GOLD DOPED 4002 CMOS DEVICES	79	[41-44]
	ELECTROSTATIC DISCHARGE (ESD) DAMAGE SUSCPETIBILITY OF THIN FILM RESISTORS AND CAPACITORS	82	[13-18]
	PREDICTION OF THIN-FILM RESISTOR BURNOUT	81	[192-197]
	BEHAVIOR OF THICK-FILM POWER RESISTORS SUBJECTED TO LARGE MOMENTARY OVERLOADS	81	[198-201]
	SQUARE PULSE AND RF PULSE OVERSTRESSING OF UHF TRANSISTORS	79	[140-146]
	A ROOM IONIZATION SYSTEM FOR ELECTROSTATIC CHARGE AND DUST CONTROL	84	[40-44]
	THE ROOM AIR IONIZATION SYSTEM, A BETTER ALTERNATIVE THAN 40% RELATIVE HUMIDITY	83	[67-75]
	ESD AND CONTAMINATION FROM CLEAN ROOM GARMENTS - PROBLEMS AND SOLUTIONS	82	[131-135]
	THE EFFECTS OF VLSI SCALING ON EOS/ESD FAILURE THRESHOLD	81	[85-89]
	ESD SUSCEPTIBILITY TESTING OF ADVANCED SCHOTTKY TTL	82	[1-12]
	ELECTROSTATIC FAILURE OF X-BAND SILICON SCHOTTKY BARRIER DIODES	79	[97-103]
	THE FORWARD-BIAS CHARACTERISTIC AS A PREDICTOR AND SCREEN OF REVERSE-BIAS SECOND BREAKDOWN	82	[71-75]
	RELIABILITY OF EOS SCREENED GOLD DOPED 4002 CMOS DEVICES	79	[41-44]
	AN EXPERIMENTAL STUDY OF THE ESD SCREENING EFFECTIVENESS OF ANTI-STATIC BAGS	84	[78-84]
	SECONDARY DISCHARGE: A NEW JEOPARDY AND A NEW TOOL	84	[131-135]
	CALCULATIONS OF SECOND BREAKDOWN IN SILICON DIODES AT MICROWAVE FREQUENCIES	83	[102-107]
	MODELING AND TESTING FOR SECOND BREAKDOWN PHENOMENA	83	[108-117]
	TEMPERATURE AT SECOND BREAKDOWN AT A WELL-DEFINED SITE	83	[118-121]
	THE FORWARD-BIAS CHARACTERISTIC AS A PREDICTOR AND SCREEN OF REVERSE-BIAS SECOND BREAKDOWN	82	[71-75]
	MODELING OF CURRENT AND THERMAL MODE SECOND BREAKDOWN PHENOMENA	82	[76-81]
	SECOND BREAKDOWN IN SWITCHING TRANSISTORS	82	[91-93]
	SOME DESIGN CRITERIA FOR AVOIDING SECOND BREAKDOWN IN BIPOLAR DEVICES	80	[117-121]
	EFFECT OF JUNCTION SPIKES AND DOPING LEVEL ON THE SECOND BREAKDOWN	80	[122-129]
	SUSCEPTIBILITY OF SILICON-ON-SAPPHIRE DIODES		
	OSCILLATING VOLTAGE PULSES AND SECOND BREAKDOWN	80	[130-139]
	DOPING PROFILES AND SECOND BREAKDOWN	79	[109-115]
	REVERSE-BIAS SECOND BREAKDOWN IN POWER TRANSISTORS	79	[116-121]
	AN ELECTROTHERMAL MODEL FOR CURRENT FILAMENTATION IN SECOND BREAKDOWN OF SILICON-ON-SAPPHIRE DIODES	79	[126-132]
	THE ANALYSIS AND ELIMINATION OF EOS INDUCED SECONDARY FAILURE MECHANISMS	79	[205-209]

KEYWORD IN TITLE INDEX

<u>SEQUENCE NO.</u>	<u>TITLE</u>	<u>YEAR</u>	<u>PAGES</u>
	SECONDARY DISCHARGE: A NEW JEOPARDY AND A NEW TOOL	84	[131-135]
	ANALYSIS AND ELIMINATION OF EOS INDUCED SECONDARY FAILURE MECHANISMS	79	[205-209]
OR			
	TERMINATION OF THRESHOLD ENERGIES AND DAMAGE MECHANISMS IN SEMICONDUCTOR DEVICES SUBJECTED TO VOLTAGE TRANSIENTS	84	[157-164]
	SEMICONDUCTOR JUNCTION NON-LINEAR FAILURE POWER THRESHOLDS: WUNSCH-BELL REVISITED	83	[122-127]
	STUDY OF ESD LATENT DEFECTS IN SEMICONDUCTORS	83	[198-204]
	IMITATIONS IN MODELING ELECTRICAL OVERSTRESS FAILURE IN SEMICONDUCTOR DEVICES	82	[19-33]
	OVERVIEW OF EOS EFFECTS ON SEMICONDUCTOR DEVICES	81	[120-131]
	SEMICONDUCTOR DEVICE FAILURE CRITERIA FOR SINUSOIDAL STRESSES	81	[139-144]
	FAILURE ANALYSIS OF SEMICONDUCTOR DEVICES IN EOS/ESD TESTING	81	[219-224]
	ON-LINEAR KINETICS OF SEMICONDUCTOR JUNCTION THERMAL FAILURE	81	[242-245]
	SD SENSITIVITY AND LATENCY EFFECTS OF SOME HCMOS INTEGRATED CIRCUITS	84	[196-201]
	SD SENSITIVITY OF COMPLEX ICS	83	[128-133]
	SD SENSITIVITY OF NMOS LSI CIRCUITS AND THEIR FAILURE CHARACTERISTICS	83	[185-197]
	ELECTROSTATIC SENSITIVITY OF VARIOUS INPUT PROTECTION NETWORKS	80	[95-103]
	4E DIELECTRIC STRENGTH OF SiO2 IN A CMOS TRANSISTOR STRUCTURE	79	[176-182]
	ALCULATIONS OF SECOND BREAKDOWN IN SILICON DIODES AT MICROWAVE FREQUENCIES	83	[102-107]
	ODELING OF EOS IN SILICON DEVICES	81	[132-138]
	OS DAMAGE IN SILICON SOLAR CELLS	81	[209-235]
	EFFECT OF JUNCTION SPIKES AND DOPING LEVEL ON THE SECOND BREAKDOWN	80	[122-129]
	USCEPTIBILITY OF SILICON-ON-SAPPHIRE DIODES		
	4E GENERATION OF ELECTROSTATIC CHARGES IN SILICONE ENCAPSULANTS DURING CYCLIC ASEOUS PRESSURE TESTS	79	[22-26]
	ELECTROSTATIC FAILURE OF X-BAND SILICON SCHOTTKY BARRIER DIODES	79	[97-103]
	V ELECTROTHERMAL MODEL FOR CURRENT FILAMENTATION IN SECOND BREAKDOWN OF SILICON-ON-SAPPHIRE DIODES	79	[126-132]
	ODELING OF ELECTRICAL OVERSTRESS IN SILICON DEVICES	79	[133-139]
	ELECTROSTATIC DISCHARGE PROTECTION USING SILICON TRANSIENT SUPPRESSORS	79	[193-197]
	OS DAMAGE IN SILICON SOLAR CELLS	81	[209-235]
	SOLAR CELL ELECTRICAL OVERSTRESS ANALYSIS	80	[149-153]
	RIBOELECTRIC TESTING FOR ELECTROSTATIC CHARGES ON MATERIALS AT KENNEDY SPACE CENTER	84	[58-63]
	ONTROLLING ELECTROSTATIC PROBLEMS IN THE FABRICATION AND HANDLING OF SPACECRAFT HARDWARE	79	[4-6]
ON			
	ASIC SPECIFICATION FOR ESD PROTECTION IN INDUSTRY	82	[136-141]
	4E DEFICIENCIES IN MILITARY SPECIFICATION MIL-B-81705: CONSIDERATIONS AND A SIMPLE MODEL FOR STATIC PROTECTION	79	[45-54]
	HAZARDS OF STATIC CHARGES AND FIELDS AT THE WORK STATION	84	[7-19]

AD-A158 114 SEARCH AND RETRIEVAL INDEX TO EOS/ESD SYMPOSIUM
PROCEEDINGS - 1979 TO 1984(U) RELIABILITY ANALYSIS
CENTER GRIFFISS AFB NY R E RASH ET AL. 15 APR 85
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SEARCH AND RETRIEVAL INDEX TO EOS/ESD SYMPOSIUM
PROCEEDINGS - 1979 TO 1984(U) RELIABILITY ANALYSIS
CENTER GRIFFISS AFB NY R E RASH ET AL. 15 APR 85
RAC-TR5-4 F30602-84-C-0162 F/G 9/

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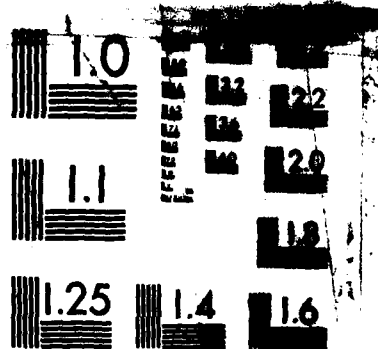
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MICROCOPY RESOLUTION TEST CHART
NATIONAL BUREAU OF STANDARDS-1963-A

KEYWORD IN TITLE INDEX

KEYWORD DOCUMENT-SEQUENCE NO.	TITLE	YEAR	PAGES
STATIC			
18305- 8	STATIC-ELECTRIC CHARACTERIZATION OF SEMI-INSULATING MATERIALS	84	[45-49]
18305-13	A MATERIAL EVALUATION PROGRAM FOR DECORATIVE STATIC CONTROL TABLE TOP LAMINATES	84	[85-93]
18305-17	DESIGNING TO AVOID STATIC - ESD TESTING OF DIGITAL DEVICES	84	[112-123]
18172- 6	ESD BY STATIC INDUCTION	83	[29-36]
18172-10	STATIC SURVEY METERS	83	[63-66]
18214-13	TEST METHODS FOR STATIC CONTROL PRODUCTS	82	[94-109]
17516- 1	PASSIVE STATIC PROTECTION: THEORY AND PRACTICE	80	[1-11]
17516-31	STATIC CONTROL SYSTEMS	80	[213-217]
17515- 4	STATIC CONTROL USING TOPICAL ANTISTATS	79	[13-21]
17515- 9	THE DEFICIENCIES IN MILITARY SPECIFICATION MIL-B-81705: CONSIDERATIONS AND A SIMPLE MODEL FOR STATIC PROTECTION	79	[45-54]
STATION			
18305- 2	HAZARDS OF STATIC CHARGES AND FIELDS AT THE WORK STATION	84	[7-19]
STATISTIC			
17515-29	STATISTICAL FAILURE ANALYSIS OF MILITARY SYSTEMS FOR HIGH-ALTITUDE EMP	79	[198-204]
STEP			
17517-17	SUSCEPTIBILITY OF ICS IN ESD STEP-STRESS TESTS	81	[106-113]
STRAP			
18305-14	A WRIST STRAP LIFE TEST PROGRAM	84	[94-96]
17516-32	AN EVALUATION OF WRIST STRAP PARAMETERS	80	[218-224]
STRESS			
17517-21	SEMICONDUCTOR DEVICE FAILURE CRITERIA FOR SINUSOIDAL STRESSES	81	[139-144]
STRUCTURE			
18172-25	USING SCR'S AS TRANSIENT PROTECTION STRUCTURES IN INTEGRATED CIRCUITS	83	[177-180]
17516-14	LSI DESIGN CONSIDERATIONS FOR ESD PROTECTION STRUCTURES RELATED TO PROCESS AND LAYOUT VARIATIONS	80	[87-94]
17515-25	THE DIELECTRIC STRENGTH OF SIO2 IN A CMOS TRANSISTOR STRUCTURE	79	[176-182]
SUBSTRATE			
18305-23	DEGRADATION BY ESD TRANSIENTS OF THE SUBSTRATE BIAS VOLTAGE OF NMOS 8085-TYPE MICROPROCESSORS	84	[165-178]
SUPPRESSOR			
17516- 6	PROTECTION LEVEL COMPARISONS FOR VOLTAGE TRANSIENT SUPPRESSORS (120 V, AC TYPE)	80	[35-43]
17515-28	ELECTROSTATIC DISCHARGE PROTECTION USING SILICON TRANSIENT SUPPRESSORS	79	[193-197]
SURFACE			
18214-17	CHARACTERIZATION OF ESD SAFE REQUIREMENTS FOR FLOOR SURFACES	82	[124-130]
17515- 3	ELECTROSTATIC CONDUCTIVITY CHARACTERISTICS OF WORKBENCH-TOP SURFACE MATERIALS	79	[7-12]
SURGE			
17516- 7	GAS TUBE SURGE ARRESTERS FOR CONTROL OF TRANSIENT VOLTAGES	80	[44-53]
17516-26	SURGE TESTS ON PLUG-IN TRANSFORMERS	80	[176-183]
SUSCEPTIBILITY			
18305-24	DEVICE ESD SUSCEPTIBILITY TESTING AND DESIGN HARDENING	84	[179-188]

KEYWORD IN TITLE INDEX

KEYWORD DOCUMENT-SEQUENCE NO.	TITLE	YEAR	PAGES
SUSCEPTIBILITY			
18214- 1	ESD SUSCEPTIBILITY TESTING OF ADVANCED SCHOTTKY TTL	82	[1-12]
17517-17	SUSCEPTIBILITY OF ICS IN ESD STEP-STRESS TESTS	81	[106-113]
17516-16	SUPRISING PATTERNS OF CMOS SUSCEPTIBILITY TO ESD AND IMPLICATIONS ON LONG-TERM RELIABILITY	80	[104-111]
17516-19	EFFECT OF JUNCTION SPIKES AND DOPING LEVEL ON THE SECOND BREAKDOWN	80	[122-129]
	SUSCEPTIBILITY OF SILICON-ON-SAPPHIRE DIODES		
17515-24	SUSCEPTIBILITY OF LSI MOS TO ELECTROSTATIC DISCHARGE AT ELEVATED TEMPERATURE	79	[168-175]
SWITCH			
18214-12	SECOND BREAKDOWN IN SWITCHING TRANSISTORS	82	[91-93]
SYSTEM			
18305- 7	A ROOM IONIZATION SYSTEM FOR ELECTROSTATIC CHARGE AND DUST CONTROL	84	[40-44]
18172-11	THE ROOM AIR IONIZATION SYSTEM, A BETTER ALTERNATIVE THAN 40% RELATIVE HUMIDITY	83	[67-75]
18214-27	ELECTROSTATIC DISCHARGE IMMUNITY IN COMPUTER SYSTEMS	82	[185-189]
18214-28	ELECTRICAL GROUNDING IN LARGE INSTRUMENTATION SYSTEMS	82	[190-202]
17516-21	ASSESSING ELECTRICAL OVERSTRESS EFFECTS ON ELECTRONIC SYSTEMS	80	[140-148]
17516-31	STATIC CONTROL SYSTEMS	80	[213-217]
17515-29	STATISTICAL FAILURE ANALYSIS OF MILITARY SYSTEMS FOR HIGH-ALTITUDE EMP	79	[198-204]
TECHNIQUE			
18214-22	ESD MINIMIZATION TECHNIQUE FOR MOS MANUFACTURING FINAL TEST AREA	82	[157-164]
17516-24	TEST WAVEFORMS AND TECHNIQUES TO ASSESS THE THREAT TO ELECTRONIC DEVICES OF LIGHTNING-INDUCED TRANSIENTS	80	[161-166]
17515-11	EFFECTS OF ELECTRICAL OVERSTRESS ON DIGITAL BIPOLAR MICROCIRCUITS AND ANALYSIS TECHNIQUES FOR FAILURE SITE LOCATION	79	[64-77]
TEMPERATURE			
18172-17	TEMPERATURE AT SECOND BREAKDOWN AT A WELL-DEFINED SITE	83	[118-121]
17515-24	SUSCEPTIBILITY OF LSI MOS TO ELECTROSTATIC DISCHARGE AT ELEVATED TEMPERATURE	79	[168-175]
TEST			
18305- 3	TEST EQUIPMENT--A SOURCE OF ESD!!	84	[20-21]
18305-14	A WRIST STRAP LIFE TEST PROGRAM	84	[94-96]
18172- 7	CONSTRUCTION AND APPLICATION OF A TESTER FOR MEASURING EOS/ESD THRESHOLDS TO 15KV	83	[37-47]
18214-13	TEST METHODS FOR STATIC CONTROL PRODUCTS	82	[94-109]
18214-22	ESD MINIMIZATION TECHNIQUE FOR MOS MANUFACTURING FINAL TEST AREA	82	[157-164]
17517-17	SUSCEPTIBILITY OF ICS IN ESD STEP-STRESS TESTS	81	[106-113]
17516-24	TEST WAVEFORMS AND TECHNIQUES TO ASSESS THE THREAT TO ELECTRONIC DEVICES OF LIGHTNING-INDUCED TRANSIENTS	80	[161-166]
17516-26	SURGE TESTS ON PLUG-IN TRANSFORMERS	80	[176-183]
17515- 5	THE GENERATION OF ELECTROSTATIC CHARGES IN SILICONE ENCAPSULANTS DURING CYCLIC GASEOUS PRESSURE TESTS	79	[22-26]
TESTING			
18305-10	TRIBOELECTRIC TESTING FOR ELECTROSTATIC CHARGES ON MATERIALS AT KENNEDY SPACE CENTER	84	[58-63]
18305-15	TESTING OF ELECTROSTATIC MATERIALS FED. STD. 101C, METHOD 4046.1	84	[97-103]
18305-16	CRITICAL CONSIDERATIONS FOR ESD TESTING	84	[104-111]
18305-17	DESIGNING TO AVOID STATIC - ESD TESTING OF DIGITAL DEVICES	84	[112-123]
18305-24	DEVICE ESD SUSCEPTIBILITY TESTING AND DESIGN HARDENING	84	[179-188]
18172- 8	A PROGRAMMABLE EQUIPMENT FOR ELECTROSTATIC DISCHARGE TESTING TO HUMAN BODY MODELS	83	[48-55]
18172-16	MODELING AND TESTING FOR SECOND BREAKDOWN PHENOMENA	83	[108-117]
18214- 1	ESD SUSCEPTIBILITY TESTING OF ADVANCED SCHOTTKY TTL	82	[1-12]
18214- 4	ELECTRICAL OVERSTRESS THRESHOLD TESTING	82	[34-40]

KEYWORD IN TITLE INDEX

KEYWORD			
<u>DOCUMENT-SEQUENCE NO.</u>	<u>TITLE</u>	<u>YEAR</u>	<u>PAGES</u>
TESTING			
17517-31	FAILURE ANALYSIS OF SEMICONDUCTOR DEVICES IN EOS/ESD TESTING	81	[219-224]
17516-27	MICROCIRCUIT ELECTRICAL OVERSTRESS TOLERANCE TESTING AND QUALIFICATION	80	[184-188]
THERMAL			
18214-10	MODELING OF CURRENT AND THERMAL MODE SECOND BREAKDOWN PHENOMENA	82	[76-81]
17517-35	NON-LINEAR KINETICS OF SEMICONDUCTOR JUNCTION THERMAL FAILURE	81	[242-245]
THICK			
17517-27	BEHAVIOR OF THICK-FILM POWER RESISTORS SUBJECTED TO LARGE MOMENTARY OVERLOADS	81	[198-201]
THIN			
18214- 2	ELECTROSTATIC DISCHARGE (ESD) DAMAGE SUSCEPTIBILITY OF THIN FILM RESISTORS AND CAPACITORS	82	[13-18]
17517-26	PREDICTION OF THIN-FILM RESISTOR BURNOUT	81	[192-197]
TRANSIENT			
18305-20	PROTECTION OF COMPONENTS AGAINST ELECTRICAL OVERSTRESS (EOS) AND TRANSIENTS IN MONITORS	84	[136-143]
18305-22	DETERMINATION OF THRESHOLD ENERGIES AND DAMAGE MECHANISMS IN SEMICONDUCTOR DEVICES SUBJECTED TO VOLTAGE TRANSIENTS	84	[157-164]
18305-23	DEGRADATION BY ESD TRANSIENTS OF THE SUBSTRATE BIAS VOLTAGE OF NMOS 8085-TYPE MICROPROCESSORS	84	[165-178]
18172-24	METAL OXIDE VARISTORS FOR TRANSIENT PROTECTION OF 3 TO 5-VOLT INTEGRATED CIRCUITS	83	[168-176]
18172-25	USING SCR'S AS TRANSIENT PROTECTION STRUCTURES IN INTEGRATED CIRCUITS	83	[177-180]
18214-11	A PROBABILISTIC ESTIMATOR FOR BOUNDING TRANSISTOR EMITTER-BASE JUNCTION TRANSIENT-INDUCED FAILURES	82	[82-90]
17517- 9	CHO-TRAP, A NOVEL VOLTAGE TRANSIENT PROTECTION PACKAGING MATERIAL	81	[49-56]
17516- 5	TRANSIENT PROTECTION WITH ZNO VARISTORS: TECHNICAL CONSIDERATIONS	80	[26-34]
17516- 6	PROTECTION LEVEL COMPARISONS FOR VOLTAGE TRANSIENT SUPPRESSORS (120 V, AC TYPE)	80	[35-43]
17516- 7	GAS TUBE SURGE ARRESTERS FOR CONTROL OF TRANSIENT VOLTAGES	80	[44-53]
17516-24	TEST WAVEFORMS AND TECHNIQUES TO ASSESS THE THREAT TO ELECTRONIC DEVICES OF LIGHTNING-INDUCED TRANSIENTS	80	[161-166]
17516-33	MEASUREMENT OF FAST TRANSIENTS AND APPLICATION TO HUMAN ESD	80	[225-230]
17515-28	ELECTROSTATIC DISCHARGE PROTECTION USING SILICON TRANSIENT SUPPRESSORS	79	[193-197]
TRANSISTOR			
18214-11	A PROBABILISTIC ESTIMATOR FOR BOUNDING TRANSISTOR EMITTER-BASE JUNCTION TRANSIENT-INDUCED FAILURES	82	[82-90]
18214-12	SECOND BREAKDOWN IN SWITCHING TRANSISTORS	82	[91-93]
17517-22	DETERMINING AN EMITTER-BASE FAILURE THRESHOLD DISTRIBUTION OF NPN TRANSISTORS	81	[145-150]
17516-10	FAILURE THRESHOLD DISTRIBUTIONS IN BIPOLAR TRANSISTORS	80	[59-66]
17516-17	HIGH-FIELD PHENOMENA AND FAILURE MECHANISMS IN BIPOLAR TRANSISTORS	80	[112-116]
17515-17	REVERSE-BIAS SECOND BREAKDOWN IN POWER TRANSISTORS	79	[116-121]
17515-21	SQUARE PULSE AND RF PULSE OVERSTRESSING OF UHF TRANSISTORS	79	[140-146]
17515-25	THE DIELECTRIC STRENGTH OF SiO2 IN A CMOS TRANSISTOR STRUCTURE	79	[176-182]
17515-27	THE PHANTOM EMITTER-AN ESD-RESISTANT BIPOLAR TRANSISTOR DESIGN AND ITS APPLICATIONS TO LINEAR INTEGRATED CIRCUITS	79	[188-192]
TRIBOELECTRIC			
18305-11	TRIBOELECTRIC CHARGE: ITS ESD ABILITY AND A MEASUREMENT METHOD FOR ITS PROPENSITY ON PACKING MATERIALS	84	[64-77]
17516- 3	ESD DAMAGE FROM TRIBOELECTRICALLY CHARGED IC PINS	80	[17-22]
VLSI			
18305-27	A CMOS VLSI ESD INPUT PROTECTION DEVICE, DIPIDW	84	[202-209]

KEYWORD IN TITLE INDEX

KEYWORD				
<u>DOCUMENT-SEQUENCE NO.</u>	<u>TITLE</u>	<u>YEAR</u>	<u>PAGES</u>	
VLSI				
17517-13	THE EFFECTS OF VLSI SCALING ON EOS/ESD FAILURE THRESHOLD	81	[85-89]	
WRIST				
18305-14	A WRIST STRAP LIFE TEST PROGRAM	84	[94-96]	
17516-32	AN EVALUATION OF WRIST STRAP PARAMETERS	80	[218-224]	
X-BAND				
17515-14	ELECTROSTATIC FAILURE OF X-BAND SILICON SCHOTTKY BARRIER DIODES	79	[97-103]	

Section 6:

CHRONOLOGICAL LIST OF PAPERS

CHRONOLOGICAL LIST OF PAPERS 1984

<u>DOCUMENT-SEQUENCE NO.</u>	<u>TITLE</u>	<u>PAGES</u>
18305-27	A CMOS VLSI ESD INPUT PROTECTION DEVICE, DIFIDW	[202-209]
<u>AUTHOR(S)</u> :	RICHARDSON,L. SIMCOE,R. CHI,K.	
<u>COMPANY</u> :	DIGITAL EQUIPMENT CORPORATION (DEC)	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
INPUT PROTECTION	[ESD, DEVICE, PROTECTIVE DEVICES/INPUT PROTECTION]	
18305-26	ESD SENSITIVITY AND LATENCY EFFECTS OF SOME HCMOS INTEGRATED CIRCUITS	[196-201]
<u>AUTHOR(S)</u> :	CROCKETT,R.G.M. SMITH,J.G. HUGHES,J.F.	
<u>COMPANY</u> :	UNIVERSITY OF SOUTHAMPTON	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
MOSFET C	[FIELD EFFECT,(FET), SEMICONDUCTOR TECH.]	
MICROCIRCUIT	[SEMICONDUCTOR DEVICE]	
STEP STRESS	[TEST TECHNIQUES FOR REL. ASSESSMENT, SEMICONDUCTOR TECH.]	
18305-25	A FAILURE ANALYSIS METHODOLOGY FOR REVEALING ESD DAMAGE TO INTEGRATED CIRCUITS	[189-195]
<u>AUTHOR(S)</u> :	TAYLOR,R.G. WOODHOUSE,J. FEASEY,P.R.	
<u>COMPANY</u> :	BRITISH TELECOM	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
ELECTRO-THERMOMIGRATION	[ESD, DEVICE, FAILURE MODES]	
HUMAN BODY ESD MODEL	[ESD, DEVICE, TESTING METHODS]	
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
MOSFET C	[FIELD EFFECT,(FET), SEMICONDUCTOR TECH.]	
MICROCIRCUIT	[SEMICONDUCTOR DEVICE]	
18305-24	DEVICE ESD SUSCEPTIBILITY TESTING AND DESIGN HARDENING	[179-188]
<u>AUTHOR(S)</u> :	DECHIARO,L.F.	
<u>COMPANY</u> :	BELL LABORATORIES	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
OXIDATION	[CHEMICAL FAILURE PHENOMENA, SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
FAILURE MODES	[FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
FAILURE ANALYSIS TECHNIQUES	[FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
MICROCIRCUIT	[SEMICONDUCTOR DEVICE]	
18305-23	DEGRADATION BY ESD TRANSIENTS OF THE SUBSTRATE BIAS VOLTAGE OF NMOS 8085-TYPE MICROPROCESSORS	[165-178]
<u>AUTHOR(S)</u> :	SHAW,R.N. ENOCH,R.D. TAYLOR,R.G.	
<u>COMPANY</u> :	BRITISH TELECOM	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
CIRCUIT BOARD	[NON-ELECTRONICS]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
HUMAN BODY ESD MODEL	[ESD, DEVICE, TESTING METHODS]	
METALLIZATION MELT	[ESD, DEVICE, FAILURE MODES]	
ESD STD AND HANDBOOK	[ESD, STANDARDS, HANDBOOKS, MANUALS]	
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
MICROCIRCUIT	[SEMICONDUCTOR DEVICE]	

CHRONOLOGICAL LIST OF PAPERS 1984

DOCUMENT-SEQUENCE NO.	TITLE	PAGES
18305-22	DETERMINATION OF THRESHOLD ENERGIES AND DAMAGE MECHANISMS IN SEMICONDUCTOR DEVICES SUBJECTED TO VOLTAGE TRANSIENTS	[157-164]
AUTHOR(S) : ROBERTS,B.C.		
COMPANY : ERA TECHNOLOGY, LTD.		
INDEX TERM	CATEGORIES	
EOS/ESD	[SEMICONDUCTOR TECH.]	
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
MOSFET N	[FIELD EFFECT,(FET), SEMICONDUCTOR TECH.]	
MICROCIRCUIT	[SEMICONDUCTOR DEVICE]	
18305-21	AN EVALUATION OF EOS FAILURE MODELS	[144-156]
AUTHOR(S) : PIERCE,D.G. PERILLAT,J. SHILEY,W.L.		
COMPANY : BOOZ, ALLEN & HAMILTON		
INDEX TERM	CATEGORIES	
BIPOLAR	[COMPONENT TYPE]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
EMP - ELECTROMAGNETIC PULSE	[ESD, EOS/ESD PHYSICS]	
EOS - ELECTRICAL OVERSTRESS	[ESD, EOS/ESD PHYSICS]	
MOSFET C	[FIELD EFFECT,(FET), SEMICONDUCTOR TECH.]	
TRANSISTOR	[DISCRETE SEMICONDUCTOR, SEMICONDUCTOR DEVICE]	
MICROCIRCUIT	[SEMICONDUCTOR DEVICE]	
18305-20	PROTECTION OF COMPONENTS AGAINST ELECTRICAL OVERSTRESS (EOS) AND TRANSIENTS IN MONITORS	[136-143]
AUTHOR(S) : FOERSTER,G.		
COMPANY : RCA		
INDEX TERM	CATEGORIES	
EOS/ESD	[SEMICONDUCTOR TECH.]	
ELECTROSTATIC SIMULATOR	[ESD, DEVICE, TESTING METHODS]	
EOS - ELECTRICAL OVERSTRESS	[ESD, EOS/ESD PHYSICS]	
MODELS/THEORY/EQUATIONS	[REL. MODELING TECHNIQUES, REL. MODELS/DATA/ANALYSIS]	
18305-19	SECONDARY DISCHARGE: A NEW JEOPARDY AND A NEW TOOL	[131-135]
AUTHOR(S) : LAFFERTY,D.		
COMPANY : INTEL		
INDEX TERM	CATEGORIES	
CIRCUIT BOARD	[NON-ELECTRONICS]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
CHARGE DEVICE MODEL	[ESD, DEVICE, TESTING METHODS]	
DECAY TIME	[ESD, MATERIALS AND EQUIPMENT, TESTING]	
PROTECTIVE WORK BENCH SURFACE	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
RELATIVE HUMIDITY	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]	
TRIOBOELECTRIC CHARGING	[ESD, EOS/ESD PHYSICS]	
NONELECTRONICS		
MICROCIRCUIT	[SEMICONDUCTOR DEVICE]	
18305-18	EMI CHARACTERISTICS OF ESD IN A SMALL AIR GAP --ARP GOVERNS THE EMI--	[124-130]
AUTHOR(S) : HONDA,M. KAWAMURA,T.		
COMPANY : NIPPON UNIVAC KAISHA, LTD.		
INDEX TERM	CATEGORIES	
EOS/ESD	[SEMICONDUCTOR TECH.]	
EMI - ELECTROMAGNETIC INTERFACE	[ESD, EOS/ESD PHYSICS]	
PACKAGE	[SEMICONDUCTOR TECH.]	
MICROCIRCUIT	[SEMICONDUCTOR DEVICE]	
TESTING TOOLS & TECHNIQUES	[SEMICONDUCTOR TECH.]	

CHRONOLOGICAL LIST OF PAPERS 1984

<u>DOCUMENT-SEQUENCE NO.</u>	<u>TITLE</u>	<u>PAGES</u>
18305-17	DESIGNING TO AVOID STATIC - ESD TESTING OF DIGITAL DEVICES	[112-123]
<u>AUTHOR(S)</u> :	DASH,G.R.	
<u>COMPANY</u> :	DASH, STRAUS, & GOODHUE, INC.	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
ELECTRICAL FAILURE PHENOMENA	[SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
ELECTROSTATIC SIMULATOR	[ESD, DEVICE, TESTING METHODS]	
HUMAN BODY ESD MODEL	[ESD, DEVICE, TESTING METHODS]	
18305-16	CRITICAL CONSIDERATIONS FOR ESD TESTING	[104-111]
<u>AUTHOR(S)</u> :	HYATT,H.M.	
<u>COMPANY</u> :	EXPERIMENTAL PHYSICS CORPORATION	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
DESIGN CONSIDERATIONS	[SEMICONDUCTOR TECH.]	
TOLERANCES	[DESIGN CONSIDERATIONS, SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
ELECTROSTATIC SIMULATOR	[ESD, DEVICE, TESTING METHODS]	
HUMAN BODY ESD MODEL	[ESD, DEVICE, TESTING METHODS]	
EMI - ELECTROMAGNETIC INTERFACE	[ESD, EOS/ESD PHYSICS]	
RELATIVE HUMIDITY	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]	
18305-15	TESTING OF ELECTROSTATIC MATERIALS FED. STD. 101C, METHOD 4046.1	[97-103]
<u>AUTHOR(S)</u> :	BAUMGARTNER,G. HAVERMANN,R.	
<u>COMPANY</u> :	LOCKHEED	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
CONDUCTIVE ESD PROTECTIVE MATERIAL	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
DECAY TIME	[ESD, MATERIALS AND EQUIPMENT, TESTING]	
ESD PROTECTIVE MATERIAL	[ESD, MATERIALS AND EQUIPMENT, TESTING]	
ESD STD AND HANDBOOK	[ESD, STANDARDS, HANDBOOKS, MANUALS]	
SURFACE RESISTIVITY	[ESD, MATERIALS AND EQUIPMENT, TESTING]	
TRIOBOELECTRIC CHARGING	[ESD, EOS/ESD PHYSICS]	
TESTING TOOLS & TECHNIQUES	[SEMICONDUCTOR TECH.]	
18305-14	A WRIST STRAP LIFE TEST PROGRAM	[94-96]
<u>AUTHOR(S)</u> :	HOHL,A.P.	
<u>COMPANY</u> :	RCA	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
GROUNDING STRAPS	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
WRIST STRAP	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
TESTING TOOLS & TECHNIQUES	[SEMICONDUCTOR TECH.]	
18305-13	A MATERIAL EVALUATION PROGRAM FOR DECORATIVE STATIC CONTROL TABLE TOP LAMINATES	[85-93]
<u>AUTHOR(S)</u> :	SAFEER,N.I. MILEHAM,J.R.	
<u>COMPANY</u> :	SPAULDING FIBRE COMPANY, INC.	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
DECAY TIME	[ESD, MATERIALS AND EQUIPMENT, TESTING]	
GROUNDING METHODS	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]	
PROTECTIVE WORK BENCH SURFACE	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
SURFACE RESISTIVITY	[ESD, MATERIALS AND EQUIPMENT, TESTING]	
LIFE	[TEST TECHNIQUES FOR REL. ASSESSMENT, SEMICONDUCTOR TECH.]	
TESTING TOOLS & TECHNIQUES	[SEMICONDUCTOR TECH.]	

CHRONOLOGICAL LIST OF PAPERS 1984

<u>DOCUMENT-SEQUENCE NO.</u>	<u>TITLE</u>	<u>PAGES</u>
18305-12	AN EXPERIMENTAL STUDY OF THE ESD SCREENING EFFECTIVENESS OF ANTI-STATIC BAGS	[78-84]
<u>AUTHOR(S)</u> : HOLMES,G.C.	HUFF,P.J. JOHNSON,R.L.	
<u>COMPANY</u> : BRITISH TELECOM		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
BULK CONDUCTIVE PLASTIC	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
PROTECTIVE BAGS	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
TRIBOELECTRIC CHARGING	[ESD, EOS/ESD PHYSICS]	
18305-11	TRIBOELECTRIC CHARGE: ITS ESD ABILITY AND A MEASUREMENT METHOD FOR ITS PROPENSITY ON PACKING MATERIALS	[64-77]
<u>AUTHOR(S)</u> : HUNTSMAN,J.R.		
<u>COMPANY</u> : 3M		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
DECAY TIME	[ESD, MATERIALS AND EQUIPMENT, TESTING]	
PROTECTIVE BAGS	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
SURFACE RESISTIVITY	[ESD, MATERIALS AND EQUIPMENT, TESTING]	
TRIBOELECTRIC CHARGING	[ESD, EOS/ESD PHYSICS]	
LOGISTICS	[SYSTEMS]	
18305-10	TRIBOELECTRIC TESTING FOR ELECTROSTATIC CHARGES ON MATERIALS AT KENNEDY SPACE CENTER	[58-63]
<u>AUTHOR(S)</u> : GOMPF,R.H.		
<u>COMPANY</u> : CONSULTANT		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
DECAY TIME	[ESD, MATERIALS AND EQUIPMENT, TESTING]	
RELATIVE HUMIDITY	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]	
SURFACE RESISTIVITY	[ESD, MATERIALS AND EQUIPMENT, TESTING]	
TRIBOELECTRIC CHARGING	[ESD, EOS/ESD PHYSICS]	
PACKAGE	[SEMICONDUCTOR TECH.]	
MICROCIRCUIT	[SEMICONDUCTOR DEVICE]	
18305- 9	ESTIMATION OF DISCHARGE ENERGY RELEASED FROM CHARGED INSULATOR	[50-57]
<u>AUTHOR(S)</u> : TABATA,Y.		
<u>COMPANY</u> : MINISTRY OF LABOUR		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
INDUCTIVE CHARGING	[ESD, EOS/ESD PHYSICS]	
TESTING TOOLS & TECHNIQUES	[SEMICONDUCTOR TECH.]	
18305- 8	STATIC-ELECTRIC CHARACTERIZATION OF SEMI-INSULATING MATERIALS	[45-49]
<u>AUTHOR(S)</u> : JONASSEN,N.		
<u>COMPANY</u> : TECHNICAL UNIVERSITY OF DENMARK		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
DECAY TIME	[ESD, MATERIALS AND EQUIPMENT, TESTING]	
ESD PROTECTIVE MATERIAL	[ESD, MATERIALS AND EQUIPMENT, TESTING]	
SURFACE RESISTIVITY	[ESD, MATERIALS AND EQUIPMENT, TESTING]	

CHRONOLOGICAL LIST OF PAPERS 1984

DOCUMENT-SEQUENCE NO.	TITLE	PAGES
18305- 7	A ROOM IONIZATION SYSTEM FOR ELECTROSTATIC CHARGE AND DUST CONTROL	[40-44]
<u>AUTHOR(S)</u> : UNGER, B.A.	CHEMELLI, R.G.	BOSSARD, P.R.
<u>COMPANY</u> : BELL COMMUNICATIONS RESEARCH, INC.		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
AIR IONIZER	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
DECAY TIME	[ESD, MATERIALS AND EQUIPMENT, TESTING]	
ION ELECTRONICS		
TESTING TOOLS & TECHNIQUES	[SEMICONDUCTOR TECH.]	
18305- 6	EFFECTS OF AIR IONS AND ELECTRIC FIELDS ON HEALTH AND PRODUCTIVITY	[34-39]
<u>AUTHOR(S)</u> : CARLTON, R.M.		
<u>COMPANY</u> : AMERICAN INSTITUTE OF MEDICAL CLIMATOLOGY (AIMC)		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
AIR IONIZER	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
STATIC CONTROL	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]	
FABRICATION PROCESSES & TECHNIQUES	[SEMICONDUCTOR TECH.]	
MICROCIRCUIT	[SEMICONDUCTOR DEVICE]	
18305- 5	ELECTROSTATIC MEASUREMENT FOR PROCESS CONTROL	[25-33]
<u>AUTHOR(S)</u> : BAUMGARTNER, G.		
<u>COMPANY</u> : LOCKHEED		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
ELECTROSTATIC CHARGE DETECTOR	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
HUMAN BODY ESD MODEL	[ESD, DEVICE, TESTING METHODS]	
EOS - ELECTRICAL OVERSTRESS	[ESD, EOS/ESD PHYSICS]	
TRIBOELECTRIC CHARGING	[ESD, EOS/ESD PHYSICS]	
PROCESS CONTROL/SPECIFICATION	[FABRICATION PROCESSES & TECHNIQUES, SEMICONDUCTOR TECH.]	
TEST EQUIPMENT	[TESTING TOOLS & TECHNIQUES, SEMICONDUCTOR TECH.]	
TEST TECHNIQUES	[TESTING TOOLS & TECHNIQUES, SEMICONDUCTOR TECH.]	
18305- 4	ESD DAMAGE, DOES IT HAPPEN ON PCBs?	[22-23]
<u>AUTHOR(S)</u> : THOMPSON, W.H.		
<u>COMPANY</u> : U.S. AIR FORCE		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
BOARD	[LEVEL OF ASSEMBLY]	
CIRCUIT BOARD	[NON-ELECTRONICS]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
ASSEMBLY & EQUIPMENT ESD CLASSIFICATION	[ESD, DEVICE, TESTING METHODS]	
EMI - ELECTROMAGNETIC INTERFACE	[ESD, EOS/ESD PHYSICS]	
EMP - ELECTROMAGNETIC PULSE	[ESD, EOS/ESD PHYSICS]	
MICROCIRCUIT	[SEMICONDUCTOR DEVICE]	
18305- 3	TEST EQUIPMENT--A SOURCE OF ESD!!	[20-21]
<u>AUTHOR(S)</u> : SAUERS, J.P.		
<u>COMPANY</u> : MAGNAVOX		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
ELECTROSTATIC CHARGE DETECTOR	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
ESD STD AND HANDBOOK	[ESD, STANDARDS, HANDBOOKS, MANUALS]	
MICROCIRCUIT	[SEMICONDUCTOR DEVICE]	
TEST EQUIPMENT	[TESTING TOOLS & TECHNIQUES, SEMICONDUCTOR TECH.]	

CHRONOLOGICAL LIST OF PAPERS 1984

<u>DOCUMENT-SEQUENCE NO.</u>	<u>TITLE</u>	<u>PAGES</u>
8305- 2	HAZARDS OF STATIC CHARGES AND FIELDS AT THE WORK STATION	{7-19 }
<u>UTHOR(S)</u> :	KOLYER, J.M. ANDERSON, W.E. WATSON, D.E.	
<u>OMPANY</u> :	ROCKWELL	

<u>INDEX TERM</u>	<u>CATEGORIES</u>
OS/ESD	[SEMICONDUCTOR TECH.]
IR IONIZER	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]
ELECTROSTATIC CHARGE DETECTOR	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]
SD PROTECTIVE MATERIAL	[ESD, MATERIALS AND EQUIPMENT, TESTING]
ROTECTED ESD AREA	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]
ROTECTIVE BAGS	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]
JRFACE RESISTIVITY	[ESD, MATERIALS AND EQUIPMENT, TESTING]
RIST STRAP	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]
ABRICATION PROCESSES & TECHNIQUES	[SEMICONDUCTOR TECH.]
ABRICATION EQUIPMENT	[FABRICATION PROCESSES & TECHNIQUES, SEMICONDUCTOR TECH.]
DSFET	[FIELD EFFECT, (FET), SEMICONDUCTOR TECH.]
ALITY ASSURANCE	[SYSTEMS]

8305- 1	A REALISTIC AND SYSTEMATIC ESD CONTROL PLAN	{1-6 }
<u>UTHOR(S)</u> :	DANGELMAYER, G.T.	
<u>OMPANY</u> :	ATT	

<u>INDEX TERM</u>	<u>CATEGORIES</u>
ST	[SYSTEMS]
S/ESD	[SEMICONDUCTOR TECH.]
ARGE DEVICE MODEL	[ESD, DEVICE, TESTING METHODS]
MAN BODY ESD MODEL	[ESD, DEVICE, TESTING METHODS]
D CONTROL PROGRAM	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]
ATIC CONTROL	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]
ALITY ASSURANCE	[SYSTEMS]

CHRONOLOGICAL LIST OF PAPERS 1983

<u>DOCUMENT-SEQUENCE NO.</u>	<u>TITLE</u>	<u>PAGES</u>
18172-28	A STUDY OF ESD LATENT DEFECTS IN SEMICONDUCTORS	[198-204]
<u>AUTHOR(S)</u> : BEALL, J.	BOWERS, J.	ROSSI, M.
<u>COMPANY</u> : MARTIN MARIETTA		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
DIELECTRIC BREAKDOWN	[ESD, DEVICE, FAILURE MODES]	
LATENT ESD FAILURE	[ESD, DEVICE, FAILURE MODES]	
OVERSTRESS	[FAILURE CAUSE, FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
GUIDE/PROCEDURE	[REFERENCE DOCUMENT]	
SEMICONDUCTOR DEVICE		
LIFE	[TEST TECHNIQUES FOR REL. ASSESSMENT, SEMICONDUCTOR TECH.]	
OPERATIONAL TEST	[TEST TECHNIQUES FOR REL. ASSESSMENT, SEMICONDUCTOR TECH.]	
TEST SPECIFICATION	[TESTING TOOLS & TECHNIQUES, SEMICONDUCTOR TECH.]	
18172-27	ESD SENSITIVITY OF NMOS LSI CIRCUITS AND THEIR FAILURE CHARACTERISTICS	[185-197]
<u>AUTHOR(S)</u> : ENOCH, R.D.	SHAW, R.N.	TAYLOR, R.G.
<u>COMPANY</u> : BRITISH TELECOM		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
HUMAN BODY ESD MODEL	[ESD, DEVICE, TESTING METHODS]	
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
FAILURE CHARACTERIZATION	[SEMICONDUCTOR TECH.]	
FAILURE ANALYSIS RESULTS	[FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
REFERENCE DOCUMENT		
DIGITAL LSI	[MICROCIRCUIT, SEMICONDUCTOR DEVICE]	
TESTING TOOLS & TECHNIQUES	[SEMICONDUCTOR TECH.]	
18172-26	A SUMMARY OF MOST EFFECTIVE ELECTROSTATIC DISCHARGE PROTECTION CIRCUITS FOR MOS MEMORIES AND THEIR OBSERVED FAILURE MODES	[181-184]
<u>AUTHOR(S)</u> : DUVVURY, C.	ROUNTREE, R.N.	WHITE, L.S.
<u>COMPANY</u> : TEXAS INSTRUMENTS (TI)		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
CIRCUIT PROTECTION DEVICES	[NON-ELECTRONICS]	
DESIGN CONSIDERATIONS	[SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
DIELECTRIC BREAKDOWN	[ESD, DEVICE, FAILURE MODES]	
FAILURE MODES	[FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
FAILURE ANALYSIS RESULTS	[FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
GUIDE/PROCEDURE	[REFERENCE DOCUMENT]	
MICROCIRCUIT	[SEMICONDUCTOR DEVICE]	
18172-25	USING SCR'S AS TRANSIENT PROTECTION STRUCTURES IN INTEGRATED CIRCUITS	[177-180]
<u>AUTHOR(S)</u> : AVERY, L.R.		
<u>COMPANY</u> : RCA		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
DESIGN CONSIDERATIONS	[SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
TRANSIENT SUPPRESSORS	[ESD, DEVICE, PROTECTIVE DEVICES/INPUT PROTECTION]	
GUIDE/PROCEDURE	[REFERENCE DOCUMENT]	
SEMICONDUCTOR DEVICE		
MICROCIRCUIT	[SEMICONDUCTOR DEVICE]	

CHRONOLOGICAL LIST OF PAPERS 1982

<u>UMENT-SEQUENCE NO.</u>	<u>TITLE</u>	<u>PAGES</u>
14- 1	ESD SUSCEPTIBILITY TESTING OF ADVANCED SCHOTTKY TTL	{ 1-12 }
<u>HOR(S)</u> :	DENSON,W.K. DEY,K.A.	
<u>PANY</u> :	IIT RESEARCH INSTITUTE	

<u>EX TERM</u>	<u>CATEGORIES</u>
/ESD	[BIPOLAR, COMPONENT TYPE]
RGE DEVICE MODEL	[SEMICONDUCTOR TECH.]
STD AND HANDBOOK	[ESD, DEVICE, TESTING METHODS]
SUSCEPTIBILITY TESTING	[ESD, STANDARDS, HANDBOOKS, MANUALS]
ROCIRCUIT	[ESD, DEVICE, TESTING METHODS]
T TECHNIQUES FOR REL. ASSESSMENT	[SEMICONDUCTOR DEVICE]
P STRESS	[SEMICONDUCTOR TECH.]
TING TOOLS & TECHNIQUES	[TEST TECHNIQUES FOR REL. ASSESSMENT, SEMICONDUCTOR TECH.]
	[SEMICONDUCTOR TECH.]

CHRONOLOGICAL LIST OF PAPERS 1982

DOCUMENT-SEQUENCE NO.	TITLE	PAGES
214- 5 LATENT ESD FAILURES THOR(S) : MCATEER,O.J. MPANY : WESTINGHOUSE	TWIST,R.E. WALKER,R.C.	[41-48]
DEX TERM MPONENT LIABILITY CONDARY BREAKDOWN S/ESD TENT ESD FAILURE D STD AND HANDBOOK D SUSCEPTIBILITY TESTING ERSTRESS ILURE MODES PERENCE DOCUMENT FE ST EQUIPMENT	CATEGORIES [LEVEL OF ASSEMBLY] [DESIGN CONSIDERATIONS, SEMICONDUCTOR TECH.] [ELECTRICAL FAILURE PHENOMENA, SEMICONDUCTOR TECH.] [SEMICONDUCTOR TECH.] [ESD, DEVICE, FAILURE MODES] [ESD, STANDARDS, HANDBOOKS, MANUALS] [ESD, DEVICE, TESTING METHODS] [FAILURE CAUSE, FAILURE ANALYSIS, SEMICONDUCTOR TECH.] [FAILURE ANALYSIS, SEMICONDUCTOR TECH.] [TEST TECHNIQUES FOR REL. ASSESSMENT, SEMICONDUCTOR TECH.] [TESTING TOOLS & TECHNIQUES, SEMICONDUCTOR TECH.]	
214- 4 ELECTRICAL OVERSTRESS THRESHOLD TESTING THOR(S) : HAYS,R.A. MPANY : U.S. AIR FORCE		[34-40]
DEX TERM MPUTER AIDED DESIGN,(CAD) S/ESD S - ELECTRICAL OVERSTRESS D SUSCEPTIBILITY TESTING ERSTRESS STING TOOLS & TECHNIQUES	CATEGORIES [DESIGN TOOLS & TECHNIQUES, SEMICONDUCTOR TECH.] [SEMICONDUCTOR TECH.] [ESD, EOS/ESD PHYSICS] [ESD, DEVICE, TESTING METHODS] [FAILURE CAUSE, FAILURE ANALYSIS, SEMICONDUCTOR TECH.] [SEMICONDUCTOR TECH.]	
214- 3 LIMITATIONS IN MODELING ELECTRICAL OVERSTRESS FAILURE IN SEMICONDUCTOR DEVICES THOR(S) : HORGAN,E.L. ADAMS,O.E. ROWAN,W.H. MPANY : TRW		[19-33]
DEX TERM S/ESD D SUSCEPTIBILITY TESTING ERMAL SECONDARY BREAKDOWN NSCH BELL MODEL ERSTRESS DELS/THEORY/EQUATIONS MICONDUCTOR DEVICE ST TECHNIQUES FOR REL. ASSESSMENT	CATEGORIES [SEMICONDUCTOR TECH.] [ESD, DEVICE, TESTING METHODS] [ESD, DEVICE, FAILURE MODES] [ESD, DEVICE, TESTING METHODS] [FAILURE CAUSE, FAILURE ANALYSIS, SEMICONDUCTOR TECH.] [REL. MODELING TECHNIQUES, REL. MODELS/DATA/ANALYSIS] [SEMICONDUCTOR TECH.]	
214- 2 ELECTROSTATIC DISCHARGE (ESD) DAMAGE SUSCPETIBILITY OF THIN FILM RESISTORS AND CAPACITORS THOR(S) : CHASE,E.W. MPANY : BELL LABORATORIES		[13-18]
DEX TERM S/ESD ARGE DEVICE MODEL MAN BODY ESD MODEL D SUSCEPTIBILITY TESTING NSCH BELL MODEL ERSTRESS PACITOR SISTOR	CATEGORIES [SEMICONDUCTOR TECH.] [ESD, DEVICE, TESTING METHODS] [ESD, DEVICE, TESTING METHODS] [ESD, DEVICE, TESTING METHODS] [ESD, DEVICE, TESTING METHODS] [FAILURE CAUSE, FAILURE ANALYSIS, SEMICONDUCTOR TECH.] [PASSIVE DEVICE, COMPONENT TYPE] [PASSIVE DEVICE, COMPONENT TYPE]	

CHRONOLOGICAL LIST OF PAPERS 1982

<u>DOCUMENT-SEQUENCE NO.</u>	<u>TITLE</u>	<u>PAGES</u>
18214- 9	THE FORWARD-BIAS CHARACTERISTIC AS A PREDICTOR AND SCREEN OF REVERSE-BIAS SECOND BREAKDOWN	[71-75]
<u>AUTHOR(S)</u>	: WARD,A.L.	
<u>COMPANY</u>	: HARRY DIAMOND LAB (HDL)	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
REVERSE BREAKDOWN	[ELECTRICAL FAILURE PHENOMENA, SEMICONDUCTOR TECH.]	
SECONDARY BREAKDOWN	[ELECTRICAL FAILURE PHENOMENA, SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
MATHEMATICAL ANALYSIS		
CHARACTERIZATION	[TEST TECHNIQUES FOR REL. ASSESSMENT, SEMICONDUCTOR TECH.]	
18214- 8	AN IMPROVED EOS CONDUCTION MODEL OF SEMICONDUCT DEVICES	[62-70]
<u>AUTHOR(S)</u>	: VOLMERANGE,H.	
<u>COMPANY</u>	: TRW	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
EMP - ELECTROMAGNETIC PULSE	[ESD, EOS/ESD PHYSICS]	
EOS - ELECTRICAL OVERSTRESS	[ESD, EOS/ESD PHYSICS]	
WUNSCH BELL MODEL	[ESD, DEVICE, TESTING METHODS]	
MATHEMATICAL ANALYSIS		
REFERENCE DOCUMENT		
MODELS/THEORY/EQUATIONS	[REL. MODELING TECHNIQUES, REL. MODELS/DATA/ANALYSIS]	
SEMICONDUCTOR DEVICE		
MICROCIRCUIT	[SEMICONDUCTOR DEVICE]	
18214- 7	MODELING METALLIZATION BURNOUT OF INTEGRATED CIRCUITS	[56-61]
<u>AUTHOR(S)</u>	: PIERCE,D.G.	
<u>COMPANY</u>	: BOOZ, ALLEN & HAMILTON	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
METALLIZATION MELT	[ESD, DEVICE, FAILURE MODES]	
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
MATHEMATICAL ANALYSIS		
METALLURGICAL FAILURE PHENOMENA	[SEMICONDUCTOR TECH.]	
MODELS/THEORY/EQUATIONS	[REL. MODELING TECHNIQUES, REL. MODELS/DATA/ANALYSIS]	
MICROCIRCUIT	[SEMICONDUCTOR DEVICE]	
18214- 6	A SUVREY OF EOS/ESD DATA SOURCES	[49-55]
<u>AUTHOR(S)</u>	: DURGIN,D.L. PELZL,R.M. THOMPSON,W.H.	
<u>COMPANY</u>	: BOOZ, ALLEN & HAMILTON	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
EMI - ELECTROMAGNETIC INTERFACE	[ESD, EOS/ESD PHYSICS]	
EMP - ELECTROMAGNETIC PULSE	[ESD, EOS/ESD PHYSICS]	
ESD STD AND HANDBOOK	[ESD, STANDARDS, HANDBOOKS, MANUALS]	
FAILURE CHARACTERIZATION	[SEMICONDUCTOR TECH.]	
DATA COLLECTION SYS./TECHNIQUES	[REL. MODELS/DATA/ANALYSIS]	
TESTING TOOLS & TECHNIQUES	[SEMICONDUCTOR TECH.]	

CHRONOLOGICAL LIST OF PAPERS 1982

DOCUMENT-SEQUENCE NO.	TITLE	PAGES
-----------------------	-------	-------

18214-13	TEST METHODS FOR STATIC CONTROL PRODUCTS	[94-109]
AUTHOR(S)	: HUNTSMAN, J.R. YENNI, D.M.	
COMPANY	: 3M	

INDEX TERM	CATEGORIES
TRADE-OFFS	[DESIGN CONSIDERATIONS, SEMICONDUCTOR TECH.]
DESIGN FOR TESTABILITY	[DESIGN CONSIDERATIONS, SEMICONDUCTOR TECH.]
EOS/ESD	[SEMICONDUCTOR TECH.]
AIR IONIZER	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]
CONDUCTIVE FOAM	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]
DIP TUBE	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]
DECAY TIME	[ESD, MATERIALS AND EQUIPMENT, TESTING]
ESD PROTECTIVE MATERIAL	[ESD, MATERIALS AND EQUIPMENT, TESTING]
RELATIVE HUMIDITY	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]
ESD STD AND HANDBOOK	[ESD, STANDARDS, HANDBOOKS, MANUALS]
SURFACE RESISTIVITY	[ESD, MATERIALS AND EQUIPMENT, TESTING]
TRIOBOELECTRIC CHARGING	[ESD, EOS/ESD PHYSICS]
WRIST STRAP	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]
QUALITY ASSURANCE	[SYSTEMS]
RELIABILITY	[SYSTEMS]
TEST TECHNIQUES FOR REL. ASSESSMENT	[SEMICONDUCTOR TECH.]

18214-12	SECOND BREAKDOWN IN SWITCHING TRANSISTORS	[91-93]
AUTHOR(S)	: SKELTON, D.J. PORTNOY, W.M.	
COMPANY	: TEXAS TECH UNIVERSITY	

INDEX TERM	CATEGORIES
SECONDARY BREAKDOWN	[ELECTRICAL FAILURE PHENOMENA, SEMICONDUCTOR TECH.]
EOS/ESD	[SEMICONDUCTOR TECH.]
EMP - ELECTROMAGNETIC PULSE	[ESD, EOS/ESD PHYSICS]
TRANSISTOR	[DISCRETE SEMICONDUCTOR, SEMICONDUCTOR DEVICE]
THERMAL	[TEST STRESS]

18214-11	A PROBABILISTIC ESTIMATOR FOR BOUNDING TRANSISTOR EMITTER-BASE JUNCTION TRANSIENT-INDUCED FAILURES	[82-90]
AUTHOR(S)	: PIERCE, D.G. MASON, R.H.	
COMPANY	: BOOZ, ALLEN & HAMILTON	

INDEX TERM	CATEGORIES
EOS/ESD	[SEMICONDUCTOR TECH.]
EOS - ELECTRICAL OVERSTRESS	[ESD, EOS/ESD PHYSICS]
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]
OVERSTRESS	[FAILURE CAUSE, FAILURE ANALYSIS, SEMICONDUCTOR TECH.]
FABRICATION PROCESSES & TECHNIQUES	[SEMICONDUCTOR TECH.]
TRANSISTOR	[DISCRETE SEMICONDUCTOR, SEMICONDUCTOR DEVICE]

18214-10	MODELING OF CURRENT AND THERMAL MODE SECOND BREAKDOWN PHENOMENA	[76-81]
AUTHOR(S)	: YEE, J.H. ORVIS, W.J. MARTIN, L.C.	
COMPANY	: LAWRENCE LIVERMORE NATIONAL LABORATORY	

INDEX TERM	CATEGORIES
SECONDARY BREAKDOWN	[ELECTRICAL FAILURE PHENOMENA, SEMICONDUCTOR TECH.]
ELECTRICAL	[TEST STRESS]
EOS/ESD	[SEMICONDUCTOR TECH.]
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]
THERMAL SECONDARY BREAKDOWN	[ESD, DEVICE, FAILURE MODES]
MATHEMATICAL ANALYSIS	
MODELS/THEORY/EQUATIONS	[REL. MODELING TECHNIQUES, REL. MODELS/DATA/ANALYSIS]
THERMAL	[TEST STRESS]

CHRONOLOGICAL LIST OF PAPERS 1982

DOCUMENT-SEQUENCE NO.	TITLE	PAGES
18214-17	CHARACTERIZATION OF ESD SAFE REQUIREMENTS FOR FLOOR SURFACES	[124-130]
AUTHOR(S) : BERBECO,G.R. COMPANY : CHARLESWATERS PRODUCT, INC.		
INDEX TERM	CATEGORIES	
DESIGN CONSIDERATIONS	[SEMICONDUCTOR TECH.]	
DESIGN FOR TESTABILITY	[DESIGN CONSIDERATIONS, SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
DECAY TIME	[ESD, MATERIALS AND EQUIPMENT, TESTING]	
FLOOR SURFACE	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
TRIPOBOELECTRIC CHARGING	[ESD, EOS/ESD PHYSICS]	
TEST TECHNIQUES FOR REL. ASSESSMENT	[SEMICONDUCTOR TECH.]	
CHARACTERIZATION	[TEST TECHNIQUES FOR REL. ASSESSMENT, SEMICONDUCTOR TECH.]	
TESTING TOOLS & TECHNIQUES	[SEMICONDUCTOR TECH.]	
18214-16	DRASTIC LOSSES OF CONDUCTIVITY IN ANTISTATIC PLASTICS	[120-123]
AUTHOR(S) : HEAD,G.O. COMPANY : LEAR SIEGLER, INC.		
INDEX TERM	CATEGORIES	
MATERIALS	[DESIGN CONSIDERATIONS, SEMICONDUCTOR TECH.]	
DESIGN FOR TESTABILITY	[DESIGN CONSIDERATIONS, SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
CONDUCTIVE ESD PROTECTIVE MATERIAL	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
DECAY TIME	[ESD, MATERIALS AND EQUIPMENT, TESTING]	
PROTECTIVE BAGS	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
SURFACE RESISTIVITY	[ESD, MATERIALS AND EQUIPMENT, TESTING]	
TRIPOBOELECTRIC CHARGING	[ESD, EOS/ESD PHYSICS]	
EVALUATION TEST	[TEST TECHNIQUES FOR REL. ASSESSMENT, SEMICONDUCTOR TECH.]	
MISC. FAILURE PHENOMENA	[SEMICONDUCTOR TECH.]	
18214-15	ELECTROACTIVE POLYMERS AS ALTERNATE ESD PROTECTIVE MATERIALS	[115-119]
AUTHOR(S) : BERNETT,M.K. RAVNER,H. WEBER,D.C. COMPANY : NAVAL RESEARCH LABORATORY (NRL)		
INDEX TERM	CATEGORIES	
MATERIALS	[DESIGN CONSIDERATIONS, SEMICONDUCTOR TECH.]	
DESIGN FOR TESTABILITY	[DESIGN CONSIDERATIONS, SEMICONDUCTOR TECH.]	
TOLERANCES	[DESIGN CONSIDERATIONS, SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
ESD PROTECTIVE MATERIAL	[ESD, MATERIALS AND EQUIPMENT, TESTING]	
SURFACE RESISTIVITY	[ESD, MATERIALS AND EQUIPMENT, TESTING]	
PACKAGE	[SEMICONDUCTOR TECH.]	
18214-14	METALLOPLASTICS	[110-114]
AUTHOR(S) : DAVENPORT,D.E. COMPANY : TRACOR MBA		
INDEX TERM	CATEGORIES	
PROCESS DESIGN	[DESIGN CONSIDERATIONS, SEMICONDUCTOR TECH.]	
DESIGN FOR TESTABILITY	[DESIGN CONSIDERATIONS, SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
ELECTROSTATIC SHIELD	[ESD, EOS/ESD PHYSICS]	
EMI - ELECTROMAGNETIC INTERFACE	[ESD, EOS/ESD PHYSICS]	
FABRICATION PROCESSES & TECHNIQUES	[SEMICONDUCTOR TECH.]	

CHRONOLOGICAL LIST OF PAPERS 1982

DOCUMENT-SEQUENCE NO.	TITLE	PAGES
18214-20	ESD IN I.C. ASSEMBLY (A BASE LINE SOLUTION)	[142-144]
AUTHOR(S) : EUKER, R.		
COMPANY : HEWLETT PACKARD		
INDEX TERM	CATEGORIES	
CIRCUIT PROTECTION DEVICES	[NON-ELECTRONICS]	
DEVELOPMENT PROGRAM	[SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
GROUNDING METHODS	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]	
RELATIVE HUMIDITY	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]	
STATIC CONTROL	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]	
PROCESS CONTROL/SPECIFICATION	[FABRICATION PROCESSES & TECHNIQUES, SEMICONDUCTOR TECH.]	
FUTURE TRENDS	[SEMICONDUCTOR TECH.]	
SEMICONDUCTOR DEVICE		
18214-19	BASIC SPECIFICATION FOR ESD PROTECTION IN INDUSTRY	[136-141]
AUTHOR(S) : PHILLIPS, L.P.		
COMPANY : GARRETT MANUFACTURING, LTD.		
INDEX TERM	CATEGORIES	
AVAILABILITY	[SYSTEMS]	
COST	[SYSTEMS]	
DEVELOPMENT PROGRAM	[SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
ESD PROTECTIVE MATERIAL	[ESD, MATERIALS AND EQUIPMENT, TESTING]	
EOS - ELECTRICAL OVERSTRESS	[ESD, EOS/ESD PHYSICS]	
PROTECTED ESD AREA	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
RELATIVE HUMIDITY	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]	
PROCESS CONTROL/SPECIFICATION	[FABRICATION PROCESSES & TECHNIQUES, SEMICONDUCTOR TECH.]	
SPECIFICATION/STANDARD	[REFERENCE DOCUMENT]	
18214-18	ESD AND CONTAMINATION FROM CLEAN ROOM GARMENTS - PROBLEMS AND SOLUTIONS	[131-135]
AUTHOR(S) : BURNETT, E.S.		
COMPANY : ARATEX		
INDEX TERM	CATEGORIES	
DESIGN CONSIDERATIONS	[SEMICONDUCTOR TECH.]	
APPLICATION FACTORS	[DESIGN CONSIDERATIONS, SEMICONDUCTOR TECH.]	
MATERIALS	[DESIGN CONSIDERATIONS, SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
ANTISTATIC GARMENTS	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
CLEAN ROOM	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
RELATIVE HUMIDITY	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]	
STATIC CONTROL	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]	
SURFACE RESISTIVITY	[ESD, MATERIALS AND EQUIPMENT, TESTING]	
QUALITY ASSURANCE	[SYSTEMS]	
MISC. FAILURE PHENOMENA	[SEMICONDUCTOR TECH.]	
CONTAMINATION	[MISC. FAILURE PHENOMENA, SEMICONDUCTOR TECH.]	

CHRONOLOGICAL LIST OF PAPERS 1982

DOCUMENT-SEQUENCE NO.	TITLE	PAGES
18214-24	CIRCUIT DESIGN FOR EOS/ESD PROTECTION	[169-174]
AUTHOR(S) :	DOMINGOS,H. RAGHAVAN,R.	
COMPANY :	CLARKSON COLLEGE	
INDEX TERM	CATEGORIES	
CIRCUIT PROTECTION DEVICES	[NON-ELECTRONICS]	
DESIGN FOR TESTABILITY	[DESIGN CONSIDERATIONS, SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
HUMAN BODY ESD MODEL	[ESD, DEVICE, TESTING METHODS]	
INPUT PROTECTION	[ESD, DEVICE, PROTECTIVE DEVICES/INPUT PROTECTION]	
OVERSTRESS	[FAILURE CAUSE, FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
FUTURE TRENDS	[SEMICONDUCTOR TECH.]	
REFERENCE DOCUMENT		
18214-23	UNIFORM ESD PROTECTION IN A LARGE MULTI-DEPARTMENT ASSEMBLY PLANT	[165-168]
AUTHOR(S) :	KIRK,W.J.	
COMPANY :	BENDIX	
INDEX TERM	CATEGORIES	
COST	[SYSTEMS]	
DEVELOPMENT PROGRAM	[SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
ESD CONTROL PROGRAM	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]	
STATIC CONTROL	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]	
REFERENCE DOCUMENT		
18214-22	ESD MINIMIZATION TECHNIQUE FOR MOS MANUFACTURING FINAL TEST AREA	[157-164]
AUTHOR(S) :	YOUN,S.Y. HARTDEGEN,N. SHARP,M.	
COMPANY :	MOSTEK	
INDEX TERM	CATEGORIES	
DESIGN FOR TESTABILITY	[DESIGN CONSIDERATIONS, SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
PROTECTIVE WORK BENCH SURFACE	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
RELATIVE HUMIDITY	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]	
STATIC CONTROL	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]	
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
TRIOBOELECTRIC CHARGING	[ESD, EOS/ESD PHYSICS]	
OVERSTRESS	[FAILURE CAUSE, FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
MICROCIRCUIT	[SEMICONDUCTOR DEVICE]	
TEST TECHNIQUES FOR REL. ASSESSMENT	[SEMICONDUCTOR TECH.]	
CONTAMINATION	[MISC. FAILURE PHENOMENA, SEMICONDUCTOR TECH.]	
PROCESS/WORKMANSHIP INDUCED	[MISC. FAILURE PHENOMENA, SEMICONDUCTOR TECH.]	
18214-21	AN EFFECTIVE ELECTROSTATIC DISCHARGE PROTECTION PROGRAM	[145-156]
AUTHOR(S) :	STRAND,C.J. TWEET,A. WEIGHT,M.E.	
COMPANY :	SPERRY UNIVAC	
INDEX TERM	CATEGORIES	
DEVELOPMENT PROGRAM	[SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
PROTECTED ESD AREA	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
STATIC CONTROL	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]	
FLOOR SURFACE	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
WRIST STRAP	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
OVERSTRESS	[FAILURE CAUSE, FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
FUTURE TRENDS	[SEMICONDUCTOR TECH.]	
HUMAN FACTORS	[SYSTEMS]	
QUALITY ASSURANCE	[SYSTEMS]	
SEMICONDUCTOR DEVICE		

CHRONOLOGICAL LIST OF PAPERS 1982

<u>DOCUMENT-SEQUENCE NO.</u>	<u>TITLE</u>	<u>PAGES</u>
18214-28	ELECTRICAL GROUNDING IN LARGE INSTRUMENTATION SYSTEMS	[190-202]
<u>AUTHOR(S)</u> :	GRUCHALLA,M.	
<u>COMPANY</u> :	EG&G WASC, INC.	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
CIRCUIT BREAKER	[CIRCUIT PROTECTION DEVICES, NON-ELECTRONICS]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
GROUNDING METHODS	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]	
REFERENCE DOCUMENT		
SYSTEM	[LEVEL OF ASSEMBLY]	
TEST TECHNIQUES FOR REL. ASSESSMENT	[SEMICONDUCTOR TECH.]	
18214-27	ELECTROSTATIC DISCHARGE IMMUNITY IN COMPUTER SYSTEMS	[185-189]
<u>AUTHOR(S)</u> :	SHEEHAN,D.K. BURROUGHS,J.E.	
<u>COMPANY</u> :	HONEYWELL	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
DESIGN FOR TESTABILITY	[DESIGN CONSIDERATIONS, SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
ESD CONTROL PROGRAM	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]	
STATIC CONTROL	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]	
FUTURE TRENDS	[SEMICONDUCTOR TECH.]	
GUIDE/PROCEDURE	[REFERENCE DOCUMENT]	
COMPUTERIZED TECH	[REL. MODELING TECHNIQUES, REL. MODELS/DATA/ANALYSIS]	
COMPUTERIZED	[DATA COLLECTION SYS./TECHNIQUES, REL. MODELS/DATA/ANALYSIS]	
18214-26	ELECTROSTATIC DISCHARGE AT THE PRODUCT LEVEL	[179-184]
<u>AUTHOR(S)</u> :	ELLIS,E.B.	
<u>COMPANY</u> :	HEWLETT PACKARD	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
DESIGN FOR TESTABILITY	[DESIGN CONSIDERATIONS, SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
ESD CONTROL PROGRAM	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]	
OVERSTRESS	[FAILURE CAUSE, FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
PROCUREMENT CONTROLS	[USER OF REL. PREDICTION MODELS]	
SYSTEM	[LEVEL OF ASSEMBLY]	
TEST PROGRAM DEVELOPMENT	[TESTING TOOLS & TECHNIQUES, SEMICONDUCTOR TECH.]	
18214-25	IN-CIRCUIT ANALYSIS OF ESD DAMAGED DEVICES	[175-178]
<u>AUTHOR(S)</u> :	SAUERS,J.P.	
<u>COMPANY</u> :	MAGNAVOX	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
DESIGN FOR TESTABILITY	[DESIGN CONSIDERATIONS, SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
ESD CONTROL PROGRAM	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]	
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
OVERSTRESS	[FAILURE CAUSE, FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
PROCESS CONTROL/SPECIFICATION	[FABRICATION PROCESSES & TECHNIQUES, SEMICONDUCTOR TECH.]	
FUTURE TRENDS	[SEMICONDUCTOR TECH.]	
MICROCIRCUIT	[SEMICONDUCTOR DEVICE]	

CHRONOLOGICAL LIST OF PAPERS 1983

DOCUMENT-SEQUENCE NO.	TITLE	PAGES
18172- 4	ANALYSIS OF ELECTROSTATIC CHARGE PROPENSITY OF FLOOR FINISHES	[17-20]
AUTHOR(S) :	LINGOUSKY, J.E. HOLT, V.E.	
COMPANY :	BELL LABORATORIES	
INDEX TERM	CATEGORIES	
MATERIALS	[DESIGN CONSIDERATIONS, SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
RELATIVE HUMIDITY	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]	
FLOOR SURFACE	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
GUIDE/PROCEDURE	[REFERENCE DOCUMENT]	
TEST PROGRAM DEVELOPMENT	[TESTING TOOLS & TECHNIQUES, SEMICONDUCTOR TECH.]	
18172- 3	THE PRODUCTION OPERATOR: WEAK LINK OR WARRIOR IN THE ESD BATTLE?	[12-16]
AUTHOR(S) :	HANSEL, G.E.	
COMPANY :	MOTOROLA	
INDEX TERM	CATEGORIES	
DEVELOPMENT PROGRAM	[SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
ESD CONTROL PROGRAM	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]	
HUMAN FACTORS	[SYSTEMS]	
REFERENCE DOCUMENT		
TEST PROGRAM DEVELOPMENT	[TESTING TOOLS & TECHNIQUES, SEMICONDUCTOR TECH.]	
18172- 2	ESD CONTROL IMPLEMENTATION AND COST AVOIDANCE ANALYSIS	[6-11]
AUTHOR(S) :	DOWNING, M.H.	
COMPANY :	LOCKHEED	
INDEX TERM	CATEGORIES	
COST	[SYSTEMS]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
ESD PROTECTIVE MATERIAL	[ESD, MATERIALS AND EQUIPMENT, TESTING]	
ESD CONTROL PROGRAM	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]	
PROTECTED ESD AREA	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
STATIC CONTROL	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]	
REFERENCE DOCUMENT		
GUIDE/PROCEDURE	[REFERENCE DOCUMENT]	
TEST EQUIPMENT	[TESTING TOOLS & TECHNIQUES, SEMICONDUCTOR TECH.]	
TEST PROGRAM DEVELOPMENT	[TESTING TOOLS & TECHNIQUES, SEMICONDUCTOR TECH.]	
18172- 1	ESD-HOW OFTEN DOES IT HAPPEN?	[1-5]
AUTHOR(S) :	DANGELMAYER, G.T.	
COMPANY :	WESTERN ELECTRIC COMPANY, INC.	
INDEX TERM	CATEGORIES	
COMPONENT	[LEVEL OF ASSEMBLY]	
DESIGN CONSIDERATIONS	[SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
HUMAN BODY ESD MODEL	[ESD, DEVICE, TESTING METHODS]	
ESD CONTROL PROGRAM	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]	
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
REFERENCE DOCUMENT		
TEST TECHNIQUES	[TESTING TOOLS & TECHNIQUES, SEMICONDUCTOR TECH.]	

CHRONOLOGICAL LIST OF PAPERS 1983

<u>DOCUMENT-SEQUENCE NO.</u>	<u>TITLE</u>	<u>PAGES</u>
18172- 8	A PROGRAMMABLE EQUIPMENT FOR ELECTROSTATIC DISCHARGE TESTING TO HUMAN BODY MODELS	[48-55]
<u>AUTHOR(S)</u> :	SHAW,R.N. ENOCH,R.D.	
<u>COMPANY</u> :	BRITISH TELECOM	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
GEOMETRIES/LAYOUT	[DESIGN CONSIDERATIONS, SEMICONDUCTOR TECH.]	
COMPUTERIZED ANALYSIS	[DESIGN TOOLS & TECHNIQUES, SEMICONDUCTOR TECH.]	
COMPUTER AIDED DESIGN,(CAD)	[DESIGN TOOLS & TECHNIQUES, SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
HUMAN BODY ESD MODEL	[ESD, DEVICE, TESTING METHODS]	
SPECIFICATION/STANDARD	[REFERENCE DOCUMENT]	
RELIABILITY MODELING TECHNIQUES	[REL. MODELS/DATA/ANALYSIS]	
COMPUTERIZED TECH	[REL. MODELING TECHNIQUES, REL. MODELS/DATA/ANALYSIS]	
TEST TECHNIQUES FOR REL. ASSESSMENT	[SEMICONDUCTOR TECH.]	
TEST SPECIFICATION	[TESTING TOOLS & TECHNIQUES, SEMICONDUCTOR TECH.]	
18172- 7	CONSTRUCTION AND APPLICATION OF A TESTER FOR MEASURING EOS/ESD THRESHOLDS TO 15KV	[37-47]
<u>AUTHOR(S)</u> :	LEE,T.W.	
<u>COMPANY</u> :	MOTOROLA	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
DESIGN FOR TESTABILITY	[DESIGN CONSIDERATIONS, SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
ELECTROSTATIC CHARGE DETECTOR	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
EOS - ELECTRICAL OVERSTRESS	[ESD, EOS/ESD PHYSICS]	
REFERENCE DOCUMENT		
TEST TECHNIQUES FOR REL. ASSESSMENT	[SEMICONDUCTOR TECH.]	
TEST TECHNIQUES	[TESTING TOOLS & TECHNIQUES, SEMICONDUCTOR TECH.]	
18172- 6	ESD BY STATIC INDUCTION	[29-36]
<u>AUTHOR(S)</u> :	CHEMELLI,R.G. UNGER,B.A. BOSSARD,P.R.	
<u>COMPANY</u> :	BELL LABORATORIES	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
CHARGE DEVICE MODEL	[ESD, DEVICE, TESTING METHODS]	
INDUCTIVE CHARGING	[ESD, EOS/ESD PHYSICS]	
ESD PROTECTIVE MATERIAL	[ESD, MATERIALS AND EQUIPMENT, TESTING]	
REFERENCE DOCUMENT		
THEORY OF OPERATION	[SEMICONDUCTOR TECH.]	
18172- 5	AIR FORCE MAINTENANCE PROGRAM FOR ELECTRICAL OVERSTRESS/ELECTROSTATIC DISCHARGE (EOS/ESD) CONTROL	[21-28]
<u>AUTHOR(S)</u> :	THOMPSON,W.H. NYBO,C.L. KELAIDIS,M.J.	
<u>COMPANY</u> :	U.S. AIR FORCE	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
DEVELOPMENT PROGRAM	[SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
ESD CONTROL PROGRAM	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]	
PROTECTED ESD AREA	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
ESD STD AND HANDBOOK	[ESD, STANDARDS, HANDBOOKS, MANUALS]	
OVERSTRESS	[FAILURE CAUSE, FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
HUMAN FACTORS	[SYSTEMS]	
QUALITY ASSURANCE	[SYSTEMS]	
GUIDE/PROCEDURE	[REFERENCE DOCUMENT]	
SPECIFICATION/STANDARD	[REFERENCE DOCUMENT]	
MAINTAINABILITY TECHNIQUES	[MAINTAINABILITY, SYSTEMS]	

CHRONOLOGICAL LIST OF PAPERS 1983

<u>DOCUMENT-SEQUENCE NO.</u>	<u>TITLE</u>	<u>PAGES</u>
18172-12	MEASURING EFFECTIVENESS OF AIR IONIZERS	[76-86]
<u>AUTHOR(S)</u> : ANTONEVICH, J.N.	BLITSHTYEN, M.	
<u>COMPANY</u> : SIMCO COMPANY		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
CONTROL	[EQUIPMENT TYPE/FUNCTION]	
APPLICATION FACTORS	[DESIGN CONSIDERATIONS, SEMICONDUCTOR TECH.]	
TOLERANCES	[DESIGN CONSIDERATIONS, SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
AIR IONIZER	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
DECAY TIME	[ESD, MATERIALS AND EQUIPMENT, TESTING]	
EOS - ELECTRICAL OVERSTRESS	[ESD, EOS/ESD PHYSICS]	
RELATIVE HUMIDITY	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]	
REFERENCE DOCUMENT		
TEST TECHNIQUES FOR REL. ASSESSMENT	[SEMICONDUCTOR TECH.]	
THEORY OF OPERATION	[SEMICONDUCTOR TECH.]	
18172-11	THE ROOM AIR IONIZATION SYSTEM, A BETTER ALTERNATIVE THAN 40% RELATIVE HUMIDITY	[67-75]
<u>AUTHOR(S)</u> : MYKKANEN, C.F.	BLINDE, D.R.	
<u>COMPANY</u> : HONEYWELL		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
CONTROL	[EQUIPMENT TYPE/FUNCTION]	
APPLICATION FACTORS	[DESIGN CONSIDERATIONS, SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
AIR IONIZER	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
DECAY TIME	[ESD, MATERIALS AND EQUIPMENT, TESTING]	
EMI - ELECTROMAGNETIC INTERFACE	[ESD, EOS/ESD PHYSICS]	
RELATIVE HUMIDITY	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]	
REFERENCE DOCUMENT		
TEST TECHNIQUES FOR REL. ASSESSMENT	[SEMICONDUCTOR TECH.]	
18172-10	STATIC SURVEY METERS	[63-66]
<u>AUTHOR(S)</u> : LONBORG, J.O.		
<u>COMPANY</u> : JET PROPULSION LABORATORY (JPL)		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
TRADE-OFFS	[DESIGN CONSIDERATIONS, SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
ELECTROSTATIC CHARGE DETECTOR	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
REFERENCE DOCUMENT		
TEST EQUIPMENT	[TESTING TOOLS & TECHNIQUES, SEMICONDUCTOR TECH.]	
18172-9	POWER FAILURE MODELING OF INTEGRATED CIRCUITS	[56-62]
<u>AUTHOR(S)</u> : ENLOW, E.W.	BUDEN, B.N. GIERI, V.A.	
<u>COMPANY</u> : BDM CORPORATION		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
ELECTRICAL	[TEST STRESS]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
EMP - ELECTROMAGNETIC PULSE	[ESD, EOS/ESD PHYSICS]	
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
GUIDE/PROCEDURE	[REFERENCE DOCUMENT]	
COMPUTERIZED TECH	[REL. MODELING TECHNIQUES, REL. MODELS/DATA/ANALYSIS]	
MICROCIRCUIT	[SEMICONDUCTOR DEVICE]	
TEST PROGRAM DEVELOPMENT	[TESTING TOOLS & TECHNIQUES, SEMICONDUCTOR TECH.]	

CHRONOLOGICAL LIST OF PAPERS 1983

<u>DOCUMENT-SEQUENCE NO.</u>	<u>TITLE</u>	<u>PAGES</u>
18172-16	MODELING AND TESTING FOR SECOND BREAKDOWN PHENOMENA	[108-117]
<u>AUTHOR(S)</u> :	ORVIS,W.J. MARTIN,L.C. YEE,J.H.	
<u>COMPANY</u> :	LAWRENCE LIVERMORE NATIONAL LABORATORY	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
COMPUTER AIDED DESIGN,(CAD)	[DESIGN TOOLS & TECHNIQUES, SEMICONDUCTOR TECH.]	
SECONDARY BREAKDOWN	[ELECTRICAL FAILURE PHENOMENA, SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
EMP - ELECTROMAGNETIC PULSE	[ESD, EOS/ESD PHYSICS]	
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
FAILURE CHARACTERIZATION	[SEMICONDUCTOR TECH.]	
TRANSISTOR	[DISCRETE SEMICONDUCTOR, SEMICONDUCTOR DEVICE]	
18172-15	CALCULATIONS OF SECOND BREAKDOWN IN SILICON DIODES AT MICROWAVE FREQUENCIES	[102-107]
<u>AUTHOR(S)</u> :	WARD,A.L.	
<u>COMPANY</u> :	HARRY DIAMOND LAB (HDL)	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
COMPONENT	[LEVEL OF ASSEMBLY]	
SECONDARY BREAKDOWN	[ELECTRICAL FAILURE PHENOMENA, SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
COMPUTERIZED	[DATA COLLECTION SYS./TECHNIQUES, REL. MODELS/DATA/ANALYSIS]	
DIODE	[DISCRETE SEMICONDUCTOR, SEMICONDUCTOR DEVICE]	
MICROWAVE	[DISCRETE SEMICONDUCTOR, SEMICONDUCTOR DEVICE]	
18172-14	COPLANAR TRIBOELECTRIFICATION OF SELECTED MATERIALS	[95-101]
<u>AUTHOR(S)</u> :	FELT,F.S.	
<u>COMPANY</u> :	MARTIN MARIETTA	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
ESD PROTECTIVE MATERIAL	[ESD, MATERIALS AND EQUIPMENT, TESTING]	
RELATIVE HUMIDITY	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]	
TRIBOELECTRIC CHARGING	[ESD, EOS/ESD PHYSICS]	
REFERENCE DOCUMENT		
THEORY OF OPERATION	[SEMICONDUCTOR TECH.]	
18172-13	PERMANENCE OF THE ANTISTATIC PROPERTY OF COMMERCIAL ANTISTATIC BAGS AND TOTE BOXES	[87-94]
<u>AUTHOR(S)</u> :	KOLYER,J.M. ANDERSON,W.E.	
<u>COMPANY</u> :	ROCKWELL	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
CIRCUIT PROTECTION DEVICES	[NON-ELECTRONICS]	
CONTROL	[EQUIPMENT TYPE/FUNCTION]	
MATERIALS	[DESIGN CONSIDERATIONS, SEMICONDUCTOR TECH.]	
TRADE-OFFS	[DESIGN CONSIDERATIONS, SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
ANTISTATIC IMPREGNATED PLASTIC	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
ESD PROTECTIVE MATERIAL	[ESD, MATERIALS AND EQUIPMENT, TESTING]	
PROTECTIVE BAGS	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
ESD STD AND HANDBOOK	[ESD, STANDARDS, HANDBOOKS, MANUALS]	
SURFACE RESISTIVITY	[ESD, MATERIALS AND EQUIPMENT, TESTING]	
TRIBOELECTRIC CHARGING	[ESD, EOS/ESD PHYSICS]	
FABRICATION PROCESSES & TECHNIQUES	[SEMICONDUCTOR TECH.]	
PKG BODY MATERIAL	[PACKAGE, SEMICONDUCTOR TECH.]	
GUIDE/PROCEDURE	[REFERENCE DOCUMENT]	
TEST TECHNIQUES FOR REL. ASSESSMENT	[SEMICONDUCTOR TECH.]	
TEST EQUIPMENT	[TESTING TOOLS & TECHNIQUES, SEMICONDUCTOR TECH.]	
TEST PROGRAM DEVELOPMENT	[TESTING TOOLS & TECHNIQUES, SEMICONDUCTOR TECH.]	
TEST TECHNIQUES	[TESTING TOOLS & TECHNIQUES, SEMICONDUCTOR TECH.]	

CHRONOLOGICAL LIST OF PAPERS 1983

<u>DOCUMENT-SEQUENCE NO.</u>	<u>TITLE</u>	<u>PAGES</u>
18172-20	ESD EVALUATION OF RADIATION-HARDENED, HIGH RELIABILITY CMOS AND MNOS ICS	[134-146]
<u>AUTHOR(S)</u> :	SODEN, J.M. STEWART, H.D. PASTOREK, R.A.	
<u>COMPANY</u> :	SANDIA LABORATORIES	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
HUMAN BODY ESD MODEL	[ESD, DEVICE, TESTING METHODS]	
ESD STD AND HANDBOOK	[ESD, STANDARDS, HANDBOOKS, MANUALS]	
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
FAILURE ANALYSIS RESULTS	[FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
REFERENCE DOCUMENT		
MICROCIRCUIT	[SEMICONDUCTOR DEVICE]	
EVALUATION TEST	[TEST TECHNIQUES FOR REL. ASSESSMENT, SEMICONDUCTOR TECH.]	
TEST TECHNIQUES	[TESTING TOOLS & TECHNIQUES, SEMICONDUCTOR TECH.]	
18172-19	ESD SENSITIVITY OF COMPLEX ICS	[128-133]
<u>AUTHOR(S)</u> :	WILSON, D.	
<u>COMPANY</u> :	MARTIN MARIETTA	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
CHARGE DEVICE MODEL	[ESD, DEVICE, TESTING METHODS]	
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
FAILURE ANALYSIS RESULTS	[FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
MICROCIRCUIT	[SEMICONDUCTOR DEVICE]	
TEST SPECIFICATION	[TESTING TOOLS & TECHNIQUES, SEMICONDUCTOR TECH.]	
18172-18	SEMICONDUCTOR JUNCTION NON-LINEAR FAILURE POWER THRESHOLDS: WUNSCH-BELL	[122-127]
	REVISITED	
<u>AUTHOR(S)</u> :	ASH, M.S.	
<u>COMPANY</u> :	TRW	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
WUNSCH BELL MODEL	[ESD, DEVICE, TESTING METHODS]	
MATHEMATICAL ANALYSIS		
SEMICONDUCTOR DEVICE		
STATISTICAL ANALYSIS		
18172-17	TEMPERATURE AT SECOND BREAKDOWN AT A WELL-DEFINED SITE	[118-121]
<u>AUTHOR(S)</u> :	STOTTS, L.J. PORTNOY, W.M.	
<u>COMPANY</u> :	TEXAS TECH UNIVERSITY	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
SECONDARY BREAKDOWN	[ELECTRICAL FAILURE PHENOMENA, SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
THERMAL SECONDARY BREAKDOWN	[ESD, DEVICE, FAILURE MODES]	
MATHEMATICAL ANALYSIS		
THERMAL STRESS/STRAIN	[MECHANICAL & PHYSICAL FAILURE PHENOMENA, SEMICONDUCTOR TECH.]	
REFERENCE DOCUMENT		
DIODE	[DISCRETE SEMICONDUCTOR, SEMICONDUCTOR DEVICE]	
THERMAL	[TEST STRESS]	

CHRONOLOGICAL LIST OF PAPERS 1983

<u>DOCUMENT-SEQUENCE NO.</u>	<u>TITLE</u>	<u>PAGES</u>
18172-24	METAL OXIDE VARISTORS FOR TRANSIENT PROTECTION OF 3 TO 5-VOLT INTEGRATED CIRCUITS	[168-176]
<u>AUTHOR(S)</u> :	MAY, J.E.	KORN, S.R.
<u>COMPANY</u> :	GENERAL ELECTRIC	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
CIRCUIT PROTECTION DEVICES	[NON-ELECTRONICS]	
APPLICATION FACTORS	[DESIGN CONSIDERATIONS, SEMICONDUCTOR TECH.]	
ELECTRICAL	[TEST STRESS]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
TRANSIENT SUPPRESSORS	[ESD, DEVICE, PROTECTIVE DEVICES/INPUT PROTECTION]	
GUIDE/PROCEDURE	[REFERENCE DOCUMENT]	
MICROCIRCUIT	[SEMICONDUCTOR DEVICE]	
18172-23	INVISIBLE EOS/ESD DAMAGE: HOW TO FIND IT	[158-167]
<u>AUTHOR(S)</u> :	BRENNAN, T.F.	
<u>COMPANY</u> :	SPERRY CORPORATION	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
EOS - ELECTRICAL OVERSTRESS	[ESD, EOS/ESD PHYSICS]	
OVERSTRESS	[FAILURE CAUSE, FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
FAILURE INDICATOR	[FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
FAILURE ANALYSIS RESULTS	[FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
REFERENCE DOCUMENT		
18172-22	EOS OR ESD: CAN FAILURE ANALYSIS TELL THE DIFFERENCE?	[154-157]
<u>AUTHOR(S)</u> :	NOEL, P.H.	DREIBELBIS, D.H.
<u>COMPANY</u> :	IBM CORPORATION	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
EOS - ELECTRICAL OVERSTRESS	[ESD, EOS/ESD PHYSICS]	
OVERSTRESS	[FAILURE CAUSE, FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
FAILURE INDICATOR	[FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
FAILURE ANALYSIS RESULTS	[FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
REFERENCE DOCUMENT		
18172-21	THE EFFECT OF ESD ON CCD RELIABILITY	[147-153]
<u>AUTHOR(S)</u> :	WHITEHEAD, A.P.	LYNCH, J.T.
<u>COMPANY</u> :	PLESSEY	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
CHARGE DEVICE MODEL	[ESD, DEVICE, TESTING METHODS]	
ESD STD AND HANDBOOK	[ESD, STANDARDS, HANDBOOKS, MANUALS]	
FAILURE ANALYSIS RESULTS	[FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
CCD	[FIELD EFFECT, (FET), SEMICONDUCTOR TECH.]	
REFERENCE DOCUMENT		
LIFE	[TEST TECHNIQUES FOR REL. ASSESSMENT, SEMICONDUCTOR TECH.]	
OPERATIONAL TEST	[TEST TECHNIQUES FOR REL. ASSESSMENT, SEMICONDUCTOR TECH.]	

CHRONOLOGICAL LIST OF PAPERS 1981

<u>DOCUMENT-SEQUENCE NO.</u>	<u>TITLE</u>	<u>PAGES</u>
17517-35	NON-LINEAR KINETICS OF SEMICONDUCTOR JUNCTION THERMAL FAILURE	[242-245]
<u>AUTHOR(S)</u> : ASH,M.S. <u>COMPANY</u> : TRW		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
WUNSCH BELL MODEL	[ESD, DEVICE, TESTING METHODS]	
OVERSTRESS	[FAILURE CAUSE, FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
MATHEMATICAL ANALYSIS		
DISCRETE SEMICONDUCTOR	[SEMICONDUCTOR DEVICE]	
17517-34	EVALUATION OF ELECTROSTATIC DISCHARGE TO 16K EPROMS	[236-241]
<u>AUTHOR(S)</u> : CHASE,E.W. <u>COMPANY</u> : BELL LABORATORIES		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
CHARGE DEVICE MODEL	[ESD, DEVICE, TESTING METHODS]	
HUMAN BODY ESD MODEL	[ESD, DEVICE, TESTING METHODS]	
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
OVERSTRESS	[FAILURE CAUSE, FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
DIGITAL LSI	[MICROCIRCUIT, SEMICONDUCTOR DEVICE]	
TEST TECHNIQUES FOR REL. ASSESSMENT	[SEMICONDUCTOR TECH.]	
17517-33	EOS DAMAGE IN SILICON SOLAR CELLS	[209-235]
<u>AUTHOR(S)</u> : PEASE,R.L. BARNUM,J. VULIET,W. <u>COMPANY</u> : MISSION RESEARCH CORPORATION		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
METALLIZATION MELT	[ESD, DEVICE, FAILURE MODES]	
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
OVERSTRESS	[FAILURE CAUSE, FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
MATHEMATICAL ANALYSIS		
RELIABILITY MODELING TECHNIQUES	[REL. MODELS/DATA/ANALYSIS]	
DETECTOR/SENSOR	[OPTOELECTRONIC, SEMICONDUCTOR DEVICE]	
17517-32	TIME-RELATED IMPROVEMENTS OF ELECTRICAL CHARACTERISTICS IN ELECTROSTATICALLY DAMAGED OPERATIONAL AMPLIFIERS	[225-228]
<u>AUTHOR(S)</u> : HEAD,G.O. <u>COMPANY</u> : LEAR SIEGLER, INC.		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
HUMAN BODY ESD MODEL	[ESD, DEVICE, TESTING METHODS]	
ESD STD AND HANDBOOK	[ESD, STANDARDS, HANDBOOKS, MANUALS]	
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
OVERSTRESS	[FAILURE CAUSE, FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	

CHRONOLOGICAL LIST OF PAPERS 1981

DOCUMENT-SEQUENCE NO.	TITLE	PAGES
17517-31	FAILURE ANALYSIS OF SEMICONDUCTOR DEVICES IN EOS/ESD TESTING	[219-224]
AUTHOR(S) : LIN,T.S.	HORGAN,E.L.	
COMPANY : TRW		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
EOS - ELECTRICAL OVERSTRESS	[ESD, EOS/ESD PHYSICS]	
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
THERMAL SECONDARY BREAKDOWN	[ESD, DEVICE, FAILURE MODES]	
FAILURE ANALYSIS RESULTS	[FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
DISCRETE SEMICONDUCTOR	[SEMICONDUCTOR DEVICE]	
STATISTICAL ANALYSIS		
TEST TECHNIQUES FOR REL. ASSESSMENT	[SEMICONDUCTOR TECH.]	
17517-30	LIGHTNING PROTECTION FOR COMPUTER DATA LINES	[212-218]
AUTHOR(S) : CLARK,O.M.		
COMPANY : GENERAL SEMICONDUCTOR INDUSTRIES		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
CIRCUIT PROTECTION DEVICES	[NON-ELECTRONICS]	
COMPUTATION	[EQUIPMENT TYPE/FUNCTION]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
TRANSIENT SUPPRESSORS	[ESD, DEVICE, PROTECTIVE DEVICES/INPUT PROTECTION]	
REFERENCE DOCUMENT		
17517-29	POTENTIAL ESD HAZARDS ASSOCIATED WITH EXPLOSIVE PRIMERS	[208-211]
AUTHOR(S) : MYKKANEN,C.F.		
COMPANY : HONEYWELL		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
HUMAN BODY ESD MODEL	[ESD, DEVICE, TESTING METHODS]	
TRIOBOELECTRIC CHARGING	[ESD, EOS/ESD PHYSICS]	
FAILURE CAUSE	[FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
REFERENCE DOCUMENT		
WEAPONS	[EQUIPMENT TYPE/FUNCTION]	
17517-28	EOS THRESHOLD DETERMINATION OF ELECTRO-EXPLOSIVE DEVICES	[202-207]
AUTHOR(S) : HAYS,R.A.		
COMPANY : U.S. AIR FORCE		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
DIELECTRIC BREAKDOWN	[ESD, DEVICE, FAILURE MODES]	
EMP - ELECTROMAGNETIC PULSE	[ESD, EOS/ESD PHYSICS]	
EOS - ELECTRICAL OVERSTRESS	[ESD, EOS/ESD PHYSICS]	
FAILURE CHARACTERIZATION	[SEMICONDUCTOR TECH.]	
MISSILE	[APPLICATION ENVIRONMENT]	
17517-27	BEHAVIOR OF THICK-FILM POWER RESISTORS SUBJECTED TO LARGE MOMENTARY OVERLOADS	[198-201]
AUTHOR(S) : MATHURIN,J.	THOMAS,R.H.	GUAY,R.H.
COMPANY : EPI TEK ELECTRONIC, LTD.		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
OVERSTRESS	[FAILURE CAUSE, FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
RESISTOR	[PASSIVE DEVICE, COMPONENT TYPE]	
REFERENCE DOCUMENT		

CHRONOLOGICAL LIST OF PAPERS 1981

<u>DOCUMENT-SEQUENCE NO.</u>	<u>TITLE</u>	<u>PAGES</u>
17517-26	PREDICTION OF THIN-FILM RESISTOR BURNOUT	[192-197]
<u>AUTHOR(S)</u> : SMITH, J.S.	LITTAU, W.R.	
<u>COMPANY</u> : LOCKHEED		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
MATHEMATICAL ANALYSIS		
RESISTOR	[PASSIVE DEVICE, COMPONENT TYPE]	
REFERENCE DOCUMENT		
17517-25	PULSE POWER RESPONSE AND DAMAGE CHARACTERISTICS OF CAPACITORS	[174-191]
<u>AUTHOR(S)</u> : TASCA, D.M.		
<u>COMPANY</u> : GENERAL ELECTRIC		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
DIELECTRIC BREAKDOWN	[ESD, DEVICE, FAILURE MODES]	
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
OVERSTRESS	[FAILURE CAUSE, FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
CAPACITOR	[PASSIVE DEVICE, COMPONENT TYPE]	
REFERENCE DOCUMENT		
17517-24	AN OVERVIEW OF EOS EFFECTS ON PASSIVE COMPONENTS	[167-173]
<u>AUTHOR(S)</u> : WUNSCH, D.C.		
<u>COMPANY</u> : BDM CORPORATION		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
EOS - ELECTRICAL OVERSTRESS	[ESD, EOS/ESD PHYSICS]	
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
FAILURE CHARACTERIZATION	[SEMICONDUCTOR TECH.]	
RESISTOR	[PASSIVE DEVICE, COMPONENT TYPE]	
RELIABILITY	[SYSTEMS]	
REFERENCE DOCUMENT		
17517-23	EOS/ESD FAILURE THRESHOLD ANALYSIS ERRORS, THEIR SOURCE, SIZE AND CONTROL	[151-166]
<u>AUTHOR(S)</u> : HORGAN, E.L.	TEMPLAR, L.C. ROWAN, W.H.	
<u>COMPANY</u> : TRW		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
SECONDARY BREAKDOWN	[ELECTRICAL FAILURE PHENOMENA, SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
EOS - ELECTRICAL OVERSTRESS	[ESD, EOS/ESD PHYSICS]	
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
RELIABILITY MODELING TECHNIQUES	[REL. MODELS/DATA/ANALYSIS]	
DISCRETE SEMICONDUCTOR	[SEMICONDUCTOR DEVICE]	
17517-22	DETERMINING AN EMITTER-BASE FAILURE THRESHOLD DISTRIBUTION OF NPN TRANSISTORS	[145-150]
<u>AUTHOR(S)</u> : ENLOW, E.W.		
<u>COMPANY</u> : BDM CORPORATION		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
WUNSCH BELL MODEL	[ESD, DEVICE, TESTING METHODS]	
FAILURE ANALYSIS TECHNIQUES	[FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
TRANSISTOR	[DISCRETE SEMICONDUCTOR, SEMICONDUCTOR DEVICE]	
WEIBULL	[STATISTICAL ANALYSIS]	

CHRONOLOGICAL LIST OF PAPERS 1981

<u>DOCUMENT-SEQUENCE NO.</u>	<u>TITLE</u>	<u>PAGES</u>
17517-21	SEMICONDUCTOR DEVICE FAILURE CRITERIA FOR SINUSOIDAL STRESSES	[139-144]
<u>AUTHOR(S)</u> : THOMAS,R.E. <u>COMPANY</u> : KAMAN SCIENCES CORPORATION		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
EMP - ELECTROMAGNETIC PULSE	[ESD, EOS/ESD PHYSICS]	
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
FAILURE CHARACTERIZATION	[SEMICONDUCTOR TECH.]	
MATHEMATICAL ANALYSIS		
DISCRETE SEMICONDUCTOR	[SEMICONDUCTOR DEVICE]	
17517-20	MODELING OF EOS IN SILICON DEVICES	[132-138]
<u>AUTHOR(S)</u> : KUSNEZOV,N. SMITH,J.S. <u>COMPANY</u> : LOCKHEED		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
EOS - ELECTRICAL OVERSTRESS	[ESD, EOS/ESD PHYSICS]	
WUNSCH BELL MODEL	[ESD, DEVICE, TESTING METHODS]	
RELIABILITY MODELING TECHNIQUES	[REL. MODELS/DATA/ANALYSIS]	
COMPUTERIZED	[DATA COLLECTION SYS./TECHNIQUES, REL. MODELS/DATA/ANALYSIS]	
SILICON	[SEMICONDUCTOR TECH.]	
17517-19	AN OVERVIEW OF EOS EFFECTS ON SEMICONDUCTOR DEVICES	[120-131]
<u>AUTHOR(S)</u> : PIERCE,D.G. DURGIN,D.L. <u>COMPANY</u> : BOOZ, ALLEN & HAMILTON		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
OXIDATION	[CHEMICAL FAILURE PHENOMENA, SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
METALLIZATION MELT	[ESD, DEVICE, FAILURE MODES]	
EMP - ELECTROMAGNETIC PULSE	[ESD, EOS/ESD PHYSICS]	
EOS - ELECTRICAL OVERSTRESS	[ESD, EOS/ESD PHYSICS]	
ESD STD AND HANDBOOK	[ESD, STANDARDS, HANDBOOKS, MANUALS]	
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
WUNSCH BELL MODEL	[ESD, DEVICE, TESTING METHODS]	
OVERSTRESS	[FAILURE CAUSE, FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
FAILURE MODES	[FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
REFERENCE DOCUMENT		
DISCRETE SEMICONDUCTOR	[SEMICONDUCTOR DEVICE]	
17517-18	ELECTRICAL OVERSTRESS INVESTIGATIONS IN MODERN INTEGRATED CIRCUIT TECHNOLOGIES	[114-119]
<u>AUTHOR(S)</u> : KARASKIEWICZ,R.J. YOUNG,P.A. ALEXANDER,D.R. <u>COMPANY</u> : BDM CORPORATION		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
RELIABILITY	[DESIGN CONSIDERATIONS, SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
INPUT PROTECTION	[ESD, DEVICE, PROTECTIVE DEVICES/INPUT PROTECTION]	
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
WUNSCH BELL MODEL	[ESD, DEVICE, TESTING METHODS]	
OVERSTRESS	[FAILURE CAUSE, FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
FUTURE TRENDS	[SEMICONDUCTOR TECH.]	
DIGITAL LSI	[MICROCIRCUIT, SEMICONDUCTOR DEVICE]	
TEST TECHNIQUES FOR REL. ASSESSMENT	[SEMICONDUCTOR TECH.]	
STEP STRESS	[TEST TECHNIQUES FOR REL. ASSESSMENT, SEMICONDUCTOR TECH.]	

CHRONOLOGICAL LIST OF PAPERS 1981

<u>DOCUMENT-SEQUENCE NO.</u>	<u>TITLE</u>	<u>PAGES</u>
17517-17	SUSCEPTIBILITY OF ICS IN ESD STEP-STRESS TESTS	[106-113]
<u>AUTHOR(S)</u> :	ENDERS,J.	
<u>COMPANY</u> :	STANDARD ELECTRIK LORENZ AG	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
PROCESS DESIGN	[DESIGN CONSIDERATIONS, SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
METALLIZATION MELT	[ESD, DEVICE, FAILURE MODES]	
RELATIVE HUMIDITY	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]	
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
OVERSTRESS	[FAILURE CAUSE, FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
GUIDE/PROCEDURE	[REFERENCE DOCUMENT]	
MICROCIRCUIT	[SEMICONDUCTOR DEVICE]	
STEP STRESS	[TEST TECHNIQUES FOR REL. ASSESSMENT, SEMICONDUCTOR TECH.]	
17517-16	DIAGNOSIS AND ANALYSIS OF EMITTER-BASE JUNCTION OVERSTRESS DAMAGE	[101-105]
<u>AUTHOR(S)</u> :	JENSEN,M.C. MILBURN,R.T.	
<u>COMPANY</u> :	MOTOROLA	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
FAILURE CAUSE	[FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
REFERENCE DOCUMENT		
TRANSISTOR	[DISCRETE SEMICONDUCTOR, SEMICONDUCTOR DEVICE]	
TEST TECHNIQUES FOR REL. ASSESSMENT	[SEMICONDUCTOR TECH.]	
17517-15	INPUT PROTECTION DESIGN FOR THE 3-MICRON NMOS PROCESS	[97-100]
<u>AUTHOR(S)</u> :	TAYLOR,R.G.	
<u>COMPANY</u> :	MOSTEK	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
CIRCUIT PROTECTION DEVICES	[NON-ELECTRONICS]	
APPLICATION FACTORS	[DESIGN CONSIDERATIONS, SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
INPUT PROTECTION	[ESD, DEVICE, PROTECTIVE DEVICES/INPUT PROTECTION]	
OVERSTRESS	[FAILURE CAUSE, FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
REFERENCE DOCUMENT		
SEMICONDUCTOR DEVICE		
TEST SPECIFICATION	[TESTING TOOLS & TECHNIQUES, SEMICONDUCTOR TECH.]	
17517-14	ON CHIP PROTECTION OF HIGH DENSITY NMOS DEVICES	[90-96]
<u>AUTHOR(S)</u> :	HULETT,T.V.	
<u>COMPANY</u> :	MOTOROLA	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
CIRCUIT PROTECTION DEVICES	[NON-ELECTRONICS]	
OXIDATION	[CHEMICAL FAILURE PHENOMENA, SEMICONDUCTOR TECH.]	
APPLICATION FACTORS	[DESIGN CONSIDERATIONS, SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
INPUT PROTECTION	[ESD, DEVICE, PROTECTIVE DEVICES/INPUT PROTECTION]	
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
OVERSTRESS	[FAILURE CAUSE, FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
REFERENCE DOCUMENT		
SEMICONDUCTOR DEVICE		
TEST TECHNIQUES	[TESTING TOOLS & TECHNIQUES, SEMICONDUCTOR TECH.]	

CHRONOLOGICAL LIST OF PAPERS 1981

<u>DOCUMENT-SEQUENCE NO.</u>	<u>TITLE</u>	<u>PAGES</u>
17517-13	THE EFFECTS OF VLSI SCALING ON EOS/ESD FAILURE THRESHOLD	[85-89]
AUTHOR(S) : PANCHOLY, R.K.		
COMPANY : ROCKWELL		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
CIRCUIT PROTECTION DEVICES	[NON-ELECTRONICS]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
DIELECTRIC BREAKDOWN	[ESD, DEVICE, FAILURE MODES]	
INPUT PROTECTION	[ESD, DEVICE, PROTECTIVE DEVICES/INPUT PROTECTION]	
METALLIZATION MELT	[ESD, DEVICE, FAILURE MODES]	
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
OVERSTRESS	[FAILURE CAUSE, FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
FABRICATION PROCESSES & TECHNIQUES	[SEMICONDUCTOR TECH.]	
REFERENCE DOCUMENT		
17517-12	SELECTION OF PACKAGING MATERIALS FOR ESD SENSITIVE ITEMS	[75-84]
AUTHOR(S) : KOLYER, J.M. ANDERSON, W.E.		
COMPANY : ROCKWELL		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
MATERIALS	[DESIGN CONSIDERATIONS, SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
ELECTROSTATIC SHIELD	[ESD, EOS/ESD PHYSICS]	
ESD PROTECTIVE MATERIAL	[ESD, MATERIALS AND EQUIPMENT, TESTING]	
PROTECTIVE BAGS	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
RELATIVE HUMIDITY	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]	
ESD STD AND HANDBOOK	[ESD, STANDARDS, HANDBOOKS, MANUALS]	
TOPICAL ANTISTATS	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
FAILURE ANALYSIS RESULTS	[FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
PACKAGE	[SEMICONDUCTOR TECH.]	
REFERENCE DOCUMENT		
EVALUATION TEST	[TEST TECHNIQUES FOR REL. ASSESSMENT, SEMICONDUCTOR TECH.]	
17517-11	INCOMING INSPECTION OF ANTISTATIC PACKAGING MATERIALS	[65-74]
AUTHOR(S) : TOPOLSKI, A.S.		
COMPANY : DU PONT		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
MATERIALS	[DESIGN CONSIDERATIONS, SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
DECAY TIME	[ESD, MATERIALS AND EQUIPMENT, TESTING]	
ELECTROSTATIC CHARGE DETECTOR	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
RELATIVE HUMIDITY	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]	
SURFACE RESISTIVITY	[ESD, MATERIALS AND EQUIPMENT, TESTING]	
VOLUME RESISTIVITY	[ESD, MATERIALS AND EQUIPMENT, TESTING]	
PACKAGE	[SEMICONDUCTOR TECH.]	
QUALITY ASSURANCE	[SYSTEMS]	
GUIDE/PROCEDURE	[REFERENCE DOCUMENT]	
EVALUATION TEST	[TEST TECHNIQUES FOR REL. ASSESSMENT, SEMICONDUCTOR TECH.]	

CHRONOLOGICAL LIST OF PAPERS 1981

<u>DOCUMENT-SEQUENCE NO.</u>	<u>TITLE</u>	<u>PAGES</u>
17517-10	EVALUATION OF INTEGRATED CIRCUIT SHIPPING TUBES	[57-64]
<u>AUTHOR(S)</u> : UNGER,B.	CHEMELLI,R.G.	BOSSARD,P.R.
<u>COMPANY</u> : BELL LABORATORIES		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
CHARGE DEVICE MODEL	[ESD, DEVICE, TESTING METHODS]	
DIP TUBE	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
HUMAN BODY ESD MODEL	[ESD, DEVICE, TESTING METHODS]	
TRIOBOELECTRIC CHARGING	[ESD, EOS/ESD PHYSICS]	
OVERSTRESS	[FAILURE CAUSE, FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
PACKAGE	[SEMICONDUCTOR TECH.]	
GUIDE/PROCEDURE	[REFERENCE DOCUMENT]	
SEMICONDUCTOR DEVICE		
17517- 9	CHO-TRAP, A NOVEL VOLTAGE TRANSIENT PROTECTION PACKAGING MATERIAL	[49-56]
<u>AUTHOR(S)</u> : PEDULLA,J.	MALINARIB,P.	
<u>COMPANY</u> : CHOMERIC, INC.		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
HUMAN BODY ESD MODEL	[ESD, DEVICE, TESTING METHODS]	
ESD PROTECTIVE MATERIAL	[ESD, MATERIALS AND EQUIPMENT, TESTING]	
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
REFERENCE DOCUMENT		
17517- 8	AN ANALYSIS OF ANTISTATIC CUSHIONING MATERIALS	[44-48]
<u>AUTHOR(S)</u> : TENZER,F.D.	HARTMANN,H.C.	JOHNSON,M.A.
<u>COMPANY</u> : PACKAGING INDUSTRIES OF CALIFORNIA		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
MATERIALS	[DESIGN CONSIDERATIONS, SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
DECAY TIME	[ESD, MATERIALS AND EQUIPMENT, TESTING]	
RELATIVE HUMIDITY	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]	
ESD STD AND HANDBOOK	[ESD, STANDARDS, HANDBOOKS, MANUALS]	
SURFACE RESISTIVITY	[ESD, MATERIALS AND EQUIPMENT, TESTING]	
TOPICAL ANTISTATS	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
TRIOBOELECTRIC CHARGING	[ESD, EOS/ESD PHYSICS]	
REFERENCE DOCUMENT		
TEST PROGRAM DEVELOPMENT	[TESTING TOOLS & TECHNIQUES, SEMICONDUCTOR TECH.]	
17517- 7	A LOW-COST PROGRAM FOR EVALUATION OF ESD PROTECTIVE MATERIALS AND EQUIPMENT	[41-43]
<u>AUTHOR(S)</u> : HEAD,G.O.		
<u>COMPANY</u> : LEAR SIEGLER, INC.		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
COST	[SYSTEMS]	
DEVELOPMENT PROGRAM	[SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
AIR IONIZER	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
CONDUCTIVE ESD PROTECTIVE MATERIAL	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
ESD PROTECTIVE MATERIAL	[ESD, MATERIALS AND EQUIPMENT, TESTING]	
ESD STD AND HANDBOOK	[ESD, STANDARDS, HANDBOOKS, MANUALS]	
SURFACE RESISTIVITY	[ESD, MATERIALS AND EQUIPMENT, TESTING]	
GUIDE/PROCEDURE	[REFERENCE DOCUMENT]	

CHRONOLOGICAL LIST OF PAPERS 1981

DOCUMENT-SEQUENCE NO.	TITLE	PAGES
17517- 6	A PRAGMATIC APPROACH TO ESD PROBLEM SOLVING IN THE MANUFACTURING ENVIRONMENT A CASE HISTORY	[34-39]
<u>AUTHOR(S)</u> :	MCALEER,R.E. LUCAS,G.H. MCDONALD,A.	
<u>COMPANY</u> :	TEXAS INSTRUMENTS (TI)	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
DEVELOPMENT PROGRAM	[SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
GROUNDING STRAPS	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
PROTECTED ESD AREA	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
PROTECTIVE WORK BENCH SURFACE	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
RELATIVE HUMIDITY	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]	
REFERENCE DOCUMENT		
17517- 5	THE ECONOMIC BENEFITS OF AN EFFECTIVE ESD AWARENESS AND CONTROL PROGRAM - AN EMPIRICAL ANALYSIS	[29-33]
<u>AUTHOR(S)</u> :	MCFARLAND,W.Y.	
<u>COMPANY</u> :	WESTERN ELECTRIC COMPANY, INC.	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
COMPONENT	[LEVEL OF ASSEMBLY]	
DEVELOPMENT PROGRAM	[SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
AIR IONIZER	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
GROUNDING STRAPS	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
ESD PROTECTIVE MATERIAL	[ESD, MATERIALS AND EQUIPMENT, TESTING]	
ESD CONTROL PROGRAM	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]	
PROTECTED ESD AREA	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
STATIC CONTROL	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]	
SENSITIVE ELECTRONIC DEVICE SYMBOLS	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
OVERSTRESS	[FAILURE CAUSE, FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
REFERENCE DOCUMENT		
17517- 4	THE PERFECT "10" - CAN YOU REALLY HAVE ONE?	[21-27]
<u>QTHOR(S)</u> :	FRANK,D.E.	
<u>COMPANY</u> :	DOUGLAS AIRCRAFT	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
COMPONENT	[LEVEL OF ASSEMBLY]	
APPLICATION FACTORS	[DESIGN CONSIDERATIONS, SEMICONDUCTOR TECH.]	
DEVELOPMENT PROGRAM	[SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
ESD CONTROL PROGRAM	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]	
PROTECTED ESD AREA	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
OVERSTRESS	[FAILURE CAUSE, FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
WORKMANSHIP	[FAILURE CAUSE, FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
QUALITY ASSURANCE	[SYSTEMS]	
REFERENCE DOCUMENT		
SEMICONDUCTOR DEVICE		

CHRONOLOGICAL LIST OF PAPERS 1981

<u>DOCUMENT-SEQUENCE NO.</u>	<u>TITLE</u>	<u>PAGES</u>
17517- 3	ANALYSIS OF ESD FAILURES	[14-20]
<u>AUTHOR(S)</u> :	MCATEER,O.J. TWIST,R.E.	
<u>COMPANY</u> :	WESTINGHOUSE	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
OVERSTRESS	[FAILURE CAUSE, FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
FAILURE ANALYSIS RESULTS	[FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
REFERENCE DOCUMENT		
MICROCIRCUIT	[SEMICONDUCTOR DEVICE]	
17517- 2	QUANTITATIVE EFFECTS OF RELATIVE & ABSOLUTE HUMIDITY ON ESD GENERATION/ SUPPRESSION	[9-13]
<u>AUTHOR(S)</u> :	BLINDE,D.R. LAVOIE,L.	
<u>COMPANY</u> :	HONEYWELL	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
DESIGN CONSIDERATIONS	[SEMICONDUCTOR TECH.]	
MATERIALS	[DESIGN CONSIDERATIONS, SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
AIR IONIZER	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
DECAY TIME	[ESD, MATERIALS AND EQUIPMENT, TESTING]	
RELATIVE HUMIDITY	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]	
STATIC CONTROL	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]	
FLOOR SURFACE	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
THEORY OF OPERATION	[SEMICONDUCTOR TECH.]	
17517- 1	A CLOSER LOOK AT THE HUMAN ESD EVENT	[1-8]
<u>AUTHOR(S)</u> :	HYATT,H.M. CALVIN,H. MELLBERG,H.	
<u>COMPANY</u> :	EXPERIMENTAL PHYSICS CORPORATION	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
DESIGN FOR TESTABILITY	[DESIGN CONSIDERATIONS, SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
HUMAN BODY ESD MODEL	[ESD, DEVICE, TESTING METHODS]	
THEORY OF OPERATION	[SEMICONDUCTOR TECH.]	
TESTING TOOLS & TECHNIQUES	[SEMICONDUCTOR TECH.]	

CHRONOLOGICAL LIST OF PAPERS 1980

<u>DOCUMENT-SEQUENCE NO.</u>	<u>TITLE</u>	<u>PAGES</u>
17516-33	MEASUREMENT OF FAST TRANSIENTS AND APPLICATION TO HUMAN ESD	[225-230]
<u>AUTHOR(S)</u> :	CALVIN,H. HYATT,H. MELLBERG,H.	
<u>COMPANY</u> :	EXPERIMENTAL PHYSICS CORPORATION	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
DESIGN FOR TESTABILITY	[DESIGN CONSIDERATIONS, SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
INDUCTIVE CHARGING	[ESD, EOS/ESD PHYSICS]	
17516-32	AN EVALUATION OF WRIST STRAP PARAMETERS	[218-224]
<u>AUTHOR(S)</u> :	SOHL,J.E.	
<u>COMPANY</u> :	HONEYWELL	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
DESIGN FOR TESTABILITY	[DESIGN CONSIDERATIONS, SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
GROUNDING STRAPS	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
WRIST STRAP	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
TEST EQUIPMENT	[TESTING TOOLS & TECHNIQUES, SEMICONDUCTOR TECH.]	
17516-31	STATIC CONTROL SYSTEMS	[213-217]
<u>AUTHOR(S)</u> :	BOLASNY,R.E.	
<u>COMPANY</u> :	SCIENTIFIC ENTERPRISES, INC.	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
EMI - ELECTROMAGNETIC INTERFACE	[ESD, EOS/ESD PHYSICS]	
STATIC CONTROL	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]	
TEST EQUIPMENT	[TESTING TOOLS & TECHNIQUES, SEMICONDUCTOR TECH.]	
17516-30	BASIC CONSIDERATIONS IN ELECTRO-THERMAL OVERSTRESS IN ELECTRONIC COMPONENTS	[206-212]
<u>AUTHOR(S)</u> :	DOMINGOS,H.	
<u>COMPANY</u> :	CLARKSON COLLEGE	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
MATERIALS	[DESIGN CONSIDERATIONS, SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
EOS - ELECTRICAL OVERSTRESS	[ESD, EOS/ESD PHYSICS]	
TRANSIENT SUPPRESSORS	[ESD, DEVICE, PROTECTIVE DEVICES/INPUT PROTECTION]	
THERMAL	[TEST STRESS]	
17516-29	FACILITY EVALUATION: ISOLATING ENVIRONMENTAL ESD PROBLEMS	[192-205]
<u>AUTHOR(S)</u> :	HALPERIN,S.A.	
<u>COMPANY</u> :	ANALYTICAL CHEMICAL LABORATORY	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
DECAY TIME	[ESD, MATERIALS AND EQUIPMENT, TESTING]	
GROUNDING STRAPS	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
ESD PROTECTIVE MATERIAL	[ESD, MATERIALS AND EQUIPMENT, TESTING]	
EMI - ELECTROMAGNETIC INTERFACE	[ESD, EOS/ESD PHYSICS]	
ESD CONTROL PROGRAM	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]	
STATIC CONTROL	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]	
TOPICAL ANTISTATS	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
RELIABILITY	[SYSTEMS]	

CHRONOLOGICAL LIST OF PAPERS 1980

<u>DOCUMENT-SEQUENCE NO.</u>	<u>TITLE</u>	<u>PAGES</u>
7516-28	AN EFFECTIVE ESD AWARENESS TRAINING PROGRAM	[189-191]
<u>AUTHOR(S)</u> : MCATEER, O.J. <u>COMPANY</u> : WESTINGHOUSE		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
ESD PROTECTIVE MATERIAL	[ESD, MATERIALS AND EQUIPMENT, TESTING]	
ESD CONTROL PROGRAM	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]	
STATIC CONTROL	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]	
REFERENCE DOCUMENT		
17516-27	MICROCIRCUIT ELECTRICAL OVERSTRESS TOLERANCE TESTING AND QUALIFICATION	[184-188]
<u>AUTHOR(S)</u> : ANTINONE, R.J. <u>COMPANY</u> : BDM CORPORATION		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
ELECTRICAL	[TEST STRESS]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
ELECTROSTATIC SIMULATOR	[ESD, DEVICE, TESTING METHODS]	
EMP - ELECTROMAGNETIC PULSE	[ESD, EOS/ESD PHYSICS]	
EOS - ELECTRICAL OVERSTRESS	[ESD, EOS/ESD PHYSICS]	
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
MICROCIRCUIT	[SEMICONDUCTOR DEVICE]	
CHARACTERIZATION	[TEST TECHNIQUES FOR REL. ASSESSMENT, SEMICONDUCTOR TECH.]	
17516-26	SURGE TESTS ON PLUG-IN TRANSFORMERS	[176-183]
<u>AUTHOR(S)</u> : KRESSLER, D.R. <u>COMPANY</u> : BELL LABORATORIES		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
INPUT PROTECTION	[ESD, DEVICE, PROTECTIVE DEVICES/INPUT PROTECTION]	
TRANSIENT SUPPRESSORS	[ESD, DEVICE, PROTECTIVE DEVICES/INPUT PROTECTION]	
TEST TECHNIQUES FOR REL. ASSESSMENT	[SEMICONDUCTOR TECH.]	
17516-25	LIGHTNING PROTECTION DESIGN FOR A PHOTOVOLTAIC CONCENTRATOR	[167-175]
<u>AUTHOR(S)</u> : CROUCH, K.E. <u>COMPANY</u> : LIGHTNING TECHNOLOGIES		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
DESIGN CONSIDERATIONS	[SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
GROUNDING METHODS	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]	
TRANSIENT SUPPRESSORS	[ESD, DEVICE, PROTECTIVE DEVICES/INPUT PROTECTION]	
17516-24	TEST WAVEFORMS AND TECHNIQUES TO ASSESS THE THREAT TO ELECTRONIC DEVICES OF LIGHTNING-INDUCED TRANSIENTS	[161-166]
<u>AUTHOR(S)</u> : HESS, R.F. <u>COMPANY</u> : SPERRY CORPORATION		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
DECAY TIME	[ESD, MATERIALS AND EQUIPMENT, TESTING]	
TRANSIENT SUPPRESSORS	[ESD, DEVICE, PROTECTIVE DEVICES/INPUT PROTECTION]	
TESTING TOOLS & TECHNIQUES	[SEMICONDUCTOR TECH.]	

CHRONOLOGICAL LIST OF PAPERS 1980

DOCUMENT-SEQUENCE NO.	TITLE	PAGES
7516-23	AN OVERVIEW OF THE SOURCES AND EFFECTS OF ELECTRICAL OVERSTRESS	[154-160]
AUTHOR(S) :	DURGIN,D.L.	
COMPANY :	BOOZ, ALLEN & HAMILTON	
INDEX TERM	CATEGORIES	
EOS/ESD	[SEMICONDUCTOR TECH.]	
EMC - ELECTROMAGNETIC COMPATIBILITY	[ESD, EOS/ESD PHYSICS]	
EMI - ELECTROMAGNETIC INTERFACE	[ESD, EOS/ESD PHYSICS]	
EMP - ELECTROMAGNETIC PULSE	[ESD, EOS/ESD PHYSICS]	
EOS - ELECTRICAL OVERSTRESS	[ESD, EOS/ESD PHYSICS]	
ESD STD AND HANDBOOK	[ESD, STANDARDS, HANDBOOKS, MANUALS]	
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
RELIABILITY	[SYSTEMS]	
SEMICONDUCTOR DEVICE		
CHARACTERIZATION	[TEST TECHNIQUES FOR REL. ASSESSMENT, SEMICONDUCTOR TECH.]	
7516-22	SOLAR CELL ELECTRICAL OVERSTRESS ANALYSIS	[149-153]
AUTHOR(S) :	SMYTH,J.B. VAN LINT,V.A.J.	
COMPANY :	MISSION RESEARCH CORPORATION	
INDEX TERM	CATEGORIES	
ELECTRICAL FAILURE PHENOMENA	[SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
ETALLIZATION MELT	[ESD, DEVICE, FAILURE MODES]	
EOS - ELECTRICAL OVERSTRESS	[ESD, EOS/ESD PHYSICS]	
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
THERMAL SECONDARY BREAKDOWN	[ESD, DEVICE, FAILURE MODES]	
MUNSCHELL MODEL	[ESD, DEVICE, TESTING METHODS]	
FAILURE ANALYSIS RESULTS	[FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
7516-21	ASSESSING ELECTRICAL OVERSTRESS EFFECTS ON ELECTRONIC SYSTEMS	[140-148]
AUTHOR(S) :	HORGAN,E.L.	
COMPANY :	TRW	
INDEX TERM	CATEGORIES	
EOS/ESD	[SEMICONDUCTOR TECH.]	
ASSEMBLY & EQUIPMENT ESD CLASSIFICATION	[ESD, DEVICE, TESTING METHODS]	
EMP - ELECTROMAGNETIC PULSE	[ESD, EOS/ESD PHYSICS]	
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
RELIABILITY	[SYSTEMS]	
SYSTEM	[LEVEL OF ASSEMBLY]	
7516-20	OSCILLATING VOLTAGE PULSES AND SECOND BREAKDOWN	[130-139]
AUTHOR(S) :	WARD,A.L.	
COMPANY :	HARRY DIAMOND LAB (HDL)	
INDEX TERM	CATEGORIES	
ELECTRICAL FAILURE PHENOMENA	[SEMICONDUCTOR TECH.]	
SECONDARY BREAKDOWN	[ELECTRICAL FAILURE PHENOMENA, SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
DECAY TIME	[ESD, MATERIALS AND EQUIPMENT, TESTING]	
ELECTRO-THERMOMIGRATION	[ESD, DEVICE, FAILURE MODES]	
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
DIODE	[DISCRETE SEMICONDUCTOR, SEMICONDUCTOR DEVICE]	

CHRONOLOGICAL LIST OF PAPERS 1980

<u>UMENT-SEQUENCE NO.</u>	<u>TITLE</u>	<u>PAGES</u>
16-19	EFFECT OF JUNCTION SPIKES AND DOPING LEVEL ON THE SECOND BREAKDOWN SUSCEPTIBILITY OF SILICON-ON-SAPPHIRE DIODES	[122-129]
<u>HOR(S)</u> :	KNIGHT,E.R. BUDENSTEIN,P.P.	
<u>PANY</u> :	AUBURN UNIVERSITY	
<u>EX TERM</u>	<u>CATEGORIES</u>	
CONDARY BREAKDOWN	[ELECTRICAL FAILURE PHENOMENA, SEMICONDUCTOR TECH.]	
/ESD	[SEMICONDUCTOR TECH.]	
SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
RMAL SECONDARY BREAKDOWN	[ESD, DEVICE, FAILURE MODES]	
DE	[DISCRETE SEMICONDUCTOR, SEMICONDUCTOR DEVICE]	
16-18	SOME DESIGN CRITERIA FOR AVOIDING SECOND BREAKDOWN IN BIPOLAR DEVICES	[117-121]
<u>HOR(S)</u> :	MATHEWS,D.	
<u>PANY</u> :	U.S. ARMY	
<u>DEX TERM</u>	<u>CATEGORIES</u>	
POLAR & FET,(BIFET,BIMOS,ETC)	[COMPONENT TYPE]	
OLAR	[COMPONENT TYPE]	
/ESD	[SEMICONDUCTOR TECH.]	
SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
ERMAL SECONDARY BREAKDOWN	[ESD, DEVICE, FAILURE MODES]	
SCH BELL MODEL	[ESD, DEVICE, TESTING METHODS]	
516-17	HIGH-FIELD PHENOMENA AND FAILURE MECHANISMS IN BIPOLAR TRANSISTORS	[112-116]
<u>HOR(S)</u> :	HOWER,P.L.	
<u>PANY</u> :	WESTINGHOUSE	
<u>DEX TERM</u>	<u>CATEGORIES</u>	
POLAR	[COMPONENT TYPE]	
CONDARY BREAKDOWN	[ELECTRICAL FAILURE PHENOMENA, SEMICONDUCTOR TECH.]	
S/ESD	[SEMICONDUCTOR TECH.]	
D SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
ILURE CHARACTERIZATION	[SEMICONDUCTOR TECH.]	
ANSISTOR	[DISCRETE SEMICONDUCTOR, SEMICONDUCTOR DEVICE]	
516-16	SUPRISING PATTERNS OF CMOS SUSCEPTIBILITY TO ESD AND IMPLICATIONS ON LONG-TERM RELIABILITY	[104-111]
<u>THOR(S)</u> :	SCHWANK,J.R. BAKER,R.P. ARMENDARIZ,M.G.	
<u>PANY</u> :	SANDIA LABORATORIES	
<u>DEX TERM</u>	<u>CATEGORIES</u>	
IDATION	[CHEMICAL FAILURE PHENOMENA, SEMICONDUCTOR TECH.]	
S/ESD	[SEMICONDUCTOR TECH.]	
D SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
DS	[FIELD EFFECT,(FET), SEMICONDUCTOR TECH.]	
CROCIRCUIT	[SEMICONDUCTOR DEVICE]	
ST TECHNIQUES FOR REL. ASSESSMENT	[SEMICONDUCTOR TECH.]	
516-15	ELECTROSTATIC SENSITIVITY OF VARIOUS INPUT PROTECTION NETWORKS	[95-103]
<u>THOR(S)</u> :	TURNER,T.E. MORRIS,S.	
<u>PANY</u> :	MOSTEK	
<u>DEX TERM</u>	<u>CATEGORIES</u>	
RCUIT PROTECTION DEVICES	[NON-ELECTRONICS]	
IDATION	[CHEMICAL FAILURE PHENOMENA, SEMICONDUCTOR TECH.]	
OMETRIES/LAYOUT	[DESIGN CONSIDERATIONS, SEMICONDUCTOR TECH.]	
S/ESD	[SEMICONDUCTOR TECH.]	
PUT PROTECTION	[ESD, DEVICE, PROTECTIVE DEVICES/INPUT PROTECTION]	
D SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	

CHRONOLOGICAL LIST OF PAPERS 1980

DOCUMENT-SEQUENCE NO.	TITLE	PAGES
16-14	LSI DESIGN CONSIDERATIONS FOR ESD PROTECTION STRUCTURES RELATED TO PROCESS AND LAYOUT VARIATIONS HOR(S) : HART,A.R. PANY : HEWLETT PACKARD	[87-94]
EX TERM	CATEGORIES	
DATION	[CHEMICAL FAILURE PHENOMENA, SEMICONDUCTOR TECH.]	
IGN CONSIDERATIONS	[SEMICONDUCTOR TECH.]	
/ESD	[SEMICONDUCTOR TECH.]	
SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
ITAL LSI	[MICROCIRCUIT, SEMICONDUCTOR DEVICE]	
16-13	SOS PROTECTION: THE DESIGN PROBLEM HOR(S) : LUISI,J.A. PANY : ROCKWELL	[81-86]
EX TERM	CATEGORIES	
CUIT PROTECTION DEVICES	[NON-ELECTRONICS]	
IGN CONSIDERATIONS	[SEMICONDUCTOR TECH.]	
/ESD	[SEMICONDUCTOR TECH.]	
UT PROTECTION	[ESD, DEVICE, PROTECTIVE DEVICES/INPUT PROTECTION]	
FET	[FIELD EFFECT,(FET), SEMICONDUCTOR TECH.]	
16-12	PROTECTION OF MOS INTEGRATED CIRCUITS FROM DESTRUCTION BY ELECTROSTATIC DISCHARGE HOR(S) : KELLER,J.K. PANY : BELL LABORATORIES	[73-80]
EX TERM	CATEGORIES	
CUIT PROTECTION DEVICES	[NON-ELECTRONICS]	
DATION	[CHEMICAL FAILURE PHENOMENA, SEMICONDUCTOR TECH.]	
/ESD	[SEMICONDUCTOR TECH.]	
IAN BODY ESD MODEL	[ESD, DEVICE, TESTING METHODS]	
SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
ROCIRCUIT	[SEMICONDUCTOR DEVICE]	
16-11	ANALYSIS OF ESD DAMAGE IN JFET PREAMPLIFIERS HOR(S) : CASTLE,G.S.P. PANY : NORTHERN TELECOM	[67-72]
EX TERM	CATEGORIES	
/ESD	[SEMICONDUCTOR TECH.]	
ALLIZATION MELT	[ESD, DEVICE, FAILURE MODES]	
SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
URE ANALYSIS RESULTS	[FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
T	[FIELD EFFECT,(FET), SEMICONDUCTOR TECH.]	
16-10	FAILURE THRESHOLD DISTRIBUTIONS IN BIPOLAR TRANSISTORS HOR(S) : ENLOV,E.W. PANY : SANDIA LABORATORIES	[59-66]
EX TERM	CATEGORIES	
POLAR	[COMPONENT TYPE]	
CTRICAL FAILURE PHENOMENA	[SEMICONDUCTOR TECH.]	
/ESD	[SEMICONDUCTOR TECH.]	
SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
NSISTOR	[DISCRETE SEMICONDUCTOR, SEMICONDUCTOR DEVICE]	
T TECHNIQUES FOR REL. ASSESSMENT	[SEMICONDUCTOR TECH.]	

CHRONOLOGICAL LIST OF PAPERS 1980

<u>DOCUMENT-SEQUENCE NO.</u>	<u>TITLE</u>	<u>PAGES</u>
17516- 9	STUDY OF EFFECTS OF ELECTRO-STATIC DISCHARGE ON SOLID-STATE DEVICES	[58]
<u>AUTHOR(S)</u> :	ZAJAC,H.	
<u>COMPANY</u> :	TEKTRONIX	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
TTL	[BIPOLAR, COMPONENT TYPE]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
INPUT PROTECTION	[ESD, DEVICE, PROTECTIVE DEVICES/INPUT PROTECTION]	
METALLIZATION MELT	[ESD, DEVICE, FAILURE MODES]	
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
TRANSISTOR	[DISCRETE SEMICONDUCTOR, SEMICONDUCTOR DEVICE]	
17516- 8	IDENTIFICATION OF LATENT ESD FAILURES	[54-57]
<u>AUTHOR(S)</u> :	WALKER,R.C.	
<u>COMPANY</u> :	IIT RESEARCH INSTITUTE	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
LATENT ESD FAILURE	[ESD, DEVICE, FAILURE MODES]	
FAILURE MODES	[FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
TESTING TOOLS & TECHNIQUES	[SEMICONDUCTOR TECH.]	
17516- 7	GAS TUBE SURGE ARRESTERS FOR CONTROL OF TRANSIENT VOLTAGES	[44-53]
<u>AUTHOR(S)</u> :	BAZARIAN,A.	
<u>COMPANY</u> :	GENERAL INSTRUMENT	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
CIRCUIT PROTECTION DEVICES	[NON-ELECTRONICS]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
INPUT PROTECTION	[ESD, DEVICE, PROTECTIVE DEVICES/INPUT PROTECTION]	
STATIC CONTROL	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]	
TRANSIENT SUPPRESSORS	[ESD, DEVICE, PROTECTIVE DEVICES/INPUT PROTECTION]	
17516- 6	PROTECTION LEVEL COMPARISONS FOR VOLTAGE TRANSIENT SUPPRESSORS (120 V, AC TYPE)	[35-43]
<u>AUTHOR(S)</u> :	HOPKINS,D.C.	
<u>COMPANY</u> :	GENERAL ELECTRIC	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
INPUT PROTECTION	[ESD, DEVICE, PROTECTIVE DEVICES/INPUT PROTECTION]	
EMI - ELECTROMAGNETIC INTERFACE	[ESD, EOS/ESD PHYSICS]	
TRANSIENT SUPPRESSORS	[ESD, DEVICE, PROTECTIVE DEVICES/INPUT PROTECTION]	
DISCRETE SEMICONDUCTOR	[SEMICONDUCTOR DEVICE]	
TEST TECHNIQUES FOR REL. ASSESSMENT	[SEMICONDUCTOR TECH.]	
17516- 5	TRANSIENT PROTECTION WITH ZNO VARISTORS: TECHNICAL CONSIDERATIONS	[26-34]
<u>AUTHOR(S)</u> :	PHILIPP,H.R. LEVINSON,L.M.	
<u>COMPANY</u> :	GENERAL ELECTRIC	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
INPUT PROTECTION	[ESD, DEVICE, PROTECTIVE DEVICES/INPUT PROTECTION]	
STATIC CONTROL	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]	
TRANSIENT SUPPRESSORS	[ESD, DEVICE, PROTECTIVE DEVICES/INPUT PROTECTION]	
DISCRETE SEMICONDUCTOR	[SEMICONDUCTOR DEVICE]	

CHRONOLOGICAL LIST OF PAPERS 1980

<u>DOCUMENT-SEQUENCE NO.</u>	<u>TITLE</u>	<u>PAGES</u>
17516- 4	ELECTROSTATIC DISCHARGE (ESD) MONITOR DESIGN	[23-25]
<u>AUTHOR(S)</u> : WU,C.	PARADISE,E.D.	
<u>COMPANY</u> : IBM CORPORATION		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
ELECTROSTATIC CHARGE DETECTOR	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
ESD CONTROL PROGRAM	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]	
TESTING TOOLS & TECHNIQUES	[SEMICONDUCTOR TECH.]	
17516- 3	ESD DAMAGE FROM TRIBOELECTRICALLY CHARGED IC PINS	[17-22]
<u>AUTHOR(S)</u> : BOSSARD,P.R.	CHEMELLI,R.G.	UNGER,B.A.
<u>COMPANY</u> : BELL LABORATORIES		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
CHARGE DEVICE MODEL	[ESD, DEVICE, TESTING METHODS]	
DIP TUBE	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
TRIBOELECTRIC CHARGING	[ESD, EOS/ESD PHYSICS]	
WUNSCH BELL MODEL	[ESD, DEVICE, TESTING METHODS]	
FAILURE MODES	[FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
PKG LID OR COVER	[PACKAGE, SEMICONDUCTOR TECH.]	
TESTING TOOLS & TECHNIQUES	[SEMICONDUCTOR TECH.]	
17516- 2	THE EFFECTS OF HIGH HUMIDITY ENVIRONMENTS ON ELECTROSTATIC GENERATION AND DISCHARGE	[12-16]
<u>AUTHOR(S)</u> : CALDERBANK,J.M.	OVERBAY,D.E.	SNYOER,H.2.
<u>COMPANY</u> : E-SYSTEMS, INC.		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
DECAY TIME	[ESD, MATERIALS AND EQUIPMENT, TESTING]	
ESD CONTROL PROGRAM	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]	
RELATIVE HUMIDITY	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]	
FLOOR SURFACE	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
MOISTURE	[TEST STRESS]	
ENVIRONMENTAL	[TEST TECHNIQUES FOR REL. ASSESSMENT, SEMICONDUCTOR TECH.]	
TESTING TOOLS & TECHNIQUES	[SEMICONDUCTOR TECH.]	
17516- 1	PASSIVE STATIC PROTECTION: THEORY AND PRACTICE	[1-11]
<u>AUTHOR(S)</u> : BERBECO,G.R.		
<u>COMPANY</u> : CHARLESWATERS PRODUCT, INC.		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
CONDUCTIVE FOAM	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
CONDUCTIVE ESD PROTECTIVE MATERIAL	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
GROUNDING METHODS	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]	
ESD CONTROL PROGRAM	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]	
PROTECTED ESD AREA	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
PROTECTIVE BAGS	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
PROTECTIVE WORK BENCH SURFACE	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
STATIC CONTROL	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]	
ESD STD AND HANDBOOK	[ESD, STANDARDS, HANDBOOKS, MANUALS]	
SURFACE RESISTIVITY	[ESD, MATERIALS AND EQUIPMENT, TESTING]	
THEORY OF OPERATION	[SEMICONDUCTOR TECH.]	

CHRONOLOGICAL LIST OF PAPERS 1979

<u>DOCUMENT-SEQUENCE NO.</u>	<u>TITLE</u>	<u>PAGES</u>
17515-30	THE ANALYSIS AND ELIMINATION OF EOS INDUCED SECONDARY FAILURE MECHANISMS	[205-209]
<u>AUTHOR(S)</u> :	MADISON, J.A.	
<u>COMPANY</u> :	WESTINGHOUSE	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
BOARD	[LEVEL OF ASSEMBLY]	
DEVELOPMENT PROGRAM	[SEMICONDUCTOR TECH.]	
SECONDARY BREAKDOWN	[ELECTRICAL FAILURE PHENOMENA, SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
EOS - ELECTRICAL OVERSTRESS	[ESD, EOS/ESD PHYSICS]	
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
OVERSTRESS	[FAILURE CAUSE, FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
FAILURE ANALYSIS RESULTS	[FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
GUIDE/PROCEDURE	[REFERENCE DOCUMENT]	
17515-29	STATISTICAL FAILURE ANALYSIS OF MILITARY SYSTEMS FOR HIGH-ALTITUDE EMP	[198-204]
<u>AUTHOR(S)</u> :	CABAYAN, H.S. DEADRICK, F.J. MARTIN, L.C.	
<u>COMPANY</u> :	LAWRENCE LIVERMORE NATIONAL LABORATORY	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
APPLICATION FACTORS	[DESIGN CONSIDERATIONS, SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
EMP - ELECTROMAGNETIC PULSE	[ESD, EOS/ESD PHYSICS]	
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
FAILURE CAUSE	[FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
FAILURE ANALYSIS RESULTS	[FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
17515-28	ELECTROSTATIC DISCHARGE PROTECTION USING SILICON TRANSIENT SUPPRESSORS	[193-197]
<u>AUTHOR(S)</u> :	CLARK, O.M.	
<u>COMPANY</u> :	GENERAL SEMICONDUCTOR INDUSTRIES	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
CIRCUIT PROTECTION DEVICES	[NON-ELECTRONICS]	
PROCESS DESIGN	[DESIGN CONSIDERATIONS, SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
TRANSIENT SUPPRESSORS	[ESD, DEVICE, PROTECTIVE DEVICES/INPUT PROTECTION]	
FUTURE TRENDS	[SEMICONDUCTOR TECH.]	
REFERENCE DOCUMENT		
17515-27	THE PHANTOM EMITTER-AN ESD-RESISTANT BIPOLAR TRANSISTOR DESIGN AND ITS APPLICATIONS TO LINEAR INTEGRATED CIRCUITS	[188-192]
<u>AUTHOR(S)</u> :	MINEAR, R.L. DODSON, G.A.	
<u>COMPANY</u> :	BELL LABORATORIES	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
GEOMETRIES/LAYOUT	[DESIGN CONSIDERATIONS, SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
OVERSTRESS	[FAILURE CAUSE, FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
REFERENCE DOCUMENT		
TRANSISTOR	[DISCRETE SEMICONDUCTOR, SEMICONDUCTOR DEVICE]	
MICROCIRCUIT	[SEMICONDUCTOR DEVICE]	
TESTING TOOLS & TECHNIQUES	[SEMICONDUCTOR TECH.]	

CHRONOLOGICAL LIST OF PAPERS 1979

DOCUMENT-SEQUENCE NO.	TITLE	PAGES
17515-26	ELECTRICAL OVERSTRESS VERSUS DEVICE GEOMETRY	[183-187]
AUTHOR(S) : PETRIZIO,C.J.		
COMPANY : RCA		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
CIRCUIT PROTECTION DEVICES	[NON-ELECTRONICS]	
GEOMETRIES/LAYOUT	[DESIGN CONSIDERATIONS, SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
INPUT PROTECTION	[ESD, DEVICE, PROTECTIVE DEVICES/INPUT PROTECTION]	
FABRICATION PROCESSES & TECHNIQUES	[SEMICONDUCTOR TECH.]	
GUIDE/PROCEDURE	[REFERENCE DOCUMENT]	
TESTING TOOLS & TECHNIQUES	[SEMICONDUCTOR TECH.]	
TEST SPECIFICATION	[TESTING TOOLS & TECHNIQUES, SEMICONDUCTOR TECH.]	
17515-25	THE DIELECTRIC STRENGTH OF SiO2 IN A CMOS TRANSISTOR STRUCTURE	[176-182]
AUTHOR(S) : SODEN,J.M.		
COMPANY : SANDIA LABORATORIES		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
DIELECTRIC BREAKDOWN	[ESD, DEVICE, FAILURE MODES]	
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
FAILURE MODES	[FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
FABRICATION PROCESSES & TECHNIQUES	[SEMICONDUCTOR TECH.]	
REFERENCE DOCUMENT		
TRANSISTOR	[DISCRETE SEMICONDUCTOR, SEMICONDUCTOR DEVICE]	
17515-24	SUSCEPTIBILITY OF LSI MOS TO ELECTROSTATIC DISCHARGE AT ELEVATED TEMPERATURE	[168-175]
AUTHOR(S) : TENG,T. HART,A.R. MCKENNA,A.		
COMPANY : HEWLETT PACKARD		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
METALLIZATION MELT	[ESD, DEVICE, FAILURE MODES]	
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
OVERSTRESS	[FAILURE CAUSE, FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
FAILURE ANALYSIS RESULTS	[FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
MATHEMATICAL ANALYSIS		
GUIDE/PROCEDURE	[REFERENCE DOCUMENT]	
DIGITAL LSI	[MICROCIRCUIT, SEMICONDUCTOR DEVICE]	
STEP STRESS	[TEST TECHNIQUES FOR REL. ASSESSMENT, SEMICONDUCTOR TECH.]	
17515-23	DAMAGE RESPONSE OF SELECTED INTERFACE INTEGRATED CIRCUITS TO A SIMULATED EMP	[158-167]
AUTHOR(S) : FORMANEK,V.C.		
COMPANY : IIT RESEARCH INSTITUTE		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
EMP - ELECTROMAGNETIC PULSE	[ESD, EOS/ESD PHYSICS]	
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
FAILURE ANALYSIS RESULTS	[FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
REFERENCE DOCUMENT		
MICROCIRCUIT	[SEMICONDUCTOR DEVICE]	
TEST TECHNIQUES FOR REL. ASSESSMENT	[SEMICONDUCTOR TECH.]	

CHRONOLOGICAL LIST OF PAPERS 1979

<u>DOCUMENT-SEQUENCE NO.</u>	<u>TITLE</u>	<u>PAGES</u>
17515-22	MICROWAVE NANOSECOND PULSE BURNOUT PROPERTIES OF ONE MICRON MESFETS	[147-157]
<u>AUTHOR(S)</u> : WHALEN, J.J.	THORN, M.L.	RASTEFANO, E.
<u>COMPANY</u> : SUNY AT BUFFALO		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
METALLIZATION MELT	[ESD, DEVICE, FAILURE MODES]	
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
OVERSTRESS	[FAILURE CAUSE, FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
FAILURE MODES	[FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
FIELD EFFECT, (FET)	[SEMICONDUCTOR TECH.]	
REFERENCE DOCUMENT		
TESTING TOOLS & TECHNIQUES	[SEMICONDUCTOR TECH.]	
17515-21	SQUARE PULSE AND RF PULSE OVERSTRESSING OF UHF TRANSISTORS	[140-146]
<u>AUTHOR(S)</u> : WHALEN, J.J.	DOMINGOS, H.	
<u>COMPANY</u> : SUNY AT BUFFALO		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
EMP - ELECTROMAGNETIC PULSE	[ESD, EOS/ESD PHYSICS]	
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
OVERSTRESS	[FAILURE CAUSE, FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
GUIDE/PROCEDURE	[REFERENCE DOCUMENT]	
TRANSISTOR	[DISCRETE SEMICONDUCTOR, SEMICONDUCTOR DEVICE]	
TESTING TOOLS & TECHNIQUES	[SEMICONDUCTOR TECH.]	
17515-20	MODELING OF ELECTRICAL OVERSTRESS IN SILICON DEVICES	[133-139]
<u>AUTHOR(S)</u> : KUSENEZOV, N.	SMITH, J.S.	
<u>COMPANY</u> : LOCKHEED		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
DIELECTRIC BREAKDOWN	[ESD, DEVICE, FAILURE MODES]	
OVERSTRESS	[FAILURE CAUSE, FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
COMPUTERIZED TECH	[REL. MODELING TECHNIQUES, REL. MODELS/DATA/ANALYSIS]	
MODELS/THEORY/EQUATIONS	[REL. MODELING TECHNIQUES, REL. MODELS/DATA/ANALYSIS]	
SEMICONDUCTOR DEVICE		
17515-19	AN ELECTROTHERMAL MODEL FOR CURRENT FILAMENTATION IN SECOND BREAKDOWN OF SILICON-ON-SAPPHIRE DIODES	[126-132]
<u>AUTHOR(S)</u> : BARUAH, A.	BUDENSTEIN, P.P.	
<u>COMPANY</u> : AUBURN UNIVERSITY		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
COMPUTERIZED ANALYSIS	[DESIGN TOOLS & TECHNIQUES, SEMICONDUCTOR TECH.]	
SECONDARY BREAKDOWN	[ELECTRICAL FAILURE PHENOMENA, SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
DECAY TIME	[ESD, MATERIALS AND EQUIPMENT, TESTING]	
MATHEMATICAL ANALYSIS		
GUIDE/PROCEDURE	[REFERENCE DOCUMENT]	
COMPUTERIZED TECH	[REL. MODELING TECHNIQUES, REL. MODELS/DATA/ANALYSIS]	
DIODE	[DISCRETE SEMICONDUCTOR, SEMICONDUCTOR DEVICE]	

CHRONOLOGICAL LIST OF PAPERS 1979

DOCUMENT-SEQUENCE NO.	TITLE	PAGES
17515-18	HUMAN FACTORS IN ELECTROSTATIC DISCHARGE PROTECTION	[122-125]
<u>AUTHOR(S)</u> :	SCHNETKER,T.R.	
<u>COMPANY</u> :	GOULD	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
APPLICATION FACTORS	[DESIGN CONSIDERATIONS, SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
CONDUCTIVE ESD PROTECTIVE MATERIAL	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
INPUT PROTECTION	[ESD, DEVICE, PROTECTIVE DEVICES/INPUT PROTECTION]	
ESD CONTROL PROGRAM	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]	
STATIC CONTROL	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]	
HELICOPTOR	[APPLICATION ENVIRONMENT]	
GUIDE/PROCEDURE	[REFERENCE DOCUMENT]	
PROCUREMENT CONTROLS	[USER OF REL. PREDICTION MODELS]	
TEST TECHNIQUES FOR REL. ASSESSMENT	[SEMICONDUCTOR TECH.]	
17515-17	REVERSE-BIAS SECOND BREAKDOWN IN POWER TRANSISTORS	[116-121]
<u>AUTHOR(S)</u> :	BLACKBURN,D.L. BERNING,D.W.	
<u>COMPANY</u> :	NATIONAL BUREAU OF STANDARDS (NBS)	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
SECONDARY BREAKDOWN	[ELECTRICAL FAILURE PHENOMENA, SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
THERMAL SECONDARY BREAKDOWN	[ESD, DEVICE, FAILURE MODES]	
TRANSISTOR	[DISCRETE SEMICONDUCTOR, SEMICONDUCTOR DEVICE]	
TEST TECHNIQUES FOR REL. ASSESSMENT	[SEMICONDUCTOR TECH.]	
17515-16	DOPING PROFILES AND SECOND. BREAKDOWN	[109-115]
<u>AUTHOR(S)</u> :	WARD,A.L.	
<u>COMPANY</u> :	HARRY DIAMOND LAB (HDL)	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
SECONDARY BREAKDOWN	[ELECTRICAL FAILURE PHENOMENA, SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
COMPUTERIZED TECH	[REL. MODELING TECHNIQUES, REL. MODELS/DATA/ANALYSIS]	
GRAPHICAL TECHNIQUES	[REL. MODELING TECHNIQUES, REL. MODELS/DATA/ANALYSIS]	
DIODE	[DISCRETE SEMICONDUCTOR, SEMICONDUCTOR DEVICE]	
EVALUATION TEST	[TEST TECHNIQUES FOR REL. ASSESSMENT, SEMICONDUCTOR TECH.]	
17515-15	ESD SUSCEPTIBILITIES OF HIGH PERFORMANCE ANALOG INTEGRATED CIRCUITS	[104-108]
<u>AUTHOR(S)</u> :	MOON,M.G.	
<u>COMPANY</u> :	HARRIS	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
DESIGN FOR TESTABILITY	[DESIGN CONSIDERATIONS, SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
DIELECTRIC BREAKDOWN	[ESD, DEVICE, FAILURE MODES]	
HUMAN BODY ESD MODEL	[ESD, DEVICE, TESTING METHODS]	
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
OVERSTRESS	[FAILURE CAUSE, FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
MICROCIRCUIT	[SEMICONDUCTOR DEVICE]	
TEST TECHNIQUES FOR REL. ASSESSMENT	[SEMICONDUCTOR TECH.]	

CHRONOLOGICAL LIST OF PAPERS 1979

DOCUMENT-SEQUENCE NO.	TITLE	PAGES
17515-14	ELECTROSTATIC FAILURE OF X-BAND SILICON SCHOTTKY BARRIER DIODES	[97-103]
<u>AUTHOR(S)</u> : ANAND,Y. <u>COMPANY</u> : MICROWAVE ASSOCIATES, INC. <u>(J)</u>		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
METALLIZATION MELT	[ESD, DEVICE, FAILURE MODES]	
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
OVERSTRESS	[FAILURE CAUSE, FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
REFERENCE DOCUMENT		
DIODE	[DISCRETE SEMICONDUCTOR, SEMICONDUCTOR DEVICE]	
CHARACTERIZATION	[TEST TECHNIQUES FOR REL. ASSESSMENT, SEMICONDUCTOR TECH.]	
17515-13	FAILURE ANALYSIS OF MICROCIRCUITS SUBJECTED TO ELECTRICAL OVERSTRESS	[88-96]
<u>AUTHOR(S)</u> : UETSUKI,T. MITANI,S. <u>COMPANY</u> : HITACHI		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
DESIGN FOR TESTABILITY	[DESIGN CONSIDERATIONS, SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
INPUT PROTECTION	[ESD, DEVICE, PROTECTIVE DEVICES/INPUT PROTECTION]	
EOS - ELECTRICAL OVERSTRESS	[ESD, EOS/ESD PHYSICS]	
WUNSCH BELL MODEL	[ESD, DEVICE, TESTING METHODS]	
OVERSTRESS	[FAILURE CAUSE, FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
CHART/DIAGRAM	[REFERENCE DOCUMENT]	
FMEA/FMECA,(FAILURE MODE EFFECTS)	[REL. MODELING TECHNIQUES, REL. MODELS/DATA/ANALYSIS]	
MICROCIRCUIT	[SEMICONDUCTOR DEVICE]	
TEST TECHNIQUES FOR REL. ASSESSMENT	[SEMICONDUCTOR TECH.]	
17515-12	DYNAMIC WAVEFORM CHARACTERISTICS OF PERSONNEL ELECTROSTATIC DISCHARGE	[78-87]
<u>AUTHOR(S)</u> : KING,M.W. <u>COMPANY</u> : CONSULTANT		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
EMP - ELECTROMAGNETIC PULSE	[ESD, EOS/ESD PHYSICS]	
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
OVERSTRESS	[FAILURE CAUSE, FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
FABRICATION PROCESSES & TECHNIQUES	[SEMICONDUCTOR TECH.]	
NOTICE/BULLETIN	[REFERENCE DOCUMENT]	
TEST TECHNIQUES FOR REL. ASSESSMENT	[SEMICONDUCTOR TECH.]	
17515-11	EFFECTS OF ELECTRICAL OVERSTRESS ON DIGITAL BIPOLAR MICROCIRCUITS AND ANALYSIS	[64-77]
TECHNIQUES FOR FAILURE SITE LOCATION <u>AUTHOR(S)</u> : RUTHERFORD,D.H. PERKINS,J.F. <u>COMPANY</u> : RAYTHEON		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
METALLIZATION MELT	[ESD, DEVICE, FAILURE MODES]	
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
OVERSTRESS	[FAILURE CAUSE, FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
DIGITAL LSI	[MICROCIRCUIT, SEMICONDUCTOR DEVICE]	
SCREENING	[TEST TECHNIQUES FOR REL. ASSESSMENT, SEMICONDUCTOR TECH.]	

CHRONOLOGICAL LIST OF PAPERS 1979

<u>DOCUMENT-SEQUENCE NO.</u>	<u>TITLE</u>	<u>PAGES</u>
17515-10	ELECTRO-STATIC DISCHARGE AND CMOS LOGIC	[55-63]
<u>AUTHOR(S)</u> :	BRANBERG,G.	
<u>COMPANY</u> :	HEWLETT PACKARD	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
LATENT ESD FAILURE	[ESD, DEVICE, FAILURE MODES]	
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
OVERSTRESS	[FAILURE CAUSE, FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
REFERENCE DOCUMENT		
MICROCIRCUIT	[SEMICONDUCTOR DEVICE]	
WEIBULL	[STATISTICAL ANALYSIS]	
TEST TECHNIQUES FOR REL. ASSESSMENT	[SEMICONDUCTOR TECH.]	
17515- 9	THE DEFICIENCIES IN MILITARY SPECIFICATION MIL-B-81705: CONSIDERATIONS AND A SIMPLE MODEL FOR STATIC PROTECTION	[45-54]
<u>AUTHOR(S)</u> :	YENNI,D.M. HUNTSMAN,J.R.	
<u>COMPANY</u> :	3M	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
BULK CONDUCTIVE PLASTIC	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
CONDUCTIVE ESD PROTECTIVE MATERIAL	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
ELECTROSTATIC SHIELD	[ESD, EOS/ESD PHYSICS]	
ESD PROTECTIVE MATERIAL	[ESD, MATERIALS AND EQUIPMENT, TESTING]	
PROTECTIVE BAGS	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
ESD STD AND HANDBOOK	[ESD, STANDARDS, HANDBOOKS, MANUALS]	
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
TRIOBOELECTRIC CHARGING	[ESD, EOS/ESD PHYSICS]	
PROCESS CONTROL/SPECIFICATION	[FABRICATION PROCESSES & TECHNIQUES, SEMICONDUCTOR TECH.]	
SPECIFICATION/STANDARD	[REFERENCE DOCUMENT]	
TEST SPECIFICATION	[TESTING TOOLS & TECHNIQUES, SEMICONDUCTOR TECH.]	
17515- 8	RELIABILITY OF EOS SCREENED GOLD DOPED 4002 CMOS DEVICES	[41-44]
<u>AUTHOR(S)</u> :	MC CULLOUGH,D.T. LANE,C.H. BLORE,R.A.	
<u>COMPANY</u> :	ROME AIR DEVELOPMENT CENTER (RADC)	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
EOS/ESD	[SEMICONDUCTOR TECH.]	
ESD STD AND HANDBOOK	[ESD, STANDARDS, HANDBOOKS, MANUALS]	
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]	
OVERSTRESS	[FAILURE CAUSE, FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
PROCUREMENT CONTROLS	[USER OF REL. PREDICTION MODELS]	
DIGITAL LSI	[MICROCIRCUIT, SEMICONDUCTOR DEVICE]	
SCREENING	[TEST TECHNIQUES FOR REL. ASSESSMENT, SEMICONDUCTOR TECH.]	
17515- 7	MODULE ELECTROSTATIC DISCHARGE SIMULATOR	[36-40]
<u>AUTHOR(S)</u> :	MADZY,T.M. PRICE,L.A.	
<u>COMPANY</u> :	IBM CORPORATION	
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
BIPOLAR	[COMPONENT TYPE]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
ELECTROSTATIC SIMULATOR	[ESD, DEVICE, TESTING METHODS]	
HUMAN BODY ESD MODEL	[ESD, DEVICE, TESTING METHODS]	
OVERSTRESS	[FAILURE CAUSE, FAILURE ANALYSIS, SEMICONDUCTOR TECH.]	
FABRICATION EQUIPMENT	[FABRICATION PROCESSES & TECHNIQUES, SEMICONDUCTOR TECH.]	
FIELD EFFECT,(FET)	[SEMICONDUCTOR TECH.]	
FUTURE TRENDS	[SEMICONDUCTOR TECH.]	
TEST PROGRAM DEVELOPMENT	[TESTING TOOLS & TECHNIQUES, SEMICONDUCTOR TECH.]	

CHRONOLOGICAL LIST OF PAPERS 1979

DOCUMENT-SEQUENCE NO.	TITLE	PAGES
17515- 6	PROPOSED MIL-STD AND MIL-HDBK FOR AN ELECTROSTATIC DISCHARGE CONTROL PROGRAM - BACKGROUND AND STATUS	[27-35]

AUTHOR(S) : MC MAHON,E.J. BHAR,T.N. OISHI,T.
 COMPANY : RELIABILITY SCIENCES, INC.

INDEX TERM	CATEGORIES
DESIGN CONSIDERATIONS	[SEMICONDUCTOR TECH.]
EOS/ESD	[SEMICONDUCTOR TECH.]
ESD PROTECTIVE MATERIAL	[ESD, MATERIALS AND EQUIPMENT, TESTING]
ESD CONTROL PROGRAM	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]
PROTECTED ESD AREA	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]
STATIC CONTROL	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]
ESD STD AND HANDBOOK	[ESD, STANDARDS, HANDBOOKS, MANUALS]
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]
OVERSTRESS	[FAILURE CAUSE, FAILURE ANALYSIS, SEMICONDUCTOR TECH.]
PROCESS CONTROL/SPECIFICATION	[FABRICATION PROCESSES & TECHNIQUES, SEMICONDUCTOR TECH.]
SPECIFICATION/STANDARD	[REFERENCE DOCUMENT]
REL. STANDARDS	[USER OF REL. PREDICTION MODELS]
SEMICONDUCTOR DEVICE	

17515- 5	THE GENERATION OF ELECTROSTATIC CHARGES IN SILICONE ENCAPSULANTS DURING CYCLIC GASEOUS PRESSURE TESTS	[22-26]
----------	---	----------

AUTHOR(S) : DERMARDEROSIAN,A. RIDEOUT,L.
 COMPANY : RAYTHEON

INDEX TERM	CATEGORIES
TRADE-OFFS	[DESIGN CONSIDERATIONS, SEMICONDUCTOR TECH.]
EOS/ESD	[SEMICONDUCTOR TECH.]
ELECTROSTATIC SIMULATOR	[ESD, DEVICE, TESTING METHODS]
ESD SUSCEPTIBILITY TESTING	[ESD, DEVICE, TESTING METHODS]
TRIOBOELECTRIC CHARGING	[ESD, EOS/ESD PHYSICS]
PKG ENCAPSULANT	[PACKAGE, SEMICONDUCTOR TECH.]
REFERENCE DOCUMENT	
ENVIRONMENTAL	[TEST TECHNIQUES FOR REL. ASSESSMENT, SEMICONDUCTOR TECH.]

17515- 4	STATIC CONTROL USING TOPICAL ANTISTATS	[13-21]
----------	--	----------

AUTHOR(S) : HALPERIN,S.A.
 COMPANY : ANALYTICAL CHEMICAL LABORATORY

INDEX TERM	CATEGORIES
APPLICATION FACTORS	[DESIGN CONSIDERATIONS, SEMICONDUCTOR TECH.]
EOS/ESD	[SEMICONDUCTOR TECH.]
DECAY TIME	[ESD, MATERIALS AND EQUIPMENT, TESTING]
RELATIVE HUMIDITY	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]
TOPICAL ANTISTATS	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]
TRIOBOELECTRIC CHARGING	[ESD, EOS/ESD PHYSICS]
GUIDE/PROCEDURE	[REFERENCE DOCUMENT]
TEST TECHNIQUES FOR REL. ASSESSMENT	[SEMICONDUCTOR TECH.]
EVALUATION TEST	[TEST TECHNIQUES FOR REL. ASSESSMENT, SEMICONDUCTOR TECH.]

CHRONOLOGICAL LIST OF PAPERS 1979

<u>DOCUMENT-SEQUENCE NO.</u>	<u>TITLE</u>	<u>PAGES</u>
17515- 3	ELECTROSTATIC CONDUCTIVITY CHARACTERISTICS OF WORKBENCH-TOP SURFACE MATERIALS	[7-12]
<u>AUTHOR(S)</u> : BRIGGS,C.		
<u>COMPANY</u> : CHARLES STARK DRAPER LABORATORIES		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
MATERIALS	[DESIGN CONSIDERATIONS, SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
CONDUCTIVE ESD PROTECTIVE MATERIAL	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
GROUNDING METHODS	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]	
ESD PROTECTIVE MATERIAL	[ESD, MATERIALS AND EQUIPMENT, TESTING]	
PROTECTED ESD AREA	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
PROTECTIVE WORK BENCH SURFACE	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
RELATIVE HUMIDITY	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]	
TOPICAL ANTISTATS	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
FABRICATION PROCESSES & TECHNIQUES	[SEMICONDUCTOR TECH.]	
GUIDE/PROCEDURE	[REFERENCE DOCUMENT]	
17515- 2	CONTROLLING ELECTROSTATIC PROBLEMS IN THE FABRICATION AND HANDLING OF SPACECRAFT	[4-6]
HARDWARE		
<u>AUTHOR(S)</u> : STORM,D.C.		
<u>COMPANY</u> : AEROSPACE CORPORATION		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
DESIGN CONSIDERATIONS	[SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
AIR IONIZER	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
GROUNDING STRAPS	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
ESD PROTECTIVE MATERIAL	[ESD, MATERIALS AND EQUIPMENT, TESTING]	
ESD CONTROL PROGRAM	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]	
PROTECTED ESD AREA	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
SENSITIVE ELECTRONIC DEVICE SYMBOLS	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
WRIST STRAP	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE]	
FUTURE TRENDS	[SEMICONDUCTOR TECH.]	
GUIDE/PROCEDURE	[REFERENCE DOCUMENT]	
SPACE	[APPLICATION ENVIRONMENT]	
17515- 1	AN EFFECTIVE ESD AWARENESS TRAINING PROGRAM	[1-3]
<u>AUTHOR(S)</u> : MCATEER,O.J.		
<u>COMPANY</u> : WESTINGHOUSE		
<u>INDEX TERM</u>	<u>CATEGORIES</u>	
DEVELOPMENT PROGRAM	[SEMICONDUCTOR TECH.]	
EOS/ESD	[SEMICONDUCTOR TECH.]	
ESD CONTROL PROGRAM	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]	
STATIC CONTROL	[ESD, MATERIALS AND EQUIPMENT, PROTECTIVE TECHNIQUES]	
GUIDE/PROCEDURE	[REFERENCE DOCUMENT]	
RELIABILITY MANAGEMENT TECH	[USER OF REL. PREDICTION MODELS]	
TEST TECHNIQUES FOR REL. ASSESSMENT	[SEMICONDUCTOR TECH.]	

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